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# NASCAP Programmer's Reference Manual

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### NASCAP PROGRAMMER'S REFERENCE MANUAL\*

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#### SUMMARY

The <u>NASA Charging Analyzer Program (NASCAP)</u> is a computer program designed to model the electrostatic charging of complicated three-dimensional objects, both in a test tank and at geosynchronous altitudes.

This document is a programmer's reference manual and user's guide. It is designed as a reference to experienced users of the code, as well as an introduction to its use for beginners.

All of the many capabilities of NASCAP are covered in detail, together with examples of their use. These include the definition of objects, plasma environments, potential calculations, particle . emission and detection simulations and charging analysis.

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#### 1. NASCAP OVERVIEW

#### 1.1 WHAT IS NASCAP?

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NASCAP, the <u>NASA Charging Analyzer Program</u>, is a computer program designed to simulate spacecraft charging. Spacecraft charging is the build-up of electrostatic potentials on the surfaces of spacecraft exposed to a plasma environment. This occurs when charged particles from the plasma collect on the exposed surface. Both the sign and the magnitude of the potential acquired from exposure to the same plasma may differ for different surface materials, or for different areas of the same material due to shadowing or electrostatic effects. Thus a complicated object composed of more than one material may charge non-uniformly leading to <u>differential</u> charging, i.e., potential differences between different parts of the object. Differential charging can cause electrical discharges that may be damaging to satellite systems.

For objects as structurally complicated as man-made satellites and other spacecraft, predicting their interaction with a surrounding plasma in a test tank or space environment becomes a very complex problem. The purpose of NASCAP is to solve this problem and calculate such observable quantities as electric potentials and currents to and from the spacecraft. NASCAP is an important tool for the analysis of spacecraft charging and the interplay between the various mechanisms responsible.

#### 1.2 THE PHYSICS OF SPACECRAFT CHARGING

The atmosphere around the earth at geosynchronous altitude consists of a low density, energetic plasma. Both electron and ion components of the plasma have similar Maxwellian-like spectra, so that the flux of the much lighter electrons greatly exceeds that of the ions. If the collection of charge were due only to primary plasma currents, all materials would charge to negative potentials of a few

times the plasma temperature. However, the impact of both primary electrons and ions on the exposed surface causes the ejection of low energy (<10 eV) <u>secondary</u> electrons into space. Impacting electrons can also be reflected as <u>backscatter</u>. These mechanisms all act as additional sources of positive current. In sunlight, photoelectrons ejected from the surface also act as a source of positive current. Photoelectrons, like secondary electrons, have low energy. Finally, current may flow to and from a surface from other parts of the object via bulk and/or surface conduction. The net current (i) to any surface is the algebraic sum of these contributions:

inet = ielectrons + ions + ielectrons + ions
primary + iprimary + isecondary + isecondary
+ ielectrons + iconductivity + iphotoemission

If  $i_{net}$  is initially negative, the exposed surface will begin to acquire a negative potential. As the magnitude of the potential increases the net current is attenuated, until it eventually approaches zero and the surface potential remains at a steady equilibrium value. Equilibrium potentials of up to -10 kV have been observed in geosynchronous earth orbit.

If  $i_{net}$  is initially positive, the exposed surface will begin to acquire a positive potential. However, large positive equilibrium potentials are not normally achieved. This is because low energy secondary and photoemissions provide the dominant contribution to a positive current. As soon as the surface reaches a potential greater than the energy of the emitted electrons (5 or 10 eV) they can no longer escape and charging stops. In this case equilibrium is determined by the suppression of low energy emission due to the surface's own electric field. A similar suppression effect may occur due to the electric fields of neighboring negatively charged surfaces. This adds to the complexity of the situation for charging

of complicated objects and makes spacecraft charging a truly three-dimensional problem.

#### 1.3 NASCAP CAPABILITIES

NASCAP is a collection of the various models and algorithms needed to simulate the charging of a complex object. The various formulations are written to levels of accuracy and approximation appropriate to solving problems for geosynchronous-like conditions in a reasonable amount of computer time. The NASCAP user has a great deal of flexibility in applying these capabilities to his particular problem. Among NASCAP's capabilities are:

- To define complex objects from fairly simple input.
- To define properties of materials relevant to spacecraft charging.
- To calculate electrostatic potentials around complex objects.
- To calculate shadowing of one part of an object by another.
- To calculate primary currents incident on spacecraft surfaces from a plasma or from a point source.
- To calculate secondary and backscattered electron currents.
- To calculate conductivity, biasing, and grounding currents.
- To calculate charge accumulation and resulting surface potentials.
- To calculate trajectories of charged particles incident upon, or emitted from, specified surfaces.
- To meaningfully communicate results through printed output, graphical output, and interactive post-processors.

These capabilities satisfy the requirements for study of the processes and the consequences of spacecraft charging.

#### 1.4 THE NASCAP PHYSICAL MODEL

NASCAP objects are defined within a three-dimensional cuboidal grid (rather like a shoe box). The grid is composed of many thousands of identical cubes or volume elements stacked together. Objects are defined by filling or partially filling the cubes. For example, a quasi-sphere is shown in Figure 1.1. The exterior surfaces of the filled volume elements form the exposed surface of the object. Thus, the object surface consists of rectangular or triangular patches called <u>surface cells</u>. In addition to the cubic elements, NASCAP allows arbitrarily narrow cylindrical booms and thin plates to be defined. The definition of NASCAP objects is discussed in detail in Chapter 3.



Figure 1.1. A quasi-sphere.

NASCAP calculates the potentials and currents for an object that has been exposed to a plasma environment for a chosen period of time or <u>timestep</u>. The initial conditions at the beginning of the timestep may be specified by the user or may be remembered from the previous timestep calculation. Similarly the results predicted for the end of the current timestep may be used as the initial condition for the next, and so on. By using a sequence of timesteps, a user may follow the dynamics of the approach to equilibrium as well as being able to examine the equilibrium state itself. The shorter the timesteps chosen, the more will be needed to reach equilibrium and the greater the detail of the dynamic charging behavior calculated.

For each timestep, or cycle, NASCAP calculates the total amount of charge that collects on each surface cell. This is determined from the net current at the beginning of the cycle, taking into account all of the contributions mentioned above. The variation of the net incident current as the surface potential changes during the cycle can also be taken into account. The charge collected is translated into a new set of surface potentials via a detailed resistive-capacitive electrical model of the satellite. Poisson's equation is then solved using the new (fixed) surface potentials to give new updated potentials in the space surrounding the object. The new potential and electric field values imply a new set of currents in the next cycle. Equilibrium is achieved when currents and potentials reach steady values for consecutive timesteps. The details of the many sophisticated physical models that are part of NASCAP are discussed in the later chapters. However, there are a number of assumptions built in that define the physical regime where NASCAP works best.

#### 1.5 THE NASCAP PHYSICAL REGIME

NASCAP assumes orbit-limited spherical probe current collection. This is a good approximation for convex objects with radius of curvature smaller than the Debye length of the ambient plasma. Hence NASCAP works well for small objects (with dimensions of a few meters or less) in geosynchronous orbit (where Debye lengths are typically hundreds of meters). While NASCAP can simulate charging, taking into account a space charge sheath surrounding the object, it is primarily designed for the low density, high temperature plasmas found at geosynchronous altitudes where space charge can be ignored. The range of physical regimes where NASCAP can be most profitably used is discussed at length in Reference 1.

### 1.6 THE NASCAP FAMILY

In addition to the large NASCAP code described in this manual, there are three preprocessors and two postprocessors to aid in the use of NASCAP and the interpretation of NASCAP results. We provide very brief descriptions of these below.

#### 1.6.1 MATCHG

MATCHG is an interactive code for the study of material-environment interactions in a zero-dimensional sense. It accepts the same material definition as NASCAP, and provides the same environment types. For simple cases, use of MATCHG can obviate the use of NASCAP, while for complex cases, it can aid the user to anticipate and understand NASCAP results.

1.6.2 FILES

FILES is a utility to aid in the maintenance (assign, copy, delete) of NASCAP restart files.

#### 1.6.3 OBJCHECK

OBJCHECK is a semi-interactive version of the object definition portion of NASCAP.

#### 1.6.4 CONTOURS

CONTOURS is an interactive contour plotting package. Because it makes use of available geometrical information, CONTOURS provides plots of electrostatic potential superior to those provided directly by NASCAP.

#### 1.6.5 TERMTALK

TERMTALK is an interactive routine which extracts information from NASCAP restart files. It can provide flux breakdown for a chosen surface; time history of potential, flux, or field for chosen surfaces; ordering of surfaces by potential, flux, or field; and definition of surface cell subsets.

### 2. NASCAP COMMAND STRUCTURE

### 2.1 EXECUTING NASCAP (OR HOW DO I RUN NASCAP?)

NASCAP is delivered as one executable program element, or in the language of UNIVAC and CDC, as an 'absolute'. To run NASCAP one needs only to "execute" that element. For example, in the UNIVAC world if the NASCAP absolute resides as element 'NASCAP\*NASCAP.ABS' then

@XOT NASCAP\*NASCAP.ABS

will initiate a NASCAP run. Such a run can be carried out interactively, or in batch mode. Running NASCAP interactively can be fun for very simple objects, but involves many minutes (perhaps hours) staring at an inactive screen for more complex examples. Most NASCAP runs are carried out in batch mode.

Suppose you do start an interactive run and enter the line above (or its equivalent). What happens next? Nothing: NASCAP is waiting for you to tell it what to do.

2.2 KEYWORDS (OR HOW DO I TELL NASCAP WHAT TO DO?)

NASCAP has a very limited vocabulary. It understands only a small set of words. These are called <u>keywords</u>.

The keywords tell NASCAP exactly what you want it to do. There are a number of very basic steps the program must do to provide you, the user, with potentials and currents. These include:

1. Understand the object you wish to analyze.

- 2. Calculate its capacitances.
- 3. Understand the plasma environment you wish to study, and then go ahead and calculate the potentials on the object resulting from its interaction with the plasma.

Not all of these basic steps need be repeated with each execution of the program. For example, you may wish to study the interaction of the same sphere with different plasma environments. It is more

efficient to do this without defining the same object and then recalculating its capacitances each time. In other words, it would be convenient if NASCAP could do steps 1, 2 and 3 just once and then repeat step 3 with different environments. To enable it to do this, NASCAP is broken up internally into several <u>modules</u>, each of which is activated, or executed, by its <u>primary keyword</u>.

### 2.3 NASCAP MODULES

There are thirteen <u>NASCAP modules</u>. Each performs a specific task, may require additional input of its own, and may require output from other modules. (This is explained later for each module.) There is only one module that <u>must</u> be executed in every NASCAP run and it must always be executed <u>first</u>. This is the module <u>RDOPT</u>, which reads the many run options that the user may specify. (More about RDOPT and run options later in Chapter 6.)

The RDOPT module is executed, and options are read, by entering the keyword 'RDOPT' as NASCAP input. So if you are running NASCAP interactively and you type RDOPT, NASCAP will finally do something. It will read the options from file 26 (more about files later too!) and echo them back to you. Exactly the same thing happens in batch mode. The word 'RDOPT' should follow the statement beginning the execution of the NASCAP "absolute". 'RDOPT' is then followed by other primary keywords describing the sequence of operations appropriate to your problem. The primary keywords are summarized in Table 2.1.

The actual potential and current calculations are carried out by module TRILIN. Before TRILIN can be successfully executed however, it requires knowledge of the object at hand and its capacitances. This information is generated by the execution of modules OBJDEF (OBJect DEFinition) and CAPACI (CAPACItances) respectively, and is written out by them to their output files (output files are explained in Section 2.6). Unless these files are available to TRILIN it cannot be executed successfully.

The files needed by TRILIN can be generated by executing OBJDEF and CAPACI in the same NASCAP run, or by executing them in a previous run and saving their output files. Whether in the same run or in separate runs, the modules RDOPT, OBJDEF and CAPACI must be executed in that historical order for each new object defined before attempting to execute TRILIN. Once OBJDEF and CAPACI have been executed, and their files established, subsequent runs can skip straight from RDOPT to TRILIN.

2.4 THE NASCAP RUNSTREAM

The sequence of primary keywords that tell NASCAP what modules to execute form the <u>NASCAP runstream</u>. The simplest runstream consists of just two keywords:

RDOPT

END

RDOPT <u>must always</u> be the first keyword encountered in <u>any</u> run, and all runs <u>must</u> be terminated with the card 'END'.

The runstream above will not do any actual calculations. Module RDOPT will be executed, and read input from the run options file (2.6). NASCAP will then print out the resulting option values, will assign required scratch and restart files, and exit.

A more typical runstream has the form COMMENT first run RDOPT OBJDEF CAPACI TRILIN END

These four modules must be executed in this order to obtain currents and potentials. Note that the word

#### COMMENT

is also a primary keyword. It is read and has no effect. This allows

parts of the NASCAP runstream to be labeled with reminders. The same effect could be achieved with two separate runs, i.e.:

COMMENT first run RDOPT OBJDEF CAPACI END

followed by

COMMENT second run RDOPT TRILIN END

(Note that RDOPT is executed in both runs.) Further potential calculations can be made with more runs of the form RDOPT

TRILIN END

Once OBJDEF and CAPACI have been executed once, and their output files saved, TRILIN can be executed by itself.

The remaining modules are all optional, in the sense that they are not <u>necessary</u> to calculate potentials. They too, however, must be executed according to their order of precedence.

2.5 ORDERS OF PRECEDENCE (OR WHAT COMES AFTER RDOPT?)

Table 2.2 summarizes the formal rules of precedence. The second column gives the module that <u>must</u> precede execution of the module at hand, and the third column the module that it logically precedes. For example HIDCEL, which calculates the shadowing of an object in sunlight prior to the calculation of its photoemission, <u>must</u> be preceded by OBJDEF. Otherwise there would be no object to shadow.

It logically precedes TRILIN, since TRILIN uses the shadowing information to calculate the photocurrent. If we were going to use HIDCEL in a full NASCAP run, it would come between OBJDEF and TRILIN.

. OBJDEF . . HIDCEL . . . TRILIN

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However, OBJDEF must be preceded by RDOPT. Furthermore we must execute CAPACI for each new object. CAPACI and HIDCEL both have the same order of precedence, and so both of the following sequences of cards are acceptable:

RDOPT	RDOPT
OBJDEF	OBJDEF
HIDCEL	CAPACI
CAPACI	HIDCEL
TRILIN	TRILIN
END	END

Table 2.2 contains enough information to determine unambiguously an acceptable sequence of primary keywords in all cases.

It is possible to make multiple calls to the same module in the same runstream. For example, when using ROTATE this is required.

COMMENT rotate run RDOPT OBJDEF CAPACI HIDCEL TRILIN ROTATE TRILIN ROTATE TRILIN END

This run calls TRILIN three times, with the sun at different angles to the object. The orientation of the sun is calculated by ROTATE to simulate a spinning satellite.

### 2.6 FILES

NASCAP generates large amounts of information in the form of lists and arrays as each of the modules are executed; too much information to be held in program memory. To overcome this problem NASCAP stores information by writing it out to a file, and reads it back into memory only when needed. Writing to files also allows modules to share information with each other, both in the same run and separate runs.

The UNIVAC version of NASCAP assigns all of its own (temporary) output (or scratch) files. Versions running under other operating systems require the user to pre-assign these files. A list of output files is shown in Table 2.3. There are a minimum of 14. Some options require additional output files. (This is explained in sections dealing with those options.)

Input files must be assigned (and written) by the user. There are three principle input files: The object definition file, the flux definition file and the run options file.

The object definition file contains sets of secondary keywords and parameters that define the structure of the object. This is read by module OBJDEF and is discussed in detail in Chapter 3.

The flux definition file also consists of secondary keywords and parameters. It defines the plasma spectrum and its angular distribution, in space or in a test tank. This is read by module TRILIN and is discussed in Chapter 5.

The run option file is read by RDOPT and lists the options chosen by the user, from the many available that control the way the program runs. Each option is specified with a secondary keyword. This is explained in Section 6.1.

The default input file numbers for each primary keyword are shown in Table 2.4. The input file numbers can be specified by the user simply by following the primary keyword by the file or unit number; e.g.,

RDOPT 24

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will cause the RDOPT module to search for input in file 24 instead of the default file 26.

FILE 5 is the NASCAP runstream; i.e., RDOPT 5

will cause the cards following 'RDOPT 5' in the NASCAP runstream to be read by module RDOPT. In the same way

**OBJDEF 5** 

will cause module OBJDEF to read cards from the keyword runstream, and so on. In this way all NASCAP input can be included in one self-contained runstream. For example:

```
@ XQT NASCAP*NASCAP.ABS (UNIVAC)
{
RDOPT 5
rdopt options (Chapter 6)
END
{
OBJDEF 5
object definition cards (Chapter 3)
END
CAPACI
HIDCEL
{
TRILIN 5
plasma environment cards (Chapter 5)
END
```

END

NASCAP also assigns names to each file number. For example, file 22 read by TRILIN is called IFLUX. The default file (number 22) can be changed by setting IFLUX to a different value. IFLUX and the other files may be set by the user as run options. (This is discussed in Chapter 6 dealing with RDOPT and run options in detail.) Changing IFLUX from 22 to, say <n>, causes the default TRILIN file to be changed from 22 to <n> for that particular run only. So multiple calls to TRILIN will read from file <n> each time if no file number is included after the keyword; e.g.,

TRILIN

TRILIN

will read from the new default <n>. Including a file number after the keyword has the same effect as changing IFLUX.

The names of each file are included in Tables 2.3 and 2.4. Table 2.5 gives a list of spare file numbers available to the user up to 49. The following discussion assumes the user will use the default file numbers for NASCAP output files.

#### 2.7 RESTART FILES

If NASCAP information is intended for use in subsequent runs some of the output files must be made permanent and saved. Only six need to be saved. These are called the restart files. They are files

10, 15, 16, 17, 21, 27 (and 19 for runs specifying TANK). These files store, among other things, the object definition and capacitance information that allow TRILIN to be executed in runs subsequent to OBJDEF and CAPACI. They also allow information from previous TRILIN cycles (or timesteps) to be used by new TRILIN executions, and to continue charging sequences from where previous runs left off. This is carried out using the RESTART option discussed in Section 6.2.9.

It is also often useful to save file 2. This allows graphical output to be replotted later (see Chapter 9).

#### 2.8 TECHNICAL DISCUSSION

All NASCAP output files are sequential files accessed by Fast I/O routines, except file 21 (and 38). File 21 is a random access file. In the UNIVAC version of NASCAP the routines FASTRW, FASREW, FASPOS are used to access all files. In CDC versions, BUFFER IN and BUFFER OUT (MSIO for file 21) perform this function. The random access file 21 contains surface cell information and other run parameters in individual records. The record "housekeeping" is carried out by routine CELLIO. Access calls always occur via this routine. The information stored in each record is summarized in Table 2.6.

### 2.9 SUMMARY

NASCAP is divided into thirteen MODULES, each of which is activated by its primary keyword. NASCAP runstreams consist of a control card to execute the program "absolute", followed by a sequence of primary keywords. The execution of the NASCAP modules and hence the order of the keywords must follow certain rules of <u>precedence</u>. NASCAP reads and writes information to files. If six of these files (the restart files) are made permanent, separate runs may share information.
### TABLE 2.1. NASCAP MODULES AND PRIMARY KEYWORDS

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Module and Keyword	Task	Additional Input
CAPACI	Calculates object capacitances	No
DETECT	Enables DETECTOR run option	Yes. Default - assumes input follows keyword (Unit 5)
HIDCEL	Calculates the shadowing of an object illuminated by the sun	Νο
IPS	Sets up initial potentials other than zero on surface cells	Yes. Default - assumes input follows keyword (Unit 5)
NEWMAT	Defines new material properties	Yes. (No default - input file must be specified)
OBJDEF	Reads and processes object definition information	Yes. Default - read object definition from file 20
RDOPT	Reads run option and initializes program parameters	Yes. Default - read option from file 26
ROTATE	Causes NASCAP to model a rotating object	Yes. (No default - input file must be specified)
SATPLT	Produces plots and pictures of the object	No
SPIN	Causes NASCAP to model a rotating object by averaging the effect of the sun and magnetic field over one rotation	Yes. (No default - input file must be specified)
STRESS	Searches for insulating cells having the highest internal stress	Yes. (No default - input file must be specified)
TANK	Defines a test tank environ- ment with multiple particle guns	Yes. Default - read gun definitions from file 22
TRILIN	Reads parameters describing the plasma environment and cal- culates potentials and currents	Yes. Default - read environment from file 22

### TABLE 2.2. PRECEDENCE OF PRIMARY KEYWORDS

Keyword	Must Be Preceded By	Logically Precedes
CAPACI	OBJDEF	TRILIN or IPS
DETECT	TRILIN (or IPS)	(None)
HIDCEL	OBJDEF	TRILIN
IPS	CAPACI	TRILIN or DETECT
NEWMAT	OBJDEF	TRILIN
OBJDEF	RDOPT	CAPACI
RDOPT	(None)	(A11)
ROTATE	TRILIN	TRILIN
SATPLT	OBJDEF	(None)
SPIN	OBJDEF .	TRILIN
STRESS	TRILIN	(None)
TANK	RDOPT	TRILIN*
TRILIN	CAPACI	DETECT
COMMENT	(None)	(None)

\* If shadowing options HIDCEL, SPIN or ROTATE are chosen, they must follow TANK before TRILIN.

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### TABLE 2.3. NASCAP OUTPUT FILES

Default File No	. <u>File Name</u>	Written_By	Read By	Information Content
2	None	OBJDEF SATPLT HIDCEL *ROTATE SPIN DETECT TRILIN *when plot options are	NASCAP*PLOTREAD. (Chapter 9)	NASCAP graphics calls.
		specified		
10 (RESTAR	IP T)	{ TRILIN CAPACI IPS	TRILIN CAPACI IPS	Conjugate gradient scratch file (Sec- tion 3.15). Con- tains <u>potential</u> array on completion of TRILIN, CAPACI or IPS.
11	IAUN	TRILIN CAPACI IPS	{ TRILIN CAPACI IPS	Conjugate gradient scratch file (Sec- tion 3.15).
		SPIN	SPIN	SPIN scratch file - used to store shadowing information.
12	IR	TRILIN CAPACI IPS	TRILIN CAPACI IPS	Conjugate gradient scratch file (Sec- tion 3.15).
13	IU	(TRILIN CAPACI IPS	(TRILIN CAPACI IPS	Conjugate gradient scratch file (Sec- tion 3.15).

Default File No.	File Name	Written By	Read By	Information Content
14	ISPARE	TRILIN CAPACI IPS	(TRILIN CAPACI IPS	Conjugate gradient scratch file (Sec- tion 3.15).
		HIDCEL SPIN TANK SATPLT ROTATE	HIDCEL SPIN TANK SATPLT ROTATE	Scratch file for shadowing information.
15 (RESTART)	IROUS	TRILIN CAPACI IPS	(TRILIN CAPACI IPS	Charge density array.
16 (RESTART)	IPQCND	TRILIN	Associated inde- pendent program 'TERMTALK'	TERMTALK infor- mation (Section
17 (RESTART)	ILTBL	OB JDE F	OBJDEF CAPACI TRILIN IPS DETECT	Object volume element table (LTBL).
18	IOBJ	None	None	Reserved for future use.
19 (RESTART when 'TANK' is specified)	IOBPLT	TANK	TRILIN	Beam shadowing information.

### TABLE 2.3. NASCAP OUTPUT FILES (CONTINUED)

### TABLE 2.3. NASCAP OUTPUT FILES (CONCLUDED)

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Default <u>File No.</u>	File Name	<u>Written By</u>	Read By	Information Content
21 (RESTART)	ICNOW	ר ד <b>א</b>	A11	Individual cell information (Section
25	IDIV	TRILIN CAPACI IPS	(TRILIN CAPACI (IPS	D <sup>2</sup> (Scaled conjugate gra- dient array).
27 (RESTART)	IAREA	OB JDE F	(TRILIN CAPACI IPS	Boom conjugate gradient ma- trices.
28	IPART	TRILIN	DETECT	Particle plot- ting informa- tion.
38	None	DETECT	(User program)	Particle trajec- tory information (Chapter 7).
46	None	END	-	EXEC file to automatically execute PLOTREAD.

### TABLE 2.4. USER INPUT FILES

NASCAP Name	Default File Number	Read By	Information Content
None	5	Main Program	NASCAP KEYWORDS and runstream (cannot be changed).
ISPECTR	9	TRILIN in 'UPDATE' or 'DIRECT' modes (Chapter 5)	Environment informa- tion (Chapter 5).
ISAT	20	OB J DE F	Object definition statements (Chapter 3).
IFLUX	22	TRILIN or TANK	Environment informa- tion (Chapter 5).
IKEYWD	26	RDOPT	User specified options (Chapter 6).
None	None	TRILIN - when EMITTER option is enabled	Emitter information (Chapter 7).
None	None	DETECT	Detector information (Chapter 7).
None	None	NEWMAT	Material properties (Chapter 4).
None	None	IPS	Initial potential speci- fications (Chapter 8).
None	None	ROTATE	ROTATE parameters (Chapter 8).
None	None	SPIN	SPIN parameters (Chapter 8).

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TABLE 2.5.	SPARE FILES	AVAILABLE TO	THE USER
1	30	37	47
3	31	39	48
4*	32	40**	49
8	33	42	
23	34	43	
24	35	44	
29	36	45	

- Files 6 and 7 are reserved for printed and punched (not used) output, respectively.
- \*\* File 41 is used by the 'DISSPLA' graphics package and is best avoided.

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### TABLE 2.6. FILE 21 RECORDS

Record No.	Record ID	Length	Content
1	VINS	1024	Potentials of insulating surface cells (V)
2	VPTS	1024	Not used
3	EINS	1024	Electric field external to insulating surface cells (V mesh <sup>-1</sup> )
4	ATOT	1250	Areas of surface cells (mesh) <sup>2</sup>
5	AREA	1250	Fraction of the area of surface cells sunlit
6	C-INF	1024	Capacitance of insulating cells to plasma ground or tank wall (code units)
7	DPTLST	500	List of double points (see 3.13)
8	C-COND	1024	Capacitance from the surface of an insulating cell to its underlying conductor (code units)
9	FLUX	1250	Explicit net particle flux to each surface cell (code units)
10	DQEMIT	1024	Change in charge due to low energy emitted electron for each insulating cell (code units)
11	DQ	1024	Change in charge for each insulating cell (code units)
12	PTLIST	1024	List of all points that are corners of insulating surface cells
13	ΑΡΤ	1024	Areas associated with above points (PTLIST) (mesh) <sup>2</sup>

### TABLE 2.6. FILE 21 RECORDS (CONTINUED)

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Record No.	Record ID	Length	Content
14	LINS	1024	List of insulating surface cell numbers
15	VBOOM	100	Potentials of the boom cells (V)
16	SIGMA	1024	(Not used)
17	EBOOM	100	Electric fields external to boom surface cells (V mesh <sup>-1</sup> )
18	DFDV	1024	Flux derivatives for insulating surface cells
19	CSCOND	15	Capacitance of each conductor to plasma ground or test tank wall (code units)
20	CIJSMA	15	Stray capacitances of conductor to spacecraft ground (code units)
21	SCMAT	9537	Conductivity matrix (code units)
22	SCLI ST	9537	Sparseness pattern of conductivity matrix (who connects to whom)
23	CPTLST	1024	List of surface points which are not corners of insulating cells
24	BINF	1 <b>41</b>	BINF common block — boom parameters
25	BSHAD	100	Shadowing factors for boom cells

### TABLE 2.6. FILE 21 RECORDS (CONTINUED)

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Record No.	Record ID	Length	Content
26	XFLUX	200	Explicit net flux for boom cells (code units)
27	PPEE	500	Potentials for bottom point of a double point (conjugate gradient)
28	PYOU	500	Vector U (conjugate gradient) for bottom points
29	PARR	500	Vector R (conjugate gradient) for bottom points
30	PAUN	500	Vector AU (conjugate gradient <u>)</u> for bottom points
31	PDIV	500	Vector D <sup>2</sup> (scaled conjugate gradient) for bottom points
32	PROUS	500	Charge densities for bottom points (code units)
33	VCELLS	1250	Potentials of surface cells (V)
34	ECELLS	1250	External electric fields of surface cells V (mesh <sup>-1</sup> )
35	PZLIST	500	List of bottom points held at fixed potentials
36	ZLIST	1024	List of top points held at fixed potentials
37	RFLAGS	1	Type of shadowing performed
38	SURF3	1251	Common block - number of surface cells (1) and surface cell list (1250)
39	MATLS	316	Material properties (MATLS common block) (see Chapter 4)
40	VTXL	6200	Vertex surface cell list
41	BOOMS	111	Common block - boom information

### TABLE 2.6. FILE 21 RECORDS (CONTINUED)

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Record No.	Record ID	Length	Content
42	SILHOU	6289	Non-hidden line object plotting information
43	BLOCKS	597	Common block - volume cell information
44	TIMHIS	150	Elapsed time for each cycle performed so far (seconds)
45	QSUHIS	150	Total charge on the object at each cycle (code units)
<b>46</b>	RELSAV	35	Time and conductor potentials and charges for current cycle (volts and code units)
47	INTSAV	35	Cycle number, number of conductors, etc.
48	RDOTSV	100	Residuals for each conjugate gradient iteration
49	CAPRDO	100	Residuals from each conjugate gradient iteration called from CAPACI
50	PCONSV	2250	Conductor potential for each cycle completed (V)
51	PHCMAT	9537	Conductivity matrix including photoconductivity (code units)
52	CNDCUR	60	Currents to each conductor (A)
53	FIFLUX	1350	Average flux to each surface cell during the previous timestep (A m <sup>-2</sup> )
54	SCOPT	5	Common block - screening options
55	GUNS	181	Common block – multigun definition information
56	FIN	1250	Incident electron current to surface cells (A m <sup>-2</sup> )

## TABLE 2.6. FILE 21 RECORDS (CONCLUDED)

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Record No.	Record ID	Length	Content
57	FOU	1250	Secondary electron current from surface cells (A m <sup>-2</sup> )
58	FINP	1250	Incident ion current to surface cells (A m <sup>-2</sup> )
59	FOUP	1250	Secondary electron current due to ion impact from surface cells (A m <sup>-2</sup> )
60	FELB	1250	Backscatter from surface cells (A m <sup>-2</sup> )
61	PCURR	1250	Photocurrent from surface cells (A m <sup>-2</sup> )
62	BFIN	250	Incident electron current to boom cells (A m <sup>-2</sup> )
63	BFOU	250	Secondary electron current from boom cells (A m <sup>-2</sup> )
64	BFIP	250	Incident ion current to boom cells (A m <sup>-2</sup> )
65	BFOP	250	Secondary electron current due to ion impact on boom cells (A m <sup>-2</sup> )
66	BFEL	250	Backscatter from boom cells (A m <sup>-2</sup> )
67	BPCU	250	Photocurrent from boom cells (A m <sup>-2</sup> )
68	ANIP	4	Anisotropic flux parameters
69	TNKSZ	5	Grid truncation information
70	CLST	1024	Field-induced bulk conductivity of insulating cells (code units)
71	FINER	61	(Not used by NASCAP)
72	MCOND	286	Common block - capacitance between conductors and fixing information

#### 3. DEFINING OBJECTS

#### 3.1 COMPUTATIONAL SPACE

NASCAP calculates the electric potential in the space surrounding an object as well as the potential of the object itself. Before it can determine these potentials NASCAP must first recognize and understand both the object defined and the amount of surrounding space to be included in the calculations. The total amount of space (including that filled by the object) included in the potential calculation is called the <u>computational space</u>. The edges of the space form the outer boundary.

3.2 THE GRID

The computational space used by NASCAP is a three-dimensional Cartesian space. Any point may be determined by specifying its coordinates according to three mutually perpendicular axes X, Y and Z. If all three axes have the same scale we may imagine the space to be subdivided into many small identical cubic volumes (with the length of cube's side equal to one axis unit). These cubic volumes are called volume elements. This is shown in Figure 3.1. The corners of the volume elements are points in the coordinate system or <u>nodal</u> (or <u>grid</u>) <u>points</u>. Each grid point is described by its X, Y, Z coordinates. For example, the grid point labeled in Figure 3.1 is (5, 6, 8). The grid points and the volume elements filling the space between them form a computational grid (or just a grid).

The default NASCAP grid has dimensions  $17 \times 17 \times 33$ . This means that there are 17 points (and hence 16 length units) in the X and Y directions and 33 points (32 length units) in the Z direction (a "shoe box-like" space). The number of points in the Z direction can also be specified by the user to be a number less than 33 (6.4.8). The length unit, or distance along the axes between points, is called the grid spacing or 'XMESH'. XMESH is determined by the user as a run





option (6.4.15). It may be any positive value, and so the computational space may be any physical size. However, as the absolute size of XMESH is increased the smallest amount of volume that can be recognized by NASCAP (the volume of a volume element) is also increased. This means that any interesting and/or important physical phenomena that occur on length scales much smaller than XMESH become too detailed for NASCAP to model - or resolve. Increasing XMESH decreases the resolution of the NASCAP calculations.

To overcome this problem and allow NASCAP to include large amounts of computational space without sacrificing resolution everywhere, <u>nested grids</u> are allowed. Two grids are said to be nested when one exists inside the other. NASCAP allows up to five nested grids. Each shares a common origin at the center of the innermost grid. The grid spacing is successively doubled from grid to grid. For example, consider grid 2 to extend from -8 to +8 in the X and Y directions and -16 to +16 in the Z direction in its own (doubled) coordinates, and the inner grid (grid 1) to extend to and from the same values in grid 1 coordinates. In grid 2 coordinates grid 1 extends from -4 to +4 in X and Y and -8 to +8 in Z only, while in grid 1 coordinates grid 2 extends from -16 to +16 and -32 to +32. The same relationships then apply to grid 2 and 3, 3 and 4, and so on. A two-dimensional illustration of nested grids is shown in Figure 3.2.

Nested grids allow a small XMESH and hence high resolution for the innermost grid while allowing NASCAP to incorporate large amounts of space (with coarser resolution) far from the origin. This arrangement is particularly well suited to the calculation of potentials of satellite-sized objects exposed to the long (many meters) Debye length plasmas found at geosynchronous altitudes.



Figure 3.2. Cross-section of grid, showing first four embedded meshes.

#### 3.3 OBJECTS

All NASCAP objects are confined to the space inside the innermost 17 x 17 x 33 grid. Only BOOMS (see Section 3.6) are allowed to extend into outer grids. If "empty space" and "object" both coexist in the same computational space what makes objects distinguishable? The answer is that NASCAP can distinguish between volume elements that are <u>filled</u> (with object) and those that are <u>empty</u> (except for ambient plasma of course). Once we have this distinction it is easy to see how objects can be constructed by filling in collections of volume elements. For example, a simple cuboid may be constructed by filling in 2 x 3 x 4 = 24 elements as shown in Figure 3.3.

While arrangements of completely filled and completely empty cubes can be quite versatile in representing objects of many different shapes, more sophisticated representations are possible if we allow cubes to be partially filled (or as a pessimist might say, partially empty). Only three partially filled cubes are allowed. These are shown in Figure 3.4.

While it is easy to see how objects might be constructed by filling or partially filling individual volume elements, a command structure that required the user to specify every element comprising an object would be very cumbersome to use.



Figure 3.3. Cuboid made by filling in twenty-four volume elements.



Figure 3.4. Four shapes of volume cells considered by the NASCAP code: (a) empty cube; (b) wedge-shaped cell with 110 surface; (c) tetrahedron with 111 surface; (d) truncated cube with 111 surface.

#### 3.4 BUILDING BLOCKS

To greatly simplify the user definition of objects NASCAP pre-defines commonly used shapes built up from individual elements. These shapes are called NASCAP BUILDING BLOCKS. There are six.

Cuboid Octagon Quasisphere Tetrahedron Wedge FIL111

These are shown in Figure 3.5. These basic shapes can be defined to be any size (within the inner grid). NASCAP automatically includes the correct number of individual elements for the size of building block chosen by the user.

3.5 COMMANDS (OR HOW DO I ACTUALLY DEFINE AN OBJECT?)

The NASCAP module OBJDEF is responsible for recognizing and understanding the OBJect DEFined by the user. Just as the primary keyword (Chapter 2), 'OBJDEF' in the main runstream causes OBJDEF to be executed, so secondary keywords are used to give instructions to the OBJDEF module. As explained in Chapter 2, OBJDEF reads information from a file whose default number is 20. This is called the <u>object definition file</u> and consists of a collection of secondary keywords and associated parameters.

Each <u>building block</u> has its own <u>keyword</u>. For example, the quasi-sphere is associated with the word QSPHERE, and the cuboid (rectangular parallelepiped) with the word RECTAN. The building blocks and their keywords are summarized in Table 3.1.

Once OBJDEF has read a building block keyword from the object definition file, it then expects to find several more lines (or cards) setting the block parameters. These might include the dimensions of



Figure 3.5. The six building block types are shown here. The uppermost object shows a FIL111 smoothing a corner. Below, from left to right are quasi-sphere, octagon right cylinder, tetrahedron, wedge, and rectangular parallelepiped.

### TABLE 3.1. NASCAP BUILDING BLOCKS AND THEIR KEYWORDS

Keyword	<b>Building Block Description</b>
BOOM	Long thin BOOM
FIL111	Smooth inside of a diagonal corner
OCTAGON	Right octagonal cylinder
PATCHR	Surface of a rectangle
PATCHW	Diagonal face of a wedge
PLATE	Arbitrarily thin plate or cuboid
QSPHERE	Quasisphere
RECTAN	Cuboid or rectangular parallelepiped
TETRAH	Tetrahedron
WEDGE	Wedge derived from half a cube

the building block, its orientation and the materials that cover its surface. (Surface materials are discussed in Chapter 4.) Finally, OBJDEF expects to find a line 'ENDOBJ' telling it that no more information referring to the present block is coming and to expect the next building block keyword. The information to be entered in the object definition file for each building block is summarized in Table 3.2. Note that numbers and words may be separated by one or more spaces on the same line. (Input is free-format.)

### 3.6 BOOMS, PLATES AND PATCHES

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A careful inspection of Table 3.1 will show that there are some building blocks that are not derived from cubic volume elements. These are the BOOM, PLATE, PATCHR and PATCHW.

BOOMs are long cylindrical projections that may have an arbitrary radius. They may only lie along the X, Y, or Z directions. Unlike any of the other building blocks they may extend beyond the innermost grid.

PLATEs are arbitrarily thin cuboids (RECTANS). They are assumed to have only a top and a bottom, the sides being of negligible height. They always lie in one of the axis planes (XY, XZ, YZ).

PATCHR and PATCHW are the surfaces only of a cuboid and wedge, respectively. They are used to change the surface material patterns of existing building blocks and should never be defined in spaces not already occupied by solid objects. (Objects defined to occupy the same space are explained in Section 4.7.)

### **OBJECT DEFINITION—FILE 20**

All integer input-except for "radius" and "materialname." See NASCAP Users Manual for information on material parameters.

OBJECT DEFINITION SYNTAX	OBJECT DEFINITION EXAMPLES
RECTAN CORNER x y z DELTAS Δx Δy Δz (UP TO 6 SURFACE CARDS) ENDOBJ	RECTAN CORNER 3 -2 8 DELTAS 1 2 4 SURFACE + X ALUMINUM SURFACE - X ALUMINUM SURFACE - Y ALUMINUM SURFACE + Z ALUMINUM SURFACE - Z ALUMINUM SURFACE - Z ALUMINUM
WEDGE CORNER x y z FACE materialname normal (type 110) LENGTH Δx Δy Δz (UP TO 4 SURFACE CARDS) ENDOBJ	WEDGE CORNER -3 2 1 FACE SIO2 -1 -1 0 LENGTH 1 1 3 SURFACE +X SIO2 SURFACE +Y SIO2 SURFACE +Z GOLD SURFACE -Z SIO2 ENDOBJ

TETRAH CORNER x y z. FACE materialname normal (type 111) LENGTH **A**x (UP TO 3 SURFACE CARDS) ENDOBJ

OCTAGON AXIS x y z x' y' z' WIDTH w SIDE s (UP TO 3 SPECIAL SURFACE CARDS "+". "-". or ..C..) ENDOBJ

#### BOOM

AXIS x y z x' y' z' RADIUS radius (floating point) SURFACE materialname ENDOBJ

OSPHERE CENTER x y z DIAMETER d SIDE s MATERIAL materialname ENDOBJ

MUM NUM NUM NUM NUM NUM TETRAH CORNER -3 -2 8 FACE KAPTON 1 1 -1 LENGTH 2 SURFACE - X TEFLON SURFACE - Y KAPTON SURFACE + Z TEFLON ENDOBJ OCTAGON AXIS 3, 2, -6 3. 2, -9 WIDTH 3 SIDE 1 SURFACE + SILVER SURFACE - SILVER SURFACE C MAGNES ENDOBJ BOOM AXIS 0, 6, 0 0, 12, 0 RADIUS 25 SURFACE ALUMINUM ENDOBJ **OSPHERE CENTER 0, 0, 0** DIAMETER 4 SIDE -2 MATERIAL NPAINT

ENDOBJ

#### **OBJECT DEFINITION OBJECT DEFINITION** SYNTAX **EXAMPLES**

#### FIL111 CORNERLINE x y z x' y' z' FACE materialname normal (type 111) ENDOBJ

PLATE CORNER x y z DELTAS Δx Δy Δz TOP  $\pm \begin{pmatrix} x \\ y \end{pmatrix}$  materialname

BOTTOM  $\pm \begin{pmatrix} x \\ y \end{pmatrix}$  materialname ENDOBJ

PATCHR CORNER x y z DELTAS Δx Δy Δz (UP TO 6 SURFACE CARDS) ENDOBJ

PATCHW CORNER x y z FACE materialname normal (type 110) LENGTH AX AY AZ (UP TO 4 SURFACE CARDS) ENDOBJ

FIL111 CORNER 3. 2, 6, -5, 4, 6 FACE SOLAR -1. -1. -1 ENDOBJ

PLATE CORNER -1 -1 -10 DELTAS 2 2 0 TOP + Z CPAINT BOTTOM - Z CPAINT ENDOBJ

PATCHR CORNER 3 -2 8 DELTAS 1 0 1 SURFACE -Y SCREEN ENDOBJ

PATCHW CORNER - 3 2 7 FACE AQUADG -1 -1 0 LENGTH 1 1 1 ENDOBJ

NOTES: "normal" is three values. each either +1, 0, or -1SURFACE CARD has the following format: SURFACE ± (Ŷ ) materialname

SPECIAL SURFACE CARD is: SURFACE (È) materialname

#### OTHER OBJECT DEFINITION COMMANDS

ENDSAT COMMENT OFFSET i j k CONDUCTOR n

DELETE 11 K unrecognized word

Must be last card in file. No effect. Moves coordinate origin. Sets number of underlying conductor (1<u>< n ≤ 15).</u> Deletes surfaces, leaving empty cell. Assumed to be name of new surface material. Next card scanned for parameters.

### 3.7 FIL111 AND TRANSPARENT ANTENNA SURFACES

#### 3.7.1 FIL111

FIL111 is a special shape designed to fill in "steps" whose corner line runs at 45° to the grid lines in any axis plane (i.e., XY, ZY, XZ) (Figure 3.6a). There are two kind of "steps" that can occur between NASCAP building blocks. For example, a small cuboid on top of another creates four "steps" that lie along grid lines (Figure 3.6b). These may be "filled in" or smoothed by defining a WEDGE to lie along the <u>corner line</u> of the step. A second type of step is possible however when, for example, a tetrahedron or octagon is defined to sit on top of another building block. These steps have corner lines that run at 45° between grid lines. This is shown in Figure 3.6c. Such steps can be smoothed or filled in by a combination of tetrahedra and truncated cubes. This combination is supplied as the building block FIL111.

#### 3.7.2 TRANSPARENT ANTENNA SURFACES

Antenna surface cells may be square (defined by the PLATE subroutine), rectangular (defined by the ASLANT subroutine), or equilateral triangle (defined by the ATET subroutine). No provision is made for right triangle antenna cells. Antenna surface cells are automatically treated as two-sided by NASCAP; only one side of the surface should be defined. Antenna surfaces should not be used to supersede solid surfaces, although solid surfaces may supersede antenna surfaces. Mesh surfaces are marked by bit 4 of the surface cell word (equivalent to adding 16 to the material number). HIDCEL draws the cell outlines of antenna cells, except, of course, where they are shadowed by solid objects. For line-plot devices such drawings can be a bit messy; plots are far better on color-fill devices. For material plots, mesh surfaces are treated as non-transparent.



Figure 3.6a. A FIL111 building block all by itself.



Figure 3.6b. "Steps" along grid lines.



Figure 3.6c. "Steps" along 45° angle lines.

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3.8 BUILDING BLOCK PARAMETERS (OR WHO'S ON NEXT?)

The very center of the 17 x 17 x 33 inner grid is assumed to be the origin of the coordinate system 0, 0, 0. Hence the grid itself extends from -8 to +8 in the X and Y directions and from -16 to +16 in the Z direction. This coordinate system is used to specify the position and size of the building blocks in the parameter "cards" or lines following the building block keyword. Let us examine the definition of each building block in detail to see how this works.

3.8.1 RECTAN

The following cards define a cuboid or rectangular parallelepiped:

RECTAN CORNER x y z DELTAS  $\Delta x$ ,  $\Delta y$ ,  $\Delta z$ SURFACE +X GOLD SURFACE -Y KAPTON (Four more SURFACE cards for -X, +Y, +Z, -Z) ENDOBJ

Notes:

- 1. RECTAN: is the building block keyword.
- 2. CORNER x y z: defines the coordinate of the lowest indexed corner of the cuboid (the one so that if you added up x + y + z it would give the lowest (least positive) number).
- 3. DELTAS  $\Delta x$ ,  $\Delta y$ ,  $\Delta z$ : gives the length of sides of the cuboid along the X, Y and Z axes. (Note that the edges of the cuboid must lie in the direction of the three axes.)
- 4. SURFACE +X GOLD: assigns the material GOLD (see Chapter 4) to the surface of the cuboid whose normal points in the +X direction. There are up to six surfaces that may be assigned materials (+X, -X, +Y, -Y, +Z, -Z). All surfaces that will eventually become a surface of the finished object (rather than become a connection to another building block) <u>must</u> be assigned a material. (For surfaces that are shared with other building blocks the material assigned is ignored.)

As an example, the following cards:

RECTANCORNER-42-1DELTAS325SURFACE+XGOLDSURFACE+YGOLDSURFACE+ZGOLDSURFACE-XGOLDSURFACE-YGOLDSURFACE-ZGOLDSURFACE-ZGOLDENDOBJ

define a gold bar extending from -4 to -1 in the X direction, 2 to 4 in the Y direction and -1 to +4 in the Z direction (Figure 3.7).

3.8.2 PATCHR

PATCHR is defined in exactly the same way as RECTAN. PATCHR CORNER x y z DELTAS Δx Δy Δz <SURFACE card(s) (usually just one)> {e.g., SURFACE +X GOLD ENDOBJ

PATCHR should only be defined within an existing object (see 4.7).



Figure 3.7. RECTAN.

3.8.3 WEDGE

The following cards define a right angled wedge: WEDGE CORNER x y z FACE KAPTON 1 1 0 LENGTH Δx Δy Δz {SURFACE +X TEFLON {Up to four SURFACE cards> ENDOBJ

Notes:

- 1. WEDGE: is the building block keyword.
- 2. CORNER x y z: defines the lowest indexed vertex of the right angled corner of the wedge (see note 2, 3.8.1).
- 3. FACE KAPTON 110: contains two pieces of information:

a. 'KAPTON' assigns the material KAPTON to the surface of the face of the wedge. (The face is the sloping surface of the wedge.)

b. '1 1 O' defines the direction of the normal to the face and hence the orientation of the wedge itself. The normal may point in any of the following directions only:

 $\begin{array}{c} \pm 1, \ \pm 1, \ 0\\ \pm 1, \ 0, \ \pm 1\\ 0, \ \pm 1, \ \pm 1 \end{array}$ 

(For those of you not familiar with the '1 1 0' notation a '1 1 0' normal is a vector pointing to the coordinates X = 1, Y = 1 and Z = 0 from the origin.)

4. LENGTH  $\Delta x$ ,  $\Delta y$ ,  $\Delta z$ : gives the lengths of the sides of the wedge parallel to the X, Y and Z axes. To maintain symmetry two of these must be equal (i.e., the two right triangle sides).

5. SURFACE +X TEFLON: assigns the material 'TEFLON' (Chapter 4) to the surface whose normal points in the positive X direction. There are up to four remaining surfaces that may be assigned materials (see 3.8.1, note 4). These all have normals pointing along one of the axis directions. Along which axis direction they point depends on the orientation of the wedge or the choice of normal for the face (note 2). The possible combinations of face directions and remaining surface directions are summarized in Table 3.3. Cards defining materials for non-existent faces are ignored.

As an example, the following cards:

```
WEDGE
CORNER 0 0 0
FACE GOLD 1 1 0
LENGTH 2 2 2
SURFACE -X GOLD
SURFACE -Y GOLD
SURFACE +Z GOLD
SURFACE -Z GOLD
ENDOBJ
```

define a wedge covered in gold with the origin as one of its corners and a face whose normal points between the X and Y axes in the XY plane. This is shown in Figure 3.8.

3.8.4 PATCHW

PATCHW is defined in exactly the same way as a wedge.
PATCHW
CORNER x y z
FACE GOLD 1 -1 0
LENGTH Δx Δy Δz
<Up to four SURFACE cards (usually just one)>
ENDOBJ

Like PATCHR (3.8.2) it may only be used to define a wedge inside another building block. This is explained further in Section 4.7.

# TABLE 3.3. DIRECTIONS OF SURFACE NORMALS ASSOCIATED WITH ALLOWED WEDGE ORIENTATION

Normal of WEDGE Face	Normals of Four Remaining Surfaces
1 1 0	-X, -Y, Z, -Z
-1 1 0	X, -Y, Z, -Z
1 -1 0	-X, Y, Z, -Z
-1 -1 0	X, Y, Z, -Z
1 0 1	-X, Y, -Y, -Z
-1 0 1	X, Y, -Y, -Z
1 0 -1	-X, Y, -Y, Z
-1 0 -1	X, Y, -Y, Z
0 1 1	X, -X, -Y, -Z
0 -1 1	X, -X, Y, -Z
0 1 -1	X, -X, -Y, Z
0 -1 -1	X, -X, -Y, -Z

•



Figure 3.8. Wedge defined with surface normal 1,1,0 and corner 0,0,0.

The following cards define a tetrahedron: TETRAH CORNER x y z FACE ALUMINUM 1 1 -1 LENGTH AX SURFACE -X TEFLON SURFACE -Y TEFLON SURFACE +Z TEFLON ENDOBJ

Notes:

- 1. TETRAH is the building block keyword.
- 2. CORNER x y z: defines the coordinates of the right angled corner of the tetrahedron. There is only one of these. (It corresponds to the corner of the partially filled cubic volume element that is actually filled.)
- 3. FACE 1 1 -1: assigns the material ALUMINUM to the unique face of the tetrahedron opposite the right angled corner. '1 1 -1' gives the direction of this face's surface normal and hence the orientation of the tetrahedron. The following directions only are allowed:

<u>+1, +1, +1</u>

(This notation is the same as explained in 3.8.3, note 3.)

- 4. LENGTH  $\Delta x$ : gives the length of the sides along the X, Y and Z axis directions. (These must all be equal to preserve symmetry.)
- 5. SURFACE -X TEFLON: assigns the material teflon to the remaining surface with surface normal pointing along the negative X axis direction. Up to three surfaces remain to be assigned materials (see 3.8.1, note 2). The surface normals of these surfaces depend on the orientation of the tetrahedron and hence the normal of the "face". Table 3.4 summarizes these relationships. Definitions of non-existent surfaces are ignored.

## TABLE 3.4. DIRECTIONS OF SURFACE NORMALS ASSOCIATED WITH ALLOWED TETRAHEDRON ORIENTATIONS

-

Normal of TETRAHedron Face	Normals of Three Remaining Surfaces
1 1 1	-X, -Y, -Z
-1 1 1	X, -Y, -Z
1 -1 1	-X, Y, -Z
1 1 -1	-X, -Y, Z
-1 -1 1	X, Y, -Z
-1 1 -1	X, -Y, Z
1 -1 -1	-X, Y, Z
-1 -1 -1	X, Y, Z

As an example, the following cards:

```
TETRAH
CORNER 0 0 0
FACE KAPTON 1 1 1
LENGTH 2
SURFACE KAPTON -X
SURFACE KAPTON -Y
SURFACE KAPTON -Z
ENDOBJ
```

define a tetrahedron with its right angle corner at the origin and the normal of the opposite face pointing between the positive X, Y and Z axes. This is shown in Figure 3.9.

### 3.8.6 OCTAGON

```
The following cards define a right octagonal cylinder:
OCTAGON
AXIS x y z x'y'z'
WIDTH w
SIDE s
SURFACE + GOLD
SURFACE - GOLD
SURFACE C GOLD
ENDOBJ
```

Notes:

- 1. OCTAGON: is the building block keyword.
- 2. AXIS x y z x' y' z': defines both the direction of the symmetry axis and the height of the cylinder. The symmetry axis must be parallel to one of the axis directions. Thus two of the coordinate pairs (x, x'), (y, y') and (z, z') must be identical. For example,


Figure 3.9. Tetrahedron defined with its "corner" at 000 and a surface normal 111.

'AXIS 6 3 -2 7 4 -2'

would define an axis that was not parallel to the X, Y or Z directions. However,

'AXIS 6 3 -2 7 3 -2'

defines an axis parallel to the X direction and is acceptable.

The height of the cylinder is given by the difference in coordinates along the axis direction. (For example, in the case above, the axis is one mesh unit long.)

- 3. WIDTH w: gives the width of the octagonal cross-section of the cylinder as w. If WIDTH is chosen to be odd, the axis must be moved or the sides of the cylinder will lie halfway across a volume element. NASCAP <u>automatically moves</u> the axis +1/2 a mesh unit in each direction in the plane perpendicular to it.
- 4. SIDE s: gives the length of one of the sides of the octagonal cross-section that lies in an axis direction. The symmetry relationship between the width and the sides of the cross-section is shown in Figure 3.10. To maintain this relationship the side must always be an even number of mesh units less than the width. This means that they both either must be odd or both even numbers of mesh units.
- 5. SURFACE + GOLD: assigns the material GOLD to the <u>top</u> surface of the cylinder. '-' and 'C' replacing the '+' assign surface materials to the bottom or side cylindrical surface, respectively. Only those surfaces that will eventually become surfaces of the completed object need be assigned a material.

As an example, the following cards:

OCTAGON AXIS 2 -4 6 2 -4 10 WIDTH 5 SIDE 3 SURFACE + TEFLON SURFACE - TEFLON SURFACE C TEFLON ENDOBJ

defines a right octagonal cylinder covered in teflon. The symmetry axis lies along the Z direction and the height of the cylinder is four mesh units. Because the WIDTH is odd the axis is imagined to pass through the point 2 1/2, -3 1/2 in the X Y plane. Hence the top and



Figure 3.10. Top of an OCTAGON.

bottom faces run from X = 0 to X = 5 and from Y = -6 to Y = -1. The coordinates of the top of the cylinder are shown in Figure 3.10. A three-dimensional view is shown in Figure 3.11.

3.8.7 QSPHERE

The following cards define a quasisphere: QSPHERE CENTER x y z DIAMETER d SIDE s MATERIAL SiO2 ENDOBJ

Notes:

- 1. QSPHERE: is the building block keyword.
- 2. CENTER x y z: defines the center of the sphere to be at coordinates X, Y, Z.
- 3. DIAMETER d: defines the diameter of the sphere to be d mesh units. The quasisphere can be thought of as an octagonal cross-section (like the top of an OCTAGON (see 3.8.6)) rotated about an axis in the cross-section plane. The diameter then corresponds to the WIDTH for a two-dimensional octagonal section. The same restrictions then apply: An odd value for the DIAMETER causes NASCAP to automatically move the CENTER by +1/2 a mesh unit in the X, Y and Z directions.
- 4. SIDE s: sets the length of a side lying in one of the axis planes (e.g., X Y plane). Like the OCTAGON, the SIDE and DIAMETER must differ by an even number of mesh units.
- 5. MATERIAL SIO2: assigns the material SIO2 to the whole sphere surface.

As an example, the following cards:

QSPHERE		
CENTER 1	-3	5
DIAMETER	7	
SIDE 3		
MATERIAL	SILV	ER
ENDOBJ		



Figure 3.11. OCTAGON.

define a silver sphere centered at 1 1/2, -2 1/2 and 5 1/2. The sphere extends along the axis direction as follows:

```
x from -2 to 5
y from -6 to 1
z from 2 to 9
(See Figure 3.12.)
3.8.8 FIL111
The following cards define a FIL111:
FIL111
CORNERLINE x y z x' y' z'
FACE KAPTON 1 -1 -1
ENDOBJ
```

Notes:

- 1. FIL111: is the building block keyword.
- 2. CORNERLINE x y z x' y' z': defines both the length and the direction of the "step" FIL111 is to fill. The line must lie in one of the axis planes (XY, XZ, YZ) and must have a direction lying 45° to two of the axes. This means that one pair of the coordinates (x', x), (y, y') (z, z') must be identical and the other two pairs must differ by the same magnitude. For example,

'CORNERLINE 1 2 3 4 5 6'

is unacceptable since all three coordinate pairs change. The following correct example

'CORNERLINE 1 2 3 -1 4 3'

defines a line in the XY plane (Z is constant) with  $\Delta x = -2$ , and  $\Delta y = +2$ . Hence the line is  $2\sqrt{2}$  units in length and runs at  $45^{\circ}$  between the positive Y axis and the negative X axis.

- 3. FACE KAPTON 1 -1 -1: assigns the material KAPTON to the exposed surfaces of the FIL111 and defines its orientation via the surface normal of its exposed face: 1 -1 -1. The surface normal can only be combinations of
  - <u>+1</u> <u>+1</u> <u>+1</u>



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Figure 3.12. QSPHERE.

Only certain choices of corner line direction are consistent with each choice of FACE normal. If we subtract the  $x \neq z$ , x'y'z' coordinates defined in corner line  $\Delta x = x' - x$  $\Delta y = y' - y$  $\Delta z = z' - z$ then the surface normal  $n_1 n_2 n_3$  (e.g., 1 1 1) must be orthogonal to  $\Delta x$ ,  $\Delta y$ ,  $\Delta z$ , i.e.,  $\Delta x \cdot n_1 + \Delta y \cdot n_2 + \Delta z \cdot n_3 = 0.$ With the choice 1 2 3 -1 4 3 for the corner line coordinates only  $1 \quad 1 \quad +1 \text{ or } -1 \quad -1 \quad +1 \text{ faces are permissible}$ , e.g., -2. -1 + 2. -1 + 0. +1 = 0.However, with -1 +1 +1 -2. -1 + 2.1 + 0. +1 = 4the vectors are not orthogonal and so are not allowed. As an example, the following cards: **FIL111** CORNERLINE 1 4 -6 1 7 -3 FACE GOLD -1 1 -1 ENDOBJ defines a FIL111 covered with gold smoothing a step with a corner line

running from 1 4 -6 in the YZ plane, between the positive Y and Z axis to 1 7 -3. The face of the FIL111 points in the negative X and Z directions and positive Y direction. (See Figure 3.13.)



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Figure 3.13. FIL111.

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The following cards define a PLATE:

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PLATE

CORNER X Y Z

DELTAS \Delta X \Delta Y \Delta Z

TOP \frac{+}{\begin{pmatrix} X \\ Y \\ Z \end{pmatrix}} ALUMIN

BOTTOM \frac{+}{\begin{pmatrix} X \\ Y \\ Z \end{pmatrix}} KAPTON
```

ENDOBJ

Notes:

- 1. PLATE: is the building block keyword.
- 2. CORNER x y z: defines the vertex of the thin plate with the lowest indices (see 3.8.1, note 2).
- 3. DELTAS  $\Delta x \quad \Delta y \quad \Delta z$ : defines the length of the plate along the three axis directions. A PLATE may be thought of as a cuboid (or RECTAN) (see 3.8.1) with zero thickness in one direction. Hence one of  $\Delta x$ ,  $\Delta y$  and  $\Delta z$  must be zero. For example, if  $\Delta y$  is chosen to be zero the PLATE will lie in the xz plane.
- 4.

TOP 
$$\pm \begin{pmatrix} X \\ Y \\ Z \end{pmatrix}$$
 ALUMIN:

assigns the material ALUMIN to the TOP surface of the plate. The "TOP" surface may be either in a + or - axis direction. This choice is arbitrary unless a "double point" conflict is possible. Double point conflicts are explained in Section 3.10.

5. BOTTOM  $\pm \begin{pmatrix} X \\ Y \\ Z \end{pmatrix}$  KAPTON:

assigns the material KAPTON to the other side of the plate. If "top" were chosen as +X then bottom must be -X, and so on. Note that the choice of x, y or z must coincide with the  $\Delta x$ ,  $\Delta y$  or  $\Delta z$  chosen to be zero.

As an example, the cards

PLATE CORNER 0 0 0 DELTAS 0 2 2 TOP -X TEFLON BOTTOM +X GOLD ENDOBJ

defines a 2 x 2 thin plate with gold on the +X side and teflon on the -X side lying in the YZ plane. (See Figure 3.14.)

3.8.10 BOOM

The following cards define a thin BOOM: BOOM AXIS x y z x' y' z' RADIUS 0.25 SURFACE SIO2 ENDOBJ

Notes:

1. BOOM: is the building block keyword.

AXIS x y z x' y' z': defines the length and orientation of the boom. x y z and x' y' z' are the coordinates of the beginning and end. They must be chosen so that the boom direction coincides with one of the axes.

BOOMS are the only building blocks that can extend into outer grids. This may be done in two ways.

a. The AXIS coordinates may be specified in inner grid units. For example

'AXIS 0 0 0 0 0 20'

defines a BOOM that ends at the +10 grid point of the second grid in the Z direction. (Recall that the second grid has twice the inner grid spacing.) Care must be taken, however, not to define the end of the boom <u>between</u> outer grid points. For example

'AXIS 0 0 0 0 0 21'



Figure 3.14. PLATE.

defines a boom that ends halfway between two second grid points and is illegal.

b. A second method avoids this problem. The same boom may be defined using two additional parameters or "grid numbers".

'AXIS 0 0 0 1 0 0 10 2'

This has the format

'AXIS x y z ng x' y' z' ng'

where ng is the starting grid number and ng' is the ending grid number.  $x \ y \ z$  are now in ng coordinates and  $x' \ y' \ z'$  are in ng' coordinates. Booms are not allowed to pass from outer grids <u>to</u> inner grids.

3. RADIUS 0.25: defines the radius of the thin cylindrical boom to be 0.25 mesh units. The radius may be any floating point number.

4. SURFACE SIO2: assigns the material SIO2 to the BOOM surface.

As an example, the following cards

BOOM AXIS -6 0 2 -6 0 32 RADIUS 0.1 SURFACE KAPTON ENDOBJ

define a boom along the X axis with radius 0.1 inner mesh units, covered with kapton. It runs from X = -6 in the inner mesh to X = -10in the third mesh. (See Figure 3.15).



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Figure 3.15. BOOM.

## 3.8.11 SQUARE ANTENNA MESH

Square (type [100]) mesh surfaces are defined using the PLATE module by replacing the TOP/BOTTOM specification by an ANTENNA card:

Syntax	Example			
PLATE	PLATE			
CORNER X1 X2 X2	CORNER	_4	-5	-6
DELTAS $d_1 d_2 d_3$	DELTAS	0	3	5
ANTENNA matl	ANTENNA	GOLD		
ENDOBJ	ENDOBJ			

Note that one of  $(d_1, d_2, d_3)$  must be zero, and the surface normal direction is not specified.

## 3.8.12 RECTANGULAR ANTENNA MESH

Rectangular (type [110]) mesh surfaces are defined using the ASLANT subroutine, which is syntactically similar to the WEDGE subroutine. It must be particularly noted that the CORNER is not located on (or even near) the mesh surface, but is the corner of the WEDGE of which the antenna surface would be the slanted face:

Syntax		Example		
ASLANT	AS	SLANT		
CORNER X1 X2 X2	CC	DRNER 5	-3	-3
FACE matl $n_1$ n	n F/	ACE KAPTON -1	0	1
LENGTH d <sub>1</sub> d <sub>2</sub> d <sub>2</sub>		NGTH 4	6	4
ENDOBJ	E	NDOBJ		

Note that the two  $d_i$ 's corresponding to nonzero  $n_i$ 's must be equal. ASLANT will not accept additional surface cards.

## 3.8.13 TRIANGULAR ANTENNA MESH

Equilateral triangle (type [111]) mesh surfaces are defined using the ATET subroutine, which is syntactically similar to the TETRAH subroutine. It must be particularly noted that the CORNER is not located on (or even near) the mesh surface, but is the corner of the TETRAH of which the antenna surface would be the slanted face:

S	Syntax	Examp	ole		
ATET		ATET			
CORNER	x <sub>1</sub> x <sub>2</sub> x <sub>3</sub>	CORNER	5	-3	5
FACE	matl n <sub>1</sub> n <sub>2</sub> n <sub>3</sub>	FACE AQUADG	-1	1	-1
LENGTH	d	LENGTH 3			
ENDOBJ		ENDOBJ			

ATET will not accept any additiinal surface cards.

## 3.8.14 EXAMPLES OF TRANSPARENT ANTENNA BLOCKS

Figures 3.16a-h show MATPLT and HIDCEL views of the examples given in subsections 3.8.11, 3.8.12, and 3.8.13.

FOR X VALUES BETHEEN 1 AND 17







FOR X VALUES BETHEEN 1 AND 17



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17. 16. 15. 14. 누 I**3**. 12. u. 10. 9. 8. 7. 6. Æ HHA 5. 4. 3. 2. 1. 11. 13. 15. 17. 19. 21. 23. 25. 27. 29. 31. 33. (b) 3. 5. 7. 9. ι. -z-





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17. 18. 15.

14. 14. 13. 12. 11. 10. 9. 8. 7. 6. 5. 4. 3. 2. 1.



7.

FOR Y VALUES BETWEEN 1 AND 17

-Z-

3. 5.

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HITTERIAL LESEDO

3 NOUN



9. 11. 13. 15. 17. 19. 21. 23. 25.

SURFACE CELL HATERIAL COMPOSITION AS VIENED FROM THE NEGATIVE Y DIRECTION



SURFACE CELL INTERTAL COMPOSITION AS VIENED FROM THE POSITIVE Y DIRECTION



27. 29. 31. 33.



Figure 3.16. (Continued)

SURFACE CELL HATERIAL COMPOSITION AS VIEWED FROM THE POSITIVE Z DIRECTION





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## 3.9 MORE OBJECT DEFINITION KEYWORDS

In addition to the building block keywords and the parameter cards that follow OBJDEF also recognizes a few other keywords. With these and the building blocks a complete <u>object definition file</u> can finally be constructed. This is discussed in Section 3.9. Let us examine the remaining keywords and their effect one by one. All of the OBJDEF keywords are summarized in Table 3.1.

#### 3.9.1 ENDSAT

Just as ENDOBJ terminates a set of building block parameter cards, so the keyword 'ENDSAT' terminates the whole object definition file. After reading an 'ENDSAT' card OBJDEF stops trying to read any more keywords from the object definition file and begins to process the information it has. Note that <u>ALL</u> object definition files <u>must</u> end with an 'ENDSAT' card.

#### 3.9.2 COMMENT

OBJDEF ignores anything written on the same 80 character line (or card) that begins with the keyword 'COMMENT'. This allows the user to include notes or reminders in long and complicated object definition files, e.g.,

> COMMENT DEFINE AXIAL BOOM BOOM AXIS -6 0 2 -8 0 2

## The card

## OFFSET x y z

relabels the grid center to be 9-x, 9-y, 17-z for a standard 17 x 17 x 35 inner grid. This result may seem rather startling until you realize that the so-called "absolute" NASCAP coordinate system labels the axes from 1 to 17 in the X and Y direction and 1 to 33 in the Z direction. In this "absolute system" the center of the grid, which we had previously labeled (0, 0, 0,) becomes (9, 9, 17). So we may move from the more intuitive 0, 0, 0 centered system to the "absolute" system with the command

OFFSET 0 0 0

To illustrate the difference the following two sets of cards define a sphere centered at the center of the grid.

Default coordinate system Absolute coordinate system

| QSPHERE         | 0FFSET 0 0 0    |
|-----------------|-----------------|
| CENTER 0 0 0    | QSPHERE         |
| DIAMETER 7      | CENTER 9 9 17   |
| SIDE 3          | DIAMETER 7      |
| MATERIAL KAPTON | SIDE 3          |
| ENDOBJ          | MATERIAL KAPTON |
|                 | ENDOBJ          |

The coordinate system may be adjusted with the OFFSET command anytime at any point between building blocks. The active system is always the default or the coordinate system defined by the most recent OFFSET. Not all inner grids need be 33 points long in the Z direction. The number of points may be chosen to be any integer of the form (4n+1),  $4 \le n \le 8$ , by the user as a run option (6.4.8). If the Z axis is chosen to be NZ points long then the default coordinate system runs from -(NZ-1)/2 (rounded down) to +(NZ-1)/2.

#### 3.9.4 CONDUCTOR

NASCAP allows for both insulating and conducting materials (Chapter 4). It assumes that all surface materials cover an underlying conductor. Up to 15 separate conductors are allowed. Each building block is associated with a particular conductor. This association is made by preceding all building block definitions associated with the first conductor with the card:

## CONDUCTOR 1

Similarly, blocks associated with a second conductor are preceded by the card

#### CONDUCTOR 2

and so on. If no CONDUCTOR card is included in the object definition file all building blocks will be associated with CONDUCTOR 1. In the same way any building blocks defined before OBJDEF encounters a card

CONDUCTOR n (n > 1)

will be associated with conductor 1. All subsequent blocks will be associated with conductor n, until another conductor card is encountered.

It is conventional to choose conductor 1 as the satellite ground conductor. Skipping conductor numbers is not recommended.

#### 3.9.5 DELETE

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DELETE allows the user to modify building blocks already defined by selectively "deleting" filled or partially filled cells (i.e., "deleting" them by making them empty).

#### DELETE x y z

empties the filled cell with the indices of its lowest index vertex given by x y z. (The lowest index vertex is the one with the sum of its X, Y and Z coordinates equal to the least positive number.) The coordinates x, y, z refer to the coordinate system presently active (i.e., the default system or that associated with the most recent OFFSET command). The DELETE command requires great care in its use.

It <u>does not</u> assign materials to surfaces that are newly exposed by the removal of a filled element. The user <u>must</u> do this by defining a new object or objects with surfaces that coincide with those newly exposed. This is most easily done by overlaying objects (4.8).

## 3.9.6 OTHER WORDS

Any other words that OBJDEF reads in the object definition file are assumed to be the names of new <u>materials</u> and OBJDEF then expects four more cards defining the material properties (4.4) to follow immediately.

## 3.10 SURFACE CELLS

The exposed faces of the filled volume elements (or of the partially filled portions of the partially filled elements) that make up an object are called the <u>surface cells</u>. Surface cells combine to form the surface area of the object. Each surface is characterized by the following information:

1. Index (number) of underlying conductor.

- X, Y, and Z coordinates of the volume cell with which it is associated.
- 3. The direction of its surface normal (in  $n_1$ ,  $n_2$ ,  $n_3$  notation, e.g, 1 -1 0).
- Material number (assigned to each material in order of their definition).

This information uniquely determines each surface cell. NASCAP assigns a number to each cell based on these properties. The cells are numbered sequentially from the lowest indexes to the highest, with property 4 changing most rapidly and property 1 least rapidly. This surface cell list is printed out by NASCAP.

Only four types of individual surface cells are possible. They are the faces of the four possible filled, or partially filled, volume elements. They are illustrated in Figure 3.17.



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Figure 3.17. Four types of surface cell

#### 3.11 DEFINING AN OBJECT

## 3.11.1 EXAMPLE: SOLID OBJECT

The input file of Figure 3.18 defines an object consisting of an ALUMINUM slab, trimmed with four KAPTON wedges and four TEFLON tetrahedra, and topped with a GOLD sphere. Three views of the resulting object are shown in Figure 3.19.

## 3.11.2 EXAMPLE: TRANSPARENT ANTENNA

Figure 3.20 is an object definition input showing how the three types of mesh cells may be joined together to make a dish-like antenna. HIDCEL plots of this object are shown in Figure 3.21. Figure 3.22 shows the same antenna mounted on a spacecraft.

| COMMENT ALUMINUM SLAE  | ٦ |                    |
|--|---|--------------------|
| CORNER -3 -4 -1<br>CELTAS 6 8 I<br>SURFACE +2 ALUMINUM<br>SURFACE -2 ALUMINUM<br>ENCORU<br>COMMENT FOUR KAPTON WEDGES        |   | CUBOID             |
| CORNER -3 -4 -1<br>FACE KAPTON -1 C 1<br>LENGTH 1 8 1<br>SURFACE -Z KAPTCN<br>ENDOEJ<br>WEDGE                                |   |                    |
| CORNER -3 -4 -1<br>FACE KAPTON C -1 1<br>LENGTH 6 1 1<br>SURFACE -2 KAPTCN<br>ENDOBJ<br>VEDGE                                |   | FOUR WEDGES        |
| CORNER 3 -4 -1<br>FACE KAPTON 1 0 1<br>LENGTH 1 8 1<br>SURFACE -Z KAPTON<br>ENDOBJ<br>WEDGE                                  |   |                    |
| CORNER -3 4 -1<br>FACE KAPTON 5 1 1<br>LENGTH 6 1 1<br>Surface -2 Kapton<br>Endorj<br>Comm <u>ent</u> four teflon tetrahedra |   |                    |
| TETRAHEDPON<br>CORNER -3 -4 -1<br>FACE TEFLON -1 -1 1<br>LENGTH 1<br>SURFACE -Z TEFLON<br>ENDORJ                             |   |                    |
| TETRAHEDPON<br>CORNER 3 -4 -1<br>FACE TEFLON 1 -1 1<br>LENGTH 1<br>SURFACE -Z TEFLON<br>ENDOBJ                               |   | FOUR<br>TETRAHEDRA |
| TETRAHEDRON<br>CORNER 3 4 -1<br>FACE TEFLON 1 1 1<br>LENGTH 1<br>SURFACE -Z TEFLON<br>ENDOBJ                                 |   |                    |
| TETRAHEDRON<br>CORNER -7 4 -1<br>FACE TEFLON -1 1 1<br>LENGTH 1<br>SURFACE -Z TEFLON<br>ENDOBU                               |   |                    |
| CUMMENT ALL TOPPED BY A GOLD SPHERE<br>CSPHERE<br>CENTER C C 2<br>CIAMETER 4<br>SIDE 2<br>MATERIAL GOLD                      |   | SPHERE             |
| ENDSAT   |   |                    |

# Figure 3.18. Object definition example.

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1.... 1.2.3.4.5.67.8.9.0.1.2.3.4.5. 1.1.2.3.4.5.

16.

18.

<u>1</u> <u>1</u> ٠ 33.

40.41.42.

43. 45. 46. 48.

45555555555678931

62. 63. 64.

9.

74-1

c.2



| COMMENT | DISH ANTENNA<br>9 9 12  |
|---------|---|
|         | CORNER -2 -2 D<br>Deltas 4 4 C<br>Antenna gold<br>Endobj      |
| ASLANI  | CORNER 2 -2 3<br>Face Gold 1 C -1<br>Length 3 4 3<br>Endobj   |
| ASLANT  | CORNER -2 -2 3<br>FACE GCLD -1 G -1<br>LENGTH 3 4 3<br>ENDOPJ |
| ASLANT  | CORNER -2 -2 3<br>FACE GOLD 0 -1 -1<br>Length 4 3 3<br>Endorj |
| ATET    | CORNER -2 2 3<br>FACE GOLD D 1 -1<br>LENGTH 4 3 3<br>ENDOBJ   |
|         | CORNER 2 2 3<br>FACE GOLD 1 1 -1<br>LENGTH 3<br>ENDOBJ        |
| 4121    | COPNEP -2 2 3<br>Face Gold -1 1 -1<br>Length 3<br>Endobj      |
| ATET    | CORNER -2 -2 3<br>FACE GOLD -1 -1 -1<br>LENGTH 3<br>ENDOBJ    |
| ATET    | CORNER 2 -2 3<br>FACE GOLD 1 -1 -1<br>LENGTH 3<br>ENDOBJ      |
| ENDSAT  |   |

Figure 3.20. Object definition input for a dish-like antenna.











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Three views of the dish-like antenna (previous two figures) mounted on a spacecraft. Figure 3.22.

## 3.12 LIMITATIONS IN OBJECT DEFINITION

It is probably fair to say that you can link building blocks together and nine times out of ten there will not be a problem. This section deals with the other one time out of ten, when what appears to be a perfectly reasonable combination of building blocks is rejected by OBJDEF. We itemize here a rather formidable list of object definition "don'ts". However, you should remember that it takes hard work to break more than one or two of these rules defining any one object if you use a little common sense.

- 1. All exposed surfaces must be assigned materials.
- 2. The parameter cards for each building block, discussed in Section 3.8, must appear in the order shown, and no other.
- 3. No surface may lie in the planes that form the boundary of the inner mesh. Surfaces may touch the boundary planes at a point or line.
- 4. Booms may not lie in the boundary planes. Booms may cross a boundary plane but only from an inner to an outer grid and not vice versa.
- 5. Booms may not lie along the edges of filled or partially filled volume elements or pass through objects.
- 6. Two booms may not share the same volume element; i.e., two parallel booms must be at least two grid units apart, and two perpendicular booms may not intersect.
- 7. Thin plates sharing the same volume element can do so only if the TOP face of one shares volume with the TOP of the other, or the BOTTOM face of one shares volume with the BOTTOM face of the other. TOP faces may not share volume elements with BOTTOM faces.

- 8. Thin plates may only intersect each other at the edges or corners.
- Double points must be assigned TOP and BOTTOM sets (see Section 3.13).
- 10. A boom cannot share a volume element with the BOTTOM of a thin plate.

(Rules 7 through 10 are all manifestations of conflicts involving double and triple points.)

3.13 DOUBLE POINTS

Thin plates may have different potentials on their two surfaces, yet they occupy only one plane of grid points. These grid points must therefore be associated with two distinct sets of potentials. For this reason they are called <u>double points</u>. The two sets of potentials associated with each half of the double points are distinguished by calling one set 'TOP' and one set 'BOTTOM'. Recall (3.8.9) that the surfaces of a thin plate may be defined as 'TOP' or 'BOTTOM' regardless of whether their surface normal points along a positive or negative axis direction: The TOP and BOTTOM definition refers to the (arbitrary) choice of which set of potentials (TOP or BOTTOM) to associate with each surface. When double points share a volume element they must all be of the same type; i.e., all TOP or all BOTTOM. This is the basis for rule 7 in Section 3.12.

Double points also occur when other building blocks touch in such a way that their single points come together to form a common vertex of two "disjoint" volume elements. By "disjoint" volume elements we mean elements physically separated from each other by solid surfaces. This is shown for two cuboids touching along one edge only in Figure 3.23. The row of points along the touching edges are double points and one set must be defined as BOTTOM. This may be done by defining a thin plate touching the common edge. If the exterior surface of the plate pointing into one of the disjoint volumes is 'BOTTOM' then the half of the double point associated with the other disjoint volume becomes 'TOP'.



Figure 3.23. Profile of two cuboids sharing a common edge and resultant double points. Heavy lines show possible orientations for the definition of a thin plate to resolve the conflict.

Because of the way surface cell potentials are assigned to the grid points the edges of thin plates are only single points. However, a thin plate touching another building block (not BOOMs!) with its edge creates a row of double points similar to that caused by two cuboids touching at an edge (Figure 3.24). These double points are automatically assigned TOP and BOTTOM sets.

#### 3.14 TRIPLE POINTS

A triple point is said to occur when a vertex is common to three or more disjoint volume elements. Triple points are illegal! The easiest way to get a triple point is to define one thin plate passing through another. This is not allowed (rule 8, Section 3.12).

## 3.15 TECHNICAL DISCUSSION

Here we examine some of the technical details of how NASCAP actually calculates potentials, and treats volumes and surfaces. The casual user may wish to omit this section.

## 3.15.1 CONJUGATE GRADIENT POTENTIAL SOLVER

Consider a charged object isolated in space. The potential  $\phi$  everywhere is given by the solution to Poisson's equation

 $\nabla^2 \phi = -\rho/\epsilon \tag{3.1}$ 

The variational principle  $\begin{bmatrix} 2 \end{bmatrix}$  associated with this equation is given by:

$$\frac{\delta}{\delta \phi} \left[ \left( \int dV \frac{1}{2} (\nabla \phi)^2 + \frac{\rho \phi}{\epsilon} \right) + \int_{C_S} \frac{\sigma \phi}{\epsilon} ds + \int_{C_B} \phi \cdot \phi \cdot dS' \right] = 0$$



Figure 3.24. Examples of plates intersecting objects.
where we integrate over both the object and boundary surfaces (c\_S, c\_B).

To simplify things for the purpose of illustration, let us fix the potentials on these surfaces and assume zero charge density. The equation then simplifies to

$$\frac{\delta}{\delta \phi} \int dV \frac{1}{2} \left( \nabla \phi \right)^2 = 0 \tag{3.2}$$

Equation (3.2) involves an integral over the volume of the computational space. One way to treat this integral is to divide the space up into finite cubic volume elements.

$$\int dV \frac{1}{2} (\nabla \phi)^{2} = \sum_{e} \int_{V_{e}} dV_{e} \frac{1}{2} (\nabla \phi)^{2}$$

In this approach the potential  $\phi$  is defined at each grid point, or node, defining the vertices of the elements. The potential inside each element is then trilinearly interpolated from the values of each of its eight vertices.

$$\phi^{e}(x,y,z) = \sum_{i \in e} N_{i}^{xyz} \phi_{i}$$

where "i" are the nodes of element "e"

$$\nabla \phi^{e}(x,y,z) = \sum_{i} \nabla N_{i}^{xyz} \phi_{i}$$

and

$$\int dV \frac{1}{2} (\nabla \phi)^2 = \sum_{e} \int dV_{e} \left| \sum_{i} \nabla N_{i}^{e}(x,y,z) \phi_{i} \right|^2$$

The quantity

$$W_{ij}^{e} = \int_{e} dV_{e} \nabla N_{i}^{xyz} \cdot \nabla N_{j}^{xyz}$$
(3.3)

is completely defined just by knowledge of the shape of the element "e" (i.e., whether the cube is empty or partially filled). The variational principle therefore becomes:

$$\frac{\delta}{\delta \phi} \left[ \sum_{j} \sum_{i} \sum_{e} W_{ij}^{e} \phi_{i} \phi_{j} = 0 \right]$$
(3.4)

Let 
$$\sum_{e} W_{ij}^{e} = M_{ij}$$
. Equation (3.4) becomes

$$\frac{\delta}{\delta \emptyset} \left[ \sum_{ij} \phi_i M_{ij} \phi_j \right] = 0 = \underset{\approx}{\mathbb{M}} \underset{\approx}{\emptyset}$$

Thus the set of  $\phi$  values at each node ( $\phi$ ) that satisfy M  $\phi$  is the solution to the Poisson equation (3.1) under conditions  $\tilde{of}$  fixed object and boundary potentials and zero charge density.

 $\underset{\approx}{\overset{\mathsf{M}}{\sim}} \overset{\mathsf{g}}{=} - \underset{\sim}{\overset{\mathsf{r}}{\sim}}$ 

The iterative scheme used is the Scaled Conjugate Gradient technique. It is based on the following equations:<sup>[3]</sup>

$$r_{0} = -\frac{M}{2} p_{0}$$

$$D_{ij} = |M_{ij}|^{-1/2} \delta_{ij}$$

$$r_{s}^{0} = p_{s} r_{0}$$

$$u_{s}^{0} = r_{s}^{0}$$

$$M_{\approx} = D M D_{\approx} S \approx \pi$$
  
Then solve iteratively:

$$a_{s}^{i} = (r_{s}^{i}, r^{i})/(u_{s}^{i}, M_{s} u_{s}^{i})$$

$$(D^{-1}p)^{i+1} = (D^{-1}p)^{i} + a_{s}^{i} p_{s}^{i}$$

$$r_{s}^{i+1} = r_{x}^{i} - a_{s}^{i} M_{s} u_{s}^{i}$$

$$b_{s}^{i} = (r_{s}^{i+1}, r_{s}^{i+1})/(r_{s}^{i}, r_{s}^{i})$$

$$u_{s}^{i+1} = r_{s}^{i+1} + b_{s}^{i} u_{s}^{i}$$

until |r| reaches a small value and the resultant p vector:

$$p^{n} = D \left( D^{-1} p \right)^{n}$$

becomes the solution to Poisson's equation.

The major computational operation in the iterative set of equations is the evaluation of the matrix-vector product M u. The

vectors p, u, and r all have the same number of elements as the number of grid points. M contains the square of this number. Such a huge array is impractical to store all at once and so M u is evaluated using the following implicit algorithm

$$r_{a} = \sum_{e} r_{e} = \sum_{e} w_{a}u_{a}$$

The residual r is constructed element by element (where the  $w_{ee}$  matrix is only 8 x 8) and then summed. The 8 x 8 "weight" matrices  $w_{e}$  may be calculated analytically for each type of empty or  $\tilde{z}e$  partially filled volume element, allowed by NASCAP. There are five of these. Filled cells are not included in the potential calculation. This is how NASCAP treats filled, partially filled and empty elements, differently.

The five standard cells are summarized below.

(Format) Description Standard Orientation

-

-

Potential Function =  $\sum_{i} N^{i} \phi_{i}$ 

Weight Matrix,  $W_{ij}$ :  $\int d\Omega |\nabla \phi|^2 = \sum_{ij} W_{ij} \phi_i \phi_j$ 

| <u>Point Index</u> | Cube Corner |
|--------------------|-------------|
| 1                  | 000         |
| 2                  | 100         |
| 3                  | 010         |
| 4                  | 1 1 0       |
| 5                  | 001         |
| 6                  | 101         |
| 7                  | 0 1 1       |
| 8                  | 1 1 1       |



Standard Cell O Empty trilinear cube Orientation: Arbitrary Potential Function:

| N <sup>i</sup>  |
|-----------------|
| (1-x)(1-y)(1-z) |
| (1-z)(1-y)x     |
| (1-x)y(1-z)     |
| (1-z)yx         |
| z(1-y)(1-x)     |
| x(1-y)(z)       |
| zy(1-x)         |
| хуz             |
|                 |

| W <sub>ij</sub> |   |
|-----------------|---|
|                 | 4 |

| 1/3   |       |       |       |       |       |     |     |
|-------|-------|-------|-------|-------|-------|-----|-----|
| 0     | 1/3   |       |       |       |       |     |     |
| 0     | -1/12 | 1/3   |       |       |       |     |     |
| -1/12 | 0     | 0     | 1/3   |       |       |     |     |
| 0     | -1/12 | -1/12 | -1/12 | 1/3   |       |     |     |
| -1/12 | 0     | -1/12 | -1/12 | 0     | 1/3   |     |     |
| -1/12 | -1/12 | 0     | -1/12 | 0     | -1/12 | 1/3 |     |
| -1/12 | -1/12 | -1/12 | 0     | -1/12 | 0     | 0   | 1/3 |
|       |       |       |       |       |       |     |     |

Standard Cell 1 Half-Empty Wedge 1 < x + y < 20 < z < 1 Orientation: Right angle along line 4-8 Potential Function: N<sup>i</sup> i 1 0 2 (1-y)(1-z)3 (1-x)(1-z)4 (x+y-1)(1-z)5 0 (1-y)z 6 (1-x)z 7 8 (x+y-1)z



| W |   |   |
|---|---|---|
|   | ٦ | J |

| 0 |       |       |       |   |      |      |
|---|-------|-------|-------|---|------|------|
| 0 | 1/4   |       |       |   |      |      |
| 0 | 1/24  | 1/4   |       |   |      |      |
| 0 | -1/8  | -1/8  | 5/12  |   |      |      |
| 0 | 0     | 0     | 0     | 0 |      |      |
| 0 | 0     | -1/24 | -1/8  | 0 | 1/4  |      |
| 0 | -1/24 | 0     | -1/8  | 0 | 1/24 | 1/4  |
| 0 | -1/8  | -1/8  | -1/12 | 0 | -1/8 | 5/12 |
|   |       |       |       |   |      |      |

| St  | andard Ce | 11 2       |           |                |          |           |         |         |  |
|-----|-----------|------------|-----------|----------------|----------|-----------|---------|---------|--|
| Cu  | be with d | liagonal 1 | ine on on | e face         |          |           |         |         |  |
| 0r  | ientation | : Line f   | rom 2 to  | 3              |          |           | Z       |         |  |
| Po  | tential F | unction:   |           |                |          |           |         | $\sim$  |  |
|     |           | i          |           | N <sup>T</sup> |          |           |         |         |  |
|     |           | 1          |           | (1-            | -x-y)(1- | -z)e(1-x- | -у)     |         |  |
|     |           | 2          |           | [x             | (1-x-y)  | +(1-y)ə   | (x+y_1) | )](1-z) |  |
|     |           | 3          |           | [у             | (1-x-y)  | +(1-x)ə   | (x+y_1) | )](1-z) |  |
|     |           | 4          |           | ( x+           | •y_1)(1- | ·z)ə(x+y- | -1)     |         |  |
|     |           | 5          |           | (1-            | -x)(1-y) | z         |         |         |  |
|     |           | 6          |           | x(]            | l-y)z    |           |         |         |  |
|     |           | 7          |           | (1-            | -x)yz    |           |         |         |  |
|     |           | 8          |           | xyz            | Z        |           |         |         |  |
| Ψ.  | .:        |            |           |                |          |           |         |         |  |
| "i, | 5/12      |            |           |                |          |           |         |         |  |
|     | -1/8      | 1/2        |           |                |          |           |         |         |  |
|     | -1/8      | 1/12       | 1/2       |                |          |           |         |         |  |
|     | 0         | -1/8       | -1/8      | 5/12           |          |           |         |         |  |
|     | 7/360     | -37/360    | -37/360   | -23/360        | 1/3      |           |         |         |  |
|     | -11/180   | -1/45      | -19/180   | -11/180        | 0        | 1/3       |         |         |  |
|     | -11/180   | -19/180    | -1/45     | -11/180        | 0        | -1/12     | 1/3     |         |  |
|     | -23/360   | -37/360    | -37/360   | 7/360          | -1/12    | 0         | 0       | 1/3     |  |



Standard Cell 3 Tetrahedron 2 < x + y + z < 3Orientation: Empty corner at point 8 Potential Function: N<sup>i</sup> i 0 1 2 0 3 0 4 1-z 5 0 6 1-у 1-x 7 8 x+y+z-2





٩,

| Standa                 | rd Cell 4 | ļ          |          |                |           |       |      |
|------------------------|-----------|------------|----------|----------------|-----------|-------|------|
| Trunca                 | ted Cube  |            |          |                |           |       |      |
| Orient                 | ation: (  | )00 corner | (point 1 | ) missing      | •         |       |      |
| Potent                 | ial Funct | tion:      |          |                |           |       |      |
|                        | i         |            |          | N <sup>ĩ</sup> |           |       |      |
|                        | 1         |            |          | 0              |           |       |      |
|                        | 2         |            |          |                |           |       |      |
|                        | 3         |            |          |                |           |       |      |
|                        | 4         |            |          | exercis        | se for re | eader |      |
|                        | 5         |            |          |                |           |       |      |
|                        | 6         |            |          |                |           |       |      |
|                        | . 7       |            |          |                |           |       |      |
|                        | 8         |            |          |                |           |       |      |
|                        |           |            |          |                |           |       |      |
| W <sub>ij</sub> :<br>0 |           |            |          |                |           |       |      |
| 0                      | 5/12      |            |          |                |           |       |      |
| 0                      | 1/72      | 5/12       |          |                |           |       |      |
| 0                      | -11/120   | -37/360    | 13/36    |                |           |       |      |
| 0                      | 1/72      | 1/72       | -1/9     | 5/12           |           |       |      |
| 0                      | -37/360   | -1/9       | -7/180   | -11/120        | 13/36     |       |      |
| 0                      | -1/9      | -11/120    | -7/180   | -37/360        | -7/180    | 13/36 |      |
| 0                      | -5/36     | -5/36      | 1/45     | -5/36          | 1/45      | 1/45  | 7/20 |

Additional Standard Cells:

Standard cell 5 (not treated by NASCAP/GEO) is a cube divided into two wedges by a slanted thin plate. In standard orientation, the "top" half corresponds to the empty portion of standard cell 1.

Standard cell 6 is a cube divided into two wedges by a slanted rectangular transparent antenna cell. It is treated by the potential solver as two complementary type 1 cells.

Cells containing equilateral triangle antenna surfaces are treated by the potential solver as empty (type 0) cells.

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Information concerning each volume element is stored in file ILTBL (Chapter 2). Each entry is bit coded as follows:

|       | CODE F   | OR ELEMENT TABLE [LTBL(NX,NY,NZ)]                                 |
|-------|----------|---|
| 5 43  | 2 109876 | 54321 0 9 8 7 65 432109876 5 43210                                |
| ł     | 4        | G FEDC B A  |
| Field | Bits     |   |
| Α     | 4-0      | Elt-type code   |
|       | 5.       | (Not used)  |
| В     | 14-6     | Orientation code  |
|       | 16–15    | (Not used)  |
| С     | 17       | Set for cells bordering the "TOP" surface of a "PLATE"            |
| D     | 18       | Set if elt is completely filled (interior)                        |
| E     | 19       | Set for an empty special (type 2) elt                             |
| F     | 20       | Set for cells bordering the "BOTTOM" surface of a "PLATE"         |
| G     | 31–21    | Index used to reference BEAMJ array to determine emitter currents |
| Н     | 34-32    | Number of surfaces pointing into volume cell                      |

#### ORIENTATION CODE

The orientation code is a nine-bit (three octal digit) code describing how a non-symmetric element may be transformed into its "standard" orientation. The transformation (consisting of rotations, inversions, and translations) to the "standard" orientation is that transformation which takes vector <u>r</u> into vector <u>s</u>, where

r = (x, y, z) $s = (q(i_1), q(i_2), q(i_3))$ 

 $i_{1} \text{ is the octal digit in bits 14-12}$   $i_{2} \text{ is the octal digit in bits 11-9}$   $i_{3} \text{ is the octal digit in bits 8-6}$   $q(1) = x \qquad q(5) = 1-x$   $q(2) = y \qquad q(6) = 1-y$   $q(3) = z \qquad q(7) = 1-z$ For example, the octal code 365 implies the transformation  $s = \begin{pmatrix} 0 & 0 & 1 \\ 0 & -1 & 0 \\ -1 & 0 & 0 \end{pmatrix} r + \begin{pmatrix} 0 \\ 1 \\ 1 \end{pmatrix}$ 

#### 3.15.4 SURFACE CELL POTENTIALS

The potentials, charge densities, etc. are stored in 17 x 17 x 33 arrays for each grid, with an entry for each grid point in free space. In addition, a separate list of potentials for each surface cell is kept (Table 2.6). The entries in the potential array for the grid points lying on the surface of the object are calculated determined by the potentials in the surface potential list. Each grid point belonging to a surface cell is assigned an "area weighted" proportion of that cell's potential. The final potential of the grid point is then the sum of contribution from all the surface cells touching it. The area weights are given by the area of the cell divided by the number of points defining the area; e.g., a point at the corner of a square cell has a weight of 0.25.

## 3.15.5 SURFACE CELL LIST

In addition to an element table list, bit-coded information concerning each surface cell is stored in array JSURF, the surface cell test. (This resides in random access file ICNOW, see Chapter 2.) The bit coding convention is shown in Figure 3.25.

|   | 5    | 43 | 2109        | 87654              | 321098                | 765432                | 109876                 | 5<br>       | <b>4</b><br> | 3210                  |   |
|---|------|----|-------------|--------------------|-----------------------|-----------------------|------------------------|-------------|--------------|-----------------------|---|
|   |      | Н  | G           | F                  | Ε                     | D                     | C                      | В           | AA           | Α                     |   |
| F | ield |    | <u>Bits</u> |                    |                       |                       |                        |             |              |                       |   |
|   | A    |    | 3–0         | Materia            | lindex                |                       |                        |             |              |                       |   |
|   | AA   |    | 4           | Set for            | transpar              | ent anten             | na surfac              | e           |              | -                     |   |
|   | В    |    | 5           | Set for<br>surface | right-tr<br>s whose e | iangular<br>enclosing | 100 surfa<br>volume ce | ces<br>11 i | and<br>s mos | for 111<br>stly empty | у |
|   | С    |    | 11–6        | Direction notation | on of sur<br>n)       | face norm             | al (in cr              | ysta        | llog         | raphic                |   |
|   | D    |    | 17–12       | Z-coord            | inate                 |                       |                        |             |              |                       |   |
|   | E    |    | 23–18       | Y-coord            | inate                 |                       |                        |             |              |                       |   |
|   | F    |    | 28-24       | X-coord            | inate                 |                       |                        |             |              |                       |   |
|   | G    |    | 32–29       | Conduct            | or index              |                       |                        |             |              |                       |   |
|   | H    |    | 34-33       | Orienta            | tion code             | e for righ            | it-triangu             | lar         | 100          | surfaces              |   |
|   |      |    |             |                    |                       |                       |                        |             |              |                       |   |

Figure 3.25. Surface cell list (JSURF) entry format.

#### Notes:

A - Gives the material number. Materials are numbered sequentially as encountered in the object definition file. Up to 15 materials are actually allowed (leaving one bit spare).

- C Two bits are taken for each crystallographic index. The rightmost of the pair for 1, 0, the leftmost for <u>+</u> (set for minus).
- D,E,F The X, Y, Z coordinates refer to the lowest index or vertex of the associated volume cell (the one whose sum of X, Y, Z coordinates would be least positive). The associated volume cell is the cell containing a slanted surface, or out of which the surface points.
- G Conductor number from 1 to 15.
- H The two bits define the location of the right angled corner in the plane of the triangle, i, j.



The rightmost bit refers to j. If i and j are related to the direction of the surface normal as follows

| <u>Normal</u> | i | <u>j</u> |  |
|---------------|---|----------|--|
| Z             | X | Y        |  |
| X             | Y | Z        |  |
| Y             | Z | x        |  |

#### 3.15.6 GEOMETRICAL ANALYSIS OF OBJECTS

Following completion of an object definition, NASCAP automatically invokes the routine GENMTL to perform a detailed geometrical analysis of the defined object. Among the functions performed are:

- Verifying that every edge (of a surface cell) has a surface on either side.
- 2. Determining multiple-defined points. (Consider a path connecting surface cells of which the point is a vertex and circumnavigating the point. If there is only one such path, the point is a "single" point. If two paths, it is a "double" point. More than two paths make the point illegal.) When double points are found, it is verified that there is no ambiguity between "top" and "bottom".

When object definition errors are found, a message is printed indicating the approximate location (in absolute coordinates) of the error. Some errors are fatal, and others merely warnings. These warnings should be taken very seriously. The object definition graphics (obtainable through the module SATPLT) are often helpful in identifying the error.

In the process of performing this analysis GENMTL forms and outputs (to file ICNOW) several lists for later use in NASCAP. These are:

PTLIST - List of points which are vertices of insulating surface or boom cells; in format

- C + 64\*((D+2\*(B+2\*(V+2\*E))) + 64\*(Z+64\*(Y+64\*(X+64\*G)))).
- C = conductor number of all neighboring cells have same underlying conductor; otherwise <math>C = 0.
- D = 1 for double point; 0 otherwise.
- B = 1 for bottom point; 0 otherwise.
- V = 0.

E = 1 if point is vertex of a conducting surface cell; E = 0 otherwise.

X, Y, Z are "absolute" [1-17, 1-17, 1-33] coordinates of point.

G = grid number (boom nodes only).

- CPTLST List of vertices of surface cells which do not appear in PTLIST. Same format as PTLIST, except V = 1.
- DPTLST List of double points in format Z + 64\*(Y+64\*X).
- LINS List of insulating surface and boom cells, in format

C + 4096\*CELLNO.

C = underlying conductor number.

CELLNO = surface cell number or NSURF + boom cell number.

VTXL - Vertex-surface cell list to be used by subroutine REFIX. Format is

2<sup>18</sup>\*[PTLIST index] + [LINS index].

Each entry in the PTLIST produces an entry in VTXL for each surface or boom cell of which it is a vertex. For conducting cells, [LINS index] is replaced by NINS + [conductor number], where NINS is the length of LINS.

- SCLIST Surface connectivity map. Contains a negative number for each LINS entry and each conductor. Each negative number is followed by positive numbers indicating LINS entries or conductors to which the negative index is linked by bulk or surface conductivity.
- SCMAT Intrinsic surface and bulk conductivity matrix, ordered as SCLIST, with diagonal elements in positions corresponding to negative SCLIST entries.

Some of the highlights of those lists (such as their length) will be printed as GENMTL is executed. Additionally, if 'PRINT OBJDEF' is specified, the full PTLIST, CPTLST, and DPTLST will be printed.

#### 4. MATERIAL PROPERTIES

#### 4.1 SURFACES, CURRENTS AND CHARGING

An object exposed to a neutral plasma may charge electrostatically as charged particles (electrons and ions) collide with, and collect on, the surface. At geosynchronous altitudes the ambient plasma consists of electrons and ions with similar distributions of energy. Since electrons are almost 2000 times less massive than the lightest ions, this means that the particle velocity distributions are not similar, and the electron flux (or current) incident on an exposed surface greatly exceeds (by a factor of  $\sqrt{1836} = 43$ ) the incident ion flux. If incident electron and ion currents were the only source of charge, all surfaces exposed to such plasmas would rapidly acquire a negative potential. However, there are several other contributions to the overall net current to the surface. These include:

- 1. Secondary emission due to primary electron impact, i<sup>§</sup>.
- 2. Secondary emission due to ion impact,  $i_D^S$ .
- 3. Backscattered primary electrons, i<sup>b</sup>.
- 4. Photoemission due to UV illumination (sunlight), i<sup>p</sup>.
- 5. Conductivity (bulk and surface), i<sup>C</sup>.

NASCAP takes all of these sources of current into account, as well as the incident primary currents, in calculating the net current to each surface cell. The mechanism for each source is discussed in detail in Section 4.8. If  $i_e$  and  $i_p$  are the incident primary electron and ion currents, respectively, the net current  $i_{net}$  to a particular surface cell is given by the equation:

 $i_{net} = i_e + i_p + i_e^s + i_p^s + i_p^b + i_p^c$ 

In most cases the incident electron current  $i_e$  is the only negative contribution. Secondary emission, backscatter and photoemission are sources of positive current since they involve the ejection of electrons from the surface back to the plasma. The incident ion flux  $(i_p)$  is also a source of positive current but the secondary emission (plus photoemission in sunlight) forms the dominant contribution. Thus the sign of the net current  $i_{net}$  depends mainly on the balance between the secondary emission current (plus photoemission) and the incident electron current.

When  $i_e exceeds i_e^s (+i^p)$  the net current is negative and the surface will begin to acquire a negative potential. As the surface becomes negatively charged both the secondary emission and the incident electron current are modified. The effect is to attenuate the net negative current and the rate of charging declines. This continues until  $i_{net} = 0$  and an equilibrium surface potential is reached. Equilibrium potentials of up to -10 kV have been observed in geosynchronous orbit.

When  $i_e$  is exceeded by  $i_e^s$   $(+i_p)$  so that the net current is positive, then the surface begins to acquire a positive potential. However, large equilibrium positive potentials are not observed. This is because the secondary emission and photoemission, which form the dominant contribution to the positive current, have low energy (<10 eV). As soon as the surface potential approaches a few eV positive the low energy emission can no longer escape and is suppressed. This causes rapid attenuation of  $i_{net}$  and equilibrium is achieved. Since an equilibrium of just a few volts positive is negligible compared with potentials of kilovolts that are typical of negative charging, surfaces with net positive currents are often said to "not charge" or "remain neutral".

#### 4.2 SURFACE CURRENTS AND MATERIAL PROPERTIES

Clearly it is important for NASCAP to include contributions from all of the important surface current sources mentioned in 4.1. Currents due to secondary emission, photoemission, backscatter, etc. all depend strongly on the nature of the material covering the surface. (The mechanisms for all of these current sources are explained in Section 4.8.)

For NASCAP to include realistic estimates of these currents in its calculations it must allow surface cells to be assigned different materials. In Chapter 3 we saw how object definition required a material name to be assigned to each exposed surface. NASCAP makes the connection between each material name and their different surface currents via a list of material properties.

#### 4.3 MATERIAL PROPERTIES

Each material name (e.g., KAPTON, GOLD, FRED (the name is arbitrary)) has associated with it a list of <u>material properties</u>. The name of each material and the values for each material property are supplied by the user in the object definition file. (This is explained in Section 4.4.) The nineteen material properties are summarized in Table 4.1. Here we examine each one in more detail.

4.3.1 DIELECTRIC CONSTANT (PROPERTY 1)

Property 1 contains the relative dielectric constant for an insulating material  $\boldsymbol{\varepsilon}_{r}$ 

$$\varepsilon_r = \frac{\varepsilon}{\varepsilon_0}$$

where  $\epsilon$  is the absolute dielectric constant and  $\epsilon_0$  is the dielectric constant of free space.  $\epsilon_r$  is dimensionless.

# TABLE 4.1.MATERIAL PROPERTIES(see Section 4.3 for notes)

| Property No. | <u>User Input Units</u>   | Description  |
|--------------|---|--|
| 1            | None  | Relative dielectric constant   |
| 2            | m   | Dielectric material thickness  |
| 3            | ohms <sup>-1</sup> m <sup>-1</sup>  | Bulk conductivity (= -1 for a metallic conductor)  |
| 4            | None  | Atomic number  |
| 5            | None  | Maximum secondary electron yield for electron impact   |
| .6           | keV   | Primary electron energy that produces maximum secondary yield  |
| 7            | angstroms   | (Range parameters (4.3)  |
| 8            | None<br>angstroms   | $R = P_{7}F^{P}8 + P_{0}F^{P}10$   |
| 10           | None  | ( , , , - , , , , , , , , , , , , , , ,  |
| 11           | None  | Secondary electron yield due to<br>impact of 1 keV protons   |
| 12           | keV   | Incident proton energy that<br>produces maximum secondary electron<br>yield                                  |
| 13           | A m <sup>-2</sup>   | Photoelectron yield for normally incident sunlight   |
| 14           | ohms square <sup>-1</sup>   | Surface resistivity (= -1 for non-conducting surface)  |
| 15           | Volts   | Maximum (absolute) potential<br>attainable before a discharge must<br>occur                                  |
| 16           | Volts   | Maximum potential difference<br>between surface and underlying<br>conductor before a discharge must<br>occur |
| 17           | ohms <sup>-1</sup> m <sup>-1</sup><br>(m <sup>2</sup> s <sup>-3</sup> )-1 | Radiation-induced conductivity coefficient (k)   |
| 18           | None  | Radiation-induced conductivity power (A)   |
| 19           | kg m-3  | Material density   |

.

#### 4.3.2 THICKNESS (PROPERTY 2)

Property 2 gives the thickness d of a dielectric film covering an underlying conductor in meters. d is arbitrary and may be chosen to be more or less than a mesh unit. However, note that NASCAP uses thin-film approximations in many of its calculations involving surfaces (Section 4.8).

#### 4.3.3 BULK CONDUCTIVITY (PROPERTY 3)

Property 3 gives the bulk conductivity  $\sigma_0$  of the surface material in ohms  $^{-1}$  m<sup>-1</sup>.  $\sigma_0$  is assumed to be the value appropriate for a sample not exposed to any radiation and not subject to any internal electric fields. Field enhancement and radiation enhancement of  $\sigma_0$  is taken into account by NASCAP internally (if these effects are selected as run options (6.3.6 and 6.3.9)). A value of -1indicates that the material is a metallic conductor.

#### 4.3.4 ATOMIC NUMBER (PROPERTY 4)

Property 4 is the atomic number for pure elements or the mean atomic number for chemical compounds; e.g., polyethylene  $(CH_2)_n$  has a mean atomic number of (6 + 1 + 1)/3 = 2.7.

4.3.5 SECONDARY YIELD (PROPERTIES 5 AND 6)

Properties 5 and 6 are the coordinates of the maximum in the secondary electron yield curve of the material. The secondary yield curve is a plot of secondary yield &

# $\delta = \frac{\text{current of secondary electrons emitted}}{\text{incident primary electron current}}$

for normally incident electrons, against the incident energy of the primary electron E. This is shown in Figure 4.5. Property 5 contains  $\delta_{max}$ , and property 6 contains  $E_{max}$  in keV.

#### 4.3.6 ELECTRON RANGE (PROPERTIES 7, 8, 9 AND 10)

Part of the secondary electron emission formulation requires an analytical form for the "range" of electrons in the material. The range is the depth to which the electrons can penetrate the material as they are continuously slowed down by losing energy to the material lattice. NASCAP uses a biexponential form. If  $P_7$ ,  $P_8$ ,  $P_9$ , and  $P_{10}$  are properties 7-10 respectively, the range R is given by

$$R = P_7 E^{P_8} + P_9 E^{P_{10}}$$

The four parameters are obtained from fits to stopping power data (Section 4.8). The range is determined in Å  $(10^{-10} \text{ m})$ . If no reliable stopping power data or four parameter fits are available, the range may be estimated from Feldman's formula<sup>[4]</sup> automatically by assigning -1 to property 7. In this mode properties 7-10 are assigned as follows:

$$P_7 = -1$$
  
 $P_8 = null$   
 $P_9 = material density (g cm-3)$   
 $P_{10} = mean atomic weight (AMU)$ 

The mean atomic weight is calculated in the same way as the mean atomic number (4.3.4) using atomic masses rather than numbers.

4.3.7 ION INDUCED SECONDARY EMISSION (PROPERTIES 11 AND 12)

Secondary emission of electrons due to ion impact is also treated using a two parameter theory (Section 4.8). Parameter 11 contains the yield for 1 keV normally incident protons and parameter 12 the proton energy that produces the maximum electron yield. The secondary emission properties due to impact of ions other than protons are assumed to be identical to the proton values.

#### 4.3.8 PHOTOEMISSION (PROPERTY 13)

Property 13 contains the yield of photoelectrons from the surface material exposed to the solar spectrum. The intensity is that measured on earth 93,000,000 miles from the sun. (Earth orbit altitudes are negligible by comparison and the intensity of the sun close to earth may be considered constant.)

#### 4.3.9 SURFACE RESISTIVITY (PROPERTY 14)

Property 14 gives the intrinsic surface resistivity in the "ohms per square". This rather odd unit is used to distinguish the resistivity coefficient (property 14) from the actual surface resistance (in ohms) calculated by NASCAP. Consider two points in a plane A and B, a distance  $L_1$  apart. If  $L_2$  is the "width" of the plane

surface resistance = surface resistivity  $x \frac{L_1}{L_2}$ i.e. ohms = (ohms per square) x geometrical factor



NASCAP uses the surface resistivity per square, times a geometrical factor it calculates to determine the surface resistance between two adjacent materials.

The intrinsic surface conductivity is due to the migration of electrons along the surface layer aided by adsorbed impurities and defects. An additional contribution is made by photo electrons "hopping" along the surface. This so-called "photosheath" conductivity is included, if requested using the run option 'EFFCON ON' (Section 6.3.4).

Surface conductivity may be omitted from the current calculations completely by choosing property 14 to be negative.

4.3.10 DISCHARGE ANALYSIS (PROPERTIES 15, 16)

Properties 15 and 16 refer to discharges. Property 15 contains the maximum absolute potential that the material may reach (in volts) before a "blowoff" of charge to space (or tank walls) must occur. Property 16 contains the maximum potential difference (in volts) that can exist between the material surface and an underlying conductor before a "punchthrough" or dielectric breakdown must occur.

If a discharge analysis is requested, upon reaching these limiting potentials NASCAP redistributes the charge in an appropriate way (6.3.3).

4.3.11 PROPERTIES 17, 18, 19, 20 (RADIATION INDUCED CONDUCTIVITY)

These four properties are all used by the radiation-induced conductivity option (6.3.9 and 4.8). The extra bulk conductivity due to irradiation of the sample with high energy electrons  $\sigma_r$  is given by

 $\sigma_r = k D^{\Delta}$ 

where D is the dose rate (energy deposited per unit mass per second) to the material from the high energy electrons. Properties 17 and 18 contain k in ohms<sup>-1</sup> m<sup>-1</sup> (m<sup>2</sup> s<sup>-3</sup>)<sup>-1</sup> (1 rad s<sup>-1</sup> =  $10^{-2}$  m<sup>2</sup> s<sup>3</sup>) and the power  $\Delta$ , respectively.

Property 19 contains the density of the material in kg m<sup>-3</sup> and is used to calculate the dose rate (4.8). Property 20 is used by NASCAP to store the original value of  $\sigma_0$  entered by the user as property 3. Property 3 is replaced by the value of the overall effective bulk conductivity, including field and radiation enhancement. No significant user input is required for property 20.

#### 4.4 DEFINING MATERIALS

New materials are defined, and their properties assigned inside the object definition file ISAT (3.5). The object definition file is read by NASCAP module OBJDEF. OBJDEF interprets any word that it does not recognize as a building block keyword (or their parameter cards (3.9.6)) as the definition of a new material name. New material names may <u>not</u> appear inside building block definitions (i.e., between a building block keyword and an 'ENDOBJ' statement).

Following the material name OBJDEF expects to find three additional cards specifying 20 constants as the material properties to be associated with the name. The 20 constants correspond to properties 1-20 and are read sequentially; i.e., the first constant read is interpreted as property 1, the second, property 2, and so on. They are arranged sequentially, eight per card, so that cards 1 and 2 each have eight numbers and card 3, four numbers. Formally each number is written in a field of up to ten characters, but NASCAP will read the cards in free format. No units need be specified. NASCAP will assume the units given in Table 4.1 and no others. For properties not requiring any input such as property 20, or properties 17-19 for conductors, some constant <u>must</u> be entered but its value is arbitrary. (NASCAP will not actually use the values entered but expects to read something.)

Once the three material property cards have been read OBJDEF is ready to accept any other keywords or more material names. NASCAP will recognize up to fifteen different materials.

Materials <u>must</u> be defined before they are referred to in any building block definition. For example, if I assign the surface of a sphere to be 'FSTUFF' with the card

#### MATERIAL FSTUFF

if 'FSTUFF' and its material properties have not been declared earlier in the object definition file, an error will occur and execution will stop. For this reason all the materials to be used are usually declared at the very beginning of the object definition file. This is shown in Figure 4.1.

#### 4.5 DEFAULT MATERIALS

There is one case where the user can forget to define his or her materials and get away with it. When OBJDEF encounters a material that hasn't been defined already, before an error occurs, it checks the following list of default materials:

> ALUMIN AQUADG CPAINT GOLD INDOX MAGNES SCREEN KAPTON NPAINT SIO2 SOLAR TEFLON SILVER

Material Name 1 {3 material property cards Material Name 2 {3 material property cards • . COMMENT DEFINE MAIN BODY CONDUCTOR 1 **OSPHERE** {parameter cards ENDOBJ RECTAN {parameter cards ENDOBJ more building blocks COMMENT DEFINE SOLAR PANEL (SEPARATE CONDUCTOR) **CONDUCTOR 2** PLATE {parameter cards ENDOBJ more building blocks COMMENT CONDUCTOR 3 more conductor segments ENDSAT

COMMENT DEFINITION OF SATELLITE "BIG EARS"

-

~ .

Figure 4.1. General form of the object definition file ISAT.

If the material is included in this list, it becomes one of the up to fifteen defined materials and its properties, stored internally, are automatically entered as OBJDEF input by the code. The properties of these materials are shown in Table 4.2. Any further reference to the material will assign the same set of properties to the surfaces concerned. If the material is not found in this list, an error will occur.

If two sets of material properties are defined with the same name, or names with the <u>same first four letters</u>, two of the fifteen possible materials are used up but only the <u>first</u> set of material properties are used. For example, if GOLD is referenced before it is defined in the runstream, the default material properties of gold will be associated with <u>all</u> gold surfaces in the object definition file. If a material called 'GOLD' or 'GOLDPD' or 'GOLDXXXX' is defined later with different properties the number of materials NASCAP thinks it has will be increased by one, but the new properties will be effectively ignored. Multiple definition of materials should be avoided. Note, however, that if any of the default materials are explicitly defined <u>before</u> they are referred to in building block definitions then NASCAP will make no attempt to find them in the list of default materials and the materials will not be multiple defined.

## 4.6 THE OBJECT DEFINITION FILE - ANOTHER EXAMPLE

We are now ready to bring together Chapters 3 and 4 and examine the structure of the object definition file ISAT. The general form is shown in Figure 4.1. The materials are defined first, followed by the building blocks associated with each separate conductor. The use of COMMENT cards allow the logic of the definition of a complex object to be followed more easily. Finally the whole file is terminated with an 'ENDSAT' statement. An actual example is shown in Figure 4.2. This object is the same as the one used in the worked example described in Chapter 11. It consists of a central RECTANgular body connected to two QSPHERES via two short BOOMS.

.92 2000. .45 2000. 88.8 10000. T PROPERTIES OF KAPTON AND ALUMINUM FROM DEFAULT TABLE. Ŧ 80 --.88 .000029 2.05 .00002 4:COMMENT SOLAR SPHERE (ON SEPARATE CONDUCTOR) 5:CONDUCTOR 2 AIAL COLD AND SOLAR EXAMPLE (CHAPTER 11) 26 is 0.02 m 79. 135. 20. 23:SURFACE -Z KAPTON 24:ENDOBJ 25:COMMENT BOOM TO KAPTON SPHERE 26:BOOM 27:AXIS 0 0 2 0 4 27:AXIS 0 0 2 0 4 28:SURFACE ALUMINUM 30:ENDOBJ 31:COMMENT BOOM TO SOLAR SPHERE E+3 244 CONDUCTOR 1 COMMENT CENTRAL CUBOID 37.COMMENT KAPTON SPHERE 38:05PHERE 33:AXIS 0 0 -2 0 0 -4 34:RADIUS 0.05 35:SURFACE ALUMINUM 36:ENDOBJ .000179 -Y KAPTON +2 KAPTON -2 KAPTON 47:CENTER 0 0 -6 48:DIAMETER 3 49:SIDE 1 50:MATERIAL SOLAR 51:ENDOBJ II:SIDE I I2:MATERIAL KAPTON 13:ENDOBJ 160. ഗ 0 9:CENTER 0 ( 521END5AT 521END5AT EOF152 01) 6 1 OSPHERE 1 102105 13:51

Object definition file. Figure 4.2. A 3D-VIEW (6.6.1) of the object produced by NASCAP is shown in Figure 4.3. A more detailed discussion of the definition of this object is given in Section 11.2.

# 4.7 OBJECTS WITHIN OBJECTS: VARIEGATED SURFACES

NASCAP makes it easy to define surfaces that are made up of more than one material. For example, we may want to define one face of a cube to be mainly KAPTON but with a patch of say GOLD in the center (Figure 4.4). We begin by defining the cube with a KAPTON face. The center surface cell is then replaced with GOLD by defining a second smaller cube <u>inside</u> the first cube. The second cube is defined so that one of its faces is coincident with the KAPTON face. The surface common to both cubes is then associated with the material on the face of the second cube, which in this case is GOLD. This is shown in Figure 4.4.

The object definition file associated with this object has the form:

| COMMENT | VARIEGATED | CUBE |
|---------|------------|------|
| RECTAN  |            |      |
| CORNER  | -2 -2 -2   |      |
| DELTAS  | 3 3 3      |      |
| SURFACE | +x KAPTON  |      |
| SURFACE | -x KAPTON  |      |
| SURFACE | +y KAPTON  |      |
| SURFACE | -y KAPTON  |      |
| SURFACE | +z KAPTON  |      |
| SURFACE | -z KAPTON  |      |
| ENDOBJ  |            |      |
| RECTAN  | -1 -1 -1   |      |
| CORNER  |            |      |
| DELTA   | 1 1 1      |      |
| SURFACE | -z GOLD    |      |
| ENDOBJ  |            |      |
| ENDSAT  |            |      |



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-

Figure 4.3. 3D-VIEW of object produced by SATPLT (hidden lines).





Figure 4.4. A variegated surface definition.

The same principle can be applied to any of the building blocks. Exposed surface cells common to two or more building blocks are assigned to the material of the most recently defined block.

Two special building blocks are supplied specifically to create variegated surfaces. PATCHR and PATCHW define a RECTAN (cuboid) and a WEDGE respectively, that may be used to "patch" other objects without adding to NASCAP's list of filled space. The use of actual RECTAN and WEDGE blocks inside others is also perfectly legitimate, but adds to the internally used list. If the list becomes too long (as it might for a complicated object) shadowing calculations are no longer possible (8.1). The use of PATCHR and PATCHW reduce the likelihood of this problem occurring.

The object shown in Figure 4.4 could also be defined using PATCHR:

| COMMENT | VAR | VARIEGATED |     | CUBE | (PATCHR) |
|---------|-----|------------|-----|------|----------|
| RECTAN  |     |            |     |      |          |
| CORNER  | -2  | -2         | -2  |      |          |
| DELTAS  | 3   | 3          | 3   |      |          |
| SURFACE | +X  | KAP        | TON |      |          |
| SURFACE | -X  | KAP        | TON |      |          |
| SURFACE | +Υ  | KAP        | TON |      |          |
| SURFACE | -Y  | KAP        | TON |      |          |
| SURFACE | +Z  | KAP        | TON |      |          |
| SURFACE | -Z  | KAP'       | TON |      |          |
| ENDOBJ  |     |            |     |      |          |
| PATCHR  |     |            |     |      |          |
| CORNER  | -1  | -1         | -1  |      |          |
| DELTAS  | 1   | 1          | 1   |      |          |
| SURFACE | -Z  | GOLI       | )   |      |          |
| ENDOBJ  |     |            |     |      |          |
| ENDSAT  |     |            |     |      |          |

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#### 4.8 TECHNICAL DISCUSSION

#### 4.8.1 SECONDARY ELECTRON EMISSION DUE TO ELECTRON IMPACT

Secondary electrons are defined as those emitted from the surface due to particle impact with energies below 50 eV. Their energy distribution is usually peaked below 10 eV. We define the secondary yield  $\delta$  as the ratio of primary to secondary electron current.

 $\delta = \frac{\text{emitted secondary current due to electron impact}}{\text{primary electron current}}$ 

NASCAP calculates the secondary electron emission yield,  $\delta$ , using the empirical formula:

$$\delta(\mathbf{e}) = C \int_{0}^{R} \left| \frac{dE}{dx} \right| e^{-\alpha X \cos \theta} dx$$

where x is the path length of penetration of a primary electron beam into the material, R is the "Range", or maximum penetration length, and  $\Theta$  is the angle of incidence of the primary electron.

This equation is based upon a simple physical model: <sup>[5]</sup>

- a. The number of secondary electrons produced by the primary beam at a distance x is proportional to the energy loss of the beam or "stopping power" of the material, |dE/dx|.
- b. The fraction of the secondaries that migrate to the surface and escape decreases exponentially with depth  $(f = e^{\alpha X \cos \theta})$ . Thus only those produced within a few multiples of the distance  $1/\alpha$  (the depth of escape) from the surface contribute significantly to the observed yield.
The range increases with the initial energy,  $E_0$ , of the incident electrons in a way that approximates a simple "power law":<sup>[4]</sup>

$$R = b E_0^n$$

where 1.0 < n < 2.0.

This equation implies a simple form for the stopping power S(E):

$$S(E) = \left| \frac{dE}{dx} \right| = \left| \frac{dR}{dE_0} \right|^{-1} = \frac{E^{1-n}}{nb}$$

Because the primary beam loses energy as it passes through the material, both E, and hence  $S(E_0, x)$ , depend on the path length x. Integrating:

$$E^{n}(x) = E_{o}^{n} - \frac{x}{b}$$
$$S(x) = \frac{1}{nb} \left(\frac{b}{R - x}\right)^{1 - 1/n}$$

The stopping power  $S(E_0,x)$  depends upon both the initial electron energy  $E_0$ , via R, and the path length x. Figure 4.5a shows schematically  $S(E_0,x)$  plotted against x for several values of  $E_0$ . Inspection of Figure 4.5a and the equation for S(x) illustrates the following points:

- 1.  $S(E_0,x)$  increases with x, slowly at first, before reaching a singularity as x approaches R.
- 2. The initial value of  $S(E_0, x)$  decreases with increasing initial energy  $E_0$ .

Both of these observations are due to the decrease in electron-atom collision cross-section with increasing energy.



Figure 4.5a. Energy deposition profiles of normally incident primary electrons for incident energies E<sup>0</sup>.



Figure 4.5b. Generalized yield curve.

The yield is only sensitive to the details of the stopping-power depth-dependence for initial energies with ranges of the same order as the escape depth,  $R \sim 1/\alpha$  (i.e., about the maximum of the yield curve). For lower energies,  $R << 1/\alpha$ , and essentially all of the primary energy is available for detectable secondary production, leading to a linear increase in yield with increasing  $E_0$ . At higher energies, where  $R >> 1/\alpha$ ,  $S(E_0,x)$  remains almost constant, at its initial value, over the depth of escape and so, along with  $S(E_0,x)$ the yield decreases as  $E_0$  increases.

NASCAP takes this into account and approximates the stopping power by a linear expansion in x, about x = 0.

$$\frac{dE}{dx} = \left(\frac{dR}{dE_o}\right)^{-1} + \left(\frac{d^2R}{dE_o^2}\right) \left(\frac{dR}{dE_o}\right)^{-3} x$$

NASCAP allows for a bi-exponential range law:

$$R = b_1 E_0^{n_1} + b_2 E_0^{n_2}$$

involving four parameters  $b_1$ ,  $b_2$ ,  $n_1$ ,  $n_2$ . The parameters are fit to reproduce range data as accurately as possible. For materials where no suitable data is available, a mono-exponential form is generated using Feldman's empirical relationships, <sup>[4]</sup> connecting b and n to atomic data.

$$b = 250 \text{ A}/_{\text{p}}\text{Z}^{n/2}$$

 $n = 1.2/(1 - 0.29 \log_{10} Z)$ 

where A is the atomic or molecular weight of the material, Z is the atomic number, and  $\rho$  is the density. The stopping power is then

obtained indirectly via the equation above. Recently good theoretical estimates of the stopping power for a number of materials have become available. <sup>[6]</sup> Comparison of these values with those implied by the range data showed significant discrepancies, particularly for those materials fit using Feldman's formula. <sup>[4]</sup> A better approach is to fit the four parameters in the equation for R directly to the stopping power data.

$$S = \left(n_{1}b_{1}E^{n_{1}-1} + n_{2}b_{2}E^{n_{2}-1}\right)^{-1}$$

## 4.8.2 SECONDARY EMISSION DUE TO ION IMPACT

Secondary emission of electrons due to ion impact is treated in a way similar to that for electron impact discussed in 4.9.1. The yield  $\triangle$  is given by

$$\Delta(\Theta) = C \int_{0}^{t} \left| \frac{dE}{dx} \right| e^{-\alpha X} \text{ sine } dx$$

The angular dependence is assumed to be a simple sine form, and the stopping power is assumed to be independent of path length x over the thickness t of the sample.

$$\left|\frac{dE}{dx}\right| = \beta E^{1/2}/(1 + E/E_{max})$$

 $E_{max}$  is the energy at the maximum in the yield curve. This is ~50 keV for most materials. A typical yield curve is shown for aluminum in Figure 4.6.





#### 4.8.3 BACKSCATTER

Backscattered electrons are those emitted from the surface with energies above 50 eV. Their energy distribution is usually peaked close to the primary incident energy and they may be considered as reflected electrons.

The large-angle scattering theory, together with Monte Carlo data and experiments by Darlington and Cosslett, <sup>[11]</sup> indicate that the angular dependence of backscattering is well described by

$$\eta(\theta) = \eta(0) \exp[\eta_1(1 - \cos\theta)]$$

where the value of  $n_1$  is, within the uncertainty in the data, what would be obtained by assuming total backscattering at glancing incidence, viz.  $n_1 = -\log n_0$ . The net albedo for an isotropic flux is then

$$A_{0} = 2[1 - n_{0}(1 - \log n_{0})]/(\log n_{0})^{2}$$

As the energy is decreased below 10 keV the backscattering increases. Data cited by Shimizu<sup>[12]</sup> indicate an increase of about 0.1, almost independent of Z. NASCAP approximates this component of backscattering by

$$s_{n_0} = 0.1 \exp[-E/5 \text{ keV}]$$

At very low energies the backscattering coefficient becomes very small and, below 50 eV, backscattering and secondary emission are indistinguishable. NASCAP takes account of this by a factor of

[(E - 50 eV)/log 20] log(E/50 eV).The formula for energy-dependent backscattering, incorporating these assumptions, is then

$$n_0 = \{ [\log(E/0.05) \ominus (E - 0.05) \ominus (1.0 - E)/\log(20) + \Theta(E - 1.0) \} \times [0.1 \exp(-E/5) + 1 - (2/e)^{.037Z} ] \}$$

where energies are measured in keV.

#### 4.8.4 PHOTOEMISSION

The user enters the yield (Y), or number of electrons emitted for a surface normally exposed to the solar spectrum, an "earth distance" from the sun. NASCAP calculates the photocurrent from a surface exposed to the sun at an angle 0, according to the formula

iphot = (Area exposed) • Y • cose

This assumes that the yield per photon is, on average, independent of  $\Theta$ .

#### 4.8.5 CONDUCTIVITY

The bulk conductivity  $\sigma_0$  is assumed constant unless the 'RADCON' and 'FLDCON' options are chosen to be 'ON' (6.3.6 and 6.3.9). With these options in force  $\sigma$  is enhanced by both fields across the dielectric film and high energy electron fluxes.

#### a. FIELD-INDUCED CONDUCTIVITY

Consider a thin dielectric film of thickness d covering an underlying conductor. If the potential of the dielectric surface  $V_s$  differs from the potential of the conductor  $V_c$ , current will flow due to bulk conductivity.

 $I_{c} = -\sigma \Delta V = -\sigma (V_{s} - V_{c})$ 

 $\sigma$  is the bulk conductivity of the sample in mhos. If  $\sigma$  is the specific conductivity in mhos m  $^{-1}$  and A is the area of the sample in m  $^2$ 

$$\sigma = \frac{\overline{\sigma A}}{d}$$

i.e. 
$$I_c = -\frac{\sigma A \cdot \Delta V}{d}$$

I depends on  $\Delta V$  in a nonlinear way due to the electric field enhancement of  $\sigma$ . Assuming a thin film, the field E is given by

$$E = \frac{\Delta V}{d}$$

Adamec and Calderwood<sup>[13]</sup> have shown that  $\sigma$  depends on E in the following way:

$$\sigma(E) = \frac{\sigma_0}{3} \left[ 2 + \cosh\left(\frac{\beta_f |E|^{1/2}}{2 kT}\right) \right]$$

where

$${}^{\beta}F = \left(\frac{|q|^3}{\pi\varepsilon}\right)^{1/2}$$

and q is the charge on the electron and  $\epsilon$  is the dielectric constant.

#### b. RADIATION-INDUCED CONDUCTIVITY

Dielectric materials have characteristically small bulk conductivities due to their electron band structure. Unlike metals, the delocalized conduction bands are empty at normal temperatures and electrons are strongly localized in the regions close to individual nuclei. However, under the influence of an exciting source non-conducting electrons can be promoted into the conduction bands, leading to an increase in the bulk conductivity. High energy electrons passing through the dielectric provide such an excitation source.

While NASCAP treats the non-penetrating ( $\leq$ 50 keV) portion of the plasma spectrum explicitly in calculating the buildup of surface charge, it presently neglects the very low fluxes of higher energy penetrating electrons, since they make a negligible contribution to the total incident charge. Recent studies<sup>[14]</sup> suggest, however, that the penetrating fluxes may influence the degree of differential charging by increasing the bulk conductivity in this way. This enhancement due to high energy electron fluxes is described as the "radiation-induced" conductivity  $\sigma_n$ .

Frederickson<sup>[15]</sup> has expressed  $\sigma_r$  in terms of the dose rate  $\tilde{D}$  and two parameters k and  $\Delta$ .

 $\sigma_r = k D^{\Delta}$ 

k and  $\Delta$  are characteristic of each material and  $\Delta$  usually lies between 0.5 and 1.0. The dose rate can be estimated from the stopping power S for electrons in the medium of interest.

S(E) = dE/dx

The dose rate is measured as energy deposited per unit mass per second (i.e., rad  $s^{-1} = 100 \text{ erg g}^{-1} s^{-1}$ ). Stopping power is measured as energy deposited per particle per unit thickness of the sample. Dividing S(E) by the density  $\rho$  of the sample gives the energy deposited per particle per unit mass of the material multiplied by unit area. The product of this quantity with the flux (particles per unit area per second) gives the required dose rate:

 $\dot{D} = flux \cdot \frac{S(E)}{\rho}$ 

The flux of incident electrons due to a plasma with distribution function f(E) is given by:

$$\langle nf \rangle = \frac{2}{m^2} \int E f(E) dE$$

$$\therefore \quad \dot{D} = \frac{2}{\rho m^2} \int E f(E) S(E) dE$$

A number of models for the energy spectrum of high energy fluxes in space have been measured. [16,17] All show a Maxwellian like behavior, i.e.,

$$f(E) = N \cdot \left(\frac{m}{2\pi T}\right)^{3/2} e^{-E/T}$$

The AE3 model<sup>[17]</sup> implies a value of  $3 \times 10^2 \text{ m}^{-3}$  for the density N and 2.5 x  $10^2$  keV for the temperature T at geosynchronous orbit. Electrons in this energy range are relativistic; i.e., their velocity is close to that of light (c) and so the weight function E in the integral above should be replaced by mc<sup>2</sup>. This is confirmed by a plot of <nf> against E which shows the same exponential behavior.

$$\therefore \quad \dot{D} = \frac{2c^2}{\rho m} \cdot N \left(\frac{m}{2\pi T}\right)^{3/2} \int_{50}^{\infty} e^{-E/T} S(E) dE$$

(where we assumed the contribution from non-penetrating electrons with energies below 50 keV is negligible).

The dose rate is calculated in NASCAP for each material by integrating the above equation, using Simpson's rule, between 50 keV and 4 T. If all energies are in keV and S(E) is in keV  $A^{-1}$  and I is the value of the integral:

$$\dot{D} = \frac{2c^2}{\rho m} N \left(\frac{m}{2\pi T}\right)^{3/2} \cdot I \ keV^2 \ A^{-1}$$

Substituting:

$$\dot{D} = 1.38 \times 10^3 \frac{N \cdot T}{\sigma T^{3/2}} m^2 s^{-3}$$

where N is in units of  $m^{-3}$ ,  $\rho$  (kg  $m^{-3}$ ) and T is in keV.

Frederickson<sup>[15]</sup> has pointed out that k is often known to within only 2 orders of magnitude and  $\triangle$  values are usually close to 1. We assume values of k = 1 x 10<sup>-17</sup> mhos cm<sup>-1</sup> (rad s<sup>-1</sup>)<sup>-1</sup> = 1 x 10<sup>-13</sup> mhos m<sup>-1</sup> (m<sup>2</sup> s<sup>-3</sup>)<sup>-1</sup> and  $\triangle$  = 1 as default material properties 17 and 18, respectively. The density  $\rho$  in kg m<sup>-3</sup> is material property 19. Since the density of plastics and other insulators depends very much on the particular sample and manufacturer, default values are chosen to be 1 x 10<sup>3</sup> kg m<sup>-3</sup>.

#### 4.8.6 ATTENUATION OF INCIDENT CURRENT

The net incident particle flux is attenuated as the surface becomes charged (either positively or negatively). This is because the flux of particles with opposite sign to the surface potential is enhanced and the flux of particles with the same sign is decreased. NASCAP assumes a <u>spherical orbit limited</u> particle collection formula. This is a good approximation for convex objects with radius of curvatures smaller than the Debye length of the ambient plasma. This is the major restriction that confines NASCAP to charging problems in the geosynchronous (long Debye length) regime. Spherical orbit limited collection gives the following form for the variation of incident current I with surface potential V:

$$J(E) = J_{0} (\varepsilon + qV) \left(1 - \frac{qV}{E+qV}\right)$$

where E is the kinetic energy of the repelled particle  $\underline{at}$  the surface, q is the sign of the charge on the particle, and E+qV is the particle's total energy. The same formula holds for attracted particles.

#### TABLE 4.2. MATERIAL PROPERTIES

1: ALUM MATERIAL INPUT VALUE CODE VALUE PROPERTY 1.00+000 (NONE) 1.30-303 METERS 1.00+000 (NONE) DIELECTRIC CONSTANT 1 1.00-002 MESH THICKNESS 2 -1.00+000 MHC/M -1.00+000 MH0/M CONDUCTIVITY 3 1.30+001 (NONE) 1.30+001 (NONE) ATOMIC NUMBER 4 COEFF 9.70-031 (NONE) 9.18+000 (NONE) 5 DELTA MAX 3.00-002 ANG-01 3.00-001 KEV >DEPTH##=1 E-MAX 6 1.23+002 ANG. 1.54+002 ANG. 7 RANGE 8.00-001 (NONE) 3.87+002 ANG. > RANGE EXPONENT 8 2.20+002 ANG. 1.76+000 (NONE) RANGE > EXPONENT 8.30-001 (NONE) 9 1.76+000 (NONE) 10 EXPONENT YIELD FOR IKEV PROTONS 2.44-001 (NONE) 2.44-001 (NONE) 11 2.33+032 KEV MAX DE/DX FOR PROTONS 2.30+002 KEV 12 4.30-085 A/M##2 PHOTOCURPENT 4.00-005 4/###2 13 -1.JU+CCG 0HMS -8.85-013 V-5/0 SUPFACE RESISTIVITY 14 1.00+064 VOLTS 2.30+003 VOLTS SPACE DISCHARGE POT\*L 1.30+034 VOLTS 15 INTERNAL DISCHARGEPOT'L 2.00+003 VOLTS 16 1+00+013 MHOMS3 1.00-013 MHCMS3 RADN INDUCEDCOND YCOEFFT 17 RADN INDUCEDCONG YPOWER 1.00+000 (NONE) 1.30+005 (NONE) 18 1.00+003 KG/M#3 1.00+003 KG/H#3 19 DENSITY 2.00+001 -1+60+000 20 MATERIAL 2: AQUA INPUT VALUE CODE VALUE PROPERTY 1.00+000 (NONE) 1.30+030 (NONE) DIELECTRIC CONSTANT 1 1.00-033 METERS -1.30+003 MHC/M 1.00-002 MESH -1.00+000 MH0/M THICKNESS 2 CONDUCTIVITY 7 6.00+000 (NONE) 6.32+000 (NONE) 4 ATOMIC NUMBER 7.56+060 (NONE) DELTA MAX SCOEFF 1.30+030 (NONE) 5 2.21-002 ANG-01 3.30-001 KEV 30EPTH##-1 E-MAX 6 5.30+002 ANG. 7 RANGE -1.30+000 ANG. > RANGE .30 (NONE) +30 ANG. EXPONENT 8 2.00+000 ANG. 1.55+000 (NONE) RANGE > EXPONENT 9 1.20+001 (NCNE) 4.55-001 (NCNE) 1.03+060 (NONE) EXPONENT 10 4.55-001 (NONE) YIELD FOR IKEV PPOTONS 11 1.40+002 KEV MAX DE/DX FOR PROTONS 1.40+002 KEV 12 2.13-305 4/###2 2.10-005 A/M##2 PHOTOCURPENT 13 -1.30+000 OH#S -8.45-013 V-5/0 SURFACE RESISTIVITY 14 1.30+004 VOLTS SPACE DISCHARGE POT\*L 1.30+034 VOLTS 15 2.30+03 VOLTS 1.00+013 MH0MS3 2.30+063 VOLTS 1.60-013 MH0MS3 INTERNAL DISCHARGEPOT\*L 16 RADN INDUCEDCOND YCOEFFT 17 1.JC+COC (NONE) RADN INDUCEDCOND YPOWER 1.00+000 (NONE) 18 1.00+003 KG/M#3 1.30+003 KG/M#3 19 DENSITY

2.30+031

20

127

-1.00+000

|                                 | MATERIAL 3: CPAI  |  |   |
|---------------------------------|---|--|---|
|                                 | PROPERTY  | INPUT VALUE  | CODE VALUE  |
| 1                               | DIELECTRIC CONSTANT   | 3.50+000 (NGNE)  | 3-53+880 (NONE)   |
| 2                               | THICKNESS   | 1.00-903 NETERS  |   |
| 3                               | CONDUCTIVITY  | -1.CO+060 NH0/M  | 1.00-002 HESH   |
| 4                               | ATOMIC NUMBER   | 5-00+000 (NCNE)  | -1.03+050 HH0/H   |
| 5                               | DELTA NAX DOOEFF  | 2-10+050 (NONE)  | 3+00+005 (NONE)   |
| 6                               | E-MAX DEPTH##-1   | 1.50-001 KEV   | 8.70-002 ANG-01   |
| 7                               | RANGE   | 7.15+561 ANG.  | 4.294571 ANG  |
| 8                               | EXPONENT > RANGE  | 6.30-001 (NONE)  | 5.52+002 ANG.   |
| 9                               | RANGE > EXPONENT  | 3.12+032 ANG.  | 6.00-001 (NONE)   |
| 10                              | EXPONENT  | 1.77+000 (NGNE)  | 1.77+500 (NONE)   |
| 11                              | VIELD FOR IKEV PROTONS  | 4.55-001 (NONE)  | 4.55-001 (NONE)   |
| 12                              | MAX DE/DX FOR PROTONS   | 1+40+092 KEV   | 1.40+0C2 KEV  |
| 13                              | PHOTOCURRENT  | 2.00-005 A/H++2  | 2.00-005 A/M##2   |
| 14                              | SURFACE RESISTIVITY   | -1.00+000 OHMS   | -3.85-013 V-5/0   |
| 15                              | SPACE DISCHARGE POT*L   | 1.30+CG4 VOLTS   | 1.00+004 VOLTS  |
| 16                              | INTERNAL DISCHARGEPOT'L   | 2+30+C33 VOLTS   | 2.00+003 VOLTS  |
| 17                              | PADN INDUCEDCOND YCOEFFT  | 1.GC-013 MH0MS3  | 1.30+013 MH0MS2   |
| 18                              | RADN INDUCEDCOND * YPOWER   | 1.00+000 (NCNE)  | 1.00+000 (NONE)   |
| 19                              | DENSITY   | 1+30+C33 KG/M#3  | 1.30+337 KG/M+3   |
| 20                              |   | 2.00+001   | -1.03+030   |
|                                 | MATERIAL 4: GOLD  |  |   |
|                                 |   |  |   |
|                                 | PROPERTY  | INPUT VALUE  |   |
| 1                               | PROPERTY<br>DIELECTRIC CONSTANT   | INPUT VALUE  | CODE VALUE  |
| 1<br>2                          | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS  | INPUT VALUE<br>1.CC+CGC (NONE)<br>1.QQ-QQ3 meters  | CODE VALUE<br>1.03+900 (None)<br>1.00=002 Mesm  |
| 1<br>2<br>3                     | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY  | INPUT VALUE<br>1.00+000 (NONE)<br>1.00-003 meters<br>-1.00+000 mm0/m   | CODE VALUE<br>1.03+90C (NONE)<br>1.00-002 Mesh<br>-1.09+000 MHC/4   |
| 1<br>2<br>3<br>4                | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER   | INPUT VALUE<br>1.00+000 (NONE)<br>1.00-003 meters<br>-1.00+000 mh0/m<br>7.90+001 (NONE)  | CODE VALUE<br>1.00+000 (NONE)<br>1.00-002 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)  |
| 1<br>2<br>3<br>4<br>5           | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF   | INPUT VALUE<br>1.CC+CQC (NONE)<br>1.00-003 meters<br>-1.CC+C00 mhd/m<br>7.90+C01 (NONE)<br>8.60-301 (NONE)   | CODE VALUE<br>1.00+002 (NONE)<br>1.00-002 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+000 (NONE)   |
| 1<br>2<br>3<br>4<br>5<br>6      | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH++-1   | INPUT VALUE<br>1.00+000 (NONE)<br>1.00-003 meters<br>-1.00+000 mm0/m<br>7.90+001 (NONE)<br>8.60-001 (NONE)<br>5.00-001 Key   | CODE VALUE<br>1.00+002 (NONE)<br>1.00-002 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+000 (NONE)<br>2.02+002 ANG-01  |
| 1234567                         | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##=1<br>RANGE  | INPUT VALUE<br>1.00+000 (NONE)<br>1.00+000 meters<br>-1.00+000 mm0/m<br>7.90+001 (NONE)<br>8.60-001 (NONE)<br>5.00-001 Kev<br>3.38+001 Ang.  | CODE VALUE<br>1.00+002 MESH<br>1.00+000 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+000 (NONE)<br>2.02+002 ANG-01<br>8.17+001 ANS.   |
| 12345678                        | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH**-1<br>RANGE<br>EXPONENT > RANGE  | INPUT VALUE<br>1.00+000 (NONE)<br>1.00+000 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-501 (NONE)<br>5.00-501 KEV<br>8.88+051 ANG.<br>9.20-501 (NONE)   | CODE VALUE<br>1.00+002 MESH<br>1.00-002 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+002 ANG-01<br>8.17+001 ANG.<br>9.25+001 ANG.   |
| 123456789                       | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT  | INPUT VALUE<br>1.00+000 (NONE)<br>1.00+000 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-001 (NONE)<br>6.00-001 KEV<br>8.88+001 ANG.<br>9.20-001 (NONE)<br>5.35+001 ANG.  | CODE VALUE<br>1.00+000 (NONE)<br>1.00+000 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+000 (NONE)<br>2.02+002 ANG-01<br>8.17+001 ANG.<br>9.25+001 (NONE)  |
| 1234567893                      | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT  | INPUT VALUE<br>1.00+000 (NONE)<br>1.00+000 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-001 (NONE)<br>6.00-001 KEV<br>8.88+001 ANG.<br>9.20-001 (NONE)<br>5.35+001 ANG.<br>1.73+000 (NONE)   | CODE VALUE<br>1.00+000 (NONE)<br>1.00+000 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+000 (NONE)<br>2.02+002 ANG-01<br>8.17+001 ANG.<br>9.25+001 (NONE)<br>1.73+000 (NONE)   |
| 1234567891011                   | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTM++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOP 1KEY PROTONS  | INPUT VALUE<br>1.00+000 (NONE)<br>1.00-003 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-001 (NONE)<br>6.00-001 KEV<br>8.88+001 ANG.<br>9.20-001 (NONE)<br>5.35+001 (NONE)<br>4.13-001 (NONE)   | CODE VALUE<br>1.00+000 (NONE)<br>1.00-002 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+000 (NONE)<br>2.02-002 ANG-01<br>8.17+001 ANG.<br>9.25+001 (NONE)<br>1.73+000 (NONE)<br>4.13-001 (NONE)  |
| 1234567893112                   | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA NAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEY PROTONS<br>MAX DE/DX FOR PROTONS   | INPUT VALUE<br>1.00+000 (NONE)<br>1.00-003 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-001 (NONE)<br>6.00-001 KEV<br>8.88+001 KEV<br>8.88+001 (NONE)<br>5.35+001 (NONE)<br>4.13-001 (NONE)<br>1.35+002 KEV  | CODE VALUE<br>1.00+00C (NONE)<br>1.00-002 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+00C (NONE)<br>2.02-002 ANG-01<br>8.17+001 ANG.<br>9.25+001 ANG.<br>9.20-001 (NONE)<br>1.73+000 (NONE)<br>4.13-001 (NONE)<br>1.55+002 KEV   |
| 12345678901123                  | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA NAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEY PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT   | INPUT VALUE<br>1.00+000 (NONE)<br>1.00-003 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-001 (NONE)<br>8.60-001 KEV<br>8.38+001 KEV<br>8.38+001 (NONE)<br>5.35+001 (NONE)<br>4.13-001 (NONE)<br>1.35+002 KEV<br>2.90-205 A/M##2   | CODE VALUE<br>1.00+00C (NONE)<br>1.00-002 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+00C (NONE)<br>2.02-002 ANG-01<br>8.17+001 ANG.<br>9.25+001 ANG.<br>9.25+001 ANG.<br>9.20-001 (NONE)<br>1.35+002 KEV<br>2.90-005 A/M##2   |
| 1234567890112345                | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOP 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE FESISTIVITY  | INPUT VALUE<br>1.00+000 (NONE)<br>1.00-003 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-001 (NONE)<br>8.60-001 KEV<br>8.38+001 ANG.<br>9.20-001 (NONE)<br>5.35+001 ANG.<br>1.73+000 (NONE)<br>4.13-001 (NONE)<br>1.35+002 KEV<br>2.90-005 A/MHH2<br>-1.00+050 OHMS                         | CODE VALUE<br>1.00+00C (NONE)<br>1.00-002 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+00C (NONE)<br>2.02+002 ANG-01<br>8.17+001 ANG.<br>9.25+001 ANG.<br>9.20-001 (NONE)<br>1.73+000 (NONE)<br>1.35+002 KEV<br>2.90-005 A/M##2<br>-8.85-013 V+5/0  |
| 1234567890112345<br>112345      | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##=1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOP 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE PESISTIVITY<br>SPACE DISCHARGE POT*L   | INPUT VALUE<br>1.00+000 (NONE)<br>1.00-003 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-001 (NONE)<br>8.60-001 KEV<br>8.88+001 ANG.<br>9.20-001 (NONE)<br>5.35+001 ANG.<br>1.73+000 (NONE)<br>4.13-001 (NONE)<br>1.35+002 KEV<br>2.90-005 A/M##2<br>-1.00+000 MMS<br>1.00+000 VOLTS        | CODE VALUE<br>1.00+00C (NONE)<br>1.00-002 MESH<br>-1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+00C (NONE)<br>2.02-002 ANG-01<br>8.17+001 ANG.<br>9.25+001 ANG.<br>9.20-001 (NONE)<br>1.73+000 (NONE)<br>1.35+002 KEV<br>2.90-005 A/M##2<br>-8.85+013 V-5/0<br>1.00+004 VOLTS  |
| 123456789311234567<br>111234567 | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEY PROTONS<br>MAX DE/DX FOR PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE PESISTIVITY<br>SPACE DISCHARGE POT'L<br>INTERNAL DISCHARGEPOT'L   | INPUT VALUE<br>1.00+000 METERS<br>-1.00+000 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-001 (NONE)<br>5.00-001 KEV<br>8.88+001 ANG.<br>9.20-001 (NONE)<br>5.35+001 (NONE)<br>4.13-001 (NONE)<br>1.35+002 KEV<br>2.90-205 A/M##2<br>-1.00+000 VOLTS<br>1.00+000 VOLTS<br>2.00+000 VOLTS    | CODE VALUE<br>1.03+90C (NONE)<br>1.00-002 MESH<br>-1.09+000 MHC/M<br>7.90+001 (NONE)<br>2.93+90C (NONE)<br>2.02+002 ANG-01<br>8.17+001 ANG.<br>9.25+001 ANG.<br>9.25+001 ANG.<br>9.20-901 (NONE)<br>1.73+000 (NONE)<br>1.35+002 KEV<br>2.90-905 A/M##2<br>-6.85-013 V-5/0<br>1.00+904 VOLTS<br>2.03+003 VOLTS   |
| 12345678931234567<br>11131567   | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##=1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOP 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE PESISTIVITY<br>SPACE DISCHARGE POT'L<br>INTERNAL DISCHARGEPOT'L<br>PACN INDUCEDCOND'YCOEFFT                           | INPUT VALUE<br>1.00+000 (NONE)<br>1.00+000 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-501 (NONE)<br>5.00-501 (NONE)<br>5.35+001 ANG.<br>1.73+000 (NONE)<br>4.13-001 (NONE)<br>1.35+002 KEV<br>2.90-205 A/M##2<br>-1.00+050 OHMS<br>1.00+050 OHMS<br>1.00+050 VOLTS<br>1.20-013 MH0HS3    | CODE VALUE<br>1.03+90C (NONE)<br>1.00-002 MESH<br>-1.09+000 MHC/M<br>7.99+001 (NONE)<br>2.93+90C (NONE)<br>2.02+002 ANG-01<br>8.17+001 ANG.<br>9.25+001 ANG.<br>9.20-901 (NONE)<br>1.73+000 (NONE)<br>1.73+000 (NONE)<br>1.35+002 KEV<br>2.90-905 A/M##2<br>-8.85-013 V-5/0<br>1.02+003 VOLTS<br>2.02+003 VOLTS<br>1.05-913 MH0MS3  |
| 12345678931123456789            | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##=1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOP 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE PESISTIVITY<br>SPACE DISCHARGE POT'L<br>INTERNAL DISCHARGEPOT'L<br>PACN INDUCEDCOND'YCOEFFT<br>PADN INDUCEDCOND'YPG=R | INPUT VALUE<br>1.00+000 (NONE)<br>1.00+000 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-501 (NONE)<br>5.00-501 (NONE)<br>5.35+001 ANG.<br>1.73+000 (NONE)<br>4.13-001 (NONE)<br>1.35+002 KEV<br>2.90-005 K/MH2<br>1.00+000 (NONE)<br>1.00+000 (NONE)<br>1.00+000 (NONE)<br>1.00+000 (NONE) | CODE VALUE<br>1.00+000 (NONE)<br>1.00+000 MHC/M<br>7.90+000 MHC/M<br>7.90+001 (NONE)<br>2.93+000 ANG-01<br>8.17+001 ANG-<br>9.25+001 ANG-<br>9.25+001 ANG-<br>9.25+001 ANG-<br>9.25+001 ANG-<br>1.73+000 (NONE)<br>1.35+002 KEV<br>2.90+005 A/M##2<br>-8.85+013 V=5/0<br>1.00+004 V0LTS<br>2.00+005 V0LTS<br>1.00+013 MH0MS3<br>1.00+006 (NONE)   |
| 123456789311234567899           | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOP 1KEY PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE PESISTIVITY<br>SPACE DISCHARGE POT*L<br>INTERNAL DISCHARGEPOT*L<br>PACN INDUCEDCOND*YCOEFFT<br>FADN INDUCEDCOND*YFO=ER<br>DENSITY              | INPUT VALUE<br>1.00+002 (NONE)<br>1.00+003 METERS<br>-1.00+000 MH0/M<br>7.90+001 (NONE)<br>8.60-001 (NONE)<br>8.60-001 KEV<br>8.88+001 ANG.<br>9.20-001 (NONE)<br>5.35+001 (NONE)<br>1.73+000 (NONE)<br>1.35+002 KEV<br>2.90-005 A/M##2<br>-1.00+000 KG/M#3<br>1.00+003 KG/M#3                     | CODE VALUE<br>1.00+000 (NONE)<br>1.00+000 MHC/M<br>7.90+001 (NONE)<br>2.93+000 (NONE)<br>2.02+002 ANG-01<br>8.17+001 ANG.<br>9.25+001 ANG.<br>9.25+001 (NONE)<br>1.73+000 (NONE)<br>1.35+002 MEV<br>2.90+005 A/M##2<br>-8.85+013 V=5/0<br>1.00+004 V0LTS<br>2.00+005 V0LTS<br>1.00+005 V0LTS<br>1.00+005 (NONE)<br>1.00+005 (NONE) |

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MATERIAL 5: INDO PROPERTY INPUT VALUE CODE VALUE 1.00+000 (NONE) DIELECTRIC CONSTANT 1.30+038 (NGNE) 1 1.30-003 METERS 1.30-002 MESH THICKNESS 2 -1.35+050 MH0/M 3 CONDUCTIVITY -1.02+000 MH0/M 2.44+001 (NONE) ATOMIC NUMBER 2.44+001 (NONE) 4 DELTA MAX COEFF 1.40+000 (NONE) 3.32+300 (NONE) 5 E-MAX >DEPTH\*\*-1 3.30-001 KEV 1.49-632 ANG-61 6 7 RANGE -1.00+000 ANG. 1.57+032 ANG. EXPONENT ), RANGE .30 (NONE) •00 ANG. 8 2.31+000 (NONE) 7.18+CGC ANG. RANGE > EXPONENT 9 1.00+000 (NONE) 5.55+001 (NCNE) EXPONENT 13 YIELD FOR IKEY PROTONS 4.95-001 (NONE) 4.90-001 (NONE) 11 MAX DE/DX FOR PROTONS 1.23+032 KEV 1.23+032 KEV 12 3.20-005 A/###2 3.20-005 4/###2 PHOTOCURRENT 13 -8.85-013 V-S/Q SURFACE RESISTIVITY -1.00+000 OHMS 14 1.00+064 VOLTS 15 SPACE DISCHARGE POT\*L 1.00+004 VOLTS INTERNAL DISCHARGEPOT\*L 2.30+003 VOLTS 2.00+003 VOLTS 16 1.00-013 MHOMS3 17 RADN INDUCEDCOND\*YCOEFFT 1.00-013 MHCMS3 RADN INDUCEDCOND\*YPOWER 1.30+000 (NONE) 1.00+080 (NONE) 18 1.03+003 KG/H#3 1+00+003 KG/M#3 19 DENSITY 2.00+091 -1.00+003 20 MATERIAL 5: MAGN CODE VALUE INPUT VALUE PROPERTY DIELECTRIC CONSTANT 1.00+000 (NONE) 1.00-003 METERS 1.03+038 (NONE) 1 1.00-002 MESH 2 THICKNESS CONDUCTIVITY -1.30+030 MHC/M -1.30+000 MH0/M 3 1.23+031 (NONE) 1.20+031 (NONE) ATOMIC NUMBER 4 5 DELTA MAX SCOEFF 9.20-001 (NGNE) 7.02+000 (NONE) 2.50-001 KEV 2.79-002 ANG-01 >DEPTH##=1 6 E-MAX 6.96+302 ANG. -1.00+000 ANG. 7 RANGE EXPONENT > RANGE .30 (NONE) .00 ANG. 8 1.74+000 ANG. 1.75+000 (NONE) RANGE > EXPONENT 9 2.43+501 (NONE) EXPONENT 1.33+000 (NONE) 10 2.44-CO1 (NONE) 2.44-001 (NONE) YIELD FOR IKEV PROTONS 11 2.30+002 KEV 4.00+005 A/\*\*\*2 2.30+002 KEV MAX DE/DX FOR PROTONS 12 4.00-005 A/M##2 13 PHOTOCURRENT -8.85-013 V-S/G SURFACE RESISTIVITY -1.00+008 OHMS 14 1.00+004 VOLTS 2.00+003 VOLTS 1.07+004 VOLTS SPACE DISCHARGE POT\*L 15 2.00+003 VOLTS 16 INTERNAL DISCHARGEPOT\*L 1.00-013 MHCMS3 1.00-013 MHOMS3 PADN INDUCEDCOND YCOEFFT 17 1.0C+838 (NONE) 1.30+000 (NONE) PADN INDUCEDCOND\*YPOWER 18 1.00+003 KG/M#3 1.00+003 KG/M#3 19 DENSITY -1.02+060 2.00+001 20

|                                 | MATERIAL 7: SCRE   |  |   |
|---------------------------------|--|--|---|
|                                 | PROPERTY   | INPUT VALUE  | CODE VALUE  |
| 1                               | GIELECTRIC CONSTANT  | 1.30+200 (NONE)  | 1.CO+GGE (NONE)   |
| 2                               | THICKNESS  | 1.CC-CO3 METERS  | 1.20-007 MESH   |
| - 3                             | CONDUCTIVITY   | -1.20+020 MH0/M  | -1.38+255 MH0/M   |
| 4                               | ATOMIC NUMBER  | 1.GC+CCG (NONE)  | 1.00+000 (NONE)   |
| 5                               | DELTA MAX COEFF  | .IG (NGNE)   | AGT (NONE)  |
| - 6                             | E-MAX DEPTH##+1  | 1.3C+000 KEV   | 1.38+301 ANG-01   |
| 7                               | RANGE  | 1.30+661 ANS.  | 1.50+0C1 ANG.   |
| 8                               | EXPONENT > RANGE   | 1.50+000 (NCNE)  | ANG.  |
| 9                               | RANGE > EXPONENT   | SC ANG.  | 1.50+000 (NONE)   |
| 10                              | EXPONENT   | 1.50+000 (NONE)  | 1-00+005 (NONE)   |
| 11                              | YIELD FOR IKEV PROTONS   | JC (NONE)  | ACC (NONE)  |
| 12                              | MAX DE/DX FOR PROTONS  | 1+30+668 KEV   | 1.60+000 KEV  |
| 13                              | PHOTOCURRENT   | +30 A/M##2   | .00 1/4##2  |
| 14                              | SURFACE RESISTIVITY  | -1.0C+005 0HMS   | -8.85-013 V-S/0   |
| 15                              | SPACE DISCHARGE POT <sup>®</sup> L   | 1.30+034 VOLTS   | 1-00+004 VOLTS  |
| 16                              | INTERNAL DISCHARGEPOT*L  | 2.20+003 VOLTS   | 2.00+003 VOLTS  |
| 17                              | RADN INDUCEDCOND*YCOEFFT   | 1.0C-013 MHCMS3  | 1.00-013 MH0MS3   |
| 18                              | RADN INDUCEDCOND*YPOWER  | 1.30+030 (NONE)  | 1.0C+GOD (NONE)   |
| 19                              | GENSITY  | 1.30+003 KG/M#3  | 1.00+003 KG/M#3   |
| 20                              |  | 2.30+031   | -1.39+060   |
|                                 |  |  |   |
|                                 | MATERIAL 8: KAPT   |  |   |
|                                 | MATERIAL B: KAPT<br>PROPERTY   | INPUT VALUE  | CODE VALUE  |
| 1                               | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT  | INPUT VALUE<br>3.55+660 (None)   | CODE VALUE<br>3.50+COD (NONE)   |
| 1 2                             | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS   | INPUT VALUE<br>3.50+000 (NONE)<br>1.27-034 Meters  | CODE VALUE<br>3.50+000 (NONE)<br>1.27-003 Mesh  |
| 1 2 3                           | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY   | INPUT VALUE<br>3.55+000 (NONE)<br>1.27-004 Meters<br>1.65-016 MH0/M  | CODE VALUE<br>3.50+000 (NONE)<br>1.27-003 MESH<br>1.00+016 MH0/M  |
| 1 2 3 4                         | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER  | INPUT VALUE<br>3.55+000 (NONE)<br>1.27-004 Meters<br>1.60-016 MH0/H<br>5.35+000 (NONE)   | CODE VALUE<br>3.50+000 (NONE)<br>1.27-003 MESH<br>1.00+016 MH0/M<br>5.00+000 (NONE)   |
| 12345                           | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF  | INPUT VALUE<br>3.55+000 (NONE)<br>1.27-004 METERS<br>1.60-016 MH0/H<br>5.35+000 (NONE)<br>2.10+000 (NONE)  | CODE VALUE<br>3.50+COD (NONE)<br>1.27-DD3 MESH<br>1.CC+C16 MH0/M<br>5.30+ODC (NONE)<br>4.36+CG1 (NONE)  |
| 123456                          | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##+1  | INPUT VALUE<br>3.55+000 (NONE)<br>1.27-004 METERS<br>1.60-016 MH0/M<br>5.35+000 (NONE)<br>2.10+000 (NONE)<br>1.50-001 KEV  | CODE VALUE<br>3.50+COD (NONE)<br>1.27-DOJ MESH<br>1.CC+C16 MH0/M<br>5.30+ODC (NONE)<br>4.36+CG1 (NONE)<br>8.74-DG2 ANG+C1   |
| 1234567                         | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##+1<br>RANGE   | INPUT VALUE<br>3.55+000 (NONE)<br>1.27-004 METERS<br>1.00-016 MH0/M<br>5.00+000 (NONE)<br>2.10+000 (NONE)<br>1.55-001 KEV<br>7.15+001 ANG.   | CODE VALUE<br>3.50+COD (NONE)<br>1.27-DOJ MESH<br>1.CC+C16 MH0/M<br>5.00+CDC (NONE)<br>4.36+CG1 (NONE)<br>8.74-DG2 ANG+C1<br>4.29+CD1 ANG.  |
| 12345678                        | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##=1<br>RANGE<br>EXPONENT > RANGE   | INPUT VALUE<br>3.5C+COD (NONE)<br>1.27-034 METERS<br>1.00-016 MH0/M<br>5.3C+GOD (NONE)<br>2.10+030 (NONE)<br>1.5C-CGI KEV<br>7.15+231 ANG.<br>6.3C-CQ1 (NONE)  | CODE VALUE<br>3.50+COD (NONE)<br>1.27-003 MESH<br>1.CC+C16 MH0/M<br>5.00+C0C (NONE)<br>4.36+CG1 (NONE)<br>8.74-CG2 ANG+C1<br>4.29+CG1 ANG.<br>5.52+CC2 ANG.   |
| 123456789                       | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##+1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT   | INPUT VALUE<br>3.5C+COO (NONE)<br>1.27-034 METERS<br>1.00-C16 MH0/M<br>5.3C+G30 (NONE)<br>2.10+C3C (NONE)<br>1.5C-C31 KEV<br>7.15+C31 ANG.<br>6.3C-C31 (NONE)<br>3.12+C32 ANG.   | CODE VALUE<br>3.50+COD (NONE)<br>1.27-003 MESH<br>1.CC+C06 MH0/M<br>5.30+COC (NONE)<br>4.36+C01 (NONE)<br>8.74-C02 ANG+C<br>4.29+C01 ANG.<br>5.52+CC2 ANG.<br>6.00-DC1 (NONE)   |
| 12345678901                     | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH***1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT   | INPUT VALUE<br>3.50+000 (NONE)<br>1.27-034 METERS<br>1.00-016 MH0/M<br>5.30+030 (NONE)<br>2.10+030 (NONE)<br>1.50-031 KEV<br>7.15+031 ANG.<br>6.30-031 (NONE)<br>3.12+032 ANG.<br>1.77+039 (NGNE)  | CODE VALUE<br>3.50+COD (NONE)<br>1.27-003 MESH<br>1.CC-016 MH0/M<br>5.00+COC (NONE)<br>4.36+CG1 (NONE)<br>8.74-002 ANG-C1<br>4.29+CG1 ANG.<br>5.52+CC2 ANG.<br>6.00-001 (NONE)<br>1.77+000 (NONE)   |
| 123456789011<br>111             | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##+1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEY PROTONS   | INPUT VALUE<br>3.5C+COD (NONE)<br>1.27-034 METERS<br>1.0C-C16 MH0/M<br>5.3C+G30 (NONE)<br>2.10+03C (NONE)<br>1.5C-C31 KEV<br>7.15+231 ANG.<br>6.3C-C31 (NONE)<br>3.12+C32 ANG.<br>1.77+C32 (NONE)<br>4.55+301 (NONE)   | CODE VALUE<br>3.50+COD (NONE)<br>1.27-003 MESH<br>1.CC=016 MH0/M<br>5.30+COC (NONE)<br>4.36+CG1 (NONE)<br>8.74-002 ANG-C1<br>4.29+CG1 ANG.<br>5.52+CC2 ANG.<br>6.00-001 (NONE)<br>1.77+000 (NONE)<br>4.55-001 (NONE)  |
| 12345678901127                  | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##+1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEY PROTONS<br>MAX DE/DX FOR PROTONS  | INPUT VALUE<br>3.50+000 (NONE)<br>1.27-034 METERS<br>1.00-016 MH0/M<br>5.30+030 (NONE)<br>2.10+030 (NONE)<br>1.50-031 (NONE)<br>3.12+032 ANG.<br>1.77+030 (NONE)<br>4.55-001 (NONE)<br>1.40+032 KEV  | CODE VALUE<br>3.50+COC (NONE)<br>1.27-903 MESH<br>1.CC=016 MH0/M<br>5.30+COC (NONE)<br>4.36+CG1 (NONE)<br>8.74-9C2 ANG-<br>5.52+CC2 ANG-<br>6.00-9C1 (NONE)<br>1.77+3G0 (NONE)<br>1.49+GG2 KEV  |
| 12345678901123<br>101123        | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEY PPOTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT  | INPUT VALUE<br>3.50+000 (NONE)<br>1.27-034 METERS<br>1.00-016 MH0/M<br>5.30+030 (NONE)<br>2.10+030 (NONE)<br>1.50-031 (NONE)<br>3.12+032 ANG.<br>1.77+030 (NONE)<br>4.55-001 (NONE)<br>1.40+032 KEV<br>2.30-035 A/M##2   | CODE VALUE<br>3.50+COD (NONE)<br>1.27-903 MESH<br>1.CC=016 MH0/M<br>5.30+OOC (NONE)<br>4.36+CG1 (NONE)<br>8.74-902 ANG-C1<br>4.29+C01 ANG.<br>5.52+CC2 ANG.<br>6.00-901 (NONE)<br>1.77+300 (NONE)<br>1.40+002 KEV<br>2.30-005 A/M##2  |
| 123456789011234<br>111234       | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH*#-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>YIELD FOR 1KEY PPOTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY   | INPUT VALUE<br>3.52+COO (NONE)<br>1.27-CO4 METERS<br>1.62-C16 MH0/M<br>5.32+GOO (NONE)<br>2.10+COC (NONE)<br>1.52-COI (NONE)<br>3.12+COI (NONE)<br>3.12+COI (NONE)<br>4.55-COI (NONE)<br>1.40+COI KEV<br>2.00-COS A/M##2<br>1.02+CI6 OHMS  | CODE VALUE<br>3.50+COC (NONE)<br>1.27-DOJ MESH<br>1.CC-O16 MH0/M<br>5.00+OCC (NONE)<br>4.36+CG1 (NONE)<br>8.74-OG2 ANG-C1<br>4.29+CG1 ANG-<br>5.52+CC2 ANG-<br>6.00-OC1 (NONE)<br>1.77+OG0 (NONE)<br>1.40+CG2 KEV<br>2.30-OD5 A/M**2<br>8.85+OOJ V-S/G  |
| 1234567890112345<br>1112345     | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH***1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>YIELD FOR 1KEY PROTONS<br>MAX DE/OX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY<br>SPACE DISCHARGE POT*L  | INPUT VALUE<br>3.52+COD (NONE)<br>1.27-CJ4 METERS<br>1.62-C16 MH0/M<br>5.32+G3D (NONE)<br>2.10+C3C (NONE)<br>1.52-CG1 KEV<br>7.15+231 ANG.<br>6.32-C31 (NONE)<br>3.12+C32 ANG.<br>1.77+C32 (NONE)<br>4.55-2C1 (NONE)<br>1.40+C32 KEV<br>2.33-CG5 A/M##Z<br>1.32+C34 VOLTS  | CODE VALUE<br>3.50+COC (NONE)<br>1.27-003 MESH<br>1.CC+C16 MH0/M<br>5.00+COC (NONE)<br>4.36+CG1 (NONE)<br>8.74-OG2 ANG+C1<br>4.29+CG1 ANG.<br>5.52+CC2 ANG.<br>6.00-OC1 (NONE)<br>1.77+OGC (NONE)<br>1.40+CG2 KEV<br>2.00-COS A/M##2<br>8.85+OO3 V-S/C<br>1.60+CO4 VOLTS                                      |
| 12345678901234567<br>111234567  | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>YIELD FOR 1KEY PROTONS<br>MAX DE/DX FOR PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY<br>SPACE DISCHARGE POT*L<br>INTERNAL DISCHARGEPOT*L                          | INPUT VALUE<br>3.5C+COD (NONE)<br>1.27-CJ4 METERS<br>1.02-C16 MH0/M<br>5.3C+CJ0 (NONE)<br>2.10+CJC (NONE)<br>1.5C-CJ1 (NONE)<br>1.5C-CJ1 (NONE)<br>3.12+CJ2 ANG.<br>1.77+CDD (NONE)<br>1.45+CC1 (NONE)<br>1.5C+CC1 (NONE)<br>1.5C+CC1 (NONE)<br>1.45+CC1 (NON | CODE VALUE<br>3.50+COC (NONE)<br>1.27-003 MESH<br>1.CC+C16 MH0/M<br>5.00+C0C (NONE)<br>4.36+CG1 (NONE)<br>8.74-OG2 ANG+C1<br>4.29+CG1 ANG.<br>5.52+CC2 ANG.<br>6.00-3C1 (NONE)<br>1.77+3GC (NONE)<br>1.77+3GC (NONE)<br>1.40+CG2 KEV<br>2.40+CG2 KEV<br>2.40+CG3 V-S/C<br>1.60+CG3 VOLTS<br>2.60+CG3 VOLTS    |
| 123456789011234567<br>111234567 | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##=1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEY PPOTONS<br>MAX DE/DX FOR PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY<br>SPACE DISCHARGE POT*L<br>INTERNAL DISCHARGEPOT*L<br>RADN INDUCEDCOND*YCOEFFT                          | INPUT VALUE<br>3.5C+COD (NONE)<br>1.27-CJ4 METERS<br>1.00-C16 MH0/M<br>5.JC+CJI (NONE)<br>2.10+CJC (NONE)<br>1.5C-CJI (NONE)<br>3.12+CJ2 ANG.<br>1.77+CJD (NONE)<br>3.12+CJ2 ANG.<br>1.77+CJD (NONE)<br>4.55-CC1 (NONE)<br>1.40+CJ2 KEV<br>2.JD-CJ5 A/M##2<br>1.0C+CI6 OHMS<br>1.0C+CJ3 VOLTS<br>2.CC+CJ3 VOLTS<br>1.0C+CJ3 MH0HS3   | CODE VALUE<br>3.50+COD (NONE)<br>1.27-903 MESH<br>1.CC+C06 MH0/M<br>5.30+OCC (NONE)<br>4.36+CG1 (NONE)<br>8.74-OG2 ANG+C1<br>4.29+CG1 ANG.<br>5.52+CC2 ANG.<br>6.00-3C1 (NONE)<br>1.77+3GD (NONE)<br>1.40+C02 KEV<br>2.30+C03 V-S/C<br>1.60+C03 VOLTS<br>2.60+CC3 VOLTS<br>1.00+C13 MHOMS3                    |
| 12345678901123456789            | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##+1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEY PPOTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY<br>SPACE DISCHARGE POT*L<br>INTERNAL DISCHARGEPOT*L<br>RADN INDUCEDCOND*YPOWER            | INPUT VALUE<br>3.5C+COO (NONE)<br>1.27-034 METERS<br>1.0C-C16 MH0/M<br>5.3C+G30 (NONE)<br>2.10+03C (NONE)<br>1.5C-C31 KEV<br>7.15+331 ANG.<br>6.3C-C31 (NONE)<br>3.12+C32 ANG.<br>1.77+C33 (NONE)<br>4.55-5C1 (NONE)<br>1.43+C32 KEV<br>2.33-C35 A/M##2<br>1.3C+C16 OHMS<br>1.3C+C33 VOLTS<br>1.3C+C33 MH0MS3<br>1.3C+C33 (NGNE)   | CODE VALUE<br>3.50+COD (NONE)<br>1.27-003 MESH<br>1.CC+C06 MH0/M<br>5.00+COC (NONE)<br>4.36+CG1 (NONE)<br>8.74-CG2 ANG+C1<br>4.29+CG1 ANG.<br>5.52+CC2 ANG.<br>6.00-DC1 (NONE)<br>1.77+CG0 (NONE)<br>1.40+CG2 KEV<br>2.30+CC3 V-S/C<br>1.00+CO3 V-S/C<br>1.00+CO3 VOLTS<br>1.00+CC3 MHCMS3<br>1.00+CC2 (NONE) |
| 123456789011234567890           | MATERIAL B: KAPT<br>PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##+1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEY PPOTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY<br>SPACE DISCHARGE POT*L<br>INTERNAL DISCHARGEPOT*L<br>RADN INDUCEDCOND*YPO#ER<br>DENSITY | INPUT VALUE<br>3.5C+COD (NONE)<br>1.27-CD4 METERS<br>1.CC-C16 MH0/M<br>5.JC+COG (NONE)<br>2.10+CDC (NONE)<br>1.5C-CCI KEV<br>7.15+CJI ANG.<br>6.CC-CCI (NONE)<br>3.12+CJ2 ANG.<br>1.77+COD (NONE)<br>4.55-CCI (NONE)<br>1.40+CC2 KEV<br>2.JD-CCS A/M##2<br>1.2C+CI6 OHMS<br>1.CC+CCI VOLTS<br>2.CC+CJ3 VOLTS<br>1.2C+CC3 (NONE)<br>1.3C+CC3 KG/H#3   | CODE VALUE<br>3.50+COD (NONE)<br>1.27-003 MESH<br>1.CC-016 MH0/M<br>5.00+OOC (NONE)<br>4.36+CG1 (NONE)<br>8.74-002 ANG-C1<br>4.29+CG1 ANG.<br>5.52+CC2 ANG.<br>6.00-001 (NONE)<br>1.77+000 (NONE)<br>1.40+002 KEV<br>2.10-005 A/M##2<br>8.85+003 V-S/G<br>1.00+C03 VOLTS<br>2.00+CC3 VOLTS<br>1.00+003 KG/M#3 |

MATERIAL 9: NPAI

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|  | PROPERTY  | INPUT VALUE   | CODE VALUE   |
|--|---|---|--|
| 1  | DIELECTRIC CONSTANT   | 3.50+000 (NONE)   | 3-50+000 (NONE)  |
| 2  | THICKNESS   | 5.00-035 METERS   | 5.30-034 MESH  |
| 3  | CONDUCTIVITY  | 5.9C-014 MH0/M  | 5.9C-014 MH0/M   |
| 4  | ATOMIC NUMBER   | 5-08+008 (NONE)   | 5-39+000 (NONE)  |
| 5  | DELTA MAX COEFF   | 2.10+900 (NCNE)   | 3-35+867 [NONE]  |
| 6  |   | 1-50-001 KEV  | 7-41-002 ANG-01  |
| 7  | RANGE   | -1.00+000 ANG.  | 1.55+033 ANG   |
| Å  | EXPONENT > PANCE  |   |  |
| ŏ  | PANGE > EXPONENT  | 1.35+000 ANC  | ANG.   |
| 10   | EVPONENT  |   | 1.SITCUS (NUNE)  |
| 11   | VIELD FOR INFU PROTONS  | 9.534000 (NONE)   | I-DU+DUD INGNE)  |
| 12   | MAY DE ADY EAR DOATONS  | 4.52-CUI (NCNE)   | 4.55-931 (NONE)  |
|  | HAA DEJUA FUR PROJUNS   | 1.49+062 KEV  | 1.4C+UJ2 KEV   |
| 13   |   | 2.00-305 A/###2   | 2.30-995 A/M##2  |
| 14   | SURFACE RESISTATION   | 1.20+013 OHMS   | 8.85+000 V-S/Q   |
| 13   | SPACE DISCHARGE PUITE   | 1.0C+C04 VOLIS  | 1.30+034 VOLTS   |
| 10   | INTERNAL DISCHARGEPOTTL   | 2.30+003 VOLTS  | 2.00+063 VOLTS   |
| 17   | RADN INDUCEDCOND YCOEFFT  | 1.00-013 MH0MS3   | 1.00-013 MHOMS3  |
| 18   | RADN INDUCEDCOND YPOWER   | 1.30+830 (NONE)   | 1.00+900 (NONE)  |
| 19   | DENSITY   | 1.30+033 KG/M#3   | 1.33+963 KG/M#3  |
| 20   |   | 2+30+061  | 5.90-014   |
|  | MATERIAL 10: SIO2   |   |  |
|  |   |   |  |
|  | PROPERTY  | INPUT VALUE   | CODE VALUE   |
| 1  | DIELECTRIC CONSTANT   | INPUT VALUE<br>4.30+030 (NONE)  | CODE VALUE<br>4-00+000 (NONE)  |
| 1<br>2   | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS  | INPUT VALUE<br>4.30+030 (NONE)<br>1.27-934 Meters   | CODE VALUE<br>4-00+000 (NONE)<br>1-27-003 MESH   |
| 1<br>2<br>3  | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY  | INPUT VALUE<br>4.30+030 (NONE)<br>1.27-334 meters<br>1.30-014 mhg/m   | CODE VALUE<br>4-30+830 (NONE)<br>1-27-903 MESH<br>1-60-614 MH0/M   |
| 1<br>2<br>3<br>4   | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER   | INPUT VALUE<br>4.30+030 (NONE)<br>1.27-334 Meters<br>1.30-014 Mhg/M<br>1.30+001 (NgNE)  | CODE VALUE<br>4-00+000 (NONE)<br>1-27-003 MESH<br>1-00-014 MH0/M<br>1-00+001 (NONE)  |
| 1<br>2<br>3<br>4<br>5  | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF   | INPUT VALUE<br>4.30+030 (NONE)<br>1.27-334 Meters<br>1.30-014 Mhg/M<br>1.30+001 (None)<br>2.40+030 (None)   | CODE VALUE<br>4-00+000 (NONE)<br>1-27-003 MESH<br>1-00-014 MH0/M<br>1-00+001 (NONE)<br>1-46+001 (NONE)   |
| 1<br>2<br>3<br>4<br>5<br>6   | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH==-1   | INPUT VALUE<br>4.30+030 (NONE)<br>1.27-334 METERS<br>1.30-014 MHG/M<br>1.30+001 (NONE)<br>2.40+030 (NONE)<br>4.30-001 KEV   | CODE VALUE<br>4.00+000 (NONE)<br>1.27-003 MESH<br>1.00-014 MH0/M<br>1.00+001 (NONE)<br>1.46+001 (NONE)<br>2.21-002 ANG-01  |
| 1<br>2<br>3<br>4<br>5<br>6<br>7  | DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##-1<br>RANGE  | INPUT VALUE<br>4.30+030 (NONE)<br>1.27-034 METERS<br>1.30-014 MHG/M<br>1.00+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.  | CODE VALUE<br>4.30+030 (NONE)<br>1.27-303 MESH<br>1.00+031 (NONE)<br>1.46+301 (NONE)<br>2.21-002 ANG-01<br>9.42+001 ANG.   |
| 1<br>2<br>3<br>4<br>5<br>6<br>7<br>8   | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE  | INPUT VALUE<br>4.30+030 (NONE)<br>1.27-034 METERS<br>1.30-014 MHG/M<br>1.00+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-031 (NONE)   | CODE VALUE<br>4.30+030 (NONE)<br>1.27-903 MESH<br>1.00+031 (NONE)<br>1.46+901 (NONE)<br>2.21-002 ANG-01<br>9.42+901 ANG.<br>3.41+002 ANG.  |
| 1<br>2<br>3<br>4<br>5<br>6<br>7<br>8<br>9  | DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT  | INPUT VALUE<br>4.30+030 (NONE)<br>1.27-334 METERS<br>1.30-014 MHG/M<br>1.00+001 (NONE)<br>2.40+030 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-031 (NONE)<br>1.83+002 ANG.  | CODE VALUE<br>4.30+250 (NONE)<br>1.27-303 MESH<br>1.00-014 MH0/M<br>1.30+031 (NONE)<br>1.46+301 (NONE)<br>2.21-002 ANG-01<br>9.42+001 ANG.<br>3.41+002 ANG.<br>8.10+301 (NONE)   |
| 1<br>2<br>3<br>4<br>5<br>6<br>7<br>8<br>9<br>10  | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT  | INPUT VALUE<br>4.30+03C (NONE)<br>1.27-334 METERS<br>1.30-014 MHG/M<br>1.00+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-031 (NONE)<br>1.83+002 ANG.<br>1.86+030 (NONE)   | CODE VALUE<br>4.00+000 (NONE)<br>1.27-003 MESH<br>1.00-014 MH0/M<br>1.00+001 (NONE)<br>1.46+001 (NONE)<br>2.21-002 ANG-01<br>9.42+001 ANG.<br>3.41+002 ANG.<br>8.10-001 (NONE)<br>1.86+000 (NONE)  |
| 1<br>2<br>3<br>4<br>5<br>6<br>7<br>8<br>9<br>10<br>11  | DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEY PROTONS  | INPUT VALUE<br>4.32+03C (NONE)<br>1.27-334 METERS<br>1.30-014 MHG/M<br>1.02+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-331 (NONE)<br>1.86+020 (NONE)<br>4.35-001 (NONE)   | CODE VALUE<br>4.00+000 (NONE)<br>1.27-003 MESH<br>1.00+001 (NONE)<br>1.46+001 (NONE)<br>2.21-002 ANG-01<br>9.42+001 ANG.<br>3.41+002 ANG.<br>8.10-001 (NONE)<br>1.86+000 (NONE)<br>4.55-001 (NONE)   |
| 1<br>2<br>3<br>4<br>5<br>6<br>7<br>8<br>9<br>10<br>11<br>12  | PROPERTY<br>DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH===1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR IKEV PROTONS<br>MAX DE/DX FOR PROTONS   | INPUT VALUE<br>4.32+03C (NONE)<br>1.27-334 METERS<br>1.30-014 MHG/M<br>1.02+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-031 (NONE)<br>1.83+002 ANG.<br>1.86+000 (NONE)<br>4.35-031 (NONE)<br>1.40+002 KEV  | CODE VALUE<br>4.00+05C (NONE)<br>1.27-003 MESH<br>1.00+001 (NONE)<br>1.46+001 (NONE)<br>2.21-002 ANG-01<br>9.42+001 ANG.<br>3.41+002 ANG.<br>8.10+001 (NONE)<br>1.36+00C (NONE)<br>4.55-001 (NONE)<br>1.40+002 KEV   |
| 1<br>2<br>3<br>4<br>5<br>6<br>7<br>8<br>9<br>10<br>11<br>12<br>13                                      | DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT   | INPUT VALUE<br>4.32+032 (NONE)<br>1.27-334 METERS<br>1.30-014 MHC/M<br>1.00+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-331 (NONE)<br>1.83+002 ANG.<br>1.86+030 (NONE)<br>4.55-031 (NONE)<br>1.45+032 KEV<br>2.30-035 A/M##2   | CODE VALUE<br>4.00+000 (NONE)<br>1.27-003 MESH<br>1.00+001 (NONE)<br>1.46+001 (NONE)<br>2.21-002 ANG-01<br>9.42+001 ANG.<br>3.41+002 ANG.<br>8.10+001 (NONE)<br>1.36+000 (NONE)<br>1.36+000 (NONE)<br>1.40+002 KEV<br>2.00-005 A/M##2  |
| 1234<br>5678<br>910111<br>1213   | DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH===1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY  | INPUT VALUE<br>4.30+03C (NONE)<br>1.27-334 METERS<br>1.30-014 MHG/M<br>1.00+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-031 (NONE)<br>1.83+002 ANG.<br>1.86+030 (NONE)<br>4.35-031 (NONE)<br>1.40+902 KEV<br>2.30-035 A/MTT2<br>1.30+019 0HMS  | CODE VALUE<br>4.3C+CCC (NONE)<br>1.27-303 MESH<br>1.0C+C14 MH0/M<br>1.3C+C01 (NONE)<br>2.21-002 ANG-01<br>9.42+001 ANG.<br>3.41+002 ANG.<br>8.1C+301 (NONE)<br>1.36+00C (NONE)<br>1.4C+C02 KEV<br>2.3C-905 A/M=+2<br>8.35+C06 V=5/C  |
| 12345678910112345  | DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH==-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>YIELD FOR 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY<br>SPACE DISCHARGE POT*L   | INPUT VALUE<br>4.30+03C (NONE)<br>1.27-034 METERS<br>1.30-014 MHG/M<br>1.00+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>1.83+002 ANG.<br>1.86+000 (NONE)<br>4.55-031 (NONE)<br>1.40+002 KEV<br>2.30-035 A/M##2<br>1.00+019 OHMS<br>1.00+004 VOLTS   | CODE VALUE<br>4.3C+CCC (NONE)<br>1.27-303 MESH<br>1.6C-C14 MH0/M<br>1.3C+C31 (NONE)<br>1.46+301 (NONE)<br>2.21-002 ANG-01<br>9.42+001 ANG.<br>3.41+602 ANG.<br>8.10-301 (NONE)<br>1.86+00C (NONE)<br>1.86+00C (NONE)<br>1.40+632 KEV<br>2.3C-305 A/M=+2<br>8.65+536 V-S/C<br>1.32+664 VOLTS  |
| 123456789<br>101123456   | DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT<br>VIELD FOR 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY<br>SPACE DISCHARGE POT^L<br>INTERNAL DISCHARGEPOT^L  | INPUT VALUE<br>4.30+03C (NONE)<br>1.27-034 METERS<br>1.30-014 MHG/M<br>1.00+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-031 (NONE)<br>1.83+002 ANG.<br>1.86+030 (NONE)<br>4.55-031 (NONE)<br>1.40+002 KEV<br>2.30-035 A/M##2<br>1.30+034 VOLTS<br>2.40+035 VOLTS<br>2.40+035 VOLTS   | CODE VALUE<br>4.30+000 (NONE)<br>1.27-903 MESH<br>1.00+001 (NONE)<br>1.46+901 (NONE)<br>2.21-002 ANG-01<br>9.42+901 ANG.<br>3.41+002 ANG.<br>8.10+901 (NONE)<br>1.36+000 (NONE)<br>1.36+000 (NONE)<br>1.40+002 KEV<br>2.30+005 A/M##2<br>8.35+006 V-S/C<br>1.30+003 VOLTS<br>2.00+003 VOLTS  |
| 123456789<br>101234567<br>11234567   | DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>VIELD FOR 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY<br>SPACE DISCHARGE POT*L<br>INTERNAL DISCHARGEPOT*L<br>RADN INDUCEDCOND*YCOEFFT  | INPUT VALUE<br>4.30+03C (NONE)<br>1.27-334 METERS<br>1.30-014 MHG/M<br>1.00+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-031 (NONE)<br>1.83+002 ANG.<br>1.86+030 (NONE)<br>1.86+030 (NONE)<br>1.45+032 KEV<br>2.30-035 A/M##2<br>1.30+019 OHMS<br>1.40+033 VOLTS<br>2.00+033 VOLTS<br>1.00-013 MHOMS3   | CODE VALUE<br>4.30+230 (NONE)<br>1.27-303 MESH<br>1.00+031 (NONE)<br>1.46+301 (NONE)<br>2.21-002 ANG-01<br>9.42+001 ANG.<br>3.41+002 ANG.<br>8.10-301 (NONE)<br>1.36+000 (NONE)<br>1.36+000 (NONE)<br>1.40+032 KEV<br>2.30-005 A/M=+2<br>8.65+306 V-S/C<br>1.30+003 VOLTS<br>2.00+303 VOLTS<br>1.00+213 MHOMS3   |
| 1234567890112345678<br>10112345678   | DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH++-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>VIELD FOR 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY<br>SPACE DISCHARGE POT*L<br>INTERNAL DISCHARGEPOT*L<br>RADN INDUCEDCOND*YPOWER   | INPUT VALUE<br>4.30+03C (NONE)<br>1.27-304 METERS<br>1.30-014 MHG/M<br>1.00+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-031 (NONE)<br>1.83+002 ANG.<br>1.86+030 (NONE)<br>1.86+030 (NONE)<br>1.40+032 KEV<br>2.30-035 A/M##2<br>1.30+019 OHMS<br>1.30+013 MHOMS3<br>1.00-913 MHOMS3<br>1.00+030 (NONE)                                       | CODE VALUE<br>4.30+230 (NONE)<br>1.27-303 MESH<br>1.00-014 MH0/M<br>1.30+031 (NONE)<br>1.46+301 (NONE)<br>2.21-002 ANG-01<br>9.42+001 ANG.<br>3.41+002 ANG.<br>8.10+001 (NONE)<br>1.40+002 (NONE)<br>1.40+002 KEV<br>2.30-005 A/M=+2<br>8.45+506 V-5/C<br>1.30+003 VOLTS<br>2.00+003 VOLTS<br>1.00+005 (NONE)  |
| 12345678901123456789<br>11123456789  | DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH==-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>VIELD FOR 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY<br>SPACE DISCHARGE POT'L<br>INTERNAL DISCHARGEPOT'L<br>RADN INDUCEDCOND'YPOWER<br>DENSITY   | INPUT VALUE<br>4.30+03C (NONE)<br>1.27-304 METERS<br>1.30-014 MHC/M<br>1.00+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-001 (NONE)<br>1.86+000 (NONE)<br>1.86+000 (NONE)<br>1.86+000 (NONE)<br>1.40+002 KEV<br>2.30-035 A/M##2<br>1.30+019 OHMS<br>1.30+004 VOLTS<br>2.00+003 VOLTS<br>1.30+020 (NONE)<br>1.30+021 MHOMS3<br>1.30+023 KG/M#3 | CODE VALUE<br>4.00+000 (NONE)<br>1.27-003 MESH<br>1.00+001 (NONE)<br>1.46+001 (NONE)<br>2.21+002 ANG-01<br>9.42+001 ANG.<br>3.41+002 ANG.<br>8.10+001 (NONE)<br>1.40+002 KEV<br>2.30+005 A/M=+2<br>8.45+006 V-S/C<br>1.20+004 VOLTS<br>2.00+003 VOLTS<br>1.00+000 (NONE)<br>1.00+000 (NONE)<br>1.00+000 K6/M=3   |
| 123456789011234567890112345678901123456789001123456789001123456789000000000000000000000000000000000000 | DIELECTRIC CONSTANT<br>THICKNESS<br>CONDUCTIVITY<br>ATOMIC NUMBER<br>DELTA MAX >COEFF<br>E-MAX >DEPTH##-1<br>RANGE<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>EXPONENT > RANGE<br>RANGE > EXPONENT<br>VIELD FOR 1KEV PROTONS<br>MAX DE/DX FOR PROTONS<br>MAX DE/DX FOR PROTONS<br>PHOTOCURRENT<br>SURFACE RESISTIVITY<br>SPACE DISCHARGE POT*L<br>INTERNAL DISCHARGEPOT*L<br>RADN INDUCEDCOND*YCOEFFT<br>PAON INDUCEDCOND*YPOWER<br>DENSITY | INPUT VALUE<br>4.32+032 (NONE)<br>1.27-334 METERS<br>1.30-014 MHC/M<br>1.00+001 (NONE)<br>2.40+000 (NONE)<br>4.30-001 KEV<br>1.16+002 ANG.<br>8.10-331 (NONE)<br>1.83+002 ANG.<br>1.86+030 (NONE)<br>1.85+031 (NONE)<br>1.45+032 KEV<br>2.30-035 KEV<br>2.30+03 VOLTS<br>1.32+034 VOLTS<br>2.30+033 KG/M#3<br>1.30+034 KG/M#3<br>2.30+001                               | CODE VALUE<br>4.00+000 (NONE)<br>1.27-003 MESH<br>1.00+001 (NONE)<br>1.46+001 (NONE)<br>2.21-002 ANG-01<br>9.42+001 ANG.<br>3.41+002 ANG.<br>8.10-001 (NONE)<br>1.86+000 (NONE)<br>1.86+000 (NONE)<br>1.40+002 KEV<br>2.00-005 A/M=+2<br>8.65+006 V-S/C<br>1.00+003 VOLTS<br>1.00+003 KO/M=3<br>1.00+003 KO/M=3<br>1.00+003 KO/M=3<br>1.00+003 KO/M=3<br>1.00+003 KO/M=3 |

#### MATERIAL 11: SOLA

|    | PROPERTY                           | INPUT VALUE                        | CODE VALUE                         |
|----|------------------------------------|------------------------------------|------------------------------------|
| 1  | DIELECTRIC CONSTANT                | 3-80+000 (NONE)                    | 3.80+000 (NONE)                    |
| 2  | THICKNESS                          | 1.79-024 METERS                    | 1.79-863 MESH                      |
| 3  | CONDUCTIVITY                       | 1.20-017 MH0/M                     | 1.30-017 MH0/M                     |
| 4  | ATOMIC NUMBER                      | 1.30+701 (NONE)                    | 1.30+001 (NONE)                    |
| 5  | DELTA MAX >COEFF                   | 2.35+022 (NONE)                    | 1.31+001 (NONE)                    |
| 6  | E-HAX DOEPTH++-1                   | 4.10-001 KEV                       | 3.17-002 ANG-C1                    |
| 7  | RANGE                              | 7.75+001 ANG.                      | 3.49+001 ANG.                      |
| 8  | EXPONENT > RANGE                   | 4.50-001 (NONE)                    | 2.70+002 ANG.                      |
| 9  | RANGE > EXPONENT                   | 1.56+032 ANG.                      | 4.50-001 (NONE)                    |
| 10 | EXPONENT                           | 1.73+030 (NONE)                    | 1.73+000 (NONE)                    |
| 11 | YIELD FOR IKEV PROTONS             | 2.44-001 (NONE)                    | 2.44-CGI (NONE)                    |
| 12 | MAX DE/DX FOR PROTONS              | 2.33+862 KEV                       | 2.30+092 KEV                       |
| 13 | PHOTOCURRENT                       | 2.30-005 A/M##2                    | 2.00-005 4/###2                    |
| 14 | SURFACE RESISTIVITY                | 1.30+C19 OH#S                      | 8.85+006 V-5/0                     |
| 15 | SPACE DISCHARGE POT <sup>*</sup> L | 1.00+004 VOLTS                     | 1.GC+CO4 VOLTS                     |
| 16 | INTERNAL DISCHARGEPOT*L            | 2.30+003 VOLTS                     | 2.38+383 VOLTS                     |
| 17 | RADN INDUCEDCOND*YCJEFFT           | I.JC-013 MHOMS3                    | 1.00-013 MHOMS3                    |
| 18 | RADN INDUCEDCOND*YPOWER            | 1.33+050 (NONE)                    | 1.33+530 (NONE)                    |
| 19 | DENSITY                            | 1.00+CC3 KG/H#3                    | 1.00+003 KG/M#3                    |
| 20 |                                    | 2.30+031                           | 1.30-017                           |
|    | MATERIAL 12: TEFL                  |                                    |                                    |
|    | PROPERTY                           | INPUT VALUE                        | CODE VALUE                         |
| 1  | DIELECTRIC CONSTANT                | 2+30+000 (NCNE)                    | 2.30+050 (NONE)                    |
| 2  | THICKNESS                          | 1.27-004 METERS                    | 1.27-383 MESH                      |
| 3  | CONDUCTIVITY                       | 1.00-016 MH0/M                     | 1.30-016 MH0/M                     |
| 4  | ATOMIC NUMBER                      | 7.00+000 (NONE)                    | 7.30+032 (NONE)                    |
| 5  | DELTA MAX DOGEFF                   | 3.00+000 (NONE)                    | 2+27+001 (NONE)                    |
| 6  | E-MAX DEPTH**-1                    | 3-30-001 KEV                       | 3.83-002 ANG-01                    |
| 7  | RANGE                              | 4.54+021 ANG.                      | 1.91+COI ANG.                      |
| 8  | EXPONENT > RANGE                   | 4.30-531 (NCNE)                    | 3.65+092 ANG.                      |
| 9  | RANGE > EXPONENT                   | 2.13+002 ANG.                      | 4.00-001 (NUNE)                    |
| 10 | EXPONENT                           | 1.77+030 (NONE)                    | 1.77+000 (NONE)                    |
| 11 | TIELD FOR IKEY PROTONS             | 4.55-001 (NGNE)                    | 4.55-001 (NUNE)                    |
| 12 | MAX DEFUX FOR PROTONS              | 1.40+002 KEV                       | 1.40+082 KEA                       |
| 13 | PHOTOCURRENT                       |                                    | 2.00-005 A/H++2                    |
| 14 | SURFACE RESISTIVITY                | 1.30+016 UMFS                      | 5.85+003 ¥=5/0                     |
| 12 | SPACE DISCHANGE PUI'L              | 7.004004 40F12                     | 1.00-004 VOLIS                     |
| 10 | INTERNAL UISCHARGEPOTTL            | 2.30+033 VVL/S                     | 1. 20-013 MUCHER                   |
| 1/ | NAUN INDUCEDCUNUTTCDEFFI           | 1.3C-CID (NOME)                    | 1.00-010 (NVHE)<br>1.00-010 SUMM22 |
| 18 | HAUN INDUCEDCONDITPOWER            | 1.2UFULU (NUNE)<br>1.304007 KG/HHT | 1.38403 KG/M47                     |
| 17 | UE42111                            | 1.007933 NG/0#3                    | 1 00-014                           |
| ZU |                                    | 2.JU+00I                           | 1+00-010                           |

### MATERIAL 13: SILV

|    | PROPERTY                 | INPUT VALUE     | CODE VALUE      |
|----|--------------------------|-----------------|-----------------|
| 1  | DIELECTRIC CONSTANT      | 1.32+066 (NONE) | 1+09+989 (NONE) |
| 2  | THICKNESS                | 1.00-003 METERS | 1.00-002 MESH   |
| 3  | CONDUCTIVITY             | -1.00+000 MH0/M | -1.00+060 MH0/M |
| 4  | ATOMIC NUMBER            | 4.70+001 (NCNE) | 4.73+901 (NONE) |
| S  | DELTA MAX COEFF          | 1.00+060 (NONE) | 3.39+000 (NONE) |
| 6  | E-MAX >DEPTH##-1         | 8.30-001 KEV    | 1.58-002 ANG-01 |
| 7  | RANGE                    | 8.45+001 ANG.   | 6.93+001 ANG.   |
| 8  | EXPONENT > RANGE         | 8.20-001 (NONE) | 1.38+002 ANG.   |
| 9  | RANGE > EXPONENT         | 7.94+001 ANG.   | 8.23-CG1 (NONE) |
| 10 | EXPONENT                 | 1.74+000 (NGNE) | 1.74+G38 (NONE) |
| 11 | YIELD FOR IKEY PROTONS   | 4.90-001 (NGNE) | 4.90-001 (NONE) |
| 12 | MAX DE/DX FOR PROTONS    | 1.23+002 KEV    | 1.23+002 KEV    |
| 13 | PHOTOCURRENT             | 2.90-005 A/M##2 | 2.90-005 4/***2 |
| 14 | SURFACE RESISTIVITY      | -1.30+030 OHMS  | -8.85-013 V-S/Q |
| 15 | SPACE DISCHARGE POT'L    | 1.00+004 VOLTS  | 1.33+004 VOLTS  |
| 16 | INTERNAL DISCHARGEPOT*L  | 2.00+003 VOLTS  | 2.30+003 VOLTS  |
| 17 | RADN INDUCEDCOND YCOEFFT | 1.CC-C13 MHOMS3 | 1.00-013 MH0MS3 |
| 18 | PADN INDUCEDCOND YPOLEP  | 1.50+080 (NONE) | 1.03+000 (NONE) |
| 19 | DENSITY                  | 1.02+063 KG/H#3 | 1.00+003 KG/M#3 |
| žα |                          | 2.00+001        | -1.35+968       |

### 5. TRILIN AND THE PLASMA ENVIRONMENT

#### 5.1 TRILIN

TRILIN is the module that calculates charging. In this sense it is at the core of the NASCAP program. It uses the object definition, capacitance and shadowing information, calculated by the modules OBJDEF, CAPACI, and HIDCEL, to determine the current collected by the object, and the electrical potential throughout the computational space.

TRILIN also reads the Flux Definition file. This is the second major user input file and describes the plasma environment.

#### 5.2 NASCAP ENVIRONMENTS

NASCAP is able to simulate the charging of objects in space and in a test tank. For charging in space the user is able to define the energy distribution function of the ambient plasma (or plasma spectrum) and its angular distribution. In a test tank the ambient plasma is derived from particle guns. Single or multiple gun tests may be simulated, involving electrons, ions or both. Each of these options is examined in detail in the following sections.

## 5.3 FLUX DEFINITION FILE

Information describing the plasma environment is written in file IFLUX (Chapter 2) and is read by NASCAP module TRILIN. TRILIN is the module that actually carries out the calculations of potentials and currents. Just like the other user input files (2.6) IFLUX contains sequences of secondary <u>keywords</u> and their parameter cards. TRILIN reads and interprets these keywords. The flux definition file IFLUX is best summarized individually for each environment type. Let us examine each of these in turn beginning with plasma spectra.

The energy distribution function of a set of like particles i,  $f_i(E)$ , is the number density having energy between E and E + dE. The flux due to these particles across any plane is given by:

$$I_{i}(E) = \frac{2\pi E}{m^{2}} f_{i}(E)$$

Each set of particles (electrons and ions) may have its own distribution function  $f_i(E)$ . NASCAP allows two types of analytical representation for  $f_i(E)$ . An arbitrary definition of  $f_i(E)$  is also possible via tabular input of  $f_i(E)$  versus E. The two analytical forms are single Maxwellian and double Maxwellian.

#### 5.4.1 SINGLE MAXWELLIAN (TYPE 2)

The SINGLE MAXWELLIAN representation has the form

$$f_{i}(E) = N_{i} \left(\frac{m_{i}}{2\pi T_{i}}\right)^{3/2} e^{-E/T_{i}}$$

where  $N_i$  is the density of particle species i,  $T_i$  is their temperature and  $m_i$  their mass.

The user is required to tell NASCAP the density and temperature for both ions and electrons. NASCAP assumes that all ions are protons!

This information is entered in the flux definition file following one of these three keywords.

SINGLE MAXWELLIAN = call single Maxwellian plasma spectrum TYPE 2

Note that only the first four characters in each word are significant.

Both are equivalent and tell TRILIN to assume a Maxwellian environment for <u>both</u> ions and electrons and to expect at least two parameter cards to follow immediately.

The parameter cards have the form: "quantity" "units" Four quantities must be specified on four cards: Electron Temperature Ion Temperature Electron Density Ion Density The units understood by TRILIN are as follows:

> Density . <u>Temperature</u> "CGS" (cm<sup>-3</sup>) "KEV" "MKS" (m<sup>-3</sup>) "EV" "JOULES" "ERGS" "KELVIN"

Each card consists of a number followed by a unit. The unit tells TRILIN whether the number refers to a temperature or a density. For example

"5 KEV" is understood as a temperature of 5 keV. But "5 MKS" is understood as a density of 5 m $^{-3}$ .

The first density and temperature read by TRILIN following the single Maxwellian keyword are assigned to the ELECTRONS. The last density and temperature are assigned to the IONS. TRILIN expects to find <u>at least one</u> density and one temperature (in which case both ions and electrons are assumed the same parameters). Any less will cause an error. More than two of either results in middle cards being ignored.

```
For example,
             SINGLE
             1. CGS
             10. KEV
             END
defines a plasma with density 1 \rm cm^{-3} and temperature 10 keV.
The file
       SINGLE
             0.1 CGS
             3.0E+5 MKS
             2000 EV
             3.5 KEV
             END
assigns the following quantities:
             Electron density N_e = 0.1 \text{ cm}^{-3}
             Electron temperature T_e = 2.0 \text{ keV}
Ion density N_i = 0.3 \text{ cm}^{-3}
             Ion temperature T_i = 3.5 \text{ keV}
The same effect is brought about with the file:
             MAXW
             2000 EV
             0.1 CGS
             3.0E+5 MKS
             3.5 KEV
             END
However
```

MAXW 3.5 KEV 2000 EV 0.1 CGS. 3.0E+5 MKS END reverses the temperatures:  $N_e = 0.1 \text{ cm}^{-3}$   $T_e = 3.5 \text{ keV}$   $N_i = 0.3 \text{ cm}^{-3}$  $T_i = 2.0 \text{ keV}$ 

Note that <u>all</u> plasma definition "blocks" are terminated with an 'END' statement.

#### 5.4.2 DOUBLE MAXWELLIAN (TYPE 4)

The double Maxwellian form is the sum of two single Maxwellians.

$$f_{i}(E) = N_{1}^{i} \left( \frac{m_{i}}{2\pi T_{1}^{i}} \right)^{3/2} e^{-E/T_{1}^{i}} + N_{2}^{i} \left( \frac{m_{i}}{2\pi T_{2}^{i}} \right)^{3/2} e^{E/T_{2}^{i}}$$

The user must specify two densities  $(N_1^i \text{ and } N_2^i)$  and two temperatures  $(T_1^i \text{ and } T_2^i)$  for each particle species. Again NASCAP assumes that all ions are protons.

This information is entered in the flux definition file following the keyword:

DOUBLE = call double Maxwellian plasma spectrum

This tells TRILIN to assume a double Maxwellian environment for <u>both</u> ions and electrons. TRILIN then expects four parameter cards to follow immediately.

The parameter cards have the form:

"species quantity units temperature units" Each card must contain a temperature and a density. Just like the single Maxwellian spectrum definition (5.4.1) the units indicate whether the preceding number is a density or a temperature. The same set of units as for a single Maxwellian are understood by TRILIN for double Maxwellian. For example

"ELECTRONS 0.1 CGS 1.E6 JOULES" defines one component of a double Maxwellian for the electrons having a density  $(N_i^e) = 0.1 \text{ cm}^{-3}$ , and a temperature  $(T_i^e)$  of  $10^6$ joules. Note that the <u>density must precede the temperature</u> definition on the card. Four parameter cards completely define the eight parameters required for a double Maxwellian. The order is unimportant since no significance is attached to which density and temperature are associated with Maxwellian components one and two. For example

| DOUBLE    |       |     |         |
|-----------|-------|-----|---------|
| ELECTRONS | 0.2E6 | MKS | 8 KEV   |
| IONS      | 6     | CGS | 0.3 KEV |
| ELECTRONS | 0.5   | CGS | 6000 EV |
| PROTONS   | 1.E6  | MKS | 10 KEV  |
| END       |       |     |         |

defines a double Maxwellian with the following parameters:

| $N_1^e = 0.2 \text{ cm}^{-3}$ | $N_1^i = 0.6 \text{ cm}^{-3}$ |
|-------------------------------|-------------------------------|
| $T_1^e = 8 \text{ keV}$       | $T_1^i = 0.3 \text{ keV}$     |
| $N_2^e = 0.5 \text{ cm}^{-3}$ | $N_2^i = 1.0 \text{ cm}^{-3}$ |
| $T_2^e = 6 \text{ keV}$       | $T_2^i = 10 \text{ keV}$      |

Note that the words 'IONS' and 'PROTONS' are interchangeable and that the whole "block" is terminated with an 'END' card.

#### 5.4.3 'DIRECT' MODE (TYPE 5)

An arbitrary plasma spectrum may be entered as tabulated data. A list of values for  $F_i(E)$ ,  $F_e(E)$  and E can be read by TRILIN and "DIRECTly" integrated (by numerical means) to provide currents. No fitting to analytical forms is involved during the integration, although a rough fit to a Maxwellian is made to provide parameters for the direct numerical integration itself. The data must be entered in a very specific format. This is given in Figure 5.1. The magnetic field vectors, sun vectors, intensity and angles mentioned are all optional. The remaining information is mandatory. The tabulated data is read from a separate file ISPCTR. The default value for ISPCTR is 9. The flux definition file IFLUX must contain the following cards:

> DIRECT YEAR <year> DAY <day> TIME <time in seconds> END

The order of the YEAR, DAY and TIME cards are irrelevant. For example DIRECT

DAY 272 YEAR 1981 TIME 60013 END

in the flux definition file will cause TRILIN to look in file ISPCTR for the tabulated data set labeled with the date Day 272 1981 and time 60013 seconds. If no such data set exists an error will occur.

'DIRECT' does not work well with data that is not fairly smooth or is highly non-Maxwellian. Both of these properties cause "multiple roots" or more than one equilibrium potential and subsequent potential calculations become unstable. It is usually preferable to fit tabulated data to double Maxwellian terms prior to using the code.

#### 5.5 ANGULAR DISTRIBUTIONS

Plasmas having the spectra described in Section 5.4 (Maxwellian, Double Maxwellian and Direct) may have one of two possible angular distribution functions.

For NASCAP operating in the DIRECT mode to be able to read in the tabulated data it must be prepared according to the following specifications and format: 1. Magnetic Tape Characteristics Spectra can be provided on a coded 9 track magnetic tape with the following characteristics: unlabelled 1600 bpi EBCDIC or ASCII coded fixed length records: 80 characters per record fixed block size: 20 records per block 2. Each data tape will consist of header records followed by repeated series of data records. The data will be read by a FORTRAN program using the FORMAT statements indicated below: HEADER RECORD 1. DETECTOR FORMAT (80A1) Identifies the detector(s) used to obtain the data. HEADER RECORD 2. SOURCE FORMAT (80A1) Identifies the individual(s) responsible for preparing the data. HEADER RECORDS 3. through 10. COMMENTS FORMAT (80A1) Any relevant information regarding the data can be included here, such as date data tape was generated, detector mode of operation, and what corrections have been applied to the raw data. HEADER RECORD 11. YEAR, DAY, SEC, FORMAT (10F8.0) Year, DAY, SEC, YEAR<sub>0</sub>, DAY<sub>0</sub>, SEC<sub>0</sub> = time of earliest spectrum on tape YEAR<sub>1</sub>, DAY<sub>1</sub>, SEC<sub>1</sub> = time of latest spectrum on tape Each series of data records will represent a complete energy scan by the detector.

Figure 5.1. Format for tabulated spectral data.

```
DATA RECORD 1. YEAR, DAY, SEC, NBINS, DELTA, VSAT, |\vec{S}|,
                 SX, SY, SZ
                                                      FORMAT (10F8.0)
     YEAR, DAY, SEC = time energy scan was begun
     NBINS = number of distinct energy bins in the scan
     DELTA = time (seconds) between each data point in the scan
              of the spectrum
     VSAT = satellite potential during scan (volts)
      |\vec{S}| = sun intensity (1.0 = full sun)
     SX, SY, SZ = normalized sun direction vector components
                   at start of scan
DATA RECORDS 2. through (NBINS+1). ENERGY, log<sub>10</sub>(F<sub>i</sub>),
                 \log_{10}(F_e), \Omega, \alpha, BX, BY, BZ FORMAT (10F8.0)
     Each of these records represents a data point on the scan
     of the energy range
     ENERGY = energy (eV)
     F_i = ion distribution function (sec<sup>3</sup>/m<sup>6</sup>)
     F_e = electron distribution function (sec<sup>3</sup>/m<sup>6</sup>)
     Ω
         = detector view angle (degrees)
     a = pitch angle (degrees)
     BX, BY, BZ = magnetic field vector components
                   (nT = 10^{-9} W/m^2)
     (The \alpha value is redundant since it can be calculated from \Omega
     and the magnetic field vector.)
DATA RECORD NBINS+2. (END OF DATA MARKER)
                                               FORMAT (10F8.0)
     This record will contain any negative real number to
     indicate the end of the spectral scan. (This record is
     redundant since NBINS is known.)
```

Figure 5.1. Format for tabulated spectral data (concluded).

### 5.5.1 ISOTROPIC INCIDENCE

NASCAP assumes an isotropic angular distribution function by default. This means that all angles of incidence ( $\Theta$ ) for collected particles are equally probable; i.e., the angular distribution function f( $\Theta$ ) is a constant. No keywords or other statements are required to specify isotropic incidence.

#### 5.5.2 ANISOTROPIC INCIDENCE

NASCAP allows for an anisotropic angular distribution function  $f(\phi)$  of the form

 $f(\phi) = a + b \cos^2 \phi.$ 

This describes a superposition of an isotropic (spherical) component and a directional (dumb-bell) component. The theoretical background to this model is discussed in Section 5.10.1. The angle  $\phi$  is the angle between a particle velocity and the magnetic field vector. The direction of the magnetic field (and hence the "aligned" direction) is chosen by the user as a run option ("B FIELD" - 6.4.1). The default direction is along the Z axis.

The remaining parameters "a" and "b" are actually just one parameter (R) for a normalized function  $f(\phi)$ . The parameter R is the ratio of directional to isotropic flux (current) components.

R = 3 b/a.

R may have different values for ions and electrons. R and hence the degree of anisotropy may also depend on the energy of the particles.

An anisotropic angular distribution function is specified by including the keyword 'ANISOTROPIC' before the END card of a plasma spectrum block. TRILIN reads the 'ANISOTROPIC' card and then expects

to find at least two parameter cards defining values for R. For example, the flux definition file:

SINGLE 0.1 KEV 0.3 KEV 0.1 CGS 0.2 CGS ANISOTROPIC KEV 1. ERATIO 0.5 KEV 2. IRATIO -0.2 END END

defines plasma with a single Maxwellian spectrum with densities and temperatures

 $N^{e} = 0.1 \text{ cm}^{-3}$   $T^{e} = 0.1 \text{ keV}$   $N^{i} = 0.2 \text{ cm}^{-3}$  $T^{i} = 0.3 \text{ keV}$ 

The angular distribution is the standard anisotropic form with a ratio

R = 0.5 (electrons)

and

R = -0.2 (ions).

Parameter cards defining ratios for electrons have the form:

"units number ERATIO number" For ions the form is similar but with keyword 'IRATIO'

"units number IRATIO number"

TRILIN expects to find at least two cards, one defining a ratio for electrons and one defining a ratio for ions. For any less than this an error will occur.

The ratio R may range from -0.9 to  $\infty$ . Negative values give "loss-cone" distributions, positive values give "gain-cone" distributions and R = 0 describes an isotropic distribution. This is discussed further in Section 5.10.1.

The first two parameters on the card specify an energy to be associated with the R value. The units of energy accepted are 'ERGS', 'JOULES', 'KEV', 'EV' and 'KELVIN'. Up to ten RATIO cards may be included in the plasma spectrum block for each species. In this way R may depend on energy. The R values known for particular energies may be entered on different cards and NASCAP will linearly interpolate between them for intermediate energies. For example, the cards

```
ANISOTROPIC
1 KEV ERATIO 1
3 KEV ERATIO 0.5
5000 EV ERATIO 0.9
0.1 KEV IRATIO 0
END
```

give the following energy dependence for R for the electrons

| Energy (keV) | R Value |
|--------------|---------|
| 0            | 1       |
| 0.5          | 1       |
| 1.0          | 1       |
| 2.0          | 0.75*   |
| 3.0          | 0.5     |
| 3.5          | 0.6*    |
| 4.0          | 0.7*    |
| 5.0          | 0.9     |
| 100.0        | 0.9     |

\*linearly interpolated values.

Note that all energies equal to and below the lowest declared energy (1.0 keV) are assigned the same R value. In the same way all energies equal to and above the highest declared energy are assigned the same associated R value. Thus if only one ratio card is declared (such as for the ions in the example above) the energy value is irrelevant since all energies are assigned the same R value.

In our example the ions are chosen to have isotropic incidence.

NASCAP does not order the cards according to energy. For sensible results the cards for each species <u>must</u> be entered in <u>ascending order</u> of energy. It is possible to read the anisotropic flux ratio (or parameter) cards from a separate file. This is achieved by including a file number after the keyword 'ANISOTROPIC', e.g.,

#### ANISOTROPIC 19

will cause TRILIN to look for parameter cards in file 19. As soon as an 'END' card is encountered TRILIN returns to the file containing the 'ANISOTROPIC' card and continues to read from there. Blocks of anisotropic flux ratio cards must <u>always</u> be terminated with an END card.

If no file number is included following the 'ANISOTROPIC' keyword, TRILIN expects the ratio cards to follow immediately in the <u>same</u> file. An 'END' card is <u>still</u> needed however. Note in our first example the presence of <u>two</u> 'END' cards: one for the anisotropic flux and one for the plasma spectrum. Figure 5.2a,b,c show three sample files associated with a DIRECT plasma spectrum and an ANISOTROPIC angular distribution.

#### 5.6 UPDATE

In Chapter 1 we discussed how NASCAP calculates currents and potentials for sequences of <u>timesteps</u>. Each timestep has a chosen duration of 'DELTA' seconds. A single NASCAP run may be made specifying that 'NCYC' cycles or timesteps should take place. The elapsed time of the charging simulation at the end of the run would then be NCYC x DELTA seconds. Parameters NCYC and DELTA are chosen by the user as run options (6.2.2 and 6.2.7). For example if NCYC is chosen to be 5 and DELTA is chosen to be 10 seconds, then at the end of the NASCAP run the elapsed time would be 5 x 10 = 50 seconds and 5 timesteps would have taken place. Sometimes NASCAP adjusts the timestep for one or two timesteps itself to accommodate rapid changes in potential (LONGTIMESTEP - Section 6.2.6). If this happens the

| inP! |   |           |                  |           |                  |                |          |          |                                       |      |
|------|---|-----------|------------------|-----------|------------------|----------------|----------|----------|---------------------------------------|------|
|      | 1:  | OETECTUR. | NURTH/SU         | NTCHOLS   | ic-y<br>Iz ucsid |                |          |          |                                       |      |
|      | 31  | COMMENTS: | SACKGROU         | NO COUNT  | SET AT           | 100            |          |          |                                       |      |
|      | 4: COMMENTS POTENTIAL ESTIMATED FROM DISTRABUTION FUN |           |                  |           |                  |                |          |          |                                       |      |
|      | SICONMENTS)NO SUN VECTOR OR ABSOLUTE ATTITUDE INFORM  |           |                  |           |                  |                |          |          |                                       |      |
|      | 7:COMMENTS)THE POTENTIAL IS CHANGING MOST RAPIDLY     |           |                  |           |                  |                |          |          |                                       |      |
|      | 8:COMMENTS WE CONE OUT OF ECLIPSE ABOUT 17:15         |           |                  |           |                  |                |          |          |                                       |      |
|      | 71  | COMMENTS  | FOR ABOU         | IT 40 MIN | NITES AFTE       | R THIS         | POTENTIA | NLS ARE  |                                       |      |
|      | 1011  | 4979-     | 171LT KUUG<br>87 | 59400     | 4979             | 87             | 63053    |          |                                       |      |
|      | 12:   | 1979      | 97               | 59473     | <b>64</b>        | 0.25           | 0.       | -1.00    | 0.00                                  | 0.00 |
|      | 13:   | -3.90     | 0.00             | 0.00      | 0.00             | 96.20          | -12.09   | -173.27  | 90.26                                 |      |
|      | 141   | -1.60     | 0.00             | -44 49    | 0.00             | 94.50          | -11.80   | -462.32  | 408.95                                |      |
|      | 161   | 4.00      | 0.00             | -12.91    | 0.00             | 86.50          | -11.30   | -162.32  | 108.75                                |      |
|      | 17:   | 7.40      | 0.00             | -14.34    | 0.00             | 96.50          | -11.90   | -162.32  | 108.95                                |      |
|      | 18:   | 11.40     | 0.00             | -14.86    | 0.00             | 86.30          | -11.80   | -149.58  | 120.12                                |      |
|      | 201   | 21.20     | 0.00             | -15.64    | 0.00             | 86.80          | -11.80   | -449.58  | 126.12                                |      |
|      | 21:   | 27.20     | 0.00             | -15.82    | 0.00             | 86.80          | -11.80   | -149.58  | 126.12                                |      |
|      | 22;   | 34.00     | 0.00             | -15.92    | 0.00             | 87.00          | -12.09   | -134.77  | 141.54                                |      |
|      | 231   | 41.70     | 0.00             | -16.03    | 0.00             | 87.00          | -12.09   | -134.77  | 141.54                                |      |
|      | 25:   | 61.30     | -12.22           | -16.08    | 0.00             | 87.00          | -12.09   | -134.77  | 141.54                                |      |
|      | 26:   | 73.10     | 0.00             | -16.14    | 0.00             | 87.20          | -42.09   | -448.75  | 455.79                                |      |
|      | 27:   | 86.60     | -12.52           | -10.10    | 0.00             | 87.20          | -12.07   | -148.75  | 155.79                                |      |
|      | 291   | 149.90    | 0.00             | -16.27    | 0.00             | 17.20          | -12.09   | -118.75  | 155.79                                |      |
|      | 30:   | 140.30    | -12.94           | -16.31    | 0.00             | 87.50          | -12.09   | -100.98  | 167.95                                |      |
|      | 31:   | 163.60    | -12.77           | -16.36    | 0.00             | 37.50<br>97 5A | -12.09   | -100.98  | 10/.75                                |      |
|      | 321   | 220.90    | -13.33           | -16.35    | 0.00             | 87.50          | -12.09   | -100.98  | 167.95                                |      |
|      | 341   | 255.90    | -12.83           | -16.37    | 0.00             | 87.70          | -12.09   | -82.02   | 175.04                                |      |
|      | 35:   | 295.90    | -42.96           | -16.43    | 0.00             | 97.70          | -12.09   | -92.02   | 478.04                                |      |
|      | 362   | 341.80    | -13.41           | -16.55    | 0.00             | 37.70          | -42.09   | -92.02   | 178.04                                |      |
|      | 38:   | 454.60    | -13.65           | -16.59    | 0.00             | 87.90          | -12.09   | -62.18   | 185.80                                |      |
|      | 39:   | \$23.50   | -13.29           | -16.70    | 0.00             | 37.90          | -12.09   | -62.18   | 185.30                                |      |
|      | 401   | 60Z.+0    | -13.39           | -16.85    | 0.00             | 8/.90          | -12.07   | -62.18   | 185.80                                |      |
|      | 42:   | 796.20    | -13.48           | -17.03    | 0.00             | 88.10          | -12.09   | -41.71   | 191.44                                |      |
|      | 43:   | 914.60    | -13.71           | -17.14    | 0.00             | 98.10          | -12.09   | -41.71   | 191.44                                |      |
|      | 44:   | 1050.20   | -13.59           | -17.26    | 0.00             | 88.10          | -12.09   | -44.74   | 194.44<br>494.54                      |      |
|      | 431   | 1203.30   | -13.63           | -47.50    | 0.00             | 38.30          | -42.09   | -20.37   | 195.00                                |      |
|      | 47 :  | 1586.90   | -13.83           | -47.70    | - 0.00 -         | 98.30 -        | -12.09   | -20.39   | 195.00                                |      |
|      | <b>48:</b>  | 1820.00   | -13.62           | -47.89    | 0.00             | 88.30          | -12.09   | -20.39   | 195.00                                |      |
|      | 50.   | 2087.00   | -13.31           | -18.20    | 0.00             | 38.30          | -12.39   | 4.05     | 496.19                                |      |
|      | 51:   | 27 42.50  | -13.95           | -48.33    | 0.00             | 98.40          | -12.39   | 1.05     | 196.19                                |      |
|      | 52:   | 3443.20   | -14.07           | -18.58    | 0.00             | 38.40          | -42.39   | 1.05     | 196.19                                |      |
|      | 53:   | 3402.00   | -44.04           | -18.30    | 0.00             | 38.40          | -42.59   | 22.37    | 195.00                                |      |
|      | 35:   | 4728.70   | -14.37           |           | 0.00             | 38.40          | -12.59   | 22.37    | +95.00                                |      |
|      | Sór   | 5417.40   | -14.33           | -19.74    | 0.00             | 88.40          | -12.69   | 22.37    | 195.00                                |      |
|      | 57:   | 5206.00   | -14.40           | -19.35    | 0.00             | 53.40          | -12.07   | 43.40    | 195.00                                |      |
|      | 591   | 3442.70-  |                  | -20.72    | 0.00             | - 38- 50-      | -42.99   | - 43.+0- | 49+ 44                                |      |
|      | áð:   | 9326.40   | -14.59           | -20.97    | 0.00             | 98.50          | -42.78   | 43.40    | 494.44                                |      |
|      | 54:4  | 10681.70  | -14.47           | -20.96    | 0.00             | 38.30          | -12.98   | 43.40    | 194.44                                |      |
|      | 43:4  | 4010.50   | -14.39           | -21.24    | 0.00             | 38.50          | -13.29   | 53.37    | 185.31                                |      |
|      | ó4 : '  | 16045.00  | -15.05           | -21.48    | 0.00             | 88.50          | -13.28   | 63.87    | 185.5                                 |      |
|      | 55: 1   | 18374.60  | -15.37           | -22.22    | 0.00             | 38.30          | -13.28   | 53.87    | 195.51                                |      |
|      | 67:2  | 24096.00  | -15.49           | -21.75    | 0.00             | 98.40          | -13.58   | 83.74    | 177.44                                |      |
|      | 68:2  | 27592.90  | -15.70           | -21.78    | 0.00             | 88.40          | -13.58   | 83.74    | 177.44                                |      |
|      | 5913  | 31596.90  | -15.30           | -22.17    | 0.00             | 88.40          | -13.38   | 83.71    | 177.44                                |      |
|      | 79:2  | 36181.50  | -16.08           | -22.28    | 0.00             | 98.50          | -13.30   | 402.94   | 167.06                                |      |
|      | 72:4  | 7441.40   | -16.02           | -23.30    | 0.00             | 88.50          | -13.58   | 102.95   | 467.0±                                |      |
|      | 73:5  | 4323.40   | -16.47           | -22.57    | 0.00             | 88.50          | -13.58   | 102.95   | 167.06                                |      |
|      | 74:0  | 52203.30  | -16.35           | -23.23    | 0.00             | 98.40<br>98.40 | -13.3/   | 120.48   | 154.70                                |      |
|      | 76:8  | 1556.60   | -47.54           | -23.28    | 0.00             | 88.40          | -13.37   | 120.48   | 154.90                                |      |
|      | 77:   | -1.       |                  |           |                  |                |          |          |                                       |      |
|      | 78:   | 1979      | 37               | 57673     | 64               | 0.25<br>90 AN  | 0.       | -1.00    | 0.00                                  | 0.00 |
|      | 301   | -1.70     | 0.00             | 0.00      | 0.00             | 70.00          | 0.95     | 163.47   | -106.53                               |      |
|      | 84:   | 1.00      | 0.00             | -11.15    | 0.00             | 90.30          | 0.95     | ·63.43   | -406.33                               |      |
|      | 82:   | 4.00      | 0.00             | -12.76    | 0.00             | 90.30          | 0.75     | 163.43   | -106.53                               |      |
|      | 33:<br>24   | 44.40     | 0.00             | -14.24    | 0.00             | 90.20          | 1.25     | 450.40   | -123.70                               |      |
|      | 35:   | 16.00     | 0.00             |           | 0.00             | 90.20          | 4.25     | 150.40   | -123.70                               |      |
|      | 36:   | 24.20     | 0.00             | -15.05    | 0.00             | 90.20          | 1.25     | 150.40   | -423.70                               |      |
|      | 87:<br>39   | 27.20     | 0.00             | -15.27    | 0.00             | 39.30          | 0.95     | 135.38   | -139.72                               |      |
|      | 39:   | 41.70     | -11.89           | -15.72    | 0.00             | 39.30          | 0.95     | 435.98   | -139.72                               |      |
|      | 90:   | 50.70     | 0.00             | -45.90    | 0.00             | 39.80          | 0.95     | .35.28   | -437.72                               |      |
|      |   | 5 4 J 7 C | 0.043            |           |                  | a              | 47.23    |          | · · · · · · · · · · · · · · · · · · · |      |

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Figure 5.2a. File 9 (ISPCTR).

A.00

.

0.00

DIRECT TIME 59473 DAY 87 YEAR 1979 ANISOTROPIC 19 END

Figure 5.2b. File 22 (IFLUX).

| KEV | 0.1   | ERATIO  | 0.9   |
|-----|-------|---------|-------|
| KEY | 0.5   | ERAT IO | 0.5   |
| KEV | 0.2   | ERATIO  | -0.2  |
| KEV | 10.0  | ERAT IO | -0.01 |
| KEV | 50.0  | ERATIO  | 0.0   |
| EV  | 1000  | IRATIO  | -0.02 |
| Eγ  | 3000  | IRAT IO | -0.05 |
| EV  | 40000 | IRAT IO | 0.06  |
| END |       |         |       |

Figure 5.2c. File 19 (IANISO).

elapsed time might be less than 50 seconds. The elapsed time is not always under the control of the user.

Usually TRILIN reads the first environment description it finds in the flux definition file (IFLUX) and uses this same plasma spectrum and angular distribution for all of the timesteps requested (NCYC). However for extended simulations of charging, the plasma environment experienced by a spacecraft may change, sometimes quite rapidly. NASCAP is able to change plasma descriptions automatically between timesteps when operated in 'UPDATE' mode.

## 'UPDATE' mode is selected by including the keywords UPDATE ON

in the options file (6.4.14). Once NASCAP is in UPDATE mode, TRILIN looks for a fresh environment after every timestep. TRILIN looks for environment parameter cards in the file ISPCTR. ISPCTR may be chosen to be any file number as a run option (6.7). The default is file 9. TRILIN begins the first timestep by reading the flux definition file however. Here it expects to find two cards:

Plasma-type keyword

TIME seconds

The first card is one of the plasma-type keywords such as 'DOUBLE' or 'DIRECT'. This tells TRILIN what type of plasma spectrum it will be looking for in ISPCTR. The second card tells TRILIN the time in seconds to begin the simulation. No 'END' card is needed to terminate the file. For example the file

#### DOUBLE

#### TIME 58003

tells TRILIN to expect parameter cards for a double Maxwellian plasma in file ISPCTR and to begin the simulation at absolute time 58003 seconds on the day of interest.

File ISPCTR contains blocks of parameter cards labeled with the times (in seconds) that the spectra they represent are associated with. The general form is given by:

TIME n {parameter cards END

TIME n'

{ parameter cards END

TIME n''

•

-

-

•

For example:

 TIME
 57050

 ELECTRONS
 0.1 CGS
 1.2 KEV

 ELECTRONS
 0.1 CGS
 2.2 KEV

 IONS
 0.1 CGS
 3.0 KEV

 IONS
 0.1 CGS
 1.0 KEV

 END
 END
 END

TIME 58000

| ELECTRONS | 0.2 | CGS  | 5.0 | KEV |
|-----------|-----|------|-----|-----|
| ELECTRONS | 0.1 | CGS  | 3.6 | KΕV |
| IONS      | 0.3 | CGS  | 1.8 | KEV |
| IONS      | 0.2 | CG S | 4.2 | KEV |
| END       |     |      |     |     |

TIME 58050

•
For the first timestep, beginning at 58003 TRILIN looks in file ISPCTR for the most <u>recent</u> spectrum before 58003 seconds. In our example this would be the one for 58000 seconds, since the next occurs at a time <u>later</u> than 58003. The four cards following the 'TIME 58000' card are read and the double Maxwellian environment parameters set. Since no anisotropic parameters are included in the 58000 block the angular distribution is assumed to be isotropic. Suppose that after the first timestep the elapsed time has been increased by 10 seconds. The new value is 58013. TRILIN again searches ISPCTR for the most recent environment before the elapsed time. Again this is the one for 58000 so the same set of parameters are read in once more. If after several timesteps the elapsed time exceeds 58050 then the next environment in the file would be read in and the parameters would change.

In this way the most up-to-date environment is always the one used by TRILIN for each cycle.

If the time chosen in the flux file to begin the simulation is <u>before</u> the earliest time in ISPCTR an error will occur. If the elapsed time exceeds the latest time the environment will remain the same as the latest available.

The environment description included in file ISPCTR must be in ascending time order. Anisotropic parameter cards may be included but they must be part of the block and not in a separate file; i.e.,

ANISOTROPIC ianiso will cause trouble in an update ISPCTR file if IANISO  $\neq$  ISPCTR.

Files of 'DIRECT' tabulated data are perfectly acceptable. In fact the ISPCTR file shown in Figure 5.2a as an example needs no modification to be read in UPDATE mode (no 'TIME' cards are needed since each block is already labeled). 'DIRECT', 'UPDATE' and 'ANISOTROPIC' cannot all be used together, however.

### 5.7 TEST TANK

The particle pushing test tank environment was among the first features of NASCAP. It was restricted to a single electron gun at the -Z boundary of the computational space firing at a convex target. The input was so complex that only a handful of guns were ever defined. A description of the original test tank capability may be found in the 1982 version of this manual. More recently, an analytic (Type 6) test tank was incorporated in NASCAP. This new facility, described in Section 5.9, allowed multiple beam electron and ion guns at arbitrary grounded locations, in or out of the computational space, and had simple, flexible input. Being an analytic method, it was fast and free of the sampling errors inherent in particle techniques. However, as it assumed a simple form for electron and magnetic fields, it was of questionable accuracy for non-convex or differentially charged objects.

During 1983 a new formulation, replacing the original Type 1, was written with the full multigun capability of the analytic method while retaining the ability to faithfully treat complex geometry and field structure by particle tracking. Efficient data storage and buffering schemes keep the time and storage requirements within practical limits, and new current sharing algorithms ameliorate sampling errors. This capability greatly expands the applicability and use of NASCAP for simulation of charging by low intensity electron and ion beams.

#### 5.8 TEST TANK (TYPE 1)

#### 5.8.1 USAGE

The usage of the new (Type 1) test tank simulation is nearly identical to the analytic (Type 6) capability. For definition of gun characteristics, etc., refer to NASCAP Programmer's Reference Manual, Section 5.9. Note that for both Type 1 and Type 6, the environment is specified by the TANK module prior to calling TRILIN, and the environment TYPE <u>must</u> be specified in the option (RDOPT) input.

The differences between Type 1 and Type 6 usage are:

- a. In the flux (TANK module) input, the NOSHADOW option should be specified. Omission of this will result in an unnecessary shadowing calculation (and accompanying plot) for each gun.
- b. In the options (RDOPT module) input, the TANKTRAJ OFF or TANKTRAJ ON specifications may be used to obtain particle trajectory plots. Presently only the X-Z projection is plotted. (Current density plots are neither available nor planned.)
- c. Three new keywords are available in the flux (TANK module) input which relate to particle tracking. These are shown in Table 5.1. The default values should be acceptable in most cases. Values within the recommended ranges will usually result in avoiding either excessive time or excessive inaccuracy in the particle current calculations.

## TABLE 5.1. PARTICLE TRACKING KEYWORDS

| Keyword | Default | Recommended Range   | Meaning   |
|---------|---------|---------------------|---|
| VCODE   | 0.2     | 0.1 < VCODE < 0.3   | Initial code velocity<br>(mesh units per ≬t)                                |
| NSTEPS  | 500     | 200 < NSTEPS < 1000 | Maximum number of pushing<br>steps per particle                             |
| NTHETA  | 8       | 5 < NTHETA < 15     | Number of particles per beam is approximately $(\pi/4)$ NTHETA <sup>2</sup> |

The parameter VCODE governs the accuracy of particle tracking, with smaller values giving more accuracy. VCODE is the initial code velocity for each particle, and will increase for attracted particles and decrease for repelled particles. We recommend that

 $(E_{f}/E_{i})^{1/2}$  VCODE < 0.5

for attracted particles, and

 $(E_f/E_i)$  VCODE > 0.1

for repelled particles, where  $E_i$  and  $E_f$  are the initial and estimated final kinetic energies.

NSTEPS is the maximum number of steps for each particle. Ample steps should be allowed for the particle to cross the computational space; a smaller VCODE requires a larger NSTEPS.

NTHETA is the number of angular points across the beam, and determines how many particles are tracked. It should be set by

D tan (2W/NTHETA) < 1

where D is the approximate gun-target distance (grid units), and W is the half-angle of the beam.

5.8.2 EXAMPLE

Figures 5.3 and 5.4 show particle trajectories and resulting potential contours for four guns illuminating a partially covered octagon. Note that the figures show the correct octagonal symmetry.



PARTICLE TRAJECTORIES

Figure 5.3. Particle trajectories for Type 1 test tank (four single-beam guns) example.



Figure 5.4. Potential contours for Type 1 test tank example.

### 5.8.3 COMPARISON - TYPE 1 VERSUS TYPE 6

It was originally expected that the new Type 1 would require far more computer time than Type 6, especially for multibeam cases. Initial experience indicates that the time difference is very moderate, with the difference very small compared to the total NASCAP running time. Also, the sampling and sharing techniques used in the new Type 1 seem successful at minimizing particle noise. In the example above, for which both methods should be reasonably accurate, nearly identical results were obtained.

We suggest that Type 1 should usually be used whenever potentials are suspected of being sufficiently non-monopole-like to affect the results. The advantage of Type 6 is that, while Type 1 guns must be located at grounded points or outside a grounded outer boundary, Type 6 calculations can often be run in fewer (usually one) grids using monopole boundary conditions (IOUTER = 2). The number of grids in the computational space is a very significant factor in the cost of running NASCAP.

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## 5.9 TEST TANK-6 (TYPE 6) - MODULE "TANK"

# 5.9.1 GENERAL CONSIDERATIONS

Test Tank-6 (TYPE 6) allows for multiple guns emitting multiple beams. Each gun may emit either electrons or ions. The currents to the surface of the object are calculated analytically rather than by particle tracking (Section 5.8) and the calculation is both faster and more economical than Test Tank-1. However no trajectory or density plots are generated and the calculation is less accurate for highly non-spherical objects (i.e., objects that are much larger in one direction than another - like a thin rod) or for cases with a great deal of differential charging.

For objects that have parts that may shield some of its surfaces from the beam particles (non-convex objects (Section 6.4.2)), optical shadowing calculations are carried out using the HIDCEL module (8.1). HIDCEL determines the fraction of each surface cell that is effectively exposed to the beam(s) and hence the fraction of the theoretical incident current actually collected. This shadowing information is stored in file IOBPLT (default file number 19).

Because of the way NASCAP is constructed it is not practical to execute HIDCEL from inside TRILIN. Instead a separate module called 'TANK' is provided to read the flux definition file IFLUX and make any calls to HIDCEL <u>before</u> TRILIN is called to actually carry out the potential calculation. Since TRILIN does not read IFLUX in a Test Tank-6 case the flux type, telling NASCAP that this is a Test Tank-6 run, must be included as a run option. The card

TYPE 6

must be included in the options file (6.4.13).

A sample runstream might have the form:

@XQT NASCAP\*NASCAP.ABS (UNIVAC ONLY)
RDOPT {file includes TYPE 6 card}
OBJDEF
CAPACI
TANK {reads IFLUX and calls HIDCEL}
TRILIN {carries out potential calculations using }
END

If the object in the tank is to be illuminated with UV light (sunlight) then any calls to HIDCEL, SPIN or ROTATE (Chapter 8) <u>must</u> come <u>after</u> the call to TANK, but before the call to TRILIN. 'TANK' destroys any previous shadowing information; e.g.,

@ XQT NASCAP\*NASCAP.ABS. RDOPT OBJDEF CAPACI TANK HIDCEL TRILIN END

The calls to HIDCEL made by TANK as part of the particle current calculation are made automatically and require no user intervention.

Subsequent Test Tank-6 runs, using the same object and the same gun and tank arrangements, may be made without a call to TANK, providing that

- a. Shadowing information on file IOBPLT(19) is saved from previous runs (i.e., IOBPLT is a restart file), or
- b. the object is convex and no shadowing takes place.

For example:

@XQT NASCAP\*NASCAP.ABS
RDOPT (Option file with 'TYPE 6' card)
TRILIN
END

5.9.2 TEST TANK-6 FLUX DEFINITION FILE

The flux definition file IFLUX, read by TANK, consists of a series of blocks, each defining a gun. Each block consists of a 'GUN AT' keyword card to start things off, followed by four parameter cards, specifying the energy, width, current and direction of the beam, or beams, the gun is to emit. These commands are summarized in Figure 5.5. The general form is as follows:

```
<species> GUN AT x y z
ENERGY e_1 e_2 \cdots e_n unit.
BEAMWIDTH b_i b_2 \cdots b_n unit.
CURRENT c_1 c_1 \cdots c_n unit
DIRECTION x y z
```

<species> GUN AT x' y' z'

END

```
OFFSET ix iy iz
      Should be first card in file. Defines position relative to
      which gun locations are defined. Default is mesh center.
      OFFSET 0 0 0 will make gun positions defined in "absolute" grid
      location.
GUN AT
                 хуZ
ELECTRON GUN AT x y z
ION GUN AT
                 хуг
      Defines position and type of gun. If gun type not specified,
      electron gun is assumed.
   .
         | e<sub>1</sub> ... e<sub>n</sub> unit
ENERGY
ENERGIES \
      Defines beam energies of gun. Unit is 'EV' or 'KEV'. The
      default unit is 'KEV'.
BEAMWIDTH(S) b<sub>1</sub> ... b<sub>n</sub> unit
      Defines half-angle of beam. Unit is assumed to be radians,
      unless 'DEGREES' is specified.
ALL BEAMWIDTHS b unit
      Assigns b as the beamwidth for all beams of this gun.
CURRENT(S) c_1 \cdots c_n
      Specifies beam currents in amperes.
ALL CURRENTS C
      Assign c as current for all beams of this gun.
NOSHADOW
      Indicates that file IOBPLT [19] already exists for guns at these
       locations.
ION MASS m unit
       Defines mass for an ion gun. Unit is assumed kilograms unless
       'AMU' is specified.
DIRECTION x y z
       Specifies direction in which gun is pointing.
 END
       Ignore subsequent cards.
```

Figure 5.5. Summary of TEST TANK (Type 1 or Type 6) flux definition cards. (See also Table 5.1.)

Notes:

1. <species> GUN AT x y z

<species> is optional and may be 'ELECTRON' or 'ION' to define an electron or ion gun, respectively. Omission of any <species> assumes an ELECTRON gun.

<x y z> define the coordinates of the gun location (in object definition inner grid coordinates - 3.2). For example:

'GUN AT -2 0 -8'

defines an electron gun at x = -2, y = 0 and z = -8. The gun may be located outside the computational space.

2. ENERGY  $e_1 e_2 e_3 \cdots e_n$  unit

This card defines the energy of the beam(s) to be emitted from the gun. Up to 30 beams may be defined. These can all come from one gun or be shared by up to ten separate guns. Each number entered after the parameter keyword 'ENERGY' defines another energy beam, and hence another beam. The <units> at the end of the energies is optional. The default units are 'KEV'. The only other acceptable unit is EV.

- 3. BEAMWIDTH b<sub>1</sub> b<sub>1</sub> ... b<sub>n</sub> <units> This card has exactly the same syntax as the ENERGY card. The number of beamwidths defined <u>must</u> correspond exactly however to the number of energies (and currents) previously defined for this particular gun. The beamwidth is the half angle of the conical beam. The unit is assumed to be RADIANS unless DEGREES is specified as <units>.
- 4. CURRENT  $c_1 c_2 \cdots c_n$ Again the syntax is similar to that for ENERGY and BEAMWIDTH. The currents of the beams must all be in amps.

5. DIRECTION x y z

This card specifies the direction in which the gun is pointing. (i.e., in coordinates with origin at the gun location, the gun is aimed at the point x y z.

The four parameter cards may be in any order. As emphasized above, the ENERGY, BEAMWIDTH and CURRENT cards must all indicate the same number of beams.

5.9.3 'ALL' CARDS

When a set of beams all have the same energies, currents or widths, it is sometimes convenient to declare these quantities using the 'ALL' keyword; e.g.,

ALL ENERGIES e units

ALL CURRENTS C

ALL BEAMWIDTHS b units

The 'ALL' cards may <u>only</u> be used <u>after</u> at least one parameter card in conventional format has been declared to establish the number of beams. For example

```
BEAMWIDTHS b<sub>1</sub> b<sub>1</sub>
ALL CURRENTS c
ALL ENERGIES e EV
is part of a block defining a gun having two beams. The same
```

definition will fail if written in the form

ALL CURRENTS c BEAMWIDTHS b<sub>1</sub> b<sub>2</sub>

ALL ENERGIES e EV

because the current is defined before the BEAMWIDTHS card establishes the number (2) of beams.

### 5.9.4 'OFFSET'

Sometimes it is convenient to change the coordinate system from the 0 0 0 centered one that is active by default to some other, before the guns are defined. (Say the absolute system.) This is achieved with the OFFSET command

'OFFSET ix iy iz' OFFSET works in the Test Tank-6 flux definition file in exactly the same way as it does in the object definition file. This is explained in Section 3.9.3.

## 5.9.5 'NOSHADOW'

The shadowing information calculated by HIDCEL depends only on the <u>location</u> of the guns defined. For multiple NASCAP runs involving the <u>same</u> number of guns at the <u>same</u> locations illuminating the <u>same</u> object the shadowing calculations need not be repeated. If keyword 'NOSHADOW' appears in the flux definition file read by TANK, no calls to HIDCEL will be made. Instead NASCAP will assume that the required shadowing information has been written to (and saved on) file IOBPLT (19) by a previous run. This feature is particularly useful for series of runs where the user wishes to change the currents, energies and/or widths of the beam, but not the location of the guns on the tank.

## 5.9.6 THE SHAPE OF THE TANK

Like Test Tank-1 the walls of the tank are defined by the boundary of the computational space (3.2). There are no restrictions on gun placement for Test Tank-6. Likewise the computational space and hence the tank itself may be any NASCAP allowed size and shape. The cylindrical tank option (6.4.12) applies to Test Tank-6 as well as Test Tank-1. If the tank walls are grounded this must be reflected in the NASCAP calculation by choosing run option IOUTER to be 0 (6.4.5). 'IOUTER 0'

# 5.9.7 TEST TANK-6 EXAMPLES

The first example defines four guns pointing at the mesh center, each from a distance of 22.6 grid units. After echoing the gun definition input (which concludes with an 'END' card or end-of-file condition), the gun characteristics are echoed for each gun, and for each beam. It is then indicated that a shadowing calculation is being performed for each gun.

The second example defines an ion gun. As the 'NOSHADOW' specification is included, the purpose of this input is presumably to change the beamwidth, current, or energy.

Example three defines a two-beam electron gun with different current and beamwidth for each energy. Example four defines a three-beam electron gun with equal currents and beamwidths.

| 1.234567890112345678901123456789011234567890112345678901 | GUN AT 0 16 16<br>ENERGY 6. KEV<br>CURRENT S.E-6<br>BEAMWIDTH 30 DEGREES<br>DIRECTION 0 -1 -1<br>GUN AT 0 -16 16<br>ENERGY 6. KEV<br>CURRENT S.E-6<br>BEAMWIDTH 30 DEGREES<br>DIRECTION 0 1 -1<br>GUN AT 0 -16 -16<br>ENERGY 6. KEV<br>CURRENT S.E-6<br>BEAMWIDTH 30 DEGREES<br>DIRECTION 0 1 1<br>GUN AT 0 16 -16<br>ENERGY 6. KEV<br>CURRENT S.E-6<br>BEAMWIDTH 30 DEGREES<br>DIRECTION 0 -1 1<br>END |
|--|---|
|  | Gun definition input for example 1.   |
| 1.<br>2.<br>3.<br>4.<br>5.<br>6.<br>7.<br>8.             | ION GUN AT -44., 0.5, 6.2<br>NOSHADOU<br>ION MASS 14 AMU<br>BEAMWIDTH 20 DEGREES<br>CURRENT 5.E-6<br>ENERGY 5000 EV<br>DIRECTION 3. 0. 1.<br>END  |
|  | Gun definition input for example 2.   |
| 1.<br>2.<br>3.<br>4.<br>5.<br>6.                         | ELECTRON GUN AT -20 0. 0.<br>DIRECTION 4 0 0<br>ENERGIES 0.4 40 KEV<br>BEAMWIDTHS 40 40 DEGREES<br>CURRENTS 1.E-6 0.5E-6<br>END   |
|  | dun derinition input ion example 3.   |

| 1. ELECTRUM GUN HI SC 35 4  |   |
|-----------------------------|---|
| 2. DIRECTION -2 -1 0        |   |
| 3. ENERGIES 5 10 20 KEV     |   |
| 4. ALL BEAMWIDTHS 25 DEGREE | S |
| 5. ALL CURRENTS 1.E-6       | • |
| 6. END                      |   |

Gun definition input for example 4.

\*\*\*\*\*TANK 5 OBJECT DEFINITION INFORMATION BEING READ FROM FILE A SHADOWING TABLE WAS PREVIOUSLY GENERATED FOR THIS OBJECT USING THE GUNS OPTION GUN AT 0 16 16 ENERGY 6. KEV CURRENT 5.E-6 BEAMWIDTH 30 DEGREES DIRECTION 0 -1 -1 GUN AT 0 -16 16 ENERGY 6. KEY CURRENT 5.E-6 BEANWIDTH 30 DEGREES DIRECTION C 1 -1 GUN AT 0 -16 -16 ENERGY 6. KEV CURRENT 5.E-6 BEANWIDTH 3G DEGREES DIRECTION 0 1 1 GUN AT 0 16 -16 ENERGY 6. KEV CURRENT 5.E-6 BEAMWIDTH 30 DEGREES DIRECTION 0 -1 1 END GUN DEFINITION ---GUN 1 HAS BEEN DEFINED AS AN ELECTRON GUN GUN IS LOCATED AT GRID COORDINATES 9.00 25.00 25.00 GUN DIRECTION IS .00 -1.00 BEAM 1: ENERGY= 6.00+003 EV .00 -1.00 -1.00 CUT-OFF ANGLE= 30.0000 DEGREES CURRENT: 5.30-006 AMPS GUN DEFINITION -----GUN 2 HAS BEEN DEFINED AS AN ELECTRON GUN GUN IS LOCATED AT GRID COORDINATES 9.00 -7.00 25.00 GUN IS EUCHTED AT AND CONTROL -1.30 GUN DIRECTION IS .CO 1.50 -1.30 BFAM 1: ENERGY= 6.30+C23 EV CURRENT= 5.30-C06 AMPS CUT-OFF ANGLET 30.0000 DEGREES BEAM 1: ENERGY= 6.00+003 EV GUN DEFINITION -----GUN 3 HAS BEEN DEFINED AS AN ELECTRON GUN GUN IS LOCATED AT GRID COORDINATES 9.30 -7.00 -7.00 .00 1.00 1.00 GUN DIRECTION IS CUT-OFF ANGLES 30.0000 DEGREES CURRENTE 5.30-006 AMPS BEAM 1: ENERGYE 6.CO+CO3 EV GUN DEFINITION -----GUN 4 HAS BEEN DEFINED AS AN ELECTRON GUN GUN IS LOCATED AT GRID COORDINATES 9.30 25.00 -7.00 GUN DIRECTION IS .OC -1.00 1.00 BEAM 1: ENERGY= 6.00+003 EV CURPENT= 5.00-006 AMPS CUT-OFF ANGLET 30.0000 DEGREES SHADDAING BEING CALCULATED FOR GUN - 1 DISTANCE EQUALS 22.627417 FINAL NA1 = ZC SHADOWING BEING CALCULATED FOR SUN 2 DISTANCE EQUALS 22.627417 20 FINAL NAL = SHADOWING EEING CALCULATED FOR SUN DISTANCE EQUALS 22.627417 3 FINAL NA1 = 20 SHADOWING BEING CALCULATED FOR GUN DISTANCE EQUALS 22.627417 FINAL NA1 = 20 Gun definition (INGUNS and GUNSHD) output for example 1.

\*\*\*\*\*TANK 5 TON GUN AT -44., 3.5, 6.2 NOSHADOw ION MASS 14 AMU BEAMWIDTH 20 DEGREES CURRENT S.E-6 ENERGY 5000 EV DIRECTION 3. S. 1. END GUN DEFINITION GUN 1 HAS BEEN DEFINED AS AN ION GUN WITH AN ION MASS= 2.34-526 KILOGRAMS. GUN IS LOCATED AT GRID COORDINATES -35.CC GUN DIRECTION IS 3.00 .00 1.00 9.50 15.29 GUN DIRECTION IS CURRENT= 5.00-CG6 AMPS CUT-OFF ANGLE= 20.0000 DEGREES BEAM 1: ENERGY= 5.00+303 EV Gun definition (INGUNS and GUNSHD) output for example 2. \*\*\*\*\*TANK 5 ELECTRON GUN AT -20 C. G. DIRECTION 1 C D ENERGIES G.1 10 KEV BEAMWIDTHS 43 13 DEGREES CURRENTS 1.8-6 G.5E-6 ENO GUN DEFINITION -----GUN 1 HAS BEEN DEFINED AS AN ELECTRON GUN GUN IS LOCATED AT GRID COORDINATES -11.02 9.00 9.00 .00 .20 GUN DIRECTION IS 1.38 BEAM 1: ENERGY= 1.CO+GO2 EV BEAM 2: ENERGY= 1.CC+GO4 EV CUT-OFF ANGLES "3.3030 DEGREES CURRENT= 1.00-CO6 AMPS CURRENT: 5.00-CUT AMPS CUT-OFF ANGLES 10.0000 DEGREES SHADD-ING BEING CALCULATED FOR GUN 1 DISTANCE EQUALS 20.000000 FINAL NA1 = 16 Gun definition (INGUNS and GUNSHD) output for example 3. \*\*\*\*\*TANK 5 ELECTRON GUN AT 50 35 4 DIRECTION -2 -1 0 ENERGIES 5 10 20 KEV ALL BEAMWIDTHS 25 DEGREES ALL CURRENTS 1.E-6 END GUN DEFINITION -----GUN 1 MAS BEEN DEFINED AS AN ELECTRON GUN GUN IS LOCATED AT GRID COORDINATES 59.00 44.00 13.00 GUN DIRECTION IS -2.00 -1.00 BEAM 1: ENERGY= 5.03+003 EV .00 CUT-OFF ANGLES 25.0000 DEGREES CURPENTE 1.00-006 AMPS CURRENT= 1.00-CO6 AMPS CURRENT= 1.00-CO6 AMPS CUT-OFF ANGLES 25+0000 DEGREES 8EAM 2: ENERGY= 1.00+004 EV 8EAM 3: ENERGY= 2.00+004 EV CUT-OFF ANGLE= 25.000 DEGREES SHADO-ING BEING CALCULATED FOR GUN 1 DISTANCE EQUALS 61.163713 FINAL NA1 = 22 Gun definition (INGUNS and GUNSHD) output for example 4.

#### 5.10 TECHNICAL DISCUSSION

### 5.10.1 ANISOTROPIC FLUX

The NASCAP model by default allows for incident electron and ion fluxes that are isotropic; i.e., all incident directions are considered equally likely. This is not usually true for orbiting satellites.

Injection of a charged particle into a static magnetic field causes the particle to follow a spiraling trajectory about the magnetic lines of force. The component of its velocity  $\vec{v}_{||}$  along the field direction is unchanged and the radius of the spiral trajectory  $r_1$  depends on the perpendicular component  $\vec{v}$ 

 $r_{L} = \frac{mv_{\perp}}{aB}$ 

Thus for a fixed velocity magnitude, |v|, injection of a flux of charged particles into a magnetic field will lead to fast moving particles (in the field direction) with small Larmor radii  $(r_L)$ , and slower particles with large radii.

Similar events occur in the earth's magnetic field. Plasma is injected into normally low-density regions and the particles begin an orbiting trajectory along the field lines. A satellite bathed in this orbiting plasma will experience a flux with two principal components:

a. A background, essentially isotropic, flux consisting of the pre-existing low density plasma, and particles from the injected plasma, that have r much greater than the spacecraft's dimensions.

b. A directional flux, aligned with the terrestrial field, consisting of particles with  $r_L$  smaller than the spacecraft dimensions. This can be a negative contribution. If some of the injected plasma has passed the poles several times, the faster moving particles will have been "filtered out" leaving a reduced flux in the field direction (a "loss-cone").

This model is too simplistic to account for all of the varied magnetic phenomena that can occur in earth orbit. However, it does illustrate the features that are desirable in a model incorporating anisotropic flux distribution.

The form introduced into the NASCAP model consists of a background isotropic component and a  $\cos^2 \theta$  distribution aligned with the field direction. The shape of such a form depends on just one parameter: the ratio of integrated flux for each component, R.

5.10.1.1 <u>The Coordinate System</u>. The most convenient coordinate system in which to represent the aligned component is the "fan"-like system shown in Figure 5.6. The angle of incidence  $\beta$  of an incoming vector  $\vec{r}$  is related to the two angles of rotation shown,  $\Theta$  and  $\phi$ , by the relationship

 $\cos\beta = \cos\theta \cos\phi$ 

Rotating the "fan" from a plane containing the surface normal to a plane containing the vector  $\vec{r}$  only partially defines the angle  $\Theta$ . The choice of  $\Theta$  becomes unique when the second rotation ( $\phi$ ) within the plane of the "fan", to reach  $\vec{r}$ , is specified. The coordinate system is chosen so that the magnetic field direction  $\vec{B}$  has  $\phi = 0$ . This provides a reference point for all other vectors in the space above the surface, and hence fully defines the  $\Theta$ ,  $\phi$  coordinate system.



Figure 5.6. The projection of an incident vector  $\vec{r}$  upon the surface normal, in the "fan-like" coordinated system.

5.10.1.2 <u>Angular Distribution Function</u>. The angular distribution function is assumed to be symmetric about the field direction, and so the aligned component depends only upon the angle  $\psi$  made between a vector  $\vec{r}$  and  $\vec{B}$ , the field direction

$$\cos\psi = \cos(e - e_0) \cos\phi$$

The form we choose for the aligned component is simply  $\cos^2\psi$ , i.e., the angular distribution function  $f(e, \phi)$  becomes

$$f(\theta, \phi) = a + b \cos^2(\theta - \theta_0) \cos^2 \phi$$

Integration over the half-sphere must be normalized to  $2\pi$ .

$$\int_{1/2} f(e, \phi) d\omega = 2\pi$$

In the "fan" coordinate system:

$$d\omega = \cos \phi \, d\phi \, de$$

$$\therefore \int_{-\pi/2}^{\pi/2} \int_{-\pi/2}^{\pi/2} \left( a + b \cos^2(e - e_0) \cos^2 \phi \cos \phi \, de \, d\phi = 2\pi \right)$$
  
$$\therefore 2\pi a + \frac{2\pi b}{3} = 2\pi$$

i.e.,

$$a + \frac{b}{3} = 1$$

We define the ratio of integrated fluxes R as

R = 
$$b/3a$$
  
a =  $1/(1 + R)$   
b =  $3R/(1 + R)$ 

Thus overall the angular distribution function depends only upon two parameters:

- 1. The angle  $\Theta_0$  between the field direction  $\vec{n}_B$  and the surface normal  $\vec{n}$ .  $\cos \Theta_0 = \vec{n}_B \cdot \vec{n}$ .
- 2. The ratio R.

While this form for  $f(e, \phi)$  cannot represent exactly all possible angular distributions it does, in a simple way, model the most commonly observed situations of enhancement of flux incident along the field lines (R is positive) and a "loss-cone" along the field direction (R is negative). This is illustrated in Figs. 5.7 to 5.10. As R increases from -0.35 to 0.5 the distribution changes from a "doughnut" shaped loss-cone to a "dumb-bell" aligned flux form.

NASCAP allows for a table of R(E) values for different incident energies to be entered. The code then automatically takes the variation in anisotropy as a function of energy into account when calculating currents.

5.10.1.3 <u>Current Collection</u>. For particles incident with an energy E, the incoming current FIN(E) is given by:

FIN(E) = F(E) 
$$\int_{-\pi/2}^{\pi/2} \int_{-\pi/2}^{\pi/2} \left( a(E) + b(E) \cos^2(\Theta - \Theta_0) \cos^2 \phi \cos^2 \phi d\Theta d\phi \right)$$

where for a Maxwellian

$$F(E) = \frac{N}{\pi} \left(\frac{T}{2\pi m}\right)^{1/2} e^{-E/T}$$

Integrating gives

$$FIN(E) = F(E) \left[ a(E) + \frac{3b(E)}{8} \left( 1 + \frac{cos 2\theta_0}{3} \right) \right]$$

Integrating over the plasma energy spectrum gives the observed incident current FIN. The emitted current is more complex since all of the integrals cannot be performed analytically.

FOUT(E) = 
$$\frac{F(E)}{\pi} \int_{-\pi/2}^{\pi/2} \int_{-\pi/2}^{\pi/2} \delta(\beta)(E) \left[ a(E) + b(E) \cos^2(\theta - \theta_0) \cos^2 \phi \right]$$
  
cose cos<sup>2</sup> \overline de d\overline  
= 2 F(E) A(E) \delta\_{ISO}(E) + \kappa(E)

For secondary electron emission, expanding  $\cos^2(\theta - \theta_0) \cos^2 \phi$ :

$$\kappa(E) = \kappa_{1}(E) + \kappa_{2}(E)$$

$$\kappa_{1}(E) = -2b(E)\cos(2\theta_{0})F(E)C$$

$$\cdot \left[\frac{C1}{Q}\left(\frac{2}{Q^{3}} - e^{-Q}\left(\frac{1}{Q} + \frac{2}{Q^{2}} + \frac{2}{Q^{3}}\right) - \frac{1}{3}\right) + \frac{C2}{Q^{2}}\left(\frac{3}{Q^{2}} - e^{-Q}\left(1 + \frac{3}{Q} + \frac{3}{Q^{2}}\right) - \frac{1}{2}\right)\right]$$

where

$$\delta(\beta) = C \cdot \left[ C1 \left( \frac{1 - e^{-Q\cos\beta}}{Q\cos\beta} \right) - C2 \left( \frac{1 - \cos\beta + 1)e^{-Q\cos\beta}}{Q^2 \cos^2\beta} \right) \right]$$

 $Q = \alpha R$  (R is the range of electrons of energy E).

$$\kappa_2(E) = \sin^2 \theta_0 \frac{F(E)}{\pi} b(E) C \left[ C1 \cdot I_1 + C2 \cdot I_2 \right]$$

The integrals  $I_1$  and  $I_2$  are integrated numerically and tabulated for various values of Q. Interpolation finds the value of each for an unknown Q.

$$I_{1} = \int_{-\pi/2}^{\pi/2} \int_{-\pi/2}^{\pi/2} \left(\frac{1 - e^{-Q}}{Q}\right) \cos^{4} \phi \, \csc \phi \, d\phi \, d\phi$$
$$I_{2} = \int_{-\pi/2}^{\pi/2} \int_{-\pi/2}^{\pi/2} \left(\frac{1 + (Q+1)e^{-Q}}{Q^{2}}\right) \cos^{4} \phi \, \csc \phi \, d\phi \, d\phi$$

By dividing the values of FOUT(E) so calculated by the incident current normalization ANGF(E)

ANGF(E) = 
$$\frac{FIN(E)}{F(E)}$$
 =  $a(E) + \frac{3b(E)}{8} \left(1 + \frac{\cos^2 \theta_0}{3}\right)$ 

we obtain the anisotropic yield for secondary emission

$$\delta_{ANISO} = \frac{FOUT(E)}{ANGF(E)}$$

The proton secondary emission is much simpler to calculate since FOUT(E) is independent of angle:

$$s_{ANISO}^{\text{proton}}(E) = \frac{FOUT(E)}{ANGF(E)} = \frac{FOUT_{ISO}(E)}{ANGF(E)}$$

The backscatter requires an additional tabulated integral:

$$\eta(\theta) = \eta_0 e^{-\log \eta_0} e^{\log \eta_0} e^{\log \eta_0}$$

... FOUT(E) = 
$$\frac{F(E)}{\pi} \eta_0(E) e^{-\log \eta_0(E)} \kappa_{\eta_1}$$

where

$$\kappa_{\eta} = \int_{-\pi/2}^{\pi/2} \int_{-\pi/2}^{\pi/2} e^{\gamma \cos \theta} \cos^{2}(\theta - \theta_{0}) \cos^{4} \phi \cos \theta d\phi d\theta$$

where

$$\gamma = \log_{\eta_0}$$

Separating as before:

$$\kappa_{\eta} = J_{1} + J_{2}$$

$$J_{1} = 2 \cos 2\theta_{0} \left[ e^{\gamma} \left( \frac{6}{\gamma^{4}} - \frac{6}{\gamma^{3}} + \frac{3}{\gamma^{2}} - \frac{1}{\gamma} \right) - \frac{6}{\gamma^{4}} \right]$$

$$J_{2} = \sin^{2}\theta_{0} \int_{-\pi/2}^{\pi/2} \int_{-\pi/2}^{\pi/2} e^{\gamma \cos \theta \cos \phi} \cos^{4}\phi \cos \theta d\phi$$

 $J_2$  is tabulated for values of  $n_0$ .



Figure 5.7. Anisotropic flux distribution with R = -0.35.







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Figure 5.10. Anisotropic flux distribution with R = 0.10.



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Figure 5.11. Anisotropic flux distribution with R = 0.50.

## 5.10.2 TEST TANK-6 (ITYPE 6)

Test Tank-1 uses particle tracking techniques to simulate an electron gun. With this method the beam electron trajectories are approximated by calculating the actual trajectories of representative beam particles. While, in principle, enough particles could be followed to make the results as accurate as desired, in practice, computer time used to calculate each representative orbit places severe restrictions on the number of test particles followed.

Following the basic philosophy that has been successful throughout NASCAP we opted to use a simplified representation of the space potentials which allows direct integration of particle orbit. Particle shadowing is included in an approximate manner using HIDCEL with the "viewer" located at the gun position. The potential is modeled by keeping only one monopole term in the multipole expansion. This is a reasonable approximation for gun to satellite distance large compared to satellite radius.

To implement the proposed method of approach, consider a point source at a distance  $r_0$  from the center of force (Figure 5.12). The rate at which the source emits electrons with kinetic energy  $E_0$  into the interval dE<sub>0</sub> and the solid angle d $\Omega_0$  is denoted by



Figure 5.12. Geometry for electron gun aimed at a sphere.

$$\frac{d^2I}{dE_0d\Omega_0} (E_0, \vec{\Omega}_0) dE_0 d\Omega_0$$

Particles leaving the source in the range dE  $d\Omega_0$  about (E, $\vec{\Omega}$  0) cross a surface element of area  $d\vec{S}$  about the point  $\vec{r} = \vec{r}(E_0, \vec{\Omega}_0)$  on a sphere of radius a with energies in the range dE. In a steady state particle conservation requires that

$$\int_{(\Delta E_0, \Delta \Omega_0)} \frac{d^2 I}{dE_0 d\Omega_0} dE_0 d\Omega_0 = \int_{(\Delta E, \Delta S)} \vec{j} \cdot d\vec{S} dE$$
$$= a^2 \int_{(\Delta E, \Delta S)} \vec{j} \cdot \vec{n} dE d\Omega$$

where  $\vec{j}$  is the current density per unit energy at  $\vec{r}, \Delta \Omega = \Delta S/a^2$  in the solid angle subtended by  $\Delta S$  at the center of force, and  $\vec{\Omega} = \vec{n} = \vec{r}/r$ is the unit vector normal to the surface of the sphere of radius r with center at the center of force. Since  $\Delta E_0$  and  $\Delta \Omega_0$  are arbitrary

$$|\mathbf{j} \cdot \mathbf{n}| = \frac{1}{a^2} \frac{d^2 \mathbf{I}}{d \mathbf{E}_0 d \Omega_0} \frac{1}{|\mathbf{J}|}$$

where

$$J = \frac{\partial}{\partial} \left( \frac{E, \vec{\Omega}}{E_{o} \vec{\Omega}_{o}} \right)$$
Once  $|j \cdot n|$  is determined, the current density  $\vec{j}$  per unit energy follows from

$$\vec{j} = |\vec{j} \cdot n| \frac{V}{\vec{v} \cdot \vec{\Omega}}$$

where  $\vec{V} = \vec{V}(E_0, \hat{\Omega}_0)$  is the velocity at  $\vec{r} = \vec{r}(E_0, \hat{\Omega})$ .

The primary problem in the determination of  $\vec{j}$  is the evaluation of the Jacobian. Consider first the case of no magnetic field and a repulsive potential V = k/r. The particles follow a hyperbolic path with the center of force at the focus. The geometry of the encounter is shown in Figure 5.13 where we also introduce the angular coordinate  $\Theta$  in terms of which the orbit is given by <sup>[18]</sup>

$$\frac{1}{r} = -\frac{mk}{g^2} (1 + \varepsilon \cos \theta) .$$

Here e is measured from the symmetry axis of the orbit, m is the particle mass,  $\ell = mv_0 r_0 \sin \alpha = (2mE_0)^{1/2} r_0 \sin \alpha$  is the angular momentum, and

$$\varepsilon = \left[1 + 4\left(1 + \frac{E_o}{V_o}\right) \frac{E_o}{V_o} \sin^2 \alpha\right]^{1/2}$$

where  $V_0 = k/r$ . In the following we shall use the orbit equation in the form

$$\cos \theta = -\frac{1}{\varepsilon} \left( \frac{2E_0}{V_0} \frac{\sin^2 \alpha}{x} + 1 \right)$$

with  $x = r/r_0$ .



Figure 5.13. Geometrical quantities used to calculate current density.

For the present problem the required Jacobian is

$$J = \frac{\partial (\cos \chi)}{\mu}$$

where

$$\cos \chi = -\cos(e - e_0)$$
  
= -(cose cose\_0 + sine sine\_0)  
 $\mu = \cos \alpha$ 

and  $\cos \theta_0$  is obtained from the equation given earlier with x = 1. We find

$$J = -\frac{1}{\varepsilon} \left[ \left( -\frac{\varepsilon}{\mu} \cos \theta + \frac{4E_{o}}{V_{o}} \frac{\mu}{x} \right) (\cos \theta_{o} - \sin \theta_{o} \ \text{ctne}) + \left( -\frac{\varepsilon}{\mu} \cos \theta_{o} + \frac{4E_{o}}{V_{o}} \mu \right) (\cos \theta - \sin \theta \ \text{ctne}_{o}) \right]$$

with

$$\frac{\varepsilon}{\mu} = -\frac{4}{\varepsilon} \left( 1 + \frac{E_0}{V_0} \right) \frac{E_0}{V_0} \mu$$

In the presence of a constant magnetic field, B, spherical symmetry of the force field is lost and the simple analytic expressions for the particle orbit are not known. The problem simplifies considerably however if the magnetic field is small in a sense that will become clear as we consider the motion observed in a system rotating at a constant angular velocity  $\vec{\omega}$ . In the rotating

system the effective force is<sup>[19]</sup>

$$F_{eff} = q \left[ \vec{E} + \frac{\vec{V}_s \vec{xB}}{c} \right] - 2m(\omega x \vec{V}_r) - m \vec{\omega} x (\vec{\omega} x \vec{r})$$

where

$$\vec{v}_r = \vec{v}_s - \omega \vec{x} \vec{r}$$

and  $\vec{v}_s$  and  $\vec{v}_r$  are the velocities of the particle relative to the space and rotating axes respectively. If we choose

$$\dot{\omega} = -\frac{qB}{2mc}$$

then

$$\vec{F}_{eff} = q\vec{E} + \vec{m}_{\omega}\vec{x}(\vec{\omega}\vec{x}\vec{r})$$

Neglecting terms of second and higher order in the B field, the equation of motion in the rotating system becomes

$$m \frac{d\vec{v}_r}{dt} = q\vec{E}$$

Thus, to the considered degree of approximation, in the rotating frame the effects of the magnetic field vanish and to the rotating observer the particle moves in a 1/r potential.

To find where a given particle strikes the body we can consider that during the particle's flight time the body rotates with constant angular velocity  $-\vec{\omega}$ . The magnitude of the rotation requires a knowledge of the flight time, which to the required order of accuracy is given by

$$t = \int_{r}^{r_0} \frac{dr}{|\vec{r}|}$$

where

$$|\dot{\mathbf{r}}| = \left[\frac{2}{m}\left(\mathbf{E}_{o} - \mathbf{V}_{o}\left(1 - \frac{\mathbf{r}_{o}}{r}\right) - \mathbf{E}_{o}\frac{\mathbf{r}_{o}^{2}}{r^{2}}\sin^{2}\alpha\right)\right]^{1/2}$$

The foregoing expressions have been programmed to determine where a particle of given initial energy and direction strike the object that is being charged. The magnitude of the current striking the body is calculated as if there were no magnetic field. Corrections for the effect of  $\vec{B}$  on the current striking the object could be made, but in view of the rough nature of the initial monopole approximation, such corrections are not warranted.

#### 5.10.3 PHYSICAL CHARACTERISTICS OF TRANSPARENT ANTENNAS

Many spacecraft have, as a dominant feature, large mesh antennas which are largely transparent to light and particles. Examples of such spacecraft include the ATS-6 satellite and the Galileo orbiter. The mesh must be conductive (in order to function as an antenna), and thus may be either pure conductor (or, equivalently, conductively coated dielectric), or dielectric-coated conductor. The main effect of this structure is to set the electrostatic potential over its area. However, although it is considered transparent as seen by the rest of the spacecraft, it does intercept some fraction of the particles and light incident on it, which, particularly in the dielectric-coated case, affects the antenna's own potential.

In NASCAP we consider an antenna mesh to intercept 20 percent of the incident fluxes. (This should be made a RDOPT parameter at some future time.) For charging purposes, the area of an antenna surface is considered to be the full surface area. Thus differential charging will take place more slowly on antenna surfaces than on solid surfaces. 199

#### 6. RUN OPTIONS

6.1 INTRODUCTION

NASCAP requires three major types of information from the user. The first two, definitions of the object and the plasma environment, are described in Chapters 3 and 5. In this chapter we describe the third type, the RUN OPTIONS, in detail.

Like the object and environment definitions, the run options are understood by NASCAP as <u>keywords</u>, read from their own file. The run options are read by a special module RDOPT from the <u>options file</u>, IKEYWD. The default file number for IKEYWD is 26. The RDOPT module must <u>always</u> be the first module to be executed in any NASCAP run. A new run always sets all the run options to their default values. Subsequent calls to RDOPT do not cancel options set in previous calls in the same run however. The options file is read until an END card or an end-of-file condition is encountered.

The run options can be classified into six groups according to their functions. These are:

- 1. Options that control the way the program proceeds.
- 2. Options that define electrical connections.
- 3. Options that define features of the environment.
- 4. Options that control printed output.
- 5. Options that control graphical output.
- 6. Options that define logical unit numbers.

The keyword and parameter syntax for <u>all</u> of the run options are summarized in Table 6.1. Tables 6.2-6.7 classify the options according to the six functions above. Let us take each group and each option in turn and examine it in detail.

# TABLE 6.1. NASCAP USER OPTIONS

# USER OPTIONS-FILE 26

Supplied in file 26—OPT file. In this section, "#" indicates integers. "<>" indicates optional input. Ellipses "..." indicate continue on same line. The most important options are RESTART, DELTA, LONGTIMESTEP, NCYC, and MESH. Options are set sequentially as read. They are remembered throughout the steps of a NASCAP execution, and may be changed by RDOPT calls at any time.

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| SYNTAX  | MEANING  | DEFAULT  | EXAMPLE  |
|---|--|--|--|
| 3D-VIEW x y z<br>3D-VIEW NONE<br>APRT grids#<br>BFIELD bx by bz<br>BIAS cond# volts   | new SATPLT view<br>clear view table<br>number grids potential print<br>constant mag field—Webers/m <sup>2</sup><br>conductor bias relative to<br>conductor 1   | 3 default views<br>3 default views<br>0<br>0, 0, 0<br>no bias            | 3D-VIEW 4.2 4.9 -8<br>3D-VIEW NONE<br>APRT 2<br>BFIELD .01 1.E-5 1.E-5<br>BIAS 2 -500  |
| CIJ conda# condb# farads<br>COMMENT <anything><br/>CONTOURS NONE<br/>CONTOURS STANDARD</anything>   | mutual conductor capacitance<br>comment—no effect<br>clear contour table<br>3 center cuts  | stray capacitance only<br>none<br>no contours<br>no contours             | CIJ 3 4 1.E-4<br>COMMENT SEPT 25 CHANGES<br>CONTOURS NONE<br>CONTOURS STANDARD   |
| CONTOURS (x)<br>  | additional contour cut   | no contours  | CONTOURS Y -1 GRIDS 3 MOD 4  |
|   | clear specific cut   | no contours  | CONTOURS X & OFF   |
| CONVEX  | convex object, self-shadowing only   | HIDCEL must be called for<br>nonzero sun intensity                       | CONVEX   |
| CONVERGENCE PLOTS ON<br>CONVERGENCE PLOTS OFF   | potential solver printer plots   | off  | CONVERGENCE PLOTS ON<br>CONVERGENCE PLOTS OFF  |
| DEADLINE hhmmss#<br>DEBYE<br>DELFAC factor<br>DELTA timestep<br>DESTINATION dest<br>DIPOLE MOMENT px py pz<br>AT x y z<br>DISCHARGE relax | finish before time of day<br>activates Debye screening<br>timestep = timestep * factor<br>initial timestep (seconds)<br>plot destination<br>magnetic dipole moment (A - M <sup>2</sup> )<br>and location<br>perform discharge analysis | none<br>no screening<br>1.<br>1.<br>none<br>none                         | DEADLINE 234500<br>DEBYE<br>DELFAC 1.5<br>DELTA .01<br>DESTINATION CALCOMP<br>DIPOLE MOMENT 1.E-2, 1.E-2, 0 AT<br>0, 0, 5<br>DISCHARGE 5 |
| EFFCON ON<br>EFFCON OFF   | effective surface conductivity   | off  | EFFCON ON<br>EFFCON OFF  |
| EMITTER unit#<br>END<br>FIXP cond# volts<br>FLOAT<br>FLOAT cond#  | activate particle emitter<br>end of input file<br>fix conductor potential<br>remove all previous FIXP and BIAS<br>float previously fixed or<br>biased conductor  | NOEMIT<br>none<br>conductor floats<br>previous status<br>previous status | EMITTER 23<br>END<br>FIXP 2 -3000<br>FLOAT<br>FLOAT 3  |
| IOUTER $\binom{2}{2}$   | 0—grounded outer boundary<br>2—monopole outer boundary   | 2. i.e., l/r potentials  | IOUTER 2   |

# TABLE 6.1. NASCAP USER OPTIONS (Concluded)

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EXAMPLE

# SYNTAX

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| SYNTAX  | MEANING  | DEFAULT                   | EXAMPLE                          |  |
|---|--|---------------------------|----------------------------------|--|
| LONGTIMESTEP <dvlim></dvlim>  | implicit charging,<br><vollage limit="" per="" timestep=""></vollage>    | NOLONG                    | LONGTIMESTEP 2000                |  |
| MATVIEW $\pm \begin{pmatrix} x \\ y \\ z \end{pmatrix}$ cuta# cutb# | additional material plot   | 6 default plots           | MATVIEW -Z -5 +5                 |  |
|   | clears MATVIEW table   | 6 default plots           | MATVIEW NONE                     |  |
| NCYC steps#   | number timesteps to run  | 1                         | NCYC 5                           |  |
| NG ands#  | number computational grids   | 2                         | NG 3                             |  |
| NOEMIT  | turn off previously defined emitter                                      | previous status           | NOEMIT                           |  |
| NOLONG  | see LONGTIMESTEP   | explicit charging         | NOLONG                           |  |
|   | see PRINT  | no extra printout         | NOPRINT POTENT                   |  |
| NOSCALE   | see SCALE  | SCALE                     | NOSCALE                          |  |
| NOSHEATH  | see SHEATH   | no sheath plot            | NOSHEATH                         |  |
| NOTIME  | see TIMER  | no timer                  | NOTIME                           |  |
| NZ zdivě  | z grid size  | 33                        | NZ 29                            |  |
| OFFSET vá vá zá   | moves coordinate origin  | center of mesh (9, 9, 17) | OFFSET 0 0 0                     |  |
| POTCON decades  | convergence of potential solver  | 8-CAPACI, 4-TRILIN        | POTCON 3                         |  |
| PRINT modulename  | diagnostic prints; modulename<br>is LIMCEL, POTENT, HIDCEL, or<br>OBJDEF | NOPRINT                   | PRINT POTENT                     |  |
| REPEAT times#   | plot repetition factor (IGS only)  | 1                         | REPEAT 3                         |  |
| RESTART   | next timestep-old problem  | new problem               | RESTART                          |  |
| 91.1  | interconductor resistance  | -                         | RIJ 1 2 3.E8                     |  |
| SCALE   | potential solver scales potential<br>and boundary conditions             | SCALE                     | SCALE                            |  |
| SECONDARY ZEMISSIONS ANGLE  | secondary formulation  |                           | SECONDARY ANGLE                  |  |
| SECONDARY CEMISSIONS NORMAL   | secondary formulation  | ANGLE                     | SECONDARY EMISSION NORMAL        |  |
|   | siot space charge density  | NOSHEATH                  | SHEATH                           |  |
|   | pior space charge density  | 1 1 1                     | SUNDIR 1 0 25                    |  |
|   |  | 0                         | SUNINT OR                        |  |
| SURFACE CORNER x# y# z#   | surface cell of interest<br>(previous object definition required)        | none                      | SURFACE CORNER 3, 3, 2 - 1, 0, 0 |  |
| SURFACE CELL cell#  | surface cell of interest   | cell #1                   | SURFACE CELL 541                 |  |
| TANKCUR OFF   | tank current contour plots   | off                       | TANKCUR OFF                      |  |
| TANKCUR ON  | · · · · · · · · · · · · · · · · · · ·                                    |                           | TANKCUR ON                       |  |
| TANKTRAJ OFF<br>TANKTRAJ ON   | lank particle trajectory plots   | off                       | TANKTRAJ OFF<br>TANKTRAJ ON      |  |
| TIMER   | execution time each module   | NOTIME                    | TIMER                            |  |
| TITIF   | plot title   | NASCAP                    | TITLE P78-2                      |  |
| TYPE type#  | environment type   | 2 (single Maxwellian)     | TYPE 6                           |  |
| YMESH unit  | physical grid spacing (meters)   | 0.1                       | XMESH .03                        |  |
| ZTRUNCATE zlo# zhi#   | truncation of outer grid   | full grid16 to +16        | ZTRUNCATE -12 +12                |  |

# TABLE 6.2. RUN OPTIONS THAT CONTROL PROGRAM PROCEDURE

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DEADLINE DELFAC DELTA EMITTER END LONGTIMESTEP/NOLONG NCYC POTCON RESTART SCALE/NOSCALE/DSCALE

# TABLE 6.3. RUN OPTIONS THAT DEFINE ELECTRICAL CONNECTIONS

BIAS CIJ DISCHARGE EFFCON FIXP FLDCON FLASHOVER FLOAT RADCON

RIJ

# TABLE 6.4. RUN OPTIONS THAT DEFINE FEATURES OF THE ENVIRONMENT AND COMPUTATIONAL SPACE

BFIELD

CONVEX

DEBYE

DIPOLE MOMENT

IOUTER

NG

NZ

OFFSET

-SECONDARYEMISSION

SUNDIR

SUNINT

TANK AXIS

TANK RADIUS

TYPE

UPDATE

XMESH

ZTRUNCATE

# TABLE 6.5. RUN OPTIONS THAT CONTROL PRINTED OUTPUT

APRT CONVERGENCE PLOTS PRINT SURFACE AT SURFACE CELL SURFACE CORNER

TIMER/NOTIMER

# TABLE 6.6. RUN OPTIONS THAT CONTROL GRAPHICAL OUTPUT

3D-VIEW

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CONTOURS

DESTINATION

MATVIEW

REPEAT

SHEATH/NOSHEATH

TANKCUR

TANKTRAJ

TITLE

# TABLE 6.7. RUN OPTIONS THAT DEFINE LOGICAL UNIT NUMBERS

IAREA IAUN ICNOW IDIV IFLUX IKEYWD ILTBL IOBJ IOBPLT IΡ IPART IPQCND IR IROUS I SAT

- **I SPARE**
- ISPCTR
- IU

# 6.2 OPTIONS THAT CONTROL PROGRAM PROCEDURES

## 6.2.1 DEADLINE

The card:

DEADLINE hhmmss

tells NASCAP to finish its run before the time 'hhmmss', e.g. DEADLINE 234500

causes NASCAP to exit cleanly before 11:45 p.m. (For example, there may be computer hardware maintenance scheduled for midnight.) The present cycle is finished, files are closed and output is printed. This enables the user to RESTART the run later. The default behavior (i.e., when no DEADLINE card is included in the options file) is to keep running until all of the requested cycles have been completed, or until NASCAP determines there is insufficient run time left to continue, regardless of the time of day.

## 6.2.2 DELTA

The card:

DELTA d

sets the length of each of the timesteps requested, to "d" seconds, e.g.,

DELTA 10

sets the length to 10 seconds. The default value (if a DELTA card is omitted completely) is 1 second.

6.2.3 DELFAC

The card:

DELFAC f

causes the length of the computational timestep DELTA to be increased by the factor f at  $\underline{end}$  of each cycle. For example the cards

#### DELTA 10

DELFAC 2

will cause a 10 second timestep for cycle 1, a 20 second timestep for cycle 2, a 40 second timestep for cycle 3, and so on. The default value of DELFAC is 1.

6.2.4 EMITTER

# Including the card

# EMITTER n

in the options file establishes a particle emitter input file n. The default value of n is 5 (the NASCAP runstream). If the EMITTER card is found by RDOPT, TRILIN will look for input defining one or more particle emitters in file n. This is discussed in detail in Chapter 7. An existing emitter can be turned off with the card

#### NOEMIT

The default behavior is to assume no emitters.

6.2.5 END

Indicates end of options file.

# 6.2.6 LONGTIMESTEP/NOLONGTIMESTEP

The rate of change of the potential V of an object being charged by a net current I is inversely proportional to its capacitance C.

 $\frac{\mathrm{d}V}{\mathrm{d}t} = \frac{\mathrm{I}}{\mathrm{C}}$ 

A spacecraft usually has a very small capacitance to infinity compared with the capacitances between its dielectric surfaces and their underlying conductors. This leads to at least two very different charging timescales. For a given current the rate of charging of the whole spacecraft with respect to the surrounding plasma is typically orders of magnitude greater than the rate of <u>differential</u> charging between different surfaces of the spacecraft. For example an initially uncharged satellite exposed to a magnetic substorm at geosynchronous orbit (i.e., exposed to a charging plasma) might charge to 3 or 4 kV in perhaps 0.1 seconds, before reaching a quasi-equilibrium based on its capacitance to infinity. However, over the next 1000 seconds differential potentials may develop between the dielectric surfaces and other parts of the spacecraft as these larger capacitances become charged.

These widely differing charging rates make the choice of timestep duration (DELTA) a delicate one. If the timestep is chosen to be much longer than the charging timescale, wild oscillations about the equilibrium potential are likely. If the timestep is chosen to be much smaller than the charging timescale, nothing physically interesting will happen until many timesteps (and much valuable computer time) have been expended. The ideal solution is to choose very short timesteps for the first few cycles, when the satellite is charging rapidly, and then to increase them once the first quasi-equilibrium is achieved and differential charging is occurring on a longer timescale. This can be done explicitly by the user, or as an alternative, NASCAP provides an option that maintains the charging rate and adjusts the timestep duration internally to avoid potential overshoot and oscillations: The card:

#### LONGTIMESTEP <dvlim>

activates this option (called the LONGTIMESTEP option). The LONGTIMESTEP option is deactivated by default, or it may be explicitly "turned off" by the card

## NOLONG (or NOLONGTIMESTEP)

The parameter <dvlim> is the maximum change in the magnitude in volts of any conductor potential that may occur during a timestep. For example, consider a surface expected to reach an equilibrium potential of -4 kV in 1 second, if dvlim is chosen to be 2000 V, and DELTA is chosen to be say 10 seconds, then LONGTIMESTEP will cut the length of the timestep back from DELTA (10 s) to approximately 0.5 seconds, a time enough for the surface to reach -2 kV and no more. Equilibrium will not be reached until the second cycle.

If dvlim had been chosen to be 1000 V then equilibrium would be reached in approximately 4 cycles with duration of around 0.25 seconds, and so on. The smaller dvlim is chosen to be the more timesteps NASCAP will take to reach equilibrium and the better resolved will be the transient charging response of the satellite. The default value of dvlim is 1000 V.

If dvlim is chosen to be too large (i.e., greater than the expected quasi-equilibrium potential) and DELTA is chosen to be longer than the active charging timescale then oscillations in the potential may still occur.

The advantage of the LONGTIMESTEP option is that it allows timesteps appropriate to the phenomena of interest. For example, a user interested only in the final steady-state potentials can cover the transient response with relatively few timesteps. These arguments apply of course to charging <u>and</u> discharging equally well. It is generally recommended that most users use the LONGTIMESTEP option most of the time.

6.2.7 NCYC

#### The card:

#### NCYC n

sets the number of charging cycles for the TRILIN module. If no card is included in the options file NCYC is assumed to be 1. Any (integral) number of cycles may be requested but it is a good practice to break a long simulation up into a number of runs of perhaps 5 or 10 cycles at most. This enables the user to more closely monitor the results and to adjust DELTA, <dvlim> (6.2.2 and 6.2.6) and other parameters where necessary.

# The card

POTCON n

says that n orders of magnitude convergence are required of the Scaled Conjugate Gradient potential solver. If not set in the options file, it will be set to 8 by CAPACI, or to 6 by IPS, or to 4 by TRILIN. These defaults have been found to be a good compromise between accurate electric field determinations (i.e., more convergence) and fast run times (i.e., less convergence).

#### 6.2.9 RESTART

Including the card

# RESTART

in the options file causes NASCAP to continue a previous run. For example, if 5 cycles were requested for a new NASCAP run and all the <u>restart files</u> were saved (2.7) a subsequent run with the same object, etc. would, by default, start with cycle 1 and the potentials all at zero; i.e., the first 5 cycles would be repeated. If, however, a 'RESTART' card is included in the options file of the second run, potential calculations will begin with <u>cycle 6</u> and the first run will be continued - just as if more than 5 cycles had been originally requested. This enables the user to break up a long (many cycle) charging simulation into a number of smaller, more manageable runs.

A run <u>cannot</u> be restarted unless the <u>restart files</u> discussed in Section 2.7, saved from the previous run, are assigned to the restart file numbers. In other words the restarted run must be able to access the information stored in the restart files.

## 6.2.10 SCALE/NOSCALE/DSCALE

The potentials in the space surrounding the object are determined iteratively from the potentials remembered from the previous timestep [Section 3.15.1] (=0 for the first timestep). The further away the initial potentials are from their iterative solution more iterations are required to achieve convergence. To a zeroth approximation the potentials in free space are proportional to the total amount of charge collected by the object. Hence a better starting point for the initial potentials in each timestep is given by scaling the values from the previous timestep as follows:

| Initial guess for<br>potentials in timestep n = | Total charge collected up to and<br>including timestep n<br>Total charge collected up to and |
|---|--|
|   | including timestep $n - 1$   |
| x   | final potentials for timestep n – 1  |

For a floating spacecraft this is automatically carried out by default, or by including the card

SCALE

Scaling is turned off if conductor 1 is at fixed potential, or if the card

#### NOSCALE

is encountered. The DSCALE option counts only charge on dielectric surfaces and is appropriate to a grounded object (i.e., in a test tank). The user need rarely specify any of these options, as NASCAP defaults are almost always adequate.

# 6.3 RUN OPTIONS THAT DEFINE ELECTRICAL CONNECTIONS

#### 6.3.1 BIAS

The card:

BIAS i v

causes conductor i to be biased by v volts relative to conductor 1. Conductor 1 is usually the spacecraft ground. For example the card

BIAS 3 -1000

causes conductor 3 to always be 1000 volts more negative than conductor 1. If conductor 1 were floating at -300 V then conductor 3 would have a potential of -1300 V. The BIAS cards for each conductor must be entered in <u>ascending</u> order. Thus any card for conductor 3 will be rejected unless conductor 2 has been biased. Cards need only be included for those conductors that the user wants to be biased. The default behavior for a conductor not biased or fixed (see FIXP) is to float independently.

#### 6.3.2 CIJ

There are two sources of capacitance between conductors. The <u>stray</u> capacitances are determined by the throughspace electric fields and geometrical relationships between conductors and are calculated by NASCAP automatically. However, the larger capacitances due to conductors being glued together or separated by dielectric films must be specified by the user. The card:

CIJ k 1 c sets this "mechanical connection" capacitance between conductor number k and 1 to c farads. For example the card:

CIJ 2 3 1.E-8

sets the "mechanical" capacitance between conductor 2 and 3 to  $1 \times 10^{-8}$  farads. This value is then added as a parallel capacitance to the stray capacitance already calculated by NASCAP.

The mechanical value usually dominates the stray value. Failure to define the mechanical value may cause differential charging between the two conductors in question to occur unrealistically fast.

When multiple definitions of capacitances are made NASCAP includes implicit as well as explicit connections in its calculation. For example

| CIJ | 1 | 2 | 1.E-3 |
|-----|---|---|-------|
| CIJ | 1 | 3 | 2.E-3 |
| CIJ | 2 | 3 | 3.E-4 |

defines explicit capacitive connections between conductors 1 and 2, 1 and 3 and 2 and 3. However, 1 is also connected to 3 via 2, and so on. The circuit diagram used by NASCAP has the form:



Stray capacitances are calculated only between the ground conductor (1) and each of the other 14. Stray capacitance between conductors 2 and 3, 3 and 4, etc. are assumed negligible.

#### 6.3.3 DISCHARGE

A discharge analysis, to take place in the LIMCEL (LONGTIMESTEP) phase of a TRILIN timestep, may be requested by the RDOPT input card DISCHARGE d

where d is a real number, 0 < d < 1. This will result in the default discharge analysis, i.e., all four types of discharges may take place

. • -

through all space, and all materials will have d as a relaxation factor. Figure 6.1 shows an example of the default discharge parameter specification.

The discharge analysis takes place in the order (1) blowoffs, (2) discharges to space (determined by material property 15), (3) punchthroughs (determined by material property 16) and (4) flashovers. Only one blowoff or discharge to space is allowed per timestep. However, the punchthrough-flashover routine will be called repeatedly until all allowed punchthrough or flashover discharges have taken place.

6.3.3.1 <u>The BLOWOFF Discharge</u>. The BLOWOFF discharge is a new type of discharge incorporated into NASCAP because it is believed to be a common type of small discharge occurring on spacecraft, and having a relatively low threshold voltage. The discharge occurs on a surface which is primarily insulating, but has some exposed conductor. When the insulator is sufficiently positive relative to the conductor, electrons will be accelerated outward from the conductor sufficient to raise the conductor potential to near plasma ground. Also, sufficient electrons will land on nearby insulator to partially discharge it, and electrons will also land on distant portions of the spacecraft.

6.3.3.2 <u>Discharge to Space</u>. Material property 15 (4.3.10) contains the maximum negative potential in volts that any surface covered with that material can reach before charge is blown off into space. On entering the discharge analysis, NASCAP searches for all surface cells with potentials more negative than their property 15 value. The ratio of their potential to property 15 defines the severity of the discharge.

Severity of discharge for cell  $i = \frac{\text{potential of cell}}{\text{property 15 of cell}}$ 

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DISCHARGE .6 END

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(a) RDOPT input for example 1 (default options).

DISCHARGE .6 END

(b) RDOPT output for example 1 (default options).

DISCHARGE PARAMETERS: DISCHARGE REGION: 1<X< 17 1<Y< 17 1<2< 33 DISCHARGE CATEGORIES: BLOWOFF-YES TO SPACE -YES PUNCHTHROUGH YES FLASHOVER -YES CONDUCTORS: 1-YES 2-YES 3-YES 4-YES 5-YES 6-YES 9-YES 7-YES 8-YES 10-YES 11-YES 12-YES 13-YES 14-YES 15-YES MATERIAL RELAX BLOWOFF ALUM .600 1-0+005 KAPT .600 1.0.005 TEFL .600 1.0+005 GOLD .600 1.0+005 SOLA .600 1.0+005

(c) LIMCEL output for example 1 (default options).

Figure 6.1. Discharge specification example 1 (default options).

•

Starting with the most severe discharge the potential on the cell is reduced to (1 - d) times its property 15 value. The charge lost is assumed blown off into space. Recall that the parameter "d" is included as part of the 'DISCHARGE' card. It gives the fraction of the potential on the surface cell that is lost during the discharge (0.1 < d < 1.0).

6.3.3.3 <u>Punchthrough Discharges</u>. The second stage of the analysis is to search for the surface cells with the most severe "punchthrough" possibilities. A "punchthrough" occurs when the potential <u>difference</u> between a dielectric surface and its underlying conductor exceeds the value stored by material property 16. The severity of a punchthrough is given by the ratio of the potential difference to property 16. The punchthrough reduces the surface potential to (1-d) times its property 16 value. The charge is partially blown off and partially redistributed to the conductor and other surfaces. After each punchthrough analysis and each charge redistribution, the cells are searched again for the most severe punchthrough condition and the analysis repeated. This continues until all punchthroughs are resolved.

6.3.3.4 <u>FLASHOVER Discharges</u>. Finally different potentials between neighboring surface cells are scanned for those that exceed the FLASHOVER threshold. This is 10,000 volts by default. It may be adjusted by including the card

#### 'FLASHOVER f'

in the options file, where f is the threshold in volts. The potential difference is reduced to (1-d) of the value f and charge is redistributed to more positive surface cells. (See also Section 6.3.7.)

6.3.3.5 <u>Revising the DISCHARGE Specifications</u>. To revise the discharge parameter specification, use the card

DISCHARGE d lun where d is a real number as above, and lun is the logical unit from which discharge specifications are to be read. If lun is specified as less than or equal to zero, specifications will be read from the same options file from which the DISCHARGE card was read.

6.3.3.5.1 <u>The RESTRICT Command</u>. RESTRICT is used to limit discharges either to a particular region of space, in which case it takes the form

RESTRICT xmin xmax ymin ymax zmin zmax where xmin, etc. are integers, or to a particular conductor, by the form

#### **RESTRICT CONDUCTOR n**

The meaning of the space restriction is that only surface cells whose associated volume cells (as denoted by their low-indexed corner) lie within the region are considered as discharge candidates. The space restriction does not apply to discharges occurring on booms.

6.3.3.5.2 <u>The IGNORE Command</u>. The IGNORE command is used to instruct NASCAP to neglect possible discharges of a particular type, on a particular conductor, or on a particular material. The possible forms are

IGNORE BLOWOFF IGNORE SPACE IGNORE PUNCHTHROUGH IGNORE FLASHOVER IGNORE CONDUCTOR n IGNORE mat1

6.3.3.5.3 <u>Material Commands</u>. Material commands are used to set the BLOWOFF threshold or the relaxation factor for individual materials. Possible forms are

```
matl IGNORE
matl x bt
matl bt x
matl x
matl bt
```

where bt is the blowoff threshold (volts, bt > 1) and x is the relaxation factor (0 < x < 1). If x is specified but not bt, bt will be set to 100,000 volts. If bt is specified but not x, x will be set to one-half.

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6.3.3.5.4 <u>The END Command</u>. The END command says to ignore subsequent cards (if in a separate file, in which case an EOF condition will accomplish the same thing) or to return to normal option reading (if in the OPTION file).

6.3.3.5.5 <u>The FLASHOVER Option</u>. FLASHOVER continues to be a regular option read by RDOPT, and having the form

FLASHOVER volts

Material-dependent thresholds are not implemented, but the region and conductor restrictions will apply. The relaxation factor will be that specified in the DISCHARGE option card. The default flashover threshold is 10,000 volts.

6.3.3.5.6 <u>Example</u>. The following example (Figure 6.2) illustrates specification of discharge options. Five materials (ALUM, KAPT, TEFL, GOLD, and SOLA) have been defined. (The default options were shown above in Figure 6.2.)

DISCHARGE .7 5 IGNORE PUNCHTHROUGH IGNORE SPACE RESTRICT CONDUCTOR 2 KAPTON .8 TEFLON 2500 SOLAR 2800 .4 NPAINT .9 4000 END END (a) RDOPT input for example 3. KEYWORD INPUT DISCHARGE .7 5 IGNORE PUNCHTHROUGH IGNORE SPACE RESTRICT CONDUCTOR 2 KAPTON .8 TEFLON 2500 SOLAR 2800 .4 NPAINT .9 4000 END DISCHARGE OPTION SUMMARY 1<X< 17 1<Y< 17 REGION RESTRICTION: 1<2< 33 COND- 3 COND- 8 COND- 5 COND- 2 YES COND- 4 NO NO COND- 1 NO NO COND- 7 COND- 9 COND-10 CONO- 6 NO NO NO NÛ NÖ COND-14 NO COND-15 COND-11 COND-12 NO COND-13 NO NO NO YES BLONOFF ONLY -TO SPACE -NO PUNCHTHROUGH -NO FLASHOVER -YES BLONOFF AT 1.00+005V0LTS KAPT FRAC= .80 .50 2.50+003VOLTS BLOWOFF AT TEFL FRAC= 2.80+003VOLTS FRAC= BLOWOFF AT SOLA •40 NPAT FRAC= .90 BLOWOFF AT 4.00+003VOLTS END (b) RDOPT output for example 3. \*\*\*#ARNING\*\*\* DISFIL - MATERIAL NPAI NOT FOUND. DISCHARGE PARAMETERS: DISCHARGE REGION: 1<X< 17 1CYC 17 1<2< 33 DISCHARGE CATEGORIES: BLOWOFF-YES TO SPACE -NO **PUNCH THROUGH** NO FLASHOVER -YES CONDUCTORS: 1-10 2-YES 3-NO 4-NO S-NO 7-NO 6-NO 8-NO 9-NO 10-NO 11-NO 12-NO 13-NO 14-NO 15-NO MATERIAL RELAX BLOWOFF ALUN .700 1.0+005 KAPT .800 1.0+005 TEFL .500 2.5+003 60LD .700 1-0+005 SOLA .400 2.8+003

(c) LIMCEL output for example 3.

Figure 6.2. Discharge specification example 3.

The card:

#### EFFCON ON

activates the photosheath contribution to the surface conductivity. The intrinsic surface conductivity, (material property 14 (4.3.9)) due to the properties of the surface material itself, is automatically included in current calculations. An additional contribution may arise when a dielectric surface emits photoelectrons and their escape is inhibited by a positive electric field. The trajectory of the emitted electron then no longer extends to infinity but instead is turned around and the electron returns to another neighboring surface cell. The magnitude of this so-called "photosheath" conductivity depends on the emitted current and the normal and transverse electric fields.

# The default operation (and the card) EFFCON OFF

cause the photosheath conductivity to be omitted from NASCAP current calculations. Including the effect can cause oscillations in surface cell potentials from cycle to cycle. This undesirable result can often be controlled by reducing DELTA (6.2.2) and/or dvlim (6.2.5). Persistent oscillation can sometimes only be overcome however by abandoning the use of the EFFCON option. In general 'EFFCON ON' should only be used when absolutely necessary, and then with care.

6.3.5 FIXP

The card:

FIXP n v

fixes the potential of conductor #n to v volts. For example FIXP 4 -6000

sets conductor 4 to a potential of -6000 volts, where it remains, fixed for all future potential calculations. The most common use of this option is to ground conductor 1 in a test tank:

#### FIXP 1 O.

The default behavior is for all conductors to float freely. (See BIAS, 6.3.1.)

6.3.6 FLDCON

The card:

#### FLDCON ON

activates the field-induced contribution to the bulk conductivity. The default behavior is to omit this contribution. The card:

#### FLDCON OFF

does this explicitly. The field-induced contribution to the bulk conductivity is discussed in detail in Chapter 4 (4.8.5).

6.3.7 FLASHOVER

#### The card:

FLASHOVER f

sets the potential difference threshold for flashover between two charged surfaces to f volts. For example

#### FLASHOVER 5000

sets the threshold to 5000 volts. The default value is 10,000 volts. Flashover analysis is described in Section 6.3.3.

## 6.3.8 FLOAT

The card:

# FLOAT <cond # >

removes the effect of all previous BIAS's and FIXP's affecting the specified conductor number. For example

#### FLOAT 4

allows a previously biased or fixed conductor 4 to float freely again. This is necessary because options FIXP and BIAS are <u>remembered</u> from previous calls to RDOPT within the same run. The card:

#### FLOAT

with no "cond#" causes all previous FIXP and BIAS commands to be cancelled for <u>all</u> conductors; i.e., all conductors float freely.

#### The card:

#### RADCON ON

activates the radiation-induced contribution to the bulk conductivity for dielectrics. The default behavior is to omit this contribution. Omission may be specified explicitly with the card

#### RADCON OFF

The radiation-induced conductivity is discussed in detail in Section 4.8.5.

#### 6.3.10 RIJ

NASCAP/GEO now has the capability of treating explicitly specified conduction among the various conducting segments. Interconductor resistances are specified in the RDOPT module in a similar manner to interconductor capacitances by the card

RIJ i j r where i, j are conductor indices, and r is the direct interconductor resistance in ohms. Resistances less than  $1\Omega$  will be ignored (i.e., considered infinite).

The RIJ and CIJ keywords differ in that, while the CIJ values have instantaneous effect, <u>changes</u> in interconductor resistance (RIJ) take effect <u>only</u> upon subsequent call to OBJDEF or NEWMAT. Like the CIJ values, all RIJ's are defaulted to zero (i.e., zero conductivity or infinite resistivity) at the beginning of each NASCAP execution, and values are remembered until exit from NASCAP. However, resistivity values processed by OBJDEF or NEWMAT, which are the only values used in actual computation, are remembered from run to run.

Use of very low resistivities to effectively short two conductors together is not recommended.

6.4 RUN OPTIONS THAT DEFINE FEATURES OF THE ENVIRONMENT AND COMPUTATIONAL SPACE

## 6.4.1 BFIELD

The card:

BFIELD  $B_x B_y B_z$ sets the magnetic field vector in the vicinity of the satellite to  $B_x$ ,  $B_y$ ,  $B_z$  where the Cartesian components  $B_x$ ,  $B_y$ ,  $B_z$  are all in Webers m<sup>-2</sup>. The default is no magnetic field; i.e., BFIELD 0 0 0

For example, the card:

```
BFIELD 1.E-5 1.E-5 0.
```

describes a field pointing between the positive X and Y axes in the XY plane with magnitude  $\sqrt{2} \times 10^{-5}$  W m<sup>-2</sup> (0.14 gauss).

The module ROTATE rotates the magnetic field direction as well as the sun direction with respect to the satellite (8.2).

## 6.4.2 CONVEX

The card:

CONVEX

causes the shadowing of surface cells from sunlight to be calculated on the basis of simple self-shadowing only – without calls to HIDCEL (8.1). Self-shadowing assumes that illumination depends only on the angle between the surface normal of a cell and the sun direction  $\Theta$ .

degree of illumination  $\propto \cos \theta$ . The default behavior is to demand a call to HIDCEL to determine cell shadowing.

6.4.3 DEBYE

# The card:

DEBYE

activates the Debye screening option. The default behavior is to

assume that the space around the object has zero charge density. This is a good approximation for environments with a <u>Debye</u> <u>length</u>  $\lambda$  much greater than a mesh unit XMESH (6.4.15). The Debye length is defined for Maxwellian environments as

$$\lambda = \left(\frac{\varepsilon_0 kT}{ne^2}\right)^{1/2} = 7.43 \times 10^3 \left(\frac{\Theta}{n}\right)^{1/2}$$

where  $\Theta$  is the plasma temperature (eV) and n is the density  $(m^{-3})$ ,

or for a double Maxwellian with components 1 and 2:

$$\frac{1}{\lambda^2} = \frac{1}{\lambda_1^2} + \frac{1}{\lambda_2^2}$$

The Debye screening option assumes a charge density  $\rho$  linear in the potential  $\phi$ :

$$\frac{\rho}{\varepsilon_0} = -\frac{\phi}{\lambda^2}$$

This is a good approximation when the Debye length  $\lambda$  is between about 2 and 20 mesh units, and the potential is at most comparable to the temperature. It can only be used with single or double Maxwellian plasma spectra (Chapter 5.4).

When the DEBYE option is specified, CAPACI (8.5) must be executed subsequently, before any new calls to TRILIN, since space-charge affects the capacitance of the object to infinity. CAPACI reads the flux definition file in this case.

For environments with  $\lambda$  less than about 2 mesh units spatial oscillations of the potential are likely to occur. NASCAP is not designed for this physical regime and should not be used in these circumstances.

The card:

DIPOLE MOMENT  $p_x p_y p_z AT \times y z$ defines a <u>magnetic</u> dipole with moment components  $p_x$ ,  $p_y$  and  $p_z$ in A-m<sup>2</sup> located at grid point x y z. For example the card: DIPOLE MOMENT 0.01 0.0 0.01 AT 5 1 2

defines a moment pointing between the X and Z axes in the XZ plane centered at grid point 5 1 2. The default is no magnetic dipoles present.

Definition of dipole moments is an additional way of specifying the magnetic field on the satellite. (See BFIELD, 6.4.1). The magnetic dipoles are usually derived from part of the satellite.

#### 6.4.5 IOUTER

The parameter IOUTER controls the boundary conditions and may take one of two values. The card:

#### IOUTER O

sets the potentials on the boundary of the computational space to zero. This so-called "grounded" outer boundary condition is usually used for TEST TANK runs.

The default behavior and the card: IOUTER 2

activate "monopole" outer boundary conditions where the boundary potentials are set to be proportionate to 1/r (where r is the distance from the mesh center). The default IOUTER = 2 is usually used for space environment cases.

The card:

OFFSET x y z

changes the origin of the coordinate system from the center of the mesh to 9-x, 9-y, 17-7 (for nz = 33). This works in exactly the same way in the <u>options</u> file as the command 'OFFSET' described in Section 3.9.3 works in the object definition file.

6.4.7 NG

The card:

NG n

sets the number of nested grids in the computational space to be n. The nesting of grids is explained in Section 3.2. While there is no theoretical limit on the number of grids n, practical considerations of storage space and execution time suggest n = 5 as an effective extreme upper limit. The default value of n is 2. One grid may be used if the object does not occupy most of it (i.e., the object on one grid is surrounded by an excess of empty space) and its differential potential does not become very large. Too little computational space causes poor representation of electrostatic fields and barrier effects, but gives greatly enhanced execution speed.

6.4.8 NZ

The card:

NZ 4n + 1

sets the number of mesh units in the Z direction for <u>all</u> grids to 4n + 1; i.e., allowable values are 17, 21, 25, 29, 33. Thirty-three is the maximum value, and the value by default. The dimensions of the grids in the X and Y directions are fixed at 17. For example the card

NZ 17

sets the number of mesh units in the Z direction to 17.

#### 6.4.9 SECONDARYEMISSION

By default, and explicitly with the card: SECONDARYEMISSION ANGLE

NASCAP calculates the secondary emission yield  $\delta$  as a function of angle and integrates  $\delta(\theta)$  over an appropriate incident flux distribution  $f(\theta)$  to obtain the overall yield  $\Delta$ .

$$\Delta = \int f(e) \ \delta(e) \ de$$

The card:

SECONDARYEMISSION NORMAL

causes  $s(\theta)$  to be set to s(0), the value for normal incidence while the incident flux is still treated as isotropic, i.e.,

 $\Delta = \delta(0) \int f(e) de$ 

Since the yield is at a minimum for normal incidence this has the effect of suppressing the positive current, and effectively leads to a more "charging" environment (see 4.1).

The ANGLE secondary formulation is the physically correct one and should be used for all realistic charging simulations.

6.4.10 SUNDIR

The card:

SUNDIR x y z

sets the direction from the spacecraft toward the sun. The magnitude is not relevant. For example

SUNDIR 2.0 2.0 0.

sets the direction of the sun between the positive X and Y axes on the XY plane. The default value is 1, 1, 1. The sun direction need only be defined when the object is to be sunlit.

6.4.11 SUNINT

The card:

#### SUNINT intens

sets the sun intensity as a fraction or multiple of the natural sun intensity one earth distance from the sun. For any earth orbit exposed to the sun this should be 1.0, since orbit altitudes are negligible compared with the distance from the earth to the sun. Sun intensities differing from 1.0 (and 0.0) are used mainly for simulations of test tank experiments using artificial UV sources, or for interplanetary spacecraft. For example

#### SUNINT 0.6

sets the sun intensity to 0.6 times its natural earth value.

The default value is 0.0.; i.e., the sun is "turned off" and the object is in shadow.

6.4.12 TANK RADIUS AND TANK AXIS

The card:

# TANK RADIUS x <METERS>

defines a cylindrical test tank environment with radius x mesh units or meters. If the word "METERS" is explicitly included on the card RDOPT assumes that x is in meters. If "METERS" is absent it assumes that x is in mesh units.

The orientation of the tank by default is with its cylindrical axis along the Z direction. The other two axis directions may be chosen as the axis by including a card of the form:

TANK AXIS a

where a is X Y or Z

The height of the cylindrical tank is given by the dimensions of the computational space in the axis direction. For example if Z is the direction of the tank axis and NZ (6.4.8) is chosen to be 25, and

the number of grids (NG) (6.4.7) is chosen to be 2, then the cylinder will be 25 outer mesh units long or 25x2xXMESH meters (see 6.4.15 for XMESH). The cylindrical tank is compatible with the ZTRUNCATE option.

The circular cross-section of the cylinder may lie outside the computational space, but this leads to its truncation (Figure 6.3), eventually becoming rectangular once more.

Specification of a cylindrical tank automatically sets IOUTER (6.4.5) to 0. In potential contour plots the tank walls are represented by a double (blue) line.

6.4.13 TYPE

The cards

TYPE 6 or TYPE 1

are used to specify a TEST TANK environment, and must be included in the options file when using the TANK module (5.9). The TYPE must be specified as 2 or 3 when using the DETECT module, and 2 or 4 when using the DEBYE option.

#### 6.4.14 UPDATE

The card:

#### UPDATE ON

activates the UPDATE feature. UPDATE allows NASCAP to automatically select the most recent environment, from a list provided by the user, as the time elapses from cycle to cycle. This is explained in detail in Section 5.6. The default behavior is to operate without the UPDATE feature activated. The same effect is brought about with the card: UPDATE OFF

6.4.15 XMESH

## The card:

XMESH n

sets the size of one inner mesh unit (see Section 3.2) to n meters.




For example

#### XMESH 0.2

sets the inner mesh unit to 0.2 m. Thus a computational space consisting of two nested 17 x 17 x 33 grids will be 17 x 2 x 0.2 = 6.8 meters wide in the X and Y direction and 33 x 2 x 0.2 = 13.6 meters wide in the Z direction.

The default value is 0.1 m.

## 6.4.16 ZTRUNCATE

The card:

#### ZTRUNCATE zlo zhi

allows the user to select the beginning and ending coordinates for the outermost grid in the Z direction. The coordinate system used is the default (with the center at 0 0 0) or the one defined by the latest 'OFFSET' card (6.4.6).

For example

#### ZTRUNCATE -15 10

defines the outer grid to run from Z = -15 (instead of Z = -16) to Z = 10 (instead of Z = 16). The outer grid must always include outermost but one. For example grid #2 extends from -8 to +8 in grid #3 units, then grid #3 can only be truncated to a minimum of +8.

# ZTRUNCATE -7, 10

for example puts one boundary of grid #3 <u>inside</u> the boundary of grid #2. This is illegal.

ZTRUNCATE is particularly useful for defining the walls of a test tank. Note that it differs from NZ (6.4.8) in that

1. <u>only</u> the outer grid is truncated.

2. the grid may be truncated asymmetrically. The default is to leave a full NZ length outer grid.

## 6.5.1 APRT

As part of its printed output NASCAP may tabulate the final potential array (i.e., the potentials at each grid point) after each TRILIN call. The card:

#### APRT n

gives the number of grids for which potentials are printed out. The default is 1, i.e., potentials are printed for just the inner grid. Potentials may be printed for all the grids requested, or for none, using this command. For example

## APRT 3

will cause potential arrays to be printed out for all three grids in a three grid problem, or just the innermost three grids in a 4 or more grid problem.

6.5.2. CONVERGENCE PLOTS

#### The card:

# CONVERGENCE PLOTS ON

causes a printer plot of the square of the residual vector  $(\vec{r} \cdot \vec{r})$  for each iteration to be produced after each cycle. The residual vector  $\vec{r}$ is explained in Section 3.15.1 dealing with the conjugate gradient potential solver. The default is not to print the plot. This result is also achieved with the card:

## CONVERGENCE PLOTS OFF

The convergence plots are only useful as a diagnostic tool, to check the conjugate gradient potential solver as working correctly. Problems in this respect are sometimes solved by increasing the maximum number of iterations using POTCON (6.2.8). The card:

PRINT <(sub)module>

causes diagnostic information to be printed out during each call to the module or submodule requested. The following four (sub)modules may be printed:

HIDCEL

OBJDEF

LIMCEL (called when LONGTIMESTEP is requested - 6.2.6)

POTENT (potential solver called from CAPACI and TRILIN) The default mode is not to print messages, except for OBJDEF, which has an intermediate level of print, from a module unless specifically requested with a PRINT card. For example

PRINT LIMCEL

causes diagnostic information to be printed on calls to TRILIN when LONGTIMESTEP has been requested (6.2.6). PRINT's can be explicitly turned off with the card:

NOPRINT <(sub)module>

For example

NOPRINT LIMCEL

cancels a previously requested PRINT LIMCEL. The information printed out is for diagnostic purposes only and is not needed for the usual operation of the code. <u>Warning</u>: The HIDCEL module is capable of producing an extremely large volume of diagnostic information.

6.5.4 SURFACE CELL

In Section 3.10 we discuss how each exposed face of a filled volume element, or surface cell, is assigned a surface cell number n. The card:

SURFACE CELL n

causes a breakdown of the net flux to surface cell number n to be printed after each cycle. Contributions from incident primary fluxes, secondary emission, backscatter and conductivity, as well as information about the surface cell itself are printed out. The format of the breakdown is shown in Figure 6.4. A card is required for each surface cell to be printed. The default when no surface cell card is included in the options file is to print a breakdown for cell #1 only.

# 6.5.5 SURFACE CORNER AND SURFACE AT

The same flux breakdown that is printed when a SURFACE CELL card is included in the options file (Figure 6.4) can also be printed using the

SURFACE CORNER x y z <norx nory norz>

card. Instead of referring to the cell according to its NASCAP assigned number (as in the case with SURFACE CELL), SURFACE CORNER refers to the cell by the coordinates of the lowest indexed corner  $(x \ y \ z)$  of its associated volume cell, and where this still does not uniquely determine it, the direction of its surface normal (norx, nory, norz). The lowest indexed corner is the one with the least positive sum of coordinates X +Y +Z. The associated volume cell is the cell in which it is located, or out of which it points.

For example, consider a cube extending one mesh unit in the positive direction from -1 -1 -1. The bottom face in the X Y plane has vertices:

The lowest indexed vertex -1 -1 -1 has a sum = -3. However two other faces in the XZ and YZ planes also share this lowest indexed vertex. To uniquely determine the XY face we must also specify its normal, which points in the -Z direction; i.e.,

norx, nory, norz  $\equiv 0 \quad 0 \quad -1$ A flux breakdown for the bottom X Y cell is requested with the card: SURFACE CORNER -1 -1 -1 0 0 -1

 $<sup>\</sup>begin{array}{rrrrr} -1 & -1 & -1 \\ 0 & -1 & -1 \\ -1 & 0 & -1 \\ 0 & 0 & -1 \end{array}$ 

004612210403 6 10 17 0 1 0 KAPT 5+28-0073 1.21-0073 1.41-0053 CODE = Location = Normal = Material = 071+003 VOLTS ""TETT" +006 VOLTS/METET = 2-344+002 VOLTS/METER = 9-598-002 L L L 1.23-008 5.255-000 5.555-000 1.116-008 1.116-008 1.116-010 POTENTIAL = -3.071 STRESS = 1.114+00 EXTERNAL FIELD = LIMITING FACTOR = FLUXES IN A/M\*\*2 INCIDENT ELECTRONS RESULTING SECONDARIES INCIDENT PROTONS BULK CONDATIES BULK CONDATIES PHOTOCURRENT . 2A NET FLUX

Figure 6.4. Flux breakdown for SURFACE CELL 28.

SURFACE CELL NO.

The coordinate system used by SURFACE CORNER is either the default system (region at mesh center) or the one defined by the most recent OFFSET card (6.4.6). SURFACE CORNER <u>cannot</u> be used until the object has been defined. Since RDOPT always precedes a call to OBJDEF this means that SURFACE CORNER can only be used in <u>subsequent</u> calls to RDOPT (perhaps in a RESTART run).

SURFACE AT is the same as SURFACE CORNER except that it uses the absolute coordinates option (See 5.8.1).

6.5.6 TIMER/NOTIME

The card:

TIMER

included in the options file causes the computer time left for the NASCAP run to be printed out after each significant step in the calculation. For example, if 400 seconds were requested for the run (using the job control language of the machine running the code) the messages like:

TIME LEFT 398 TIME LEFT 372

etc., would be printed out periodically as the run progresses. NASCAP (UNIVAC version) will not begin another TRILIN cycle when the time left is less than 300 seconds. The 300 seconds allow NASCAP to finish the cycle it is on and save all files cleanly before run time actually expires completely. Run time checks (for smaller amounts of time) also occur in the HIDCEL module (and the POTENT submodule). NASCAP (UNIVAC version) should always be run with at least ten minutes of time requested.

The default behavior, and the card: NOTIME suppress the printing of the TIME LEFT messages.

## 6.6 RUN OPTIONS THAT CONTROL GRAPHICAL OUTPUT

## 6.6.1 3D-VIEW

#### The card:

#### 3D-VIEW x y z

adds an additional perspective view to the three views of the object usually plotted by SATPLT (8.7). The coordinates  $x \ y \ z$  give the point from where object is to be observed. Up to five views may be produced by each call to SATPLT. By default the following sequence of four cards is assumed:

| 3D-VIEW | NON | E  |    |
|---------|-----|----|----|
| 3D-VIEW | 5   | 8  | -5 |
| 3D-VIEW | -5  | 8  | 5  |
| 3D-VIĖW | 2   | -5 | 5  |

This establishes the three default views usually produced by SATPLT. The card:

#### **3D-VIEW NONE**

clears all previous view entries. This card can be used in the options file to cancel the three default views. The user may then specify up to five of his own views. If no '3D-VIEW NONE' card precedes declaration of additional views, then a maximum of two may be added to the three already there. The authors recommend directions such as '1 2 3' as tending to produce aesthetically pleasing views of NASCAP object.

#### 6.6.2 CONTOURS

NASCAP can produce potential contour plots after completed cycles using the CONTOURS command. The default behavior is not to plot any potential contours. The card:

#### CONTOURS STANDARD

causes six standard contour plots to be produced <u>every</u> cycle. Plots may be made for any plane parallel to an axis plane in any grid. Up

to 14 specific plots may be requested with cards of the form:

CONTOURS  $\begin{pmatrix} X \\ Y \\ Z \end{pmatrix}$  cut # <GRIDS ng MOD n>

The X Y and Z refer to the direction of the normal to the plane in which the contours are to be plotted, and "cut# " refers to the grid point along this direction, through which the plane passes. For example, the card:

CONTOURS Y 6

chooses a plot of contours in the X Z plane passing through the point 0 6 0, i.e., a plane cutting the Y axis at point Y = 6. Since 'GRIDS' and 'MOD' are omitted, plotting occurs including all the space to the outermost grid and the plots will be produced every cycle (n = 1).

The optional keyword 'GRIDS' is used to specify the number of grids to include in the plot. The keyword 'MOD' means "produce a plot every n cycles". For example

CONTOURS Y 6 GRIDS 1 MOD 5 would produce a contour plot for the plane cutting the Y axis at Y = 6 including only the <u>inner</u> grid, every <u>five</u> cycles.

A specifically requested contour plot may be turned off with the card:

CONTOURS 
$$\begin{pmatrix} X \\ Y \\ z \end{pmatrix}$$
 cut # OFF

For example the above plot can be turned off using

#### CONTOURS Y 6 OFF

Note that all coordinates are in inner mesh units, and refer either to the default origin (grid center) or the one defined by the latest OFFSET (6.4.6).

The 'CONTOURS STANDARD' command is equivalent to the following sequence:

| CONTOURS | X | 0 | GRIDS 1 | . MOD  | 1 |  |
|----------|---|---|---------|--------|---|--|
| CONTOURS | X | 0 | GRIDS n | ig MOD | 1 |  |
| CONTOURS | Y | 0 | GRIDS 1 | . MOD  | 1 |  |
| CONTOURS | Y | 0 | GRIDS n | ig MOD | 1 |  |
| CONTOURS | Ζ | 0 | GRIDS 1 | . MQD  | 1 |  |
| CONTOURS | Z | 0 | GRIDS n | ig MOD | 1 |  |
|          |   |   |         |        |   |  |

(where  $ng \equiv outermost grid$ ).

The MOD number may be controlled by the user independently with the command:

CONTOURS STANDARD < MOD n>

For example:

CONTOURS STANDARD MOD 5

will produce the same standard six contours given above every <u>five</u> cycles instead of every cycle.

6.6.3 DESTINATION

The card:

**DESTINATION** dest

establishes the destination device for the NASCAP produced plots, such as a graphics terminal, electrostatic printer, microfiche, etc. The options 'dest' are site dependent and should be determined during installation of the code. At S-Cubed the active values for 'dest' are:

NONE - user input at run time requested (default)
COMPRS - written to file 41 (may be processed later)
CALC - the CALCOMP plotter
TEKT - the Tektronix graphics terminal
ELEC - electrostatic plotter

The mechanics of NASCAP plotting are discussed in Chapter 9.

6.6.4 MATVIEW

Module SATPLT (8.7) also produces plots showing the pattern of the different surface materials covering the satellite. The card:

MATVIEW 
$$\frac{+}{z} \begin{pmatrix} x \\ y \\ z \end{pmatrix}$$
 cuta cutb

can be included in the options file to add different views for material plots to those already selected by default. The 'X Y Z' selects the direction from which the object is to be viewed. Cuta and cutb give the coordinates (inner grid) of the observer and how far he can see along the axis chosen. For example:

MATVIEW -X -4 10

selects a view from the negative X direction with the observer at X = -4 and includes all surfaces between the observer and X = 10. The card:

MATVIEW +X -4 10

selects a view from the positive X direction with the observer at X = 10 and includes surfaces between the observer and X = -4.

The default selection of views is equivalent to the cards:

| MAT | ۷I | EW | NONE |
|-----|----|----|------|
|     |    |    |      |

| MATVIEW | +X | -8  | 8  |
|---------|----|-----|----|
| MATVIEW | -X | -8  | 8  |
| MATVIEW | +Y | -8  | 8  |
| MATVIEW | -Y | -8  | 8  |
| MATVIEW | +Z | -16 | 16 |
| MATVIEW | -Z | -16 | 16 |

The card:

#### MATVIEW NONE

cancels all previous view selections, including the six initially specified by default. Up to five views may be chosen for each of the six possible directions.

The coordinate system used is the default grid centered one (in inner grid units) or the most recent one defined by an 'OFFSET' card (6.4.6).

## 6.6.5 REPEAT

## The card:

#### REPEAT n

causes any plot to be repeated n times. The default is to make each plot just once. <u>This feature is not general and is hardware</u> <u>dependent</u>. It should be used only on sites where it is known to be implemented (e.g., NASA/Lewis).

# 6.6.6 SHEATH

## The card:

## SHEATH

activates the option that causes plots of particle trajectories and charge densities around the spacecraft to be plotted for space environments (5.4). The default behavior is not to calculate or plot these quantities. The same effect is explicitly brought about with the card:

#### NOSHEATH

## 6.6.7 TANKCUR

#### The card:

## TANKCUR ON

causes a contour plot of current density to be produced for TEST TANK-1 runs (5.8). The default behavior is not to plot this quantity. The same effect is brought about with the card: TANKCUR OFF 6.6.8 TANKTRAJ

TANKTRAJ ON and TANKTRAJ OFF are exactly analogous to the TANKCUR commands explained in 6.6.7. TANKTRAJ refers to particle trajectory plots in a TEST TANK-1 case, rather than current density.

6.6.9 TITLE

The card:

TITLE title

causes a user specified title to appear in the first frame plotted, along with the date and time of the NASCAP run. The default title is

NASCAP

The 'title' must begin in column 9. For example the card:

TITLE STAN'S TANK RUN

↑ column 9

will cause the phrase

'STAN'S TANK RUN'

to replace 'NASCAP' in the first plot frame.

6.7 OPTIONS DEFINING LOGICAL UNIT NUMBERS

The default values for the logical unit numbers of the NASCAP files are shown in Tables 2.3 and 2.4. These file numbers can be changed to other values by including cards in the run options file of the form

filename number For example the logical unit number of file IKEYWD may be changed from the default value of 26 to 46 with the card:

IKEYWD 46

The other file names shown in Table 6.7 can be used in a similar way. Some examples are:

IP 48 ISPCTR 23 IPART 42

# 6.8 OPTION CHECKLIST

The large number of NASCAP options described in this chapter is enough to befuddle even an experienced user. Clearly, some are of more importance than others. For this reason, we have divided them into four categories by frequency of use. These are shown in Table 6.8.

The "most commonly used" options should be familiar even to a beginning user. We suggest that (with the obvious exception of RESTART) they always appear in the options file, even though the defaults may be acceptable.

The "other commonly used options" control output or commonly encountered aspects of charging problems.

The "less commonly used options" are for diagnostic purposes, or require care in use, or are relatively specialized.

The "rarely used options" are those which have acceptable defaults, or serve to restore defaults, or are nearly obsolete.

Options considered totally obsolete, even though still functional, have been omitted from this manual.

TABLE 6.8A. MOST COMMONLY USED OPTIONS

DELTA

END

•

-

~

-

-

-

IOUTER

LONGT IMESTEP/NOLONGT IMESTEP

NCYC

NG

NZ

RESTART

TIMER

TYPE

XMESH

# TABLE 6.8B. OTHER COMMONLY USED OPTIONS

3D-VIEW BFIELD

BIAS

CIJ

CONTOURS

CONVEX

DESTINATION

FIXP

SUNDIR

SUNINT

SURFACE AT

SURFACE CELL

SURFACE CORNER

TANK AXIS

TANKCUR

TANK RADIUS

TANKTRAJ

TITLE

ZTRUNCATE

TABLE 6.8C. LESS COMMONLY USED OPTIONS

APRT

-

.

-

-

DEADLINE

DEBYE

DELFAC

DIPOLE MOMENT

DISCHARGE

EFFCON

EMITTER

FLASHOVER

FLDCON

IFLUX

MATVIEW

NOPRINT

OFFSET

PRINT

RADCON

RIJ

SECONDARY EMISSION

SHEATH

UPDATE

CONVERGENCE PLOTS

FLOAT

IAREA

IAUN

ICNOW

IDIV

IKEYWD

IOBJ

IOBPLT

IP

IPART

IPQCND

IR

IROUS

ISAT

ISPARE

ISPCTR

IU

NOEMITTER

NOSHEATH

NOTIMER

REPEAT

SCALE/NOSCALE/DSCALE

## 7. NASCAP PARTICLE TRACKING

#### 7.1 INTRODUCTION

NASCAP calculates particle trajectories in order to simulate particle emitters and detectors, electron guns (TYPE 1 Test Tank), and to calculate space charge density (SHEATH option). In the case of particle detectors, particles incident upon a particular surface cell are backtracked to determine their origin. This allows a statistical estimate of the arriving current as a function of parameters such as incident energy and angle of incidence. Unlike particle detectors, emission affects the object potential since a new source of current is introduced. The emitted current is taken into account in this respect. Emitted particle trajectories are calculated by NASCAP, and the trajectory plots produced can be used to estimate the emitted current returning to the spacecraft. NASCAP includes both emitted and return current in its potential calculations.

The detector simulation is activated by executing the module DETECT. The particle emitter simulation is activated by including the keyword 'EMITTER' in the run options file (6.2.4). Examples of the other two uses of particle tracking may be found elsewhere in this volume. Let's begin by discussing the DETECT module.

#### 7.2 DETECT

#### 7.2.1 OVERVIEW

The DETECT module calculates and plots incident energy flux density as a function of incident energy and direction for both ions and electrons. The energy flux density is the quantity actually measured by spacecraft particle detector experiments. It is a measure of the number of particles collected per second, times their energy (i.e., the incident current weighted by the energy of the incident particles).

NASCAP considers a detector to reside on a given surface cell. The range of incident energy and incident solid angle of the incoming particles that the detector is able to measure, is chosen by the user. DETECT then calculates the energy flux density arriving within a cone about the direction chosen, and within the energy range chosen. It takes into account deflection of the particles by electric fields due to charging on the object, deflection by magnetic fields, and "mechanical" deflection. "Mechanical" deflection occurs when a particle that would have reached the detector otherwise, collides with another piece of the spacecraft obstructing the view.

A typical field of view for a detector is shown in Figure 7.1. Particles are assumed to be collected if they arrive within a cone about the incident direction chosen. The width of the cone is given by  $\Delta \Theta$  (Figure 7.1).  $\phi$  gives the azimuthal angle of the incident direction about the surface normal. The angle  $\Theta$  is the angle between the incident direction and the surface normal of the cell chosen as the position of the detector. The integrated energy flux (i.e., the total collected by the whole cone) is calculated. Plots of differential energy flux as a function of any one of the three variables incident energy,  $\Theta$  and  $\phi$ , may be requested. (One variable becomes the plot abscissa while the other two are held fixed.)

DETECT is used to simulate the operation of particle detector experiments under spaceflight conditions, when the spacecraft is charged. It is also useful in investigating focussing and deflection effects due to charging of the spacecraft in general.

## 7.2.2. EXECUTION OF DETECT

The module DETECT must be preceded by execution of TRILIN or IPS since they both establish potentials on the surface of the spacecraft. (Exact precedence is summarized in Table 2.2.). DETECT is executed by including the card:

DETECT <n>



Figure 7.1. Typical field of view for a Detector.

in the NASCAP runstream. The optional parameter n specifies the number of the file where DETECT is to look for input. The default value of n is 5, in which case DETECT expects its input cards to follow immediately in the runstream. DETECT input must be terminated with its own 'END' card, whether it resides in file n or the NASCAP runstream. If DETECT is the last module to be executed in a NASCAP run this means that two 'END' cards are necessary to terminate the runstream: one for the DETECT file and one for the whole runstream (2.4). For example, a runstream might end as follows:



The DETECT input cards can be classified into three groups according to their function:

- (1) Definition of detector location and orientation.
- (2) Control of the particle tracking and current integration.
- (3) Control of plots produced.

We examine each of these functions in the following three sections.

# 7.2.3 DEFINITION OF THE DETECTOR

The detector may lie on the plane of any surface cell. It collects particles arriving within a cone about a chosen direction.

(This is shown in Figure 7.1). The choice of surface cell, incident direction and the width of the cone are all specified using keywords in a DETECT input file. The energy range of the incoming particles that are detected may also be chosen in this way.

Direction is specified using a cell-based polar coordinate system. In this system the surface normal defines the +Z axis. The X and Y axes lie in the surface plane. The X axis is chosen to lie on top of the projection of the surface normal in the XY plane of the computational grid, i.e., the projection of the surface X axis and the surface normal on the grid XY plane are coincident. Direction in this surface cell system is determined by the polar coordinates  $\theta$  and  $\phi$ .  $\theta$ is the angle between the normal (the Z axis) and the direction vector.  $\phi$  is the angle between the X axis and projection of the direction vector on the surface plane in a counterclockwise sense. For example, a 1 1 vector in this system would point between the positive axes and have coordinates  $\theta = 45^{\circ}$  and  $\phi = 45^{\circ}$ . The Y axis has coordinate  $\theta = 90^{\circ}$  and  $\phi = 90^{\circ}$ .

The cone about the direction vector is defined by the half-angle, or width,  $\Delta \Theta$ .

The keywords that determine these quantities have the following syntax.

7.2.3.1 DETECT

The detector input file must begin with the card DETECT

This tells the DETECT module that a new detector definition is to follow.

More than one detector can be defined within a DETECT input file. A new detector is specified by including another DETECT card.

All input cards following one DETECT are assumed to refer to that detector until another DETECT card is encountered. For example, a DETECT input file defining multiple detectors might have the form:

DETECT { PARAMETERS FOR FIRST DETECTOR DETECT { PARAMETERS FOR SECOND DETECTOR DETECT { PARAMETERS FOR THIRD DETECTOR END

Note that more than one detector may be defined for the <u>same</u> surface cell (pointing in perpendicular directions for example).

7.2.3.2 ICELL

The location of the detector is set with the card: ICELL n

The parameter n gives the surface cell number where the detector is to reside. If no ICELL card is included before the other input cards it is assumed to reside on surface cell number one by default.

Detectors on boom cells are allowed but require special treatment. This is explained in Section 7.2.4 Note that boom cells follow surface cells, i.e., an object with 158 surface cells and 13 boom cells will have boom cells numbered 159-171.

7.2.2.3 ENERGY

The detector collects particles with energy in the range from E to E + △E. The energy E is defined with the card ENERGY E where E is in eV. For example, ENERGY 2000

will set E to 2 keV. The default value assumed if no ENERGY card is included is 10 eV.

7.2.3.4 DEK

The energy accepting "width" of the detector  $\Delta E$  is determined by the value of DEK.

$$\Delta E = E \times (\frac{DEK}{100})$$

DEK is the percentage of E equal to  $\Delta E$ . It is set with the card DEK d

The default value is 0. For example, if E were set at 2 eV and DEK at 10:

ENERGY 2000 DEK 10

then the detector would collect particles with energies in the range 2000-2200 eV.

7.2.3.5 THETA

The detector collects particles that fall within a cone around a chosen direction. This direction is determined by its polar coordinates  $\phi$  and  $\theta$ , in the surface cell system described in 7.2.3. THETA ( $\theta$ ) is the angle between the chosen direction and the surface normal. It is set with the card:

THETA e

 $\Theta$  must be in degrees and lie between <u>+</u> 90. The default value is 0 (i.e., along the surface normal).

7.2.3.6 DTH

The aperture, or width of the cone about the chosen direction of the detector is determined by its half angle  $\Delta \Theta$ . This is set with the card

DTH  $\Delta \Theta$   $\Delta \Theta$  may range from 0 to 90°. The default value is 0. For example: DTH 8 sets  $\Delta \Theta$  to 8°.

7.2.3.7 PHI

The angle  $\Theta$  does not uniquely define the chosen direction. One more angle is required. The angle  $\phi$  is the angle between the projection of the chosen direction in the surface cell plane and the X axis of the surface coordinate system (in the counterclockwise sense). (See 7.2.3). This is set with the card

PHI Ø

where  $\phi$  is in degrees and may take values from 0 to 360°. The default is 0 (i.e., the chosen direction lies in the XZ plane of the surface system).

7.2.4 BOOM DETECTORS (ZETA)

Detectors are placed on booms in just the same way as other cells. They are assumed to lie at the center of the boom segment or cell specified. Since the surface of the boom is cylindrical there is no unique direction for the surface normal, and hence no unique surface cell coordinate system. This problem is overcome by defining the angle between the projection of the chosen boom surface normal and a grid axis, in the grid plane perpendicular to the boom. For example, if the boom lies along the grid Z axis the projection of the boom-normal

is in the grid XY plane, and the angle  $\zeta$ (Zeta) is measured from the grid X axis. This is shown in Figure 7.2. For booms along the other axis, the labels are cyclicly permuted.

The angle zeta is set using the card ZETA ζ The default value of zeta is 0. For example: ZETA 25 sets ζ to 25°. If the detector is not on a boom cell, ZETA is ignored.

7.2.5 CONTROL OF PARTICLE TRACKING AND CURRENT INTEGRATION

The particle tracking algorithm moves the particles in steps. The number of steps included in the trajectory calculation is chosen by the user as 'NSTP'. Each step is designed to move each particle the same distance. Thus faster moving (higher energy) particles have shorter times associated with each step. The distance associated with the steps is determined by the "code velocity" VCODE. The greater VCODE the greater the distance associated with each step.

It is important that the particles tracked from the detector move far enough to be able to reach at least the boundary of the inner grid. The choice of NSTP and VCODE should be made with this in mind. In general, the larger VCODE, the smaller NSTP may be while still allowing the particles to reach the boundary, (since the distance associated with each step is greater). However, as the step distance increases the accuracy of the calculation is decreased. Hence, there is a trade off between the number of steps (computation time) and accuracy. A good compromise can usually be made by choosing VCODE and NSTP so that particles reach the boundary in a few hundred steps.

To calculate the integrated current arriving at the detector in the range of energy and direction selected during its definition, particles must be tracked for a sample of values of E,  $\theta$  and  $\phi$ . The number of samples taken over the energy range and the range of  $\theta$ 



Figure 7.2. Boom cell coordinate system.

and  $\phi$  are specified by the user. Each new combination causes another particle to be tracked. If the number of samples to be taken in all three variables is chosen to be 10, then all 10 x 10 x 10 = 1000. combinations must be tracked. The larger the number of samples chosen the more accurate are the integrated currents calculated, but the computational effort is greatly increased.

To understand these principles more clearly, let's examine the ways the variables we have discussed are controlled.

7.2.5.1 NSTP

The number of steps to be taken for each particle in reverse trajectory calculations is set with the card:

## NSTP n

n can take values from 1 to 30,000. The default value of 500 is a reasonable choice for tracking inside the inner grid. If particles are to be tracked out to further grids at least 400 more steps should be added for each extra grid. For example, if tracking is to occur out to the third grid NSTP might be set to 1300.

#### NSTP 1300

These values assume a value of VCODE of around 0.3 (the default).

7.2.5.2 VCODE

The particle code velocity or distance moved in inner grid units per step is set with the card

#### VCODE v

The default value is 0.3 (i.e., 3 steps move a particle approximately 1 grid unit). This is a safe value to use in most applications.

For a detector on a boom in grid number IG this is automatically scaled by the mesh size  $2^{(IG-1)}$ .

7.2.5.3 NE

The number of points sampled over the energy range  $E \rightarrow E + \Delta E$ (7.2.3) is set with the card:

NE n

n may take the value 1 or any even value up to 12. The default value is 1. For example the following cards

ENERGY 2000

DEK 10

NE 4

set the energy range to 2000-2200 eV. Four representative energies are sampled within this range. If NE is 1, the (single) sample energy is chosen equal to E.

7.2.5.4 NMU2

NMU2 sets the number of points sampled over the width of the detector cone (over  $\Delta \Theta$ ).

NMU2 n n may take any positive value. The default is 1. For example: NMU2 10 sets the number of samples over A0 to 10.

7.2.5.5 NP

The number of points taken around the perimeter of the cone is set with the card

NP n

This breaks up the interval of the azimuthal angle  $\phi'$  in the <u>detector</u> coordinate system from 360° to 360°/n. The default value of n is 1, in which case  $\phi'$  is chosen to be 0. (See Figure 7.1 for definition of  $\phi'$ .)

#### 7.2.6 CONTROL OF PLOTS

Two types of DETECT plots are produced: plots of energy flux density against one of the variables E,  $\Theta$  and  $\phi$ , and particle trajectories.

The variable E,  $\Theta$ , or  $\phi$ , chosen for the plot of energy flux density is called the <u>Independent Variable</u>. The range of the independent variable and the number of points plotted are also selected by the user.

Plots are made for both ions and electrons on the same graph. The scales and pen-type can all be set by the user independently, or chosen automatically using the AUTOS option.

Particle trajectory plots show a silhouette of the spacecraft and lines representing the path of each of the particles tracked. For each request, views in each of the three grid axis planes are plotted for both electrons and ions (i.e., a total of six plots). Trajectory plots may be made in more than one grid, and in more grids than were actually included in the potential calculation in the first place (NG). This is to allow for the effect of large radius curved trajectories induced by magnetic fields. The potential v in the grids outside the outer computational grid is assumed to be derived from a monopole at the object center with charge q (equal to the total charge on the object) i.e.,

$$v = \frac{q}{4\pi\epsilon_0 r}$$

where r is the distance from the object center.

Examples of both types of plot are given in Figures 7.3 and 7.4.

Let's examine the remaining DETECT input cards that control the plots.



ENERGY FLUX IN EV/(CM2-SEC-SR-EV) AT CYCLE O MEASURED BY DETECTOR LOCATED AT CELL NUMBER 1 (INTERPOLATED AT 10 POINTS) PROTON FLUX (HERVY) SCALED BY 1.00+005 ELECTRON FLUX (LIGHT) UNSCALED.

Figure 7.3. Detector energy flux vs energy plot.



Z-AX15

~

O FOR ELECTRONS IN 1 GRIDS RECEIVED BY DETECTOR TRAJECTORIES AT CYCLE

Figure 7.4. Detector particle trajectory plot.

```
The independent variable is set with the card:
INDVAR = var
```

var may be the words ENERGY, THETA and PHI, corresponding to the choice of E,  $\Theta$  or  $\emptyset$  as the variable which energy flux density is plotted against. The default selection is ENERGY. The scale of the axis in the plot depends on the choice of variable as follows:

| Independent Variable | Independent Variable<br>Axis Scale |  |
|----------------------|------------------------------------|--|
| ENERGY (E)           | LOG                                |  |
| THETA (e)            | LINEAR                             |  |
| PHI (ø)              | LINEAR                             |  |

The dependent variable, energy flux density, is always plotted on a LOG scale.

7.2.6.2 FINALV

The range of the independent variable in the plot begins at the value chosen in the definition of the detector and ends at the value set with the card

FINALV f For example, the cards:

| THETA    | 45     |
|----------|--------|
| PHI      | 10     |
| ENERGY   | 10,000 |
| DEK      | 10     |
| INDVAR = | ENERGY |
| FINALV   | 20,000 |

define a detector direction with  $\theta = 45^{\circ}$  and  $\phi = 10^{\circ}$  (in the surface system) which remains fixed, in a plot of energy flux density against initial energy where the energy range is swept from (10keV, 11 keV) to (20 keV, 22 keV).

The default value of f is 49999 eV, since the default independent variable is ENERGY. If  $\Theta$  and  $\phi$  are chosen as independent variables FINALV <u>must be changed</u> explicitly from this default value to an acceptable limit for the variables. For  $\Theta$  acceptable limits are within + (90- $\Delta\Theta$ )°. For  $\phi$  FINALV may range from 0 to 720°.

7.2.6.3 N

The number of points included in the energy flux density plot is set with the card

N n

N has a default value of 20, and must be between 3 and 500. For example, the same plot discussed in 7.2.6.2 can be made with 50 points using the cards:

| THETA    | 45     |
|----------|--------|
| PHI      | 10     |
| ENERGY   | 10,000 |
| DEK      | 10     |
| INDVAR = | ENERGY |
| FINALV   | 20,000 |
| N        | 50     |

7.2.6.4 AUTOS

~

# The card

## AUTOS

included in the detector definition causes automatic scaling of the calculated energy flux density in the plot against the independent

variable. The default behavior is to require manual selection of scale using the FLXMAX and FLXMIN options discussed below. The use of AUTOS is highly recommended.

## 7.2.6.5 FLXMIN AND FLXMAX

The minimum and maximum values on the energy flux density axis of the plot against the independent variable may be set using FLXMIN and FLXMAX. For example, the cards

```
FLXMIN 1.E6
FLXMAX 1.E14
```

will set the minumum value to  $10^6 \text{ eV}/(\text{cm}^2 \text{ s sr eV})$  and the maximum to  $10^{14} \text{ eV}/(\text{cm}^2 \text{ s sr eV})$ . The scale is logarithmic. Default values are  $10^4$  and  $10^{12}$  respectively. These cards are ignored when the AUTOS option (7.2.6.4) is in force.

7.2.6.6 PSCALE

Since the ion fluxes are an order of magnitude or two less than the electron fluxes, and both curves are overlaid on the same set of axes, it is often convenient to scale the ion fluxes by a factor p. This is set using the card

PSCALE p For example, the card PSCALE 1.E2 will scale a proton flux of 6 x  $10^8 \text{ eV/(cm}^2 \text{ s sr eV})$  to 6 x  $10^{10}$ for the purpose of a plot. The default value is p =  $10^5$ .

7.2.6.7 LWPEN

To distinguish the ion and electron curves on the same graph, the ion energy fluxes are plotted with a broader penstroke. The number of vector points covered by the penstroke for the ion curve may be set with the card

LWPEN n
n may take a value between 1 and 10. The default is 3. Electron curves are always drawn with a width of 1.

7.2.6.8 LABABV

## If the card

#### LABABY

is included in the detector definition the headings on the plot will be omitted. This saves time when plotting on interactive graphics terminals but is apt to lead to confusion.

7.2.6.9 PRFLUX

## If the card

#### PRFLUX

is included in the detector definition values of energy flux density included in the plot will be tabulated as printed output also.

7.2.6.10 PLPART

The particle trajectory plots are not automatically produced by default. Including the card

#### PLPART

in the detector definition causes a minimum of 6 plots to be produced, giving views in each of the grid axis planes for both ions and electrons. The plots extend to the highest grid reached by any of the particles. The grids plotted can also be controlled with the following options.

#### 7.2.6.11 NGBND

The number of grids included in the plot may be set with the card

#### NGBND n

n may take <u>integer</u> values greater than 0. If n = 0 the highest grid reached by particles is automatically included. n is zero by default.

#### For example

NGBND 5

will include only the first five grids in the trajectory plots, even if some particles actually reached into grid 6 and higher.

### 7.2.6.12 NGPLOT AND NGINC

It is possible to make up to 4 different sets of plots of the same trajectories including the same or different grids. The card NGPLOT n sets the number of sets to n. n can take integer values from 1 to 4. The default is 1. The card NGINC m

sets the increment for the outer boundary for successive plots. For example, the cards

NGBND 1 NGPLOT 3

NGINC 2

will produce three sets of plots of the same trajectories with the outermost grid number IG given by

 $IG = NGBND + (I-1) \times NGINC$ (for I = 1, 2, 3)

i.e. with IG = 1, 3, and 5.

The default value of NGINC is O. NGBND, NGINC and NGPLOT must all be chosen so that IG does not exceed LIMGRD.

7.2.6.13 LIMGRD

The highest grid in which particles may be tracked is set with the card

LIMGRD n

n may take any positive value above zero. The default value is NG, the number of grids included in the computational space. LIMGRD may exceed NG, in which case a monopole potential is used beyond the computational space.

7.2.6.14 MODPAR

To save plotting time not all the line segments making up a particle trajectory need be plotted. The card

MODPAR n causes only every nth line segment to be plotted. For example MODPAR 2

causes every other line segment to be plotted. The choice of MODPAR 0

causes n to be set to  $2^{IR}$ -1, where IR is the grid number on which the plot is taking place. Then in the inner grid, all the line segments are plotted. In the 2nd grid, every other one is plotted, in the 3rd, every 4th one and so on. The default value of n is 0.

7.2.7 THE DETECT INPUT FILE: EXAMPLE

Figure 7.5 shows a sample detector input file with comments explaining each card. Figure 7.6 shows the printed output generated by the DETECT module associated with this input. A second example illustrating the use of DETECT is given in Chapter 11.

7.3 EMITTER

7.3.1 OVERVIEW

Particle emitters are defined in essentially the same way as particle detectors. The emitter is positioned on a particular surface cell, and the particles emitted from a cone about a chosen direction are tracked over a range of energies defined by the user. Those that reach the outer boundary of the computational space are considered lost to the spacecraft.

|               | M9EX 1 44444 |        | EX OF DETECTOR SURFACE CELL | INER OF ENDEPENDENT VARIABLE POINTS | INUM NUMBER OF TRAJECTORY STEPS |                    | (LOW END OF DLTCCTOR ENERGY RANGE) | (HIGH END OF DETECTOR ENERGY RANGE) | IT I XED AZ IMUTHAL ANGLED | OF TXED POLAR ANGLED | IVATE PLAT AUTA-SCALING OPTION | MEST PARTICLE TRAJECTORY PLOTS |      |  |
|---------------|--------------|--------|-----------------------------|-------------------------------------|---------------------------------|--------------------|------------------------------------|-------------------------------------|----------------------------|----------------------|--------------------------------|--------------------------------|------|--|
|               | NN S         |        | 100                         | NUM                                 | M A X                           |                    | N<br>L                             | L V                                 | UE G                       | DE G                 | A (; [                         | 10 J 21                        |      |  |
|               | 01.01.01.01  |        | 225                         | 25                                  | 150                             |                    | 10.01                              | 0.00000                             | 0.0                        | 50.0                 |                                |                                |      |  |
|               | DEF INL      |        |                             |                                     |                                 |                    |                                    |                                     |                            |                      |                                |                                |      |  |
|               | *****        |        |                             |                                     |                                 | NI, R1, Y          |                                    |                                     |                            |                      |                                |                                |      |  |
| III. III. C I | COMMENT      | COMMEN | וכנרו                       | 2                                   | NS I P                          | I = BIA DA A B = F | L'AF RGY                           | F IRAL V                            | LHT                        | L L L L              | AUTUS                          | PLEAR                          | (IN) |  |
| -             | •            | 3.     | ÷.                          | 5.                                  | <b>6</b> .                      | ٦.                 | 8.                                 | <i>.</i> .                          | 10.                        |                      | 12.                            | 13.                            | 14.  |  |

NASCAP detector keyword file to perform an energy scan over 25 points logarithmically spaced from 10 eV to 50 keV. Detector looking in the direction of the normal to surface cell 225. Figure 7.5.

DETECTOR NUMBER 1:

CELL LOCATION = 225

ENERGY FLUX INTEGRAL

| υF    | 11 | 0.00 | E V    | H         | 11 |   |
|-------|----|------|--------|-----------|----|---|
| NC TP | 11 | 161  |        | чР        | ** | - |
|       | 1  |      | 00 000 | SHMN<br>2 | 11 | - |
|       | ı  | -    |        |           |    |   |

| 4 00+08 FV    |                  |            |
|---------------|------------------|------------|
| 5             | 2                |            |
| PLOT = ENERGY | 46E = 1.00+U1 EV | 41 S       |
| F 01          | RAN              | P 0 I 1    |
| ABLE          | ABLE             | 52         |
| VARI          | VAPI             | 0 I N I    |
| INDLPENDENT   | INDEPENDENT      | IS DIVIDED |

FIXED VARIABLES

PHI = .00 0E6 INETA = 50.00 0F6 PROTON ENERGY FLUX PLOT SEPARATION SCALE FACTOR = 1.00+US PROTON ENERGY FLUX PLOT PEN LINE WIDTH = 3 RASTER INCREMENTS PARTICLE VELOCITY = .300 MESH UNITS PER STEP ENERGY FLUX SCALF RANGE IS DETERMINED AT EXECUTION TIME

\*\*\*\* PARTICLE TRAJECTORY PLOTS WILL BE PRODUCED FOR FULS DETECTOR \*\*\*\*

Figure 7.6. Example of printed output from Detector routines.

The total emitted current is considered a loss of charge (either positive or negative depending on whether ions or electrons are emitted) to the underlying conductor associated with the emitter surface cell. Particles that return to the spacecraft (i.e., collide with its surface) are considered to be a source of charge for the cells collecting them. Hence both the emission of the particles and their subsequent collection are taken into account by TRILIN in calculating currents to the object and object potential.

The emitter option should be considered a realistic model only for particle emitters operating at low current density. This is because NASCAP does not take into account the formation of space-charge barriers in front of the emitter. Space-charge effects become significant for electron emission, at currents greater than a few milliamperes and for proton emission at currents greater than about 0.1 milliamperes.

Plots of particle tracks can be produced in any number of computational grids (as selected by the user).

### 7.3.2 EXECUTING EMITTER

Unlike DETECT the emitter option is <u>not</u> a separate module. An emitter is defined and included in a TRILIN calculation by including the card

#### EMITTER <n>

in the <u>run options</u> file (6.2.4). The parameter n gives the file number where the emitter input cards are to be found. The default value of n is 5. If n = 5 is chosen the input cards must follow TRILIN in the NASCAP runstream. If the flux definition file is also file 5 (the NASCAP runstream) then the emitter input cards should follow the flux definition cards. The emitter input file, like the DETECT input file should be terminated with an 'END' card (7.2.2). The emitter input cards fall into the same three groups as for DETECT and in many cases fulfill the same functions. These are:

- (1) Definition of the emitter
- (2) Control of the particle tracking
- (3) Control of the plots produced.

We examine these in turn.

#### 7.3.3. DEFINITION OF THE EMITTER

An emitter is defined in almost exactly the same way as a detector (Figure 7.1). One difference is that the beam of emitted particles must have an energy <u>distribution</u> rather than <u>range</u>. The choice is restricted to a Gaussian or Lorentzian distribution. The beam is assumed to be emitted within a cone defined around the chosen direction. The angular distribution of the beam within this cone must also be selected. The two possible choices are a uniform distribution and one biased towards the center axis of the cone by the factor  $\cos \theta'$  (where  $\theta'$  is the angle between any direction and the center axis of the cone). This is discussed in greater detail in Section 7.4.

The direction of the emitter is defined by specifying the polar angles  $\Theta$  and  $\phi$  of the central axis of the cone, in the same cell coordinate system described for the detector (7.2.3). The first step, however, is to announce a new emitter with the EMITTER keyword. All parameters defined following EMITTER are assumed to refer to the same emitter until a further EMITTER card is encountered. In this way, more than one emitter may be defined. No two emitters may occupy surface cells associated with the <u>same</u> underlying conductor.

Just like the detector card DETECT (7.2.3.1), EMITTER must be the first card in the Emitter input file. All cards following EMITTER refer to the same emitter until a new EMITTER card is encountered. Hence more than one emitter may be defined in any one emitter input file. No two emitters may be on surface cells associated with the same conductor.

For example, an emitter file defining two emitters has the form

EMITTER

(parameters for
 first emitter

EMITTER

```
{ parameters for
      second emitter
END
```

where each emitter is associated with a different conductor.

The cards used to define the emitter are described below.

7.3.3.2 ICELL

The card

ICELL n

locates the emitter on surface cell number n. The cell may be a boom cell (but see 7.3.3.11). The default value of n (if no ICELL card is included) is n = 1.

7.3.3.3 ENERGY

The card ENERGY E sets the peak value in eV of the energy distribution of the emitted particle beam. The default value is 1000 eV. For example, ENERGY 2000

sets the peak value to 2000 eV.

7.3.3.4 JTYPE

#### The card

JTYPE n

determines the energy and angular distribution function types, discussed in 7.3.3 and 7.4. n may take integer values from 1 to 4. The default is JTYPE = 1. The significance of each value is summarized in the table below.

| Distribution Chosen                 |
|-------------------------------------|
| Uniform Angular, Gaussian energy    |
| Cosine e Angular, Gaussian energy   |
| Uniform Angular, Lorentzian energy  |
| Cosine ə Angular, Lorentzian energy |
|                                     |

#### 7.3.3.5 SIGMA

The width s in eV of the energy distribution is set with the card

SIGMA s The default value is 0.1 eV. For example, the cards ENERGY 2000 JTYPE 2 SIGMA 10

define a beam with a Gaussian energy distribution centered at 2000 eV, with a width of 10 eV (7.4) and an angular distribution weighted towards the chosen direction by  $\cos \theta$  (7.4).

C-4

7.3.3.6 PHI

The card

PHI 🖸

sets the azimuthal angle in degrees of the emitter orientation in the surface cell system. The default is  $\phi = 0^{\circ}$ . This is exactly analogous to the detector card PHI (7.2.3.7).

7.3.3.7 THETA

#### The card

THETA e

sets the polar angle  $\Theta$  (in degrees) of the emitter orientation in the surface cell system. The default is  $\Theta = 0$ . This is exactly analogous to the detector card THETA (7.2.3.5).

7.3.3.8 DTHETA

#### The card

#### DTHETA AO

sets the half-angle width of the cone about the emitter direction, in degrees. The default is  $\Delta \Theta = 0$ . This is exactly analogous to the detector card DTH (7.2.3.6).

7.3.3.9 BEAMI

The card BEAMI i sets the total emitter beam current to i amps. The default is  $i = 1 \times 10^{-6}$  amps. For example BEAM 2.E-5 sets the current to 2 x  $10^{-5}$  amps. 7.3.3.10 ISPEC

Whether the emitter emits protons or electrons is determined with the card

#### ISPEC n

where n may take the value 1 for an electron emitter and 2 for a proton emitter. The default is a proton emitter ISPEC = 2.

7.3.3.11 ZETA

If an emitter is to be defined for a boom cell, the angle zeta  $\zeta$ , fixing the surface plane, must be specified. This is explained in 7.2.4.

#### 7.3.4 CONTROL OF PARTICLE TRACKING

The particle tracking for emitters is carried out in just the same way as for detectors. Again there is a trade-off between the number of particle tracking steps taken to reach the boundary and the accuracy of the calculation. This is explained in Section 7.2.5.

The duration of the first tracking step for each particle is chosen so that the distance it moves is equal to the code velocity set by VEDOWN (rather than VCODE used for a detector). This duration is retained for further steps unless the distance moved exceeds VEDOWN or falls below VEUP when it is adjusted to fall within these limits.

The number of particles tracked by each emitter is given by the product

NPHIS x NTHETS x NENGS

where NPHIS, NTHETS AND NENGS are the number of samples in  $\phi$ ,  $\theta$  and energy. These correspond exactly to NP, NMU2, AND NE in the detector case. (7.2.5.5, 7.2.5.4, 7.2.5.3).

Let's examine these input cards more carefully.

7.3.4.1 NSTEPS

#### The card

#### NSTEPS n

sets the number of particle tracking steps to n. n may range from 1 to 2500. The default is 500. Only the first 800 steps are plotted. In all other respects NSTEPS is identical to the DETECT parameter NSTP (see 7.2.5.1).

7.3.4.2 YEDOWN

#### The card

#### VEDOWN d

sets the maximum number of mesh units that any particle may move in a single particle tracking step. Hence the particle tracking steps associated with particles having different velocities (energies) have different durations. The step duration is initially set for each particle so that it moves a distance equal to VEDOWN in the first step. If the particle is subsequently accelerated so that it would move a distance greater than VEDOWN in a step, the duration of the step is automatically cut back.

The default value is 0.3 inner mesh units. This is a reasonable value to use in most cases.

When particles enter higher grids, VEDOWN is automatically scaled by the factor  $2^{IG-1}$ , where IG is the number of the grid. For example, if the particle reaches the third grid IG = 3, and VEDOWN is scaled by  $2^2 = 4$ .

7.3.4.3 VEUP

Particles can be decelerated as well as accelerated and the card

VEUP u

sets the minimum distance that each particle must move in a particle tracking step before the step duration is automatically increased. The minimum distance in inner mesh units is defined by

The default value of VEUP is 5. Then if VEDOWN is set at 5, then the minimum distance moved by each particle is 0.3/5 = 0.06 inner mesh units.

Like VEDOWN (7.3.4.2) VEUP is scaled by the factor  $2^{IG-1}$  in grid number IG.

7.3.4.4 SCALEV

The scaling of VEDOWN and VEUP for higher grids can be changed from the factor  $2^{IG-1}$  to an arbitrary factor f with the card SCALEV f The default value is 1.0. SCALEV is only effective for grids higher than 2.

## For example, with the card SCALEV 5

VEDOWN and VEUP would be scaled by a factor  $2^{IG-1} = 2$  for the second grid but by the factor 5 for the third and higher grids.

SCALEV is a <u>global</u> command and affects <u>all</u> of the emitters in the input file.

#### The card

#### NENGS n

sets the number of energies to be sampled over the range of the energy distribution function chosen. The range is divided up into n - 1 pieces so that each corresponds to an equal weight (or number of particles). The default value is 1.

NENGS is analogous to the DETECT keyword NE (7.2.5.3).

7.3.4.6 NTHETS

#### The card

#### NTHETS n

sets the number of samples to be taken in the angle  $\Theta$  across the range of the cone  $\Delta \Theta$ . The default is 1. NTHETS is analogous to the DETECT keyword NMU2 (7.2.5.4).

7.3.4.7 NPHIS

#### The card

#### NPHIS n

sets the number of samples to be taken in the angle  $\phi'$ , (the azimuthal angle around the cone axis). The default value is 1. This is analogous to the DETECT keyword NP (7.2.5.5).

#### 7.3.4.8 CYMULT

Particles are considered lost when they pass out of the highest grid specified by LIMGRD (7.2.6.13). LIMGRD may be higher than the highest computational grid (NG). (For tracking in grids outside NG a monopole potential (7.2.6) is assumed.)

Particles are also considered lost when moving in grids higher than NG for a time longer than a limit set by the card

CYMULT n

For an environment with a non-zero magnetic field B, n corresponds to the number of "cyclotron" revolutions for the particle.

Time limit = n x 
$$\left(\frac{2\pi \cdot \text{mass}}{E \cdot B}\right)$$

When the magnetic field is zero the time limit is given by n x  $T_{NG}$ , where  $T_{NG}$  is the time spent escaping from the first NG grids (the computational space). The default is 1. For zero magnetic field CYMULT should be set to around 5.0.

#### 7.3.5 CONTROL OF PLOTS AND PRINTED OUTPUT

Emitter produces only one type of plot. This shows the trajectories of the emitted particles. Views are plotted in the three grid axis planes. The trajectories may be plotted in more than one grid, and even out to grids beyond the computational space. If trajectories extend beyond the computational space the potential is assumed to be monopole (7.2.6).

Extra printed output can be requested showing the cells affected by capture of emitted particles, and the histories of each particle emitted.

The following input cards control these features.

7.3.5.1 NGBND, NGPLOT, NGINC

The keywords NGBND, NGPLOT and NGINC control the number of grids included in the trajectory plots. These are explained in Sections 7.2.6.11 and 7.2.6.12.

#### The card

LIMGRD n

sets the number of the highest grid in which particle tracking to to take place. The default value is 6. If n exceeds 2 or NG (see 6.4.7) then a monopole potential is assumed in higher grids (7.2.6). LIMGRD is a global command (7.3.4.4).

7.3.5.3 IPLTYP

#### The card

#### IPLTYP n

sets the type of particle trajectory plots produced. n may take the values 0 or 1. If n = 0 three separate projection views for each emitter are produced. If n = 1 the plots for each emitter are combined on a single set of three projection views. IPLTYP only has an effect when more than one emitter is defined. The default value is 1 (i.e., combined emitter plots).

This is a global command (7.3.4.4).

7.3.5.4 JCYCEM

#### The card

#### JCYCEM n

causes trajectory plots to be produced for every n computational cycle. If n = 0 no plots are produced. The default value is 0 (no plots). For example the card

#### JCYCEM 2

will produce plots every other NASCAP code cycle.

This is a global command (7.3.4.4).

## If the card PRFLUX

is included in the emitter input file a list of all surface cells that capture a particle will be printed for each particle emitter. This card should usually be included in the input file. Again this is a global command (7.3.4.4).

7.3.5.6 IPRNT

#### If the card

#### IPRNT

is included in the input file a summary of each particle tracked is produced. This has the following form.

| IPHI | index | number of discrete azimuthal | angle at |
|------|-------|------------------------------|----------|
|      | which | the particle was emitted.    |          |

- ITH index number of discrete polar angle at which the particle was emitted.
- IEK index number of discrete energy at which the particle was emitted.
- VINIT initial code velocity with which particle was emitted (in inner grid units/timestep).
- VIN initial velocity with which particle was emitted (in meters/second).
- JCLAST index number of volume cell which particle was in at step just before hitting the satellite. If the trajectory was incomplete this will be 0. (Note the volume index is not necessarily the same as the surface cell index!)
- PXYZ potential (in volts) at the particle position at the last timestep completed prior to hitting the satellite or abandoning tracking.

- IR index number of grid in which the particle was in at the last timestep completed prior to hitting the satellite or abandoning tracking.
- ISTP number of discrete steps which this particle was tracked for before it hit the satellite or tracking was abandoned.

### 7.3.6 EXAMPLE OF AN EMITTER INPUT FILE

Figure 7.7 shows a sample emitter input file. Figure 7.8 shows the printed output from a completed run, and Figures 7.9 and 7.10 show two views of the <u>p</u>article trajectories.

7.4 TECHNICAL DISCUSSION

7.4.1 PARTICLE DETECTORS

## (a) Calculation of Energy Flux at a Cell Surface

In order to obtain an expression for the energy flux density measured by a detector located at a given surface cell of the satellite model it is helpful to first consider the general problem of calculating the total energy flux which is incident at the surface of the cell due to the ambient plasma environment. Let k be the unit normal vector for the surface cell. Using the cell's rectangular coordinate system (obtained by appropriate rotation of the satellite coordinate system) with the +Z axis in the direction of k, the energy flux at the cell surface center is calculated as follows:

$$\vec{E}_{0} = -k \int_{-\infty}^{\infty} \int_{-\infty}^{\infty} \int_{-\infty}^{\infty} \left( \frac{m |\vec{v}_{0}|^{2}}{2e} \right) \frac{1}{e} \left\{ (e\vec{v}_{0} \cdot \hat{k}) f_{0}(\vec{v}_{0}) \right\} d^{3} v_{0}$$

where  $\vec{E}_0$  = energy flux vector (eV/(M<sup>2</sup>-sec))at cell surface.



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Figure 7.7. Sample Emitter input file.

ELECTRON DENSITY = 1.00+006 HETER++1-3) Ion temperature = 5.00+003 electron volts

S.CO+DD3 ELECTRUN VOLTS

ELECTPON TEMPERATURE =

+++++TRILIN FLUX DEFINITION SINGLE ION DENSITY = 1.00+006 METER++(-3)

\*\*\* RESTART AT NEW CYCLE = 1

QSUMER FOUND QSUM= -1.30+DD5 CODE UNITS. AFTER SCREENING CORRECTION ISCREENING LENGTH= 2.DU+DD3 M.) QSUM= -1.3D+DD5 4\*\* QSUMO FHOM LAST CYCLE = -1.3G+DD5 \*\*\* QSUMO FHOM LAST CYCLE = -1.2969+DD5

Figure 7.8. TRILIN output with EMITTER option selected.

FOUND QSUM= -1.30+005 CODE UNITS. AFTER SCREENING CORRECTION ISCREENING LENGTH= 2.00+003 Mg) QSUM= -1.30+005 QSCALE = -1.204005 TSUM = -1.2040005 COND = -1.200+003 CCOND = 1.521+009 -5.929+003 011111120302 0 0 10 50LA 0 -1 3.98-007 AMPERES. -6.58-007 AMPERES. EXPLICITLY CALCULATED FLUXES FOR CYCLE 1 TIME = .000 SECONDS. During this timestep, nascap will take into account such additional effects as surface conductivity discharges, emitter operation, and variation of limiting factors for low-fnergy emitted electrons. NON-ZERO EMITTER SURFACE CELL CURRENT PRINT FLAG SET CODE = Location = Normal = Material = .000+003 VOLTS 0 VOLTS/METER = -2.609+003 VOLTS/METER R = 1.000+000 SECONDS. INITIAL NET CHARGING CURRENT (WITHOUT LIMITING) = Initial net charging current (with limiting) = 3,30-007 1.27-006 1.02-006 4.34-006 6.21-006 6.57-008 8.57-008 8.57-008 .000 00 1000-000 7 5.0000000+000 1.000000+003 2.000000-005 1.00+000000.1 **TIME =** POTENTIAL = -2.00 STRESS = 000 EXTERNAL FIELD = LIMITING FACTOR = -10 INCLUE FLECTRONS RESULTING SECONDARIES RESULTING SECONDARIES INCIDENT PROTONS BULK CONDUCTIVITY PHOTOCUPRENT JCYCEM SET TO ENERGY SET TO DTHETA SET 10 SIGMA SET TO BEAM1 SET TO NENGS SET TO ICELL SET TO REGIN CYCLE NO. 167 SURFACE CELL NO. FLUXES IN A/M## NET FLUX BEAMI 2.E-5 ENERGY 1000 ........ DIHETA 5 SIGMA 10 NENGS 10 JCYCFH 1 QSUMER ICELL 3 PRFLUX END

Figure 7.8. (Continued).

| PAHAMETER DEFINITION SUMMARY FOP LOW-DENSITY PARTICLE EMITTERS<br>Number of Particle emitters = 1<br>Pluts are produced every = 1 cycles<br>Trajectory plot type = 0verlay  |
|---|
| EMITTER NUMBER 1:<br>CELL LOCATION=<br>Reitter type = proton<br>Feam current =2.0G-005 amps   |
| BEAM CURPENT INTEGRAL<br>Energy=1.00+003 EV sigma=1.00+001 nem6s= 10<br>fmi= .00 deg dimeta= 5.00 deg ntmets= 1<br>tmeta= .00 deg dimeta= 5.00 deg ntmets= 1  |
| MAXIMUM INITIAL PARTICLE VELOCITY= .300 INNER GRID UNITS PER TIME-STEP<br>TIME STUP INCREASE TOLERANCE FACTOR= 5.000<br>Maximum number of particle Steps= 500<br>Cyclotron Period Limit= 1.000<br>Nighest Grid Tracking Allowed In = 66<br>Scale Factor for Velocity in Grids Above 2 = 1.000 |
| GUN TYPE= 1   |
| NEXTPA= D<br>EFPREP 2 GRIDS OUT OF 2 READ IN<br>****** EMITTER ROUTINE EXECUTION INITIATED BY EMTRUN *** ***  |
| PARTICLE EMITTER ENERGIES (EV):<br>9.8355+002 9.8964+002 9.9326+002 9.9326+002 9.9615+002 9.9875+002 1.0013+003<br>1.0038+003 1.0067+003 1.0104+003 1.0165+003 9.9326+002 9.9615+002 9.9615+002 1.0013+003  |
| PARTICLE EMITTER ENERGY WEIGHTS:<br>9.7U17-U03 4.2889-003 3.1462-003 2.6993-003 2.5264-003 2.5264-003 2.5264-003<br>2.6993-003 3.1462-003 4.2889-003 9.7017-003   |
| CUPRENT TO CELL 167 ORIGINATING FROM EMITTER 1 = .0000 AMPS. VOLUME CELL INDEX= 167 SHARED WITH O OTHER CELLS   |
| NON-ZERO SURFACE CELL CURRENT CONTRIGUTIONS FROM EMITTER NUMBER 1 SUM OF CELL CURRENTS= .000000 AMPS  |
| **** SUMMARY OF PARTICLE TRACKING FOR EMITTER 1 AT CYCLE 1 ****   |
| NUMBER OF TIMES PAPTICLE TRACKING TIME-STEP WAS INCREASED = 10<br>NUMBER OF TIMES PARTICLE TRACKING TIME-STEP WAS DECREASED = 0<br>NUMBER OF PARTICLES WHICH PASSED OUT OF SECOND MESH = 10<br>NUMBER OF TIMES CYCLOTRON I TATE USE FYCTFOFD = 10   |
| TOTAL NUMBER OF PARTICLES WHICH ESCAPED = 10 10 10 10 10 10 10 10 10 10 10 10 10  |
| MINIMUM POTENTIAL SEEN = -3.0000+003 VOLTS (DISTANCE FROM MESH CENTER = 7.3485-001 METERS)<br>Maximum fotential seen = -4.1257+602 volts (distance from mesh center = 5.0031+000 meters)<br>Average emitter ceil potential = -3.0000+003 volts  |
| ANALYTIC MAGNITUDE OF EMISSION CURRENT = 2.00000-605 AMPS<br>Numerical current Which escaped to Environment = 2.00000-005 AMPS<br>Numerical current Which Peturned to Satellite = 2.00000 AMPS<br>Total Number of Particles Tracked = 10  |

Figure 7.8. (Continued).

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EMITTER CONDUCTOR POTENTIAL = -1.0000+003 VOLTS

CALLED EMITER NECELS= 1 ICYC= 1 XMESH= 2.0000-001 NMAT= 4 NSURF= 180 410T= -1.2969+005 NX=17 NY=17 NZ=33 IER= CALLED FLEMIT IXYZ= 1 IG= 3 IGS= 4 GSCALE= 2.500000-001 IVIEW= 1 CALLED FLEMIT IXYZ= 1 IG= 3 IGS= 4 GSCALE= 2.500000-001 IVIEW= 1 CALLED FLEMIT IXYZ= 2 CALLED FLEMIT IXYZ= 2 CALLED FLEMIT IXYZ= 3 CA IN ADEMIT CURRENT TO CELL 167 CHANGED BY FLUX FROM EMITTER IFROM 7.4672+003 TO 7.4672+003 CODE UNITS

0

Figure 7.8. (Continued).

|                                 |                          |                          | 1         | EMITTERS I            | COUND BY        | ADENIT OI | I FIL | E 11       |             |          |
|---------------------------------|--------------------------|--------------------------|-----------|-----------------------|-----------------|-----------|-------|------------|-------------|----------|
| •02                             | CONDUCTOR                | EHT-INF (AH<br>2.0000-00 | PS)       | 3ARR JER (V(<br>.0000 | 123)            | SPECIES   |       | WIDTH (EV) | ENERGY (EV) | 1 S Î QN |
| TOTAL CAPA                      | LITANCE TO I             | NFINITY =                | 49.9 CODI | UNITS;                | 8.83-01         | I FARADS. | _     |            | ******      | -        |
| BADENT SET                      | CONDUCTOR                | 1 TO -2.010              | +003 VOL  | IS DUE TO (           | URRENT F        | ROM EMIT  | E R   | 1          |             |          |
| ICC6                            | RDOTR/RDOTR              | 1 = 9.61-02              | 1/ 1.60-  | 011                   |                 |           | •     |            |             |          |
| LEAVING IC(                     | 61 VCTRI                 | = +2.016+00              | 3 -2.088  | 003                   |                 |           |       |            |             |          |
| BADEMT SET                      | CONDUCTOR                | 1 TO -2.010              | +003 A0L1 | S DUE TO C            | URRENT F        | ROM EHITI | R     | _          |             |          |
| ICCG                            | ROOTR/RDOTR1             | 1 = 1.30-02              | 0/ 1.60+  | 110                   |                 |           |       |            |             |          |
| LEAVING TCC                     | 61 VCTRI                 | = -2.010+00              | 3 -2.0744 | 003                   |                 |           |       |            |             |          |
| 1006                            | RDOTR/RDOTR]             | 1 = 1.97-021             | 0/ 1.57+  | 110                   |                 |           |       |            |             |          |
| LEAVING ICC                     | 61 VCTRI                 | = -2+000+00              | 3 -2.058+ | 003                   |                 |           |       |            |             |          |
| UNEMIT: IRE<br>CONDUCTOR 1      | TE 1 DQC                 | := -5*91+005             | 00 CD=    | -1.05+006             | DFD             | VC= -5.65 | + 003 |            |             |          |
| ICC6                            | RDOTR/RDOTR1             | = 1.80-01                | 11 5.46+  | 007                   |                 |           |       |            |             |          |
| LEAVING ICC                     | 61 VCTRI                 | = -1.070+00              | 3 -2.057+ | 003                   |                 |           |       |            |             |          |
| H16H0 N                         | UNH= 2                   |                          |           |                       |                 |           |       |            |             |          |
| ICC6                            | RDOTR/RDOTR]             | = 2.56-017               | 1/ 6.02+  | 007                   |                 |           |       |            |             |          |
| LEAVING ICC                     | 61 VCTRI                 | = -1.070+003             |           | 003                   |                 |           |       |            |             |          |
| LOW4 RU                         | NL= 3                    |                          |           |                       |                 |           |       |            |             |          |
| ICCG                            | RDOTR/RDOTR1             | = 3.23-019               | / 3.56+   | 007                   |                 |           |       |            |             |          |
| LEAVING ICC                     | 61 VCTRI                 | = -1.070+003             | 1 -2.037+ | 003                   |                 |           |       |            |             |          |
| LOW4 NU                         | NL= 2                    |                          |           |                       |                 |           |       |            |             |          |
| I C C C                         | RDOTR/RDOTR1             | = 3.65-016               | 1 6.20+   | 007                   |                 |           |       |            |             |          |
| LEAVING ICC                     | 51 VCTRI                 | = -1+070+003             | -1-413+   | 003                   |                 |           |       |            |             |          |
| VFIX                            | 0 0UT OF                 | 164 NODES FIX            | EU.       |                       |                 |           |       |            |             |          |
| 1000 1                          | RDOTR/RDOTR]             | = 3.65-016               | / 6.20+1  | 107                   |                 |           |       |            |             |          |
| LLAVING ICC                     | 31 VCTRI                 | = -1.070+003             | -1.413+0  | E D(                  |                 |           |       |            |             |          |
| NO LISCHARG                     | ANAL YSIS                |                          |           |                       |                 |           |       |            |             |          |
| NO DISCHARGE                    | ANALYSIS                 |                          |           |                       |                 |           |       |            |             |          |
| 1006 1                          | POTR/RDOTRI              | = 7.04-023               | / 3.66+1  | 107                   |                 |           |       |            |             |          |
| LEAVING ICCC                    | 12 VCTRI                 | = -1.070+003             | -1.413+(  | 10.3                  |                 |           |       |            |             |          |
| AVLRAGE FLUXE                   | S TONLY AVA              | ILABLE FOR IN            | SULATING  | CELLS)                |                 |           |       |            |             |          |
| AVERAGE FLUX 1<br>New Conductor | 0 CELL 167<br>Putentials | IS 2.651-                | NU7 A/H+4 | ä                     |                 |           |       |            |             |          |
| -1.0696+00<br>-1.4126+00        | 19.1690<br>3 -1.4554     | 1+000 -2.00              | 100+000   | CONDU                 | ICTOR<br>1<br>2 |           |       |            |             |          |
|                                 |                          |                          | F         | jure 7.8.             | (Cont           | inued).   |       |            |             |          |

.

TOTAL CHANGE IN CHARGE = 3.537+DD3 CODE UNITS 6.264-DD9 Coulonds Average net charging current = <u>1</u>.253-DD9 Amperes

AVERAGE NET CHARGING CURRENT = 1.253-009 AMPERES 7.075+002 CODE UNITS/SEC. Conductor currents (AMPS; Positive into conductors);

|  | -1        | 2         |
|--|-----------|-----------|
| NET CUPRENTIAVG DQ/DT):                                | 3.25-007  | -5.15-013 |
| CONDUCTIVITY CURRENT (NEW)<br>(FROM INSULATING CELLS): | -8.95-009 | 9.60-015  |
| PLASMA CURRENT (INITIAL)                               |           |           |
| NUN DANG CELEDIS                                       | -3.63-007 | 00.       |
| REMAINDER CURRENT;                                     | 6.97-007  | -5.25-013 |

Figure 7.8. (Continued).

(Concluded) Figure 7.8

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PARTICLE TRAJECTORIES AT CYCLE I FROM I EMITTER(S) PROJECTED ONTO THE X-Y PLANE

SIX<del>U</del>-X

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Figure 7.10. Sample particle emitter trajectory plot.



 $\vec{v}_{o} = v_{x}\hat{i} + v_{y}\hat{j} + v_{z}\hat{k}$  (velocity at surface)  $d^{3}V_{o} = dv_{x} dv_{y} dv_{z}$   $f_{o}(\vec{v}_{o}) = phase space density function evaluated at the surface for particles with velocity <math>\vec{v}_{o}$ . m = mass of incident particles.

e = charge of incident particles (electrons or protons).

To evaluate the integral it is expedient to change from rectangular to spherical coordinates. The necessary substitutions are:

$$v_o = |\vec{v}_o|$$
  
 $d^3 v_o = v_o^2$  sine de dø d $v_o$   
 $(e\vec{v}_o \cdot \hat{k}) = ev_o$  cose

With these the energy flux integral transforms into

$$\vec{E}_{0} = -\hat{k} \int_{0}^{\infty} \int_{0}^{2\pi} \int_{0}^{\pi/2} \left(\frac{mv_{0}^{2}}{2e^{2}}\right) \left\{ ev_{0} \cos \theta_{0}(\theta, \phi, v_{0}) \right\} v_{0}^{2} \text{ sine de } d\phi \, dv_{0}$$

$$= -\hat{k} \int_{0}^{\infty} \int_{0}^{2\pi} \int_{0}^{\pi/2} \left(\frac{m}{2e}\right) v_{0}^{5} f_{0}(\mu, \phi, v_{0}) \frac{d\mu^{2}}{2} d\phi \, dv_{0}$$

where  $\mu = \cos \theta$ .

~

Next we change variables from  $v_0$  (the magnitude of the velocity at the surface) to  $E_0$  (the kinetic energy at the surface of the cell).

$$\frac{1}{2} \text{ m v}_0^2 = \text{e E}_0$$
 (factor e because E<sub>0</sub> is in eV)

$$dv_0 = \frac{edE_0}{my}$$

Then the energy flux integral becomes

$$\vec{E}_{0} = -\hat{k} \int_{0}^{\infty} \int_{0}^{2\pi} \int_{0}^{1} 2\left(\frac{e}{m}\right)^{2} E_{0}^{2} f_{0}(\mu, \phi, E_{0}) \frac{d\mu^{2}}{2} d\phi dE_{0}$$
$$= -\hat{k} \int_{0}^{\infty} \int_{0}^{2\pi} 2\left(\frac{e}{m}\right)^{2} E_{0}^{2} f_{0} (E_{0}, \vec{\Omega}_{0}) \mu d\Omega dE_{0}$$

where we have introduced the solid angle as an integration variable for notational convenience.

Finally we introduce the energy flux density function  $G(E,\Omega)$ . From the definition we know that

$$\vec{E}_{o} = -\hat{k} \int_{0}^{\infty} \int_{0}^{2\pi} G_{o}(E_{o}, \vec{\Omega}_{o}) \mu d\Omega dE_{o}$$

Comparison of the integrands yields the identity

$$2\left(\frac{e}{m}\right)^{2} f_{0}(E_{0}, \vec{\Omega}_{0}) = \frac{G_{0}(E_{0}, \vec{\Omega}_{0})}{E_{0}^{2}}$$

Let

This equation provides the key to correct evaluation of G at the cell surface by reverse trajectory particle tracking. Since f is a constant along a particle trajectory we have for particles emitted at the cell surface with initial energy  $E_0$  and velocity vector in the direction of  $\vec{\Omega}_0$ :

$$f_{0}(E_{0}, \vec{\Omega}_{0}) = f_{\infty} (E_{\infty}, \vec{\Omega}_{\infty})$$

$$\frac{G_{0}(E_{0}, \vec{\Omega}_{0})}{E_{0}^{2}} - \frac{G_{\infty} (E_{\infty}, \Omega_{\infty})}{E_{\infty}^{2}}$$

where

 $f_0$  = phase space density function evaluated at cell surface.  $f_{\infty}$  = phase space density function evaluated at infinity.

 $G_0$  = energy flux density function evaluated at cell surface.

 $G_{\infty}$  = energy flux density function evaluated at infinity.

 $E_0$  = initial kinetic energy of particle to be tracked.

 $E_{\infty}$  = kinetic energy of particle after reverse trajectory tracking to infinity.

 $\vec{\Omega}_0$  = initial velocity direction vector of particle at cell surface.

 $\vec{\Omega}_{\infty}$  = velocity direction vector for particle after reverse trajectory tracking to infinity.

Therefore, if the energy flux density function G is known at infinity then using reverse trajectory particle tracking the energy flux at the surface of the cell may be computed from

$$\vec{E}_{0} = -\hat{k} \int_{0}^{\infty} \int_{0}^{2\pi} E_{0}^{2} \left\{ \frac{G_{\infty}(E_{\infty}, \vec{\Omega}_{\infty})}{E^{2}} \right\} \mu d\Omega dE_{0}$$

This equation is used (with slight modification) in the following section to arrive at an expression for the energy flux density which is measured by a particle detector located on the surface cell.

## (b) Detector Energy Flux Density Measurement

Consider an ideal particle detector located at the center of a surface cell and oriented such that the +Z axis of the <u>detector's</u> rectangular coordinate system points in the direction in which the energy flux density is to be measured. Assume that the detector's rectangular coordinate system is transformed into a spherical coordinate system and that n is the unit normal pointing in the direction in which the particle detector is pointing. If the detector responds to particles having energy  $E_0$  then the measured value for the energy flux will be

$$\frac{\partial^{2} \overline{E_{0}}}{E_{0}} = -\vec{n} E_{0}^{2} \left\{ 2 \left( \frac{e}{m} \right)^{2} f_{0}(E_{0}, \vec{n}) \right\} \mu$$
$$= -\vec{n} E_{0}^{2} \left\{ \frac{G_{\infty} (E_{\infty}, \vec{\Omega}_{\infty})}{E_{\infty}^{2}} \right\} \mu$$

where

 $\dot{\vec{E}}_0$  = energy flux vector at cell surface.

 $f_0$  = phase space density function evaluated at cell surface.  $E_0$  = kinetic energy (in eV) of particles at cell surface.

- $\phi$  = azimuthal angle in detector coordinate system.
- e = polar angle in detector coordinate system.
- $E_{\infty}$  = kinetic energy (in eV) of particles after reverse trajectory tracking to infinity.
- $\vec{\Omega}_{\infty}$  = velocity direction vector for particles after reverse trajectory tracking to infinity.
- m = mass of particles.

$$G_{\infty}(E,\overline{\alpha})$$
 = energy flux density function (i.e., tabulated  
Deforest data, for example. Units are  
 $eV/(sec-cm^2-sr-eV)$ .)

In practice, a real detector responds to a finite range of particle energies and velocity vectors so that the energy flux density observed by the detector is really  $\partial^2 \dot{E}_0 / \partial E_0 \partial \Omega$  averaged over the energy and angular apertures of the detector. Thus, in general, the value which the detector yields is of the form

$$\frac{1}{\frac{\partial^{2}\vec{E}}{\partial E_{0}\partial\Omega}} = \frac{-\vec{n}\int_{0}^{\infty}\int_{0}^{2\pi} W(E_{0},\vec{\alpha}) E_{0}^{2}\left\{\frac{G_{\omega}(E_{\omega},\vec{\alpha}_{\omega})}{E^{2}}\right\} \cos\theta \,d\Omega \,dE_{0}}{\int_{0}^{\infty}\int_{0}^{2\pi}\int_{0}^{2\pi} W(E_{0},\vec{\alpha}) \,d\Omega \,dE_{0}}$$

where  $W(E_0, \vec{\alpha})$  is a weight function which describes the characteristics of the detector's energy and angular apertures.

In the current version of NASCAP it has been assumed that the energy aperture of a detector is a rectangular weight function which has a value of 1 from E to E +  $\Delta$ E and O elsewhere. The angular aperture is assumed to be a hemispherical cap of "width"  $\Delta \Theta$  in the polar angle. (The vector n passes through the center of this cap.) The weight has a value of 1 anywhere on the cap and O elsewhere. Therefore, NASCAP detectors compute the energy flux density from

$$\frac{1}{\frac{\partial^2 \dot{E}_0}{\partial E_0 \partial \Omega}} = \frac{-\dot{n} \int_{E}^{E+\Delta E} \int_{0}^{2\phi} \int_{\cos^2 \Delta \Theta}^{1} E_0^2 \left\{ \frac{G_{\infty}(E_{\infty}, \dot{\Omega}_{\infty})}{E^2} \right\} \frac{d\mu^2}{2} d\phi dE_0}{\int_{E+\Delta E} \frac{2\pi}{2\pi} \Delta \Theta} \int_{E} \sin \Theta d\Theta d\Phi_0$$

$$= \frac{-\vec{n} \int_{E}^{E+\Delta E} \int_{Cos^{2}\Delta \Theta}^{2\pi} \int_{Cos^{2}\Delta \Theta}^{1} E_{0}^{2} \left\{ \frac{G_{\infty}(E_{\infty}, \vec{\Omega}_{\infty})}{E_{\infty}^{2}} \right\} \frac{d\mu^{2}}{2} d\phi dE_{0}}{(1 - \cos \Delta \Theta) 2\pi \Delta E}$$

where  $\mu = \cos \theta$ .

This integral is evaluated by a three-dimensional approximation formula which uses the mid-point rule with  $n_{\not 0}$  points to compute the integral over  $\not 0$ , the mid-point rule with n points to compute the integral over  $\mu^2$ , and the even-order Gauss-Legendre formula with  $n_{e}$ points to compute the integral over  $E_0$ . The composite formula used is:

$$\frac{\partial^{2} \overline{\underline{z}}}{\partial E_{0} \partial \Omega} \approx -\vec{n} \left\{ \left( \frac{2\pi}{n_{\phi}} \right) \sum_{j=1}^{n_{\phi}} \frac{(1 - \cos^{2} \Delta \Theta)}{2\pi} \sum_{j=1}^{n_{\psi}} \left( \frac{\Delta E}{2} \right) \sum_{k=1}^{n_{\phi}/2} W_{k} \varepsilon_{k}^{2} \left\{ (\phi_{j}, \mu_{j}^{2}, \varepsilon_{k}) \right\} \right\}$$

$$+ W_{-k} \varepsilon_{-k}^{2} F(\emptyset_{j}, \mu_{j}^{2}, \varepsilon_{-k}) \bigg\} \frac{1}{(1 - \cos \Delta \Theta) 2\pi \Delta E}$$

$$= -\tilde{n}_{Y} \sum_{i=1}^{n_{\emptyset}} \sum_{j=1}^{n_{\psi}} \sum_{k=1}^{n_{\varepsilon}/2} \bigg\{ W_{k} \varepsilon_{k}^{2} F(\emptyset_{j}, \mu_{j}^{2}, \varepsilon_{k}) + W_{-k} \varepsilon_{-k}^{2} F(\emptyset_{j}, \mu_{j}^{2}, \varepsilon_{-k}) \bigg\}$$

where

$$\begin{aligned} & \varepsilon_{k} = \frac{\Delta E}{2} (\dot{\chi}_{k} + 1) + E \\ & \phi_{i} = \frac{2\pi}{n_{\phi}} (i - 1/2) \\ & \mu_{j}^{2} = \Delta \mu^{2} (j - 1/2) + (1 - n_{\psi} \Delta \mu^{2}) \quad \{\psi \text{ denotes } \mu^{2}\} \end{aligned}$$

and

$$\Delta \mu^{2} = (1 - \cos^{2} \delta \theta) / n_{\psi}$$
  

$$\gamma = \frac{(1 + \cos \Delta \theta)}{4 n_{\psi} n_{\phi}} \quad (\text{multiply by 10}^{-4} \text{ to put units in cm}^{-2})$$
  

$$F(\phi_{i}, \mu_{j}^{2}, \epsilon_{k}) = \frac{G_{\infty} (E_{\infty}, \vec{\Omega}_{\infty})}{E_{\infty}^{2}} | (\text{returned by FSPACE})$$
  

$$ijk$$

 $E_{\infty}$  and  $\overline{\Omega}_{\infty}$  are the final energy and velocity vector respectively of a particle after reverse trajectory tracking from the center of the surface cell (beginning with initial velocity specified by  $p_i$ ,  $\mu_j^2$ , and  $\epsilon_k$ ) to infinity.

The  $\chi_k$  and  $W_k$  are the Gauss-Legendre integration coefficients for  $n_e$  an even integer. (Note the  $\chi_k = -\chi_{-k}$  and  $W_k = W_{-k}$ .) A slightly modified formula is used to permit  $n_e = 1$ . (Also note that  $-1 \leq \chi_k \leq 1$  for all k.)

It should be noted that although the detector energy flux integral includes only contributions from the ambient plasma environment it is possible that some particle trajectories will yield E < 0. This could occur if the particle originates from another part of the satellite, for example.

For detector particle trajectory plotting purposes all particles must be tracked regardless of origin. Therefore, a test is made within the innermost integral summation loop to determine if  $E_{\infty} \ge 0$ . If it is not then no attempt is made to evaluate G and G is assumed to be 0.

## 7.4.2 PARTICLE EMITTERS

## 7.4.2.1 DISCRETE PARTICLE EMISSION ANGLES AND ENERGIES

The present version of NASCAP offers the user two choices for emission angle selection. One choice is the uniform distribution, a special case of which results in each particle representing the same solid angle fraction of the current. The other choice is a cosine e distribution in which a disproportionate number of particles are emitted at angles "close" to the axis of the hemispherical cap (Z-axis of the <u>emitter coordinate system</u>). Two choices for the energy spectrum of the beam are also provided. Either choice results in an approximate representation of a mono-energetic peak in the energy spectrum - the difference between the two choices being the mathematical form of the approximation function. The emission angles and energy distribution functions available are listed below. (Any angular dependence may be combined with any energy dependence.)

# (a) Uniform Angular Current Density Dependence

For each of  $n_{\varepsilon}$  discrete energies,  $n_{\varepsilon}$  n particles are emitted. The initial emission velocity direction vector of each particle (measured in the <u>emitter coordinate</u> system ) is

$$\hat{\vec{v}}_{ij} = (sine_j cosp_i)\hat{i} + (sine_j sinp_i)\hat{j} + (cose_j)\hat{k}$$

where
$$\phi_{i} = \frac{2\pi}{n_{\phi}} (i - 1/2)$$
  $i = 1, 2, ..., n_{\phi}$   
 $\Theta_{j} = \frac{\Delta \Theta}{n_{\Theta}} (j - 1/2)$   $j = 1, 2, ..., n_{\Theta}$ 

For the special choice of  $n_{\phi} = n_{\Theta}$  each particle represents the same solid angle fraction of the emitted current.

## (b) Cosine e Angular Current Density Dependence

For each of  $n_{\epsilon}$  discrete energies,  $n_{\phi}$  n particles are emitted. The initial velocity direction vector of each particle (measured in the <u>emitter coordinate system</u>) is

$$\vec{v}_{ij} = (sine_j cos\phi_i \hat{i} + (sine_j sin\phi_i)\hat{j} + (cose_j)\hat{k}$$

where

$$\phi_i = \frac{2\pi}{n_{\phi}} (i - 1/2)$$
  $i = 1, 2, ..., n_{\phi}$ 

$$\Theta_{j} = \sin^{-1}\left(\frac{(j-1/2) \sin \Delta \Theta}{n_{\Theta}}\right) \quad k = 1, 2, \dots, n_{\Theta}$$

# (c) Gaussian Energy Current Density Dependence

A Gaussian function may be used as an approximation to a mono-energetic spectrum. The current density function for the Gaussian approximation is

$$J(\varepsilon) = \frac{I_{B}}{\sqrt{2\pi} \sigma} \exp\left(-\frac{1}{2}\left(\frac{\varepsilon-\varepsilon_{0}}{\sigma}\right)^{2}\right)$$

where  $I_{B}$  is the total beam emission current.

$$\int_{-\infty}^{\infty} J(\varepsilon) d\varepsilon = I_B .$$

Since a real current distribution is not defined for negative energies the Gaussian function is only an approximate representation. However, one can show that

$$\lim_{\sigma \to 0} J(\varepsilon) = I_B \delta(\varepsilon - \varepsilon_0) ,$$
  
$$\int_0^{\infty} J(\varepsilon) d\varepsilon \neq I_B \quad \text{for} \quad \varepsilon_0 > 0 \text{ and } \frac{\sigma}{\varepsilon_0} << 1.$$

Thus the mono-energetic energy peak can be represented to any degree of accuracy desired simply by choosing  $\sigma/\epsilon_0$  small enough. It is worth noting that  $\sim 68$  percent of the current falls in the range  $\varepsilon = \varepsilon_0 \pm \sigma$  and  $\sqrt{92}$  percent of the current falls in the range  $\varepsilon = \varepsilon_0 + 2\sigma$ .

NASCAP chooses the discrete energy representation of the Gaussian energy distribution as follows:

$$\varepsilon_{i} = F^{-1} \left( 1 + \frac{(1/2 - i)}{n_{\varepsilon}} \right) \qquad i = 1, 2, \dots, n_{\gamma}$$

where

and

$$F(X) = \int_{X}^{\infty} \frac{1}{\sqrt{2\pi} \sigma} \exp\left\{-\frac{1}{2}\left(\frac{\varepsilon - \varepsilon_{0}}{\sigma}\right)^{2}\right\} d\varepsilon \qquad (7.1)$$

This choice results in the following equality being satisfied: F . .

$$\int_{\varepsilon_{1}}^{\varepsilon_{1}+1} J(\varepsilon) d\varepsilon = \frac{I_{B}}{n_{\varepsilon}}$$
(7.2)

where we define  $\varepsilon_0 = 0$  and  $\varepsilon_{n_r+1} = \infty$ .

ŝ

Thus each discrete energy  $\epsilon_i$  represents the same fraction  $(1/n_{\epsilon})$  of the total emitted current. Furthermore, half of this fraction is a result of energy in the range  $\epsilon_{i-1} < \epsilon \leq \epsilon_i$  and half is a result of energy in the range  $\epsilon_i \leq \epsilon < \epsilon_{i+1}$ .

# (d) Lorentzian Energy Current Density Dependence

A Lorentzian function may be used as an approximation to the mono-energetic spectrum. The current density function used by NASCAP. for the Lorentzian approximation is

$$J(\varepsilon) = \frac{\mu I_{B}}{(\pi/2 + \tan^{-1}\mu)} \left\{ \frac{\alpha^{2} \varepsilon_{0}\varepsilon}{(\varepsilon^{2} - \varepsilon_{0}^{2})^{2} + (\varepsilon_{0}\varepsilon\alpha)^{2}} \right\}$$

where  $I_R$  = total emitter beam current.

$$\mu = \sqrt{2 - \alpha^2 / \alpha} \quad \text{and} \quad \alpha = \sigma / \varepsilon_0$$

This density function has the property that

$$\lim_{\sigma \to 0} J(\varepsilon) = I_{B} \quad \delta(\varepsilon - \varepsilon_{O})$$

and

$$\int_{0}^{\infty} J(\epsilon) d\epsilon = I_{B} \text{ for all } \sigma/\epsilon_{0} < \sqrt{2}.$$

NASCAP chooses the discrete energy representation of the Lorentzian energy distribution according to Eq. (7.1) with the integrand for F(X) replaced by the Lorentzian density function divided by  $I_B$ . This choice of energies also results in the satisfaction of the equality given by Eq. (7.2).

### 8. OTHER MODULES

There are seven other NASCAP modules still left to discuss. In this chapter we tie up these loose ends. Three of the remaining modules, HIDCEL, SPIN and ROTATE all concern the illumination of the object with sunlight. NEWMAT allows you to change material properties without redefining your whole object. SATPLT lets you examine how your object looks from a number of points of view. IPS allows you to set the initial potentials of insulators and conductors to some value other than zero. CAPACI calculates the capacitances of the object. Finally STRESS searches out cells that have the greatest internal electric fields and so are most likely to "punchthrough".

Let us begin by looking at the shadowing modules.

8.1 HIDCEL

The fraction of the full sun intensity that effectively illuminates each surface cell of an object depends on its orientation, i.e., on the angle  $\Theta$  between the surface normal and the negative of the imagined velocity vector of the photons (i.e., the sun direction vector):

 $I = I_0 \cos \theta$ 

For surfaces pointing away from the sun I is zero, and they are completely in shadow.

Surfaces that point towards the sun may also be completely or partially in shadow, due to other parts of the object lying between them and the sun. This "geometrical" shadowing also contributes to the overall illumination of each cell. The module HIDCEL calculates the fraction of each surface cell that is actually illuminated by the sun as a result of geometrical shadowing. The values it calculates form the <u>'shadowing table</u>'. This is written out to file 21 (2.8) under the keywords 'AREAS' (for non-boom cells) and 'BSHAD' (for boom cells). [Table 2.6.] TRILIN then calculates the effective sun intensity (and hence photocurrent) for each cell by multiplying the shadowing table entry by the appropriate cos e factor (and SUNINT (6.4.11)).

# HIDCEL is executed by including the primary keyword HIDCEL

in the NASCAP runstream. HIDCEL is usually executed immediately before TRILIN. (Precedence of keywords is summarized in Table 2.2.) It requires no user input itself, but must be used in conjunction with the run options (Chapter 6) 'SUNINT' and 'SUNDIR'. Including the card

SUNINT s

in the options file changes the sun intensity from the default value of zero (no sun at all) to s. (This is explained in Section 6.4.11.) Once SUNINT is set to a non-zero value, photoemission will be included in TRILIN's current calculations, and TRILIN will look for a shadowing table in file 21. If no shadowing table has been created by a previous execution of HIDCEL an error will occur. This can be avoided either by making sure HIDCEL has been executed, or by including the card

#### CONVEX

(see 6.4.2) in the options file. CONVEX tells TRILIN that a shadowing table is not needed because all entries in it would be one. In other words, the object has no surfaces shielded from the sun by the rest of the object (a sphere, for example). Obviously most complex objects are not convex and for these HIDCEL should be executed. The shadowing table calculated depends on the orientation of the object with respect to the sun. This is determined by the user with the run option SUNDIR. The card

## SUNDIR x' y' z'

included in the options file changes the orientation vector defining

the direction from the spacecraft toward the sun from its default value of X = 1, Y = 1, Z = 1 to X = x', Y = y', Z = z'. (See Section 6.4.10.) Each new choice of direction <u>must</u> be accompanied by a new shadowing table. In other words if SUNDIR is changed <u>a new call to</u> <u>HIDCEL must be made</u>. Failure to do this will cause TRILIN to use the old shadowing table and calculate erroneous results with no obvious error messages. Any calls to HIDCEL for the purposes of calculating photoemission must <u>follow</u> calls to TANK but <u>precede</u> calls to TRILIN. This is discussed in Section 5.9.1.

For multiple runs using the same object and the same sun position, the same shadowing table can be used and so HIDCEL need only be executed once (in the first run). Similarly RESTARTed runs remember the shadowing table from the previous run. HIDCEL plots a 3D-VIEW (6.6.1) of the object from the sun position each time it is called, either explicitly by the user, or by other modules (TANK, SPIN, ROTATE).

A summary of HIDCEL operations is given in Figure 8.1.

## 8.2 ROTATE

The module ROTATE is a utility designed to simulate the rotation of a spacecraft in sunlight. It is used with multiple calls to TRILIN. ROTATE is executed between calls to TRILIN by including the card

### ROTATE <n>

in the NASCAP runstream. ROTATE expects to find two cards in the user input file n. There is no default value for n and n = 5 is most commonly used. The two cards following ROTATE in the NASCAP runstream are then read as ROTATE input. A segment of a NASCAP runstream using ROTATE has the general form:

HIDCEL calculates geometrical shadowing factors 1. for each surface cell (shadowing table). 2. Shadowing table stored as 'AREAS' and 'BSHAD' in File 21. Precedence: HIDCEL must be preceeded by OBJDEF and 3. logically preceeds TRILIN. 4. If SUNINT / O, then either HIDCEL must be called or CONVEX be specified as a run option. Each new choice for SUNDIR must be followed (for non-CONVEX objects) by a new call to HIDCEL. 5. 6. HIDCEL plots the view of the object from the "sun" position. 7. HIDCEL uses no input file.

Figure 8.1. HIDCEL summary.

TRILIN ROTATE 5 <sup>ω</sup>y ωx У Х Ζ TRILIN **ROTATE 5** <sup>ω</sup>z <sup>ω</sup>x<sup>ω</sup>y Ζ X У TRILIN The first card that ROTATE expects to find contains the angular velocity vector (in rad s<sup>-1</sup>)  $\omega_x \omega_y \omega_z$ . The second contains the initial sun direction for cycle 1! Obviously this remains the same for all further TRILIN cycles. For example, the sequence: TRILIN ROTATE 5 0.2 0.0 0.0 0.0 1.0 0.0 TRILIN ROTATE 5 0.2 0.0 0.0 0.0 1.0 0.0 simulates an object rotating about the X axis at 0.2 radians per second (1.9 rpm), beginning with the sun direction lying along the Y axis (in the positive sense). An initial call to TRILIN (before any call to ROTATE) is required to establish the elapsed time (usually equal to DELTA (6.2.2) - but see (6.2.6)). The subsequent call to ROTATE changes the sun direction vector and the magnetic field vector to simulate the rotation of the object by the elapsed time times the

magnitude of its angular velocity. In our example above, if the first call to TRILIN increased the elapsed time to 5 seconds, then the sun direction vector will be rotated from 0 1 0, about the X axis by 5 x 0.2 = 1.0 radian. The next call to TRILIN will then take place with the rotated sun direction vector (0 -0.54 -0.84) and so on.

Of course, changing the sun direction vector must always be accompanied by a new call to HIDCEL. ROTATE automatically calls HIDCEL to establish a new shadowing table (8.1) unless the option

#### CONVEX

has been included in the run options file. Further calls to TRILIN without any more calls to HIDCEL, SPIN or ROTATE will use the last shadowing table created by ROTATE.

If the number of cycles chosen for each call to TRILIN (NCYC 6.2.7) is greater than one, the same shadowing table will be used for each cycle, until ROTATE is called again. This will lead to significant errors unless the timestep is much shorter than the rotation period. When simulating rotation NCYC should <u>usually</u> be one.

ROTATE should always be called <u>after</u> any call to TANK (See Section 8.1).

ROTATE can be used to simulate rotation in an anisotropic plasma environment (whether there is sunlight present or not), since the direction of the aligned flux component (the magnetic field direction) is also rotated.

The calls ROTATE makes to HIDCEL generate the appropriate plots (see 8.1).

Finally, omission of any file number in the call to ROTATE causes  $\omega_x \omega_y \omega_z$  and x y z to be set at the default values, i.e.,

angular velocity =  $\omega_x \omega_y \omega_z = 0 \quad 0 \quad 2\pi/60$ (1 rpm about the Z axis)

> x y z 1 0 0(Initial sum direction along the X axis)

For example

| TRILIN |   | TR     | ILI | N     |
|--------|---|--------|-----|-------|
| ROTATE | Ξ | RC     | TAT | E 5   |
| TRILIN |   | 0      | 0   | 2π/60 |
|        |   | 1      | 0   | 0     |
|        |   | TRILIN |     |       |

A summary of ROTATE is given in Figure 8.2.

8.3 SPIN

The module SPIN creates a shadowing table (8.1) based on the <u>average</u> illumination of each surface cell over one rotation period. The card:

SPIN <n>

included in the NASCAP runstream will execute module SPIN. SPIN should preceed a call to TRILIN intended to simulate charging of an object averaged over a rotation. (Exact precedence is summarized in Table 2.2.)

Like ROTATE (8.2) SPIN expects to find two input cards in file n. n has no default and n = 5 is most commonly used. In this case, SPIN looks for the next two cards in the NASCAP runstream as input. A segment of the runstream calling SPIN has the general form:

| 1. | ROTATE simulates rotation of an object in sunlight and/or an anistropic flux.                            |
|----|--|
| 2. | Unless CONVEX is specified in the options file<br>ROTATE calls HIDCEL and creates a new shadowing table. |
| 3. | Precedence: ROTATE must be preceeded by TRILIN and logically preceeds a second call to TRILIN.           |
| 4. | ROTATE reads two cards from file n, e.g. for $n = 5$ ROTATE 5  |
|    | ω <sub>χ</sub> ω <sub>y</sub> ω <sub>z</sub> angular velocity vector (rad/5)                             |
|    | x y z initial sun direction at the beginning of cycle 1.   |
| 5. | NCYC should usually be 1.  |
| 6. | Calls to ROTATE should follow calls to TANK.   |

Figure 8.2. ROTATE summary.

SPIN 5 num хуz TRILIN The first card read by SPIN: 'num' defines the number of views of the object to be included in the rotational average. The second card: хуz defines the orientation of the spin axis. For example SPIN 5 4 0 1 0 calls for 4 views to be included in the average for rotation about the Y axis. The initial direction of the sun with respect to the satellite, or the first view, is defined by the 'SUNDIR' option, included in the options file (Section 6.4.10). For example, including the card SUNDIR 1 0 1

in the option file (IKEYWD) defines the initial view to be in the XZ plane at an angle of 45° from the positive X axis (i.e., between the positive X and Z axes). The remaining three views in our example are generated by rotating the sun direction vector by  $2\pi/num$  (=  $2\pi/4$  =  $\pi/2$ ) and making a fresh call to HIDCEL for each time. The final average will therefore be over the shadowing factors for the four orientations 45°, 135°, 225°, 315° in the XZ plane. If num had been chosen to be 3 then the three views would have been from angles 45°, 165°, 285°, and so on. The shadowing table generated by SPIN differs from that generated by HIDCEL and ROTATE since the contribution made by the angle e between the surface normal and the sun direction is

included. Recall from 8.1, this contribution is added later by TRILIN for HIDCEL and ROTATE, and the shadowing table contains only

# geometrical shadowing factors. Hence, if the object is defined as CONVEX

in the options file (6.4.2) a shadowing table is <u>still</u> compiled by SPIN, containing the average of  $\cos \theta$  over the "num" views for each call.

The maximum number of views possible is 25. The greater the number specified, the more accurate the average. For typical objects, eight views is usually sufficient.

If no file number is included in the call to SPIN, the default values of the input parameters are used. For example, the cards

> SPIN TRILIN

in the NASCAP runstream will lead to a potential calculation, using a shadowing table that is an average of eight views (the default value of "num") about the Z axis (the default rotation axis).

SPIN and ROTATE (8.2) differ in the way they model charging of an object rotating in sunlight. Often the part of the object in shadow charges negatively, while the sunlit part remains close to neutral, or is charged less, because of photoemission. Thus the potential of a particular surface cell will tend to oscillate up and down with the rotation frequency, as it moves in and out of the sun. This oscillatory potential can <u>only</u> be modeled with ROTATE, i.e., ROTATE is able to resolve charging behavior on a timescale less than a rotation period. SPIN, on the other hand, models the average behavior, i.e., behavior on a timescale longer than a rotation period. Its results are valid therefore only if charging occurs on a timescale larger than a rotation. For spacecraft spinning slower than they charge, ROTATE should be used.

Like ROTATE and HIDCEL, calls to SPIN should follow calls to TANK (see Section 5.9.1). Following a call to SPIN, the CONVEX keyword should be omitted from the runstream input.

A summary of SPIN use is given in Figure 8.3.

#### 8.4 IPS

Module IPS (Initial Potential Specification) allows you to set the initial potentials of both conductors and insulators (dielectrics) to any value. Without the use of IPS all initial potential are assumed to be zero. IPS should always be used when FIXP and/or BIAS determine non-zero initial potentials. IPS should precede a call to TRILIN and/or DETECT. Calls to TRILIN following IPS in the same run are automatically RESTARTed (6.2.9) at cycle 1. If TRILIN is to be executed in a subsequent and separate run, a RESTART card must be explicitly placed in the options file by the user. (Exact precedence is summarized in Table 2.2). The card

#### IPS <n>

in the NASCAP runstream executes module IPS. The file number n is optional and defines the file in which IPS expects to find its input cards. The default is 5, in which case IPS looks for input following immediately in the NASCAP runstream. IPS is able to interpret eight types of potential specification cards as input. These are:

```
ALL matl v
BOOM i v
BOOM CELL v
DARK matl v
END
PCOND i v
POTENTIAL v
SUNLIT matl v
SURFACE CELL v
```

We examine each of these in turn.

SPIN simulates the <u>average</u> behavior of an object 1. rotating in sunlight. Unless CONVEX is specified as a run option SPIN 2. calls HIDCEL for each view requested. Following SPIN, CONVEX should be deleted from the runstream input. Precedence: SPIN must be preceeded by OBJDEF and 3. logically preceeds TRILIN. SPIN reads two cards from file n (e.g., n = 5) 4. SPIN 5 number of views about spin axis included num in the average. x y z spin axis direction. SPIN creates a shadowing table by averaging the tables 5. created for each of num views defined by equally spaced rotations from the initial sun direction (SUNDIR) about the axis x y z. Angle effects are included. (8.3) Calls to SPIN should follow calls to TANK. 6.

Figure 8.3. SPIN summary.

The card:

PCOND i v

sets the potential of conductor number i to v volts. All of the overlying surface cells are <u>also</u> set to potential v, and any differential charging is eliminated. For example

PCOND 2 -1000

sets the conductor number 2, and all surface cells associated with conductor 2 to -1000 volts.

8.4.2 SURFACE CELL

The card

SURFACE CELL i v

sets the potential of <u>insulating</u> surface cell number i to v volts. The surface cell number is the same as that previously assigned by OBJDEF (3.10). For example:

SURFACE CELL 32 -800

sets the potential of insulating cell 32 to -800 volts.

If the surface cell chosen is not an insulator IPS prints a reminder of this fact and ignores the request.

8.4.3 BOOM CELL

The card

BOOM CELL i v

sets the potential for insulating BOOM cell i to v volts. It works in exactly the same as SURFACE CELL (8.4.2) Indeed it is formally equivalent to:

SURFACE CELL nsurf+i v

where nsurf is the number of non-boom surface cells. For example, suppose there are 300 non-boom cells on an object, and you wish to set

the fifth boom cell to -200 V. This can be achieved with the card BOOM CELL 5 -200 or equivalently with SURFACE CELL 305 -200

8.4.4 BOOM

The card:

BOOM i v

sets <u>all</u> insulating cells on BOOM i to potential v volts. The underlying conductor is unaffected. For example, the card BOOM 4 -4000

sets all insulating cells, on the 4th BOOM to appear in the object definition file (3.5), to -4000 volts.

8.4.5 ALL, DARK, SUNLIT

The card

ALL matl v

sets all the surface cells of insulating material 'matl' to v volts. Attempts to set the potentials of conducting materials (those with property 3 equal to -1 (4.3.3)) with this command are ignored and a warning message is printed. For example, the card

ALL KAPTON -1000

sets all cells with surface material Kapton to -1000 volts. The card ALL GOLD -1000

is ignored since gold is a metallic conductor (if its properties are properly defined!). The two subsets of those cells in shadow and those cells in sunlight can be set independently using the cards

DARK matl v

and

SUNLIT mat1 v

#### For example, the card

DARK KAPTON -1000

will set only the KAPTON cells that are in shadow to -1000 volts. Partially shadowed cells (i.e., those with illumination greater than zero) are considered sunlit.

#### 8.4.6 POTENTIAL

The card

#### POTENTIAL v

can be used to set any string of cells to a potential v. Immediately following this card, a second card gives the cell numbers to be set. Further cards may also follow. Up to 15 cell numbers may be written on each card. IPS will continue to read cards until an 'END' is found in place of a cell number. For example

> POTENTIAL -500 1 3 6 25 7 8 101 512 613 26 27 17 21 END

sets the potential of cells 1, 3, 6, 25, 7, 8, 101, 512, 613, 26, 24, 17, and 21 to -500 volts. (This is a particularly useful feature to use with the TERMTALK subset capability.<sup>[20]</sup>

#### 8.4.7 END

The 'END' card terminates input to the IPS module.

8.4.8 'FIXP' AND 'BIAS' CARDS

The run options FIXP and BIAS (see 6.3.5 and 6.3.1) fix the potential of a conductor and bias it relative to conductor 1 respectively.

These potentials are initially implemented in the IPS module, and will be re-implemented by any subsequent TRILIN call. However, it is possible to conflict with these specifications using the PCOND command. The following rules should be observed:

- Potentials of fixed conductors, or mutually biased systems of fixed conductors, should be specified <u>only</u> in the options file.
- Potentials of floating conductors should be specified only in the IPS file.
- If conductor 1 is at zero potential, potentials of conductors biased to it should <u>not</u> be specified in the IPS file.
- If conductor 1 is floating at non-zero potential, potentials of conductors biased to it should be individually specified in the IPS file.

## 8.4.9 IPS Files

A typical file read by IPS might have the form

| BOOM 2 -1000      |  |  |  |  |
|-------------------|--|--|--|--|
| ALL KAPTON -2000  |  |  |  |  |
| DARK TEFLON -2500 |  |  |  |  |
| DARK KAPTON -1638 |  |  |  |  |
| POTENTIAL -1770   |  |  |  |  |
| 1 180 223 6 END   |  |  |  |  |
| END               |  |  |  |  |

This file sets all the insulating cells on the second boom defined to -1000 volts. All Kapton cells are set to -2000 volts. If some of the boom cells are Kapton, the previous assignment of -1000 V will be overridden by the latest assignment of -2000 V.

Dark Teflon and Kapton cells are set to -2500 and -1638 V respectively. Again, any duplicate assignments are overridden with the latest assigned value. Thus all dark Kapton cell potentials are assigned -1638 V rather than -2000 V.

Finally, cells 1, 180, 223, and 6 are set to -1770 volts. Note that the cell number list is terminated with an 'END', as is the entire file (with a second 'END').

Potential assignments made using IPS are <u>not</u> remembered by subsequent IPS calls. IPS zeroes potentials not specified by FIXP or BIAS before beginning with its own assignments.

The IPS input commands are summarized in Figure 8-4.

8.5 CAPACI

Module CAPACI calculates the capacitance of the whole object, the individual conductors, and surface cells to infinity. In addition it calculates the capacitances between the different parts of the spacecraft. This information is all stored in file ICNOW(21) (Table 2.6).

CAPACI is usually executed after OBJDEF. It <u>must</u> be executed before TRILIN or IPS, since TRILIN uses the capacitance information stored in file 21.

No user input is normally required for CAPACI. However, if DEBYE (6.4.3) is specified as a run option, CAPACI reads the plasma environment information from the IFLUX file. The IFLUX file is then read again later by TRILIN in the normal way. PCOND i V Set conductor i and all overlying surfacea cells to potential v. i SURFACE CELL ۷ Set insulating surface cell  $\underline{i}$  to potential  $\underline{v}$ . i v BOOM CELL Set the i<sup>th</sup> boom cell to potential v. (Equivalent to SURFACE CELL [NSURF + i] v). i v BOOM Set all insulating cells on BOOM  $\underline{i}$  to potential  $\underline{v}$ . (Does not set underlying conductor.) matl v ALL matl v DARK matl v SUNLIT Sets all cells of material matl to potential v. Variants allow only dark or only sunlit cells to be set. POTENTIAL v S1 S2 ... END Set a list of surface cells to potential  $\underline{v}$ . The list appears on subsequent cards, with up to fifteen numbers per card. Processing continuers until END is encountered in place of a cell number. (The TERMTLK SUBSET capabilities might be used to generate such a list.)[20] (or @EOF) END Conclude keyword processing

Figure 8.4. IPS input commands.

8.6 NEWMAT

The module NEWMAT allows the properties of a material (Chapter 4) to be changed, without re-defining the whole object using OBJDEF (Chapter 3) again. The 19 properties that characterize each material are initially defined during the execution of OBJDEF. NEWMAT is most often used to change some of the properties in a subsequent run, prior to a new call to TRILIN. (The exact precedence of NEWMAT is summarized in Table 2.2.) NEWMAT is executed by including the card NEWMAT n

in the NASCAP runstream. The parameter n specifies the number of the file where NEWMAT expects to find its input parameters. Usually n = 5 is chosen so that NEWMAT reads the next four cards in the NASCAP runstream as input.

For example, the cards:

```
.
NEWMAT 5
KAPTON
3.5 0.000127 1.E-16 5. 2.1 0.15 71.48 0.60
312.1 1.77 0.455 140. 0.00002 1.E+16 15. 16.
1.E-13 1. 1.E+3 20.
END
```

included in the NASCAP runstream redefine the KAPTON material properties to the values given on the cards. The format for input of material properties for NEWMAT is exactly the same as in OBJDEF (4.4). The completed list of materials and properties must be terminated by an 'END' card. (Otherwise NEWMAT will assume that all further cards in the runstream are new material names.) For example, if two materials are to be re-defined, the relevant part of the runstream might have the form: NEWMAT 5 KAPTON {3 parameter cards (4.4) GOLD {3 parameter cards (4.4) END TRILIN END

There are two restrictions in the use of NEWMAT:

- 1. The names of materials cannot be changed, or new material names introduced.
- 2. The values of the bulk conductivity and surface conductivity (properties 3 and 14) may not be changed so that the material changes from an insulator to a metallic conductor or visa versa, or from a surface non-conductor to a surface conductor. In other words, the values of properties 3 and 24 may not be changed from positive values to negative values or vice versa.

Changing the sign of properties 3 and 14 cause changes in the <u>structure</u> of conductivity matrices rather than their value, and OBJDEF must be re-executed in these cases.

Note that the capacitances of the object brought about by changes in material properties are automatically accounted for by NEWMAT, and no subsequent re-execution of CAPACI is necessary.

#### 8.7 SATPLT

Module SATPLT requires no direct user input, and causes three-dimensional views of the object to be plotted, along with two-dimensional maps of the pattern of surface materials.

The nature of the views and maps are determined using the run options 3D-VIEW (6.6.1) and MATVIEW (6.6.4) respectively. If no views are specifically requested using this option, the default views discussed in 6.6.1 and 6.6.4 are produced. SATPLT is usually called after OBJDEF as an aid, to see if the object we had in mind is actually the object we defined (or to see if they at least look the same). The exact precedence is summarized in Table 2.2. The card: SATPLT

included in the runstream executes SATPLT. Examples of the plots produced are given in Chapter 9.

#### 8.8 STRESS

The module STRESS is used to determine the surface cells with internal electric fields of greatest magnitude. The internal electric field, or stress,  $E_{stress}$  is defined as

$$E_{stress} = \frac{V_c - V_s}{d}$$

where  $V_c$  is the potential of the underlying conductor,  $V_s$  is the potential of the dielectric surface and d is the thickness of the dielectric surface layer. The greater this stress field, the more likely a dielectric breakdown or "punchthrough" will occur. (See 6.3.3 discussing the NASCAP DISCHARGE analysis.)

STRESS is executed by including the card STRESS <m> in the NASCAP runstream, usually after a call to TRILIN. (Exact precedence is summarized in Table 2.2.) The only input parameter is the optional quantity m. m is the number of cells to be reported by STRESS. For example, the card

## STRESS 10

will cause the 10 cells with the greatest stress to be identified in descending order of stress field. Omission of <m> causes <u>all</u> cells to be listed in descending order of stress.

For each cell included in the list generated by STRESS, the value of its stress field and its cell number, along with its surface material, normal, vertex, and other identifying information, is printed out.

## 9. GRAPHICAL OUTPUT

Graphical output is a key component in the presentation and interpretation of NASCAP results. The plotting protocol is designed to be easily interfaced to any system's graphics library. The plots appear in four colors (black, red, green, blue) when plotted on color hardware. The types of plots produced are (1) object illustration and shadowing plots; (2) contour plots; (3) particle trajectory plots; and (4) detector plots.

## 9.1 OBJECT ILLUSTRATION AND SHADOWING PLOTS

Object illustration plots are produced by the SATPLT module (or the interactive OBJCHECK object definition program).<sup>[20]</sup> Three types of plots are produced: material plots, 3-D plots without hidden line elimination, and 3-D plots with hidden line elimination (shadowing plots).

## 9.1.1. MATERIAL PLOTS

Material plots (Figures 9.1-9.2) are designed to show the placement of materials on the object. Each of the fifteen materials is shown with different shading and (on appropriate hardware) different colors. (Materials 1, 5, 9, 13 are in black; 2, 6, 10, 14 in red; 3, 7, 11, 15 in green; and 4, 8, 12 in blue.) By default, six plots are generated showing the view from each coordinate direction. The MATVIEW keyword (6.6.4) may be used to expose surfaces which would otherwise be hidden (Figure 9.3).

## 9.1.2. 3-D PLOTS

Two types of 3-D object plots are available. The first type (Figure 9.4), plotted only by SATPLT (or OBJCHECK), plots the outline of the large blocks (RECTAN, OCTAGON, etc.) projected on a plane normal to the view direction without hidden line elimination. Booms



FOR Y VALUES BETWEEN 1 AND 17

MATERIAL LEGEND 1 MOO1 2 M002 5 1003 4 i1004 5 M005 6 M006 7 17. 1007 16. 8 15. M008 14. 13. 9 1009 12. 11. 10 10. M010 9. 11 8. M011 7. 6. 12 5. M012 4. 13 3. M013 2. 14 1. 33. 31. 27. 29. 23. 25. 21. 17. 19. 13. 15. M014 9. 11. 3. 5. 7. ι. 15 -2-M015

Figure 9.1. Material plot of an object consisting of five dumbbells. All fifteen shading patterns are illustrated.

# SURFACE CELL MATERIAL COMPOSITION AS VIEWED FROM THE POSITIVE X DIRECTION



FOR X VALUES BETWEEN 1 AND 17



Figure 9.2. Another material plot view of the object in Figure 9.1.







Figure 9.3. Material plot view of surfaces which were hidden in Figure 9.2.



Figure 9.4. Perspective view of the object in Figures 9.1-9.3, without hidden line elimination.

are omitted from this plot. The second type (Figure 9.5) plots individual surface cells and boom surfaces with hidden lines eliminated. This type of plot is also produced by calls to the HIDCEL, SPIN, ROTATE and TANK modules. The plots are from the perspective of a viewer 1000 mesh units distant, except that the TANK module places the viewer at the gun positions. On appropriate hardware, the shadowing plots are color-coded by material (as on the material plots).

## 9.2 CONTOUR PLOTS

Contour plots are produced by various portions of the TRILIN module. The quantity whose contours are most commonly plotted is the electrostatic potential. (This may also by plotted by the interactive POTPLT program.<sup>[20]</sup>) In addition, contours of space charge (calculated by the SHEATH option), and of current density (calculated by the TYPE 1 test tank) may be plotted. Contour plots include a "silhouette" of the test object.

# 9.2.1 ELECTROSTATIC POTENTIAL CONTOURS

Contours of electrostatic potential in a plane normal to one of the coordinate axes will be plotted on request. Frequency and location of plots may be controlled through the CONTOURS keyword (6.6.2). Each plot is captioned as to cycle number, time, location, and contour levels (volts). (The interactive POTPLT program also allows control over number of contours.) A potential contour plot example is shown in Figure 9.6.

It should be noted that "exact zeros" in the interior of the potential array are assumed interior to the object and are set at conductor 1 potential. This has proved a good procedure in the vast majority of cases. The user must be aware that the contour lines inside the object do not exist and should be expunged before presentation.



Figure 9.5. The view of Figure 9.4 after hidden line elimination.



Figure 9.6. Electrostatic potential contours about an object composed of two spheres. The lower sphere is at +10 V and the upper at -10 V. (a) One-grid plot; (b) Two-grid plot.





Figure 9.6. Electrostatic potential contours about an object composed of two spheres. The lower sphere is at +10 V and the upper at -10 V. (a) One-grid plot; (b) Two-grid plot.

### 9.2.2. CHARGE DENSITY CONTOUR PLOTS

Space charge density associated with low energy emitted electrons (i.e., secondary electrons and photo-electrons), is plotted by the TRILIN module when the keyword SHEATH is included in the options file (6.6.6). The contour levels are in  $coul/m^3$ . An example is shown in Figure 9.7a. The example is for the same case as Figure 9.6; most of the low-energy electrons result from sunlight incident from the +Y direction. Note that the charge density near the positive (lower) sphere is about double that near the negative (upper) sphere. The reason is seen in the accompanying particle trajectory plot, which shows electrons repelled from the negative sphere, but forming a cloud around the positive sphere.

## 9.2.3 CURRENT DENSITY CONTOUR PLOTS

Current density contour plots from the TYPE 1 test tank may be requested using the TANKCUR keyword. The plots give the Z-component of current  $(A/m^2)$  projected onto the "sample plane". Examples are shown in Figures 9.8d-f.

#### 9.2.4. CONTOUR PLOT RESOLUTION ERRORS

Contour plots are performed using straightforward bilinear interpolation. Near object surfaces, this is a far cruder model than is used internally in NASCAP (for potential calculations, particle tracking, and electrostatic field calculation). In interpreting contour plots the user should be aware of these shortcomings.

Some of these errors are shown in Figure 9.6. We have previously mentioned that the conductor 1 potential (+10V in this case) is inserted for potentials interior to the object. This results in contour lines interior to the upper (-10V) sphere. Also, the contours exterior to the upper sphere are in error near the slanted surfaces. NASCAP understands the potential at the midpoint of the



Figure 9.7. Low energy electron sheath structure for two spheres (upper at -10 V; lower at +10 V) with sunlight from +Y direction. (a) Charge density contours; (b) Electron trajectories.

Z AXIS


### PARTICLE TRAJECTORIES AT CYCLE 3 FROM 4 CELLS PROJECTED ONTO THE Y-Z PLANE

Figure 9.7. Low energy electron sheath structure for two spheres (upper at -10 V; lower at +10 V) with sunlight from +Y direction. (a) Charge density contours; (b) Electron trajectories.





slanted line to be -10 V; however its bilinearly interpolated value is about -4V. (This error is not apparent for the lower sphere because the interpolation error is less than the contour interval.) In the case of the two-grid plot (Figure 9.6b), the mesh point density is insufficient to resolve the object, so that conclusions may be drawn only about potentials distant from the object surface.

The contour routines do not recognize the existence of double points. Thus the potential beneath a thin plate will appear to vary linearly from its "top" value to the correct value one grid unit below.

The contour routines do not recognize the existence of thin booms. Thus the potential near a boom appears to vary linearly from the boom center to its correct value one grid unit away, rather than logarithmically from the boom surface.

### 9.3 PARTICLE TRAJECTORY PLOTS

Particle trajectory plots are produced by the DETECT module, and within the TRILIN module by the TYPE 1 test tank (keyword TANKTRAJ), SHEATH, and EMITTER facilities. The DETECT module plots one trajectory for each value of the independent variable for each species (Figures 9.9–9.10). The TYPE 1 test tank plots trajectories for all particles emitted with  $\phi = 0$  or  $\pi$  (Figure 9.8a-c). The SHEATH routines plot trajectories for all particles emitted from surface cells requested for output (keyword SURFACE CELL n) (Figure 9.7b). The EMITTER routines plot the trajectory of the emitted beam (absent space charge effects) (Figure 9.11).

### 9.4 DETECTOR PLOTS

The detector plots give the energy flux of electrons and ions measured by a detector as a function of a specified independent variable (energy or angle). Electrostatic, magnetic field, and particle shadowing effects are taken into account. Examples are shown in Figure 9.12. The DETECT module is more fully discussed in Chapter 7.



Figure 9.9. Trajectories for electrons received at 25 different detector energies logarithmically spaced from 10 eV to 50 keV. (Conducting object charged to -4.5 keV and no magnetic field.)

NIEXHS



TRAJECTORIES AT CYCLE & FOR PROTONS RECEIVED BY DETECTOR LOCATED AT CELL NUMBER 225 PROJECTED ONTO THE Y-2 PLANE

Figure 9.10. Trajectories for protons received at 25 different detector energies logarithmically spaced from 10 eV to 50 keV. (Conducting object charged to -4.5 keV and no magnetic field.)

NIAXHS



### PARTICLE TRAJECTORIES AT CYCLE 11 FROM 1 EMITTER(S) PROJECTED ONTO THE Y-Z PLANE CELL LOCATION AND EMITTER TYPE: 225(E)



Z-AXHS

ENERGY FLUX IN EV/(CM2-SEC-SR-EV) AT CYCLE & MEASURED BY DETECTOR LOCATED AT CELL NUMBER 225 (INTERPOLATED AT 25 POINTS) PROTON FLUX (HEAVY) SCALED BY 1.00+05 ELECTRON FLUX (LIGHT) UNSCALED.



ENERGY IN EV

Figure 9.12. Detector logarithmic energy scan. Energy and angular apertures set to zero width. Detector surface cell potential = - 4.5 keV. (Note absence of proton flux below 4.5 keV.)

### 9.5 IMPLEMENTATION: NASCAP\*PLOTREAD

The main program NASCAP does not contain any dependence on the user's locally implemented graphics library. Rather, NASCAP writes a "neutral" plot file (file 2) consisting of subroutine calls and their arguments. (A list of these subroutines appears as Table 9.1. NASCAP\*PLOTREAD contains a main program which reads file 2 and reconstructs the subroutine calls. The subroutines of NASCAP\*PLOTREAD then call the appropriate user graphics library routines.

Versions of NASCAP\*PLOTREAD have been written for the DISSPLA graphics package at S-Cubed, the IGS package at NASA/LeRC, and the PLOT\*PLOT package at Jet Propulsion Laboratory.

|            | TABLE 9.1. NASCAP-PSEUDO GRAPHICS | SUBROUTINES   |
|------------|-----------------------------------|---|
| SUBROUTINE | ARGUMENTS                         | FUNCTI ON   |
| ADF        | None                              | Eject current plot frame  |
| APRNTV     | (IDX,IDY,N,TEXT,IX,IY)            | Print horizontal or vertical plot labels  |
| AXISXV     | (X,Y,XEND)                        | Draw horizontal line  |
| AXISYV     | (X,Y,YEND)                        | Draw vertical line  |
| CONECT     | (X1,X2,Y1,Y2,SL1,SL2,NLL)         | Connect line segments for contours  |
| CURVV      | (MUD1, YGC, Y, XGC, X, N)         | Draw connected line segments  |
| DL INEV    | (N,IX,IY)                         | <pre>N = 1: Draw line to raster position IX,IY<br/>N = 0: Move to raster position IX,IY<br/>N =-1: Draw increment IX,IY<br/>N =-2: Move increment IX,IY</pre> |
| DRAWV      | (LINE,N,IX,IY,KEYPOS,KCSIZE)      | Draw vector characters  |
| FINSHV     | None                              | Close plot file; process plot destination   |
| IGFBUF     | (NWDS,NAME)                       | Process plot buffer   |
| LINEUV     | (X1,Y1,X2,Y2)                     | Draw line between two points  |
| LQUADV     | (N,X,Y)                           | Fill in a quadrangle with solid lines   |
| OUTLIN     | None                              | Draw box around plot  |
| PLOTCV     | (N,X,Y,IC)                        | Plot a character (or dot) at listed points  |
| SBLIN      | (NN,KK)                           | Print scale values for linear baseline<br>NN subdivisions<br>KK Format<br>0 16<br>1-5 F6.0 - F6.4<br>6-12 E12.1 - E12.7                                       |

.

| SETUAV (XL,XR,YB,YT<br>SETUAV (XL,XR,YB,YT<br>SETUPV None<br>SLLIN (NN,KK)<br>SWPEN (COLOR)<br>TLINEV (MODE,X2,Y2,1 | ILE 9.1. NASCAP PSEUDU-GKAPHIUS<br>UMENTS 0<br>C C C C C C C C C C C C C C C C C C C | FUNCTIONDefine user area and establish rasterCoordinatesOpen plot filePrint scale values for linear grid left lineSwitch pen colorMODE = 0Set CP = X2, Y2MODE = 1Draw line to X2, Y2 with thickness30 LW rasters |
|---|--|--|
| rypev (ITEXT,N,IX,  | , IY) W  | Write N letters of text starting at IX,IY  |

### 10. PRINTED OUTPUT

### 10.1. INTRODUCTION

The output printed by NASCAP for each module is largely self explanatory. Some lines of output bear directly on the user's problem, while others serve primarily to monitor the progress of the calculation. Only the former type of output is of interest to the everyday user of the code. In this section we provide a quick reference to the blocks of printed output produced by each module.

### 10.2 CAPACI

-

Sample output from module CAPACI is shown in Figure 10.1. The references shown are as follows:

- The inverse of the PCOND values give the capacitance of the object to infinity in code units. The code unit of capacitance is printed out by RDOPT.
- 2. This is the radius of a sphere of equivalent capacitance.
- 3. These are the stray capacitances between higher numbered conductors and conductor 1.

The remaining output is for diagnostic purposes.

Figure 10.1. CAPACI output.

### 10.3 DETECT

Figure 10.2 shows sample DETECT output. The references are as follows:

1. The DETECT input file is echoed and interpreted.

- 2. The definition of each detector is summarized.
- 3. The environment description read from IFLUX is summarized.
- 4. The energies and velocities of each particle tracked (for ions and electrons) are listed. Particles originating from the spacecraft are not included in the flux collected by the detector.

| 2                              | ICFLL SET TO 170    | INITIAL EMERGY SET TO 1.0C0000+0PD | PEM SET TO 1.0C00C0+501 | INITIAL THETA SET TO -8.80COUD+001 | DIH SET 10 1.00000+000 | INITIAL FHI SET TO .OCO3CO | NE SET TC 1 | FLUX PLOT AUTO-SCALE OFTION SET FOR THIS DETECTOR | INDEPENDENT VARIABLE FOP FLUX PLOT IS THET | FINAL VALUE OF INGEPENPENT VARIARLE SET TO 8.8U0000+001 | N SET 10 10 | FARTICLE PLOT FLAG SET FOR THIS DETECTOR | NGUND SE1 10 I | LIMGRD SET TO 2 |  |
|--------------------------------|---------------------|------------------------------------|-------------------------|------------------------------------|------------------------|----------------------------|-------------|---|--|---|-------------|--|----------------|-----------------|--|
| ######NETECT 23<br>AS6F1L @AS6 | 1111 110<br>20202 1 | ENEKGT 1                           | C.L.M. 1.U              | THE 1 A - 88                       |                        | 0 1 H d                    | NE 1        | AUTOS   | INDVAR=THETA                               | FINALV 88<br>Mart                                       |             | PLFARI                                   | NGBND 1        | LITURU 2<br>FND |  |

Figure 10.2. DETECT sample output.

PARAMETER DEFINITION SUPMARY FOR PARTICLE DETECTORS

NUMBER OF FARTICLE DETECTORS = 1

• 2

9.10910-031 KG 1.67252-027 KG \*\*\*\* PARTICLE TRAJECTORY PLOTS WILL BE PROPUCED FOR THIS DETECTOR \*\*\*\* N PROTON ENERGY FLUX PLOT SEPARATION SCALE FACTOR F1900+005 PROTON ENERGY FLUX PLOT PEN LINE WIDTH = 3 RASTER 1900+005 PARTICL VELOCIY = 300 MESH UNITS PER STEP FUGHEST GRID IN WHICH 1/P POTENTIAL TRACKING IS PERMITED = ENERGY FLUX SCALE RANGE IS DETERMINED AT FXECUTION TIME JNDEPENDENT VARJAPLENFOR PLOT 3. THETO DEG TO 8.80+001 DEG ELECTRON CHARGE = -1.60200-C19 COUL ELECTRON HASS = PROTON CHARGE = -1.60200-C19 COUL EROTON HASS = 170 NE NP NMU2 = ENERGY FLUX INTEGRAL PARAHETERS · ENERGY =1.000+000 EV SUPFACE CELL LOCATION = DE = 16.00 **\*** NSTP = 500 DTH = 1.00 PEG DETECTOR NUMBER 1: FIXED VARIABLES 

Figure 10.2. (Continued).

TPAJECTORY PLOT FRAME REPETITION OPTION ACTIVE WITH PARAMETERS SET AS FOLLOW:

GRID BOUNDARY INDEX OF FIAST FRAME (NGRND) = NUMBER OF FRAMES CENERATED (NGPLOT) = 1 GRID BOUNDARY INDEX INCRFMENT (NGINC) = 0

Figure 10.2. (Continued).

OSUMER FOUND OSUME -3.35+DC4 CODE UNITS AFTER SCREENIKG CORRECTION (SCREENING LENGTH= 2.00+003 M.) OSUM= -3.35+DD4 FLUX DEFINITION SINGLE -1.47+004 FLUX DEFINITION SINGLE 5. nn+003 ELECTRON VOLTS 5.CO+DD3 ELECTRON VOLTS 1.00+036 METER##(-3) ELECTRON TEMPERATURE = ELECTRON DENSITY : JON TEMPEGATURE =

NROOM = 2 NG= 2 XHESH= 2.0C0-001 1.00+006 HFTFR++1-3) SETBHI SET INVERSE BOOM MATRICES FOR DETECTOP/FMITTER USAGE ION DENSITY =

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NE XTPA =

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| 4 | <sup>NDGE</sup> LŞ=NJ=LPFLAG331 NĞMESHTCZFGOOGOTQQTQQCTQQLEWATTOPPSURFTTNAPP29181=-3.34876+004 T<br>PCONDE 1.5+00925+4+002 .00 .00 .00 .00 .00 .00 .00 .00 .00   | 16= 1.20920<br>.0 | 0.<br>1.00 | ••• |           | 00 |
|---|--|-------------------|------------|-----|-----------|----|
| د | A SSGFIL<br>A SSGFIL<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>ENFRAGY<br>E |                   |            |     |           |    |
| 9 | FINERGY PARTICLE TRACKING TOTALS FOR DETECTOR 1 SPECIES 1 AT CYCLE TRACKING TOTALS FOR DETECTOR 1 SPECIES 1 AT CYCLE 3 ENERGY 14.0 EV  | = 1 I HN          | - INC-     | •   | NE SCAP = | 0  |
| ~ | *****PARTICLE TWACKING TOTALS FOR DETECTOR 1 SPECIES 2 AT CYCLE 3CALLED DETECTLED REFETCALLED NETPLTLABABYECALLED RETPLTLABABYECALLED RETPLTLABABYECALLED RETPLTLABABYECALLED RETPLTLABABYECALLED RETPLTLABABYECALLED RETPLTLABABYECALLED RETPLTLABABYECALLED RETPLTLESECCEIN PLPARTDETEIN PLPARTDETE <td></td> <td>IC NINC=</td> <td>0</td> <td>NE SCAP =</td> <td>D</td>  |                   | IC NINC=   | 0   | NE SCAP = | D  |
|   | ★★★★★★ENP<br>Cend Nascapj  |                   |            |     |           |    |

Figure 10.2. (Concluded).

ªASG,A NAS€AP⇒PLOTREAD.

**AXGT NASCAP+PLOTREAD.** Gevice Option = 3.

10.4. HIDCEL

Output is shown in Figure 10.3. The output is purely diagnostic.

\*\*\*\*\*\*HIDCEL DISTANCE EQUALS 999.99998 FINAL NA1 = 62

Figure 10.3. HIDCEL output.

10.5 IPS

Sample output from module IPS is shown in Figure 10.4. The references are as follows:

- 1. The IPS input cards are echoed.
- 2. The potentials in space are set to the monopole potential with the radius and charge given.
- 3. The new surface cell potentials are summarized.
- 4. Potentials and charges on the conductors are summarized.

eeeesIPS 5

OBJECT DEFINITION INFORMATION BEING READ FROM FILE

\*\*\* INITIAL POTENTIAL SPECIFICATION \*\*\*

- 3000 -2000 KAPTON COND

-1.30+005 CODE UNITS. TOTAL CHARGE FOR INITIALLY SPECIFIED POTLNIIALS ESTIMATED TO BE

PUTENTIALS TO BE SET BY SETALL TO -1.30+UN5/14+PI+K} 2

4.00+000 CODE UNITS AVERACE RADIUS (RD) =

e

. 0N

00+000

|             |   |  |             | 0          |            |            |
|-------------|---|--|-------------|------------|------------|------------|
|             |   | 4PLETEU.<br>/ 4.85+009                               | ;           | IPSAVE = 1 |            | JPSAVE = 1 |
| I CELLS     |   | CRATIONS CON<br>04003<br>87+005                      | 1 PEAD TI   | 5PARE = 12 |            | SPARE = 12 |
| 1 - ALL 184 |   | 0018/RDRMAX<br>0018/RDRMAX<br>003 -2.00<br>009 -5.92 | RIDS OUT OF | IU = 10 I  | TED IS 0.  | IU = 14 I  |
| POTENTIALS  |   | 19 Pt<br>-1.0000                                     | 1 61        | 1 IR = 13  | CLE COMPLE | ) 1R = 13  |
| SURFACE     | 2<br>2<br>2<br>2<br>2<br>2<br>2<br>2<br>2<br>2<br>2<br>2<br>2<br>2<br>2<br>2<br>2<br>2<br>2 | PCOND =  | EFPRLF      | 11 = 11    | LAST CI    | 1P = 1(    |

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Figure 10.4. IPS sample output.

10.6 NEWMAT

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Sample NEWMAT output is shown in Figure 10.5. References are as follows:

1. NEWMAT input is echoed.

2. The property table for each redefined material is printed.

\*\*\*\*\*\*NEWMAT 5

# OBJECT DEFINITION INFORMATION BEING READ FROM FILE

1.73+000 5.35+001 9.20-001 1.80+001 8.68+001 1.70+001 8.00-001 2.00+003 8.80-001 1.00+004 1.00+000 1.00-003 -1.00+000 4.13-001 1.35+002 2+90-005 GOLD

PREPROCESSING OF MATERIAL PROPERTIES HATERIAL 1: GOLD

 $\sim$ 

| IN CONTRACTOR CONTRACT   |  |
|--|--|
| PROPERIY<br>CHUCKTEST<br>CHUCKTEST<br>CHUCKTEST<br>CHUCKTEST<br>ATOMUCATIST<br>ATOMUCATIST<br>ATOMUCATIST<br>ATOMUCATIST<br>ATOMUCANA<br>FATOMER<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>SPACE DISCHARGE POTIC<br>ATOTERREN<br>SPACE DISCHARGE POTIC<br>ATOTERREN<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATOMENT<br>FATO |  |
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NEWMAT sample output. Figure 10.5. 10.7. OBJDEF

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Sample output is shown in Figure 10.6. References are as follows:

- 1. The object definition file is echoed as read.
- Each building block definition is confirmed in <u>absolute</u> grid coordinates (centered at 9, 9, (NZ+1)/2).
- The surface cell list is printed (absolute coordinates).
  IX, IY, IZ are the coordinates of the lowest indexed vertex of the associated volume element.
- 4. The material properties are summarized.

+++++0BJDEF

COMMENT WORKED EXAMPLE (CHAPTER 10) COMMENT ZONE SIZE IS D.D2 M

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COMMENT DEFINE MATERIAL GOLD AND SOLAR

|   | 1.73+000<br>2.00+001                 | 1°00+000<br>2•00+000                 |
|---|--------------------------------------|--------------------------------------|
|   | 5+35+001<br>1-00+003                 | 1.00.003                             |
|   | 9.20-001<br>1.00+000                 | 4 • 50-001<br>1 • 00 • 000           |
|   | 8.88.001<br>1.00-013                 | 7.75.001                             |
|   | 8.00-001<br>2.00+003                 | 4 • 1 0 - 001<br>2 • 00 • 003        |
|   | 6.80+001<br>1.00+004                 | 2 • 05 • 000<br>1 • 00 • 004         |
|   | 100+001-<br>-1.00+000                | 1.00+001                             |
|   | •ERTTES<br>-1.00+000<br>2.90-005     | 2.00-005                             |
| • | ATERIAL PROI<br>1.00-003<br>1.35+002 | ATERIAL PROI<br>1.79-004<br>2.30+002 |
|   | 1.00+000<br>4.13-001                 | 3.80+000<br>2.44-001                 |
|   | 60LD                                 | SOLAR                                |

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CUMMENT PROPERTIES OF KAPTON AND ALUMINUM FROM DEFAULT TABLE. CONDUCTOR 1

COMMENT CENTRAL CUBOTO

Figure 10.6. OBJDEF.

15 (GRID | COORDINATES) 21 IGRID I COORDINATESI 1 221 00 •• 00 0-0 9 221 10 6 10 BOOM DEFINED Beginning at Extending Parallel to the 2 axis 10 22 510E = BOOM DEFINED Beginning at Extending Parallel to the 2 ax1s to 15<24 COMMENT BOOM TO KAPTON SPHERE COMMENT BOOM TO SOLAR SPHERE DEFINING Q-SPHERE CENTER = 9 0 DIANETER = 401 MATERIAL = 401 **o** m COMMENT KAPTON SPHERE OCTAGON DEFINED Axis = ( Width = RECTAN OBJECT NOW DEFINED. .05000 .05000 SURFACE +X GOLD SURFACE +X KAPTON SURFACE +Y KAPTON SURFACE +Y KAPTON SURFACE +Y KAPTON SURFACE +2 KAPTON SURFACE +2 KAPTON SURFACE -2 KAPTON ALUM ALUM **Q S P HE RE** SURF SURF B 00H RADI BOOM RADI

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Figure 10.6. (Continued).

10 22) 9 231 11) 12) 111 oi COMMENT SOLAR SPHERE FON SEPARATE CONDUCTOR) 9 22) 10 ( 9 5106 = 9 • 9 11) 10 t 10 9 22) 10 ( 51DE = 9 111 10 1 = 11) 10 ( SIDE = ŠIDE = • SOLI DEFINING Q-SPHERE CENTER = 9 DIAMETER = 5 MATERIAL = 5 ð 0 m OCTAGON DEFINED Axis = ( WIDTH = OCTAGON DEFINED Axis = { WIDTH = OCTAGON DEFINED Axis = ( Width = OCTAGON DEFINED AXIS = 1 WIDTH = OCTAGON DEFINED Axis = { Width = CONDUCTOR 2 **OSPHERE** ENDSAT

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SUPPACE CELL LISI

CONDUCTOR

MATERIAL



Figure 10.6. (Continued).



| MATERIAL           | 22200000000000000000000000000000000000         | INT MATERIAL                 |   |   |
|--------------------|--|------------------------------|---|---|
| NORMAL             |  | GRID AXIS BOOM               | ****  |   |
| 21                 | ~\$880=N0=N0=N0N0N0=N0=N0=N0=N<br>============ | 12                           | 0.0M#   |   |
| 1                  |  | λT                           | 0000  |   |
| XI                 |  | XI                           | 0000  | conduc                                    |
| CONDUCTOR          |  | CONDUCTOR                    |   | MATERIAL<br>Alun<br>Alum                  |
| 6. CELL LIST<br>0. |  | URFACE CELL LIST<br>10. CODE | 000061111123<br>0000621111124<br>000062111115<br>000062111116 | DF 800M PROPERTIES<br>RADIUS<br>.050<br>2 |
| SURF ACI           |  | BOOM S                       | 181<br>882<br>882<br>882<br>882                               | 1 151<br>Воом<br>1<br>2                   |

Figure 10.6. (Continued).

|  | Image: Sector  | ++LUNS 144<br>++LUNS                                       |
|--|--|--|
| INPUT VALUT  | 22.000 -011<br>23.000 -011<br>23.000 -011<br>23.000 -011<br>23.000 -011<br>23.000 -010<br>23.000 -010<br>23.00 | 1.00-0013<br>1.00-002<br>1.00-000<br>1.00-000<br>1.00-000<br>1.00-000<br>1.00-000<br>1.00-000<br>1.00-000<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.00-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-001<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.000-000<br>1.0000-000<br>1.000-000<br>1.0000-0000<br>1.00000000<br>1.0000000000 |
| PROPERTY<br>PROPERTY<br>PROPERTY<br>CONDUCTINIC CONSTANT<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDUCTINIC<br>CONDU | MATERIAL 2: SOLA<br>PROPERTY<br>CUNDUCTISTIC CONSTANT<br>CUNDUCTISTIC<br>ATOMIC NUTHTY<br>ATOMIC NUTHER<br>FE-HLTA MAX SCOFFF<br>FE-HLTA MAX SCOFFF<br>FANGE NE X PORCHAP-1<br>FRANGE NE X PONENT<br>FRANGE NE X PONENT<br>FRANGE STATE ON STANGE<br>FANGE NE X PONENT<br>FRANGE STATE ON STANGE<br>FANGE STATE ON STANGE<br>FANGE STATE ON STANGE<br>FANGE STATE ON STANGE<br>SURFACE FESISTIT<br>SURFACE STANGE POTIC<br>FANDN INDUCEDCOND STOPFIL<br>FANDN INDUCEDCOND STOPFIL  | PROPERTY<br>PROPERTY<br>DICLECENESS<br>CONDUCTIVITY<br>DELOHIC NUNBER<br>DELOHIC NUNBER<br>DELOHIC NUNBER<br>DELOHIC NUNBER<br>PROPENT<br>RANGE NEWN<br>RANGE NEWN NANGE<br>RANGE NEWN PROTONS<br>MAX DE VDR IME V PROTONS<br>MAX DE VDR IME V PROTONS<br>PROTOCERENT<br>SPACE DISCHARGE POTO<br>SPACE DISCHARGE POTOL<br>RADN INDUCEDCOND TY OUERT  |

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PREPROCESSING OF MATERIAL PROPERTIES 

. MATERIAL

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Figure 10.6. (Continued).

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Figure 10.6. (Concluded).

### 668 ENTRIES IN REVISED VIXL

### BOOMEJ -- 328 EDGES FOUND

## FNDSCE -- 328 SURFACE CONDUCTING EDGES FOUND

### 1.0.019 OHNS 1.0.016 OHNS SOLA HAS SURFACE RESISTIVITY OF KAPT HAS SURFACE RESISTIVITY OF

## INSLST -- 164 INSULAT

## 180 VOLUME CELLS

ADN ADN ADN

NMENON BDO

•00 • 00 •

|             | ••••••••••••••••••••••••••••••••••••   | Z.UD.ADJ<br>Numl.TB.<br>Cells found<br>Boom cells                     |
|-------------|--|---|
| IAL 4: ALUM | ERTY<br>IELECTRIC CONSTANT<br>UNDUCTISS<br>UNDUCTISS<br>IOMICATIST<br>IOMICATIST<br>IOMICANSTANT<br>IOMICANSTANT<br>IOMICANDER<br>NOE<br>NOE<br>NOE<br>NOE<br>NOE<br>NOE<br>NOE<br>NOE | D VOLUHE CELLS NUMBERED BY<br>164 INSULATING SURFACE<br>164 INCLUDING |

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MATERIAL PROPER1 

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10.8 RDOPT

Sample output is shown in Figure 10.7. References are as follows:

- 1. Option file input cards are echoed.
- 2. In UNIVAC versions temporary files are automatically assigned.
- 3. A summary of all options, including defaults, is printed.

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167 INFORMATION TO BE PRINTED. 20 INFORMATION TO BE PRINTED. 129 INFORMATION TO BE PRINTED. 28 INFORMATION TO BE PRINTED. 77 INFORMATION TO BE PRINTED. **BB INFORMATION TO BE PRINTED.** 181 INFORMATION TO BE PRINTED. WHESH D.D2 NCYC J NCYC J Delta S Surface Cell 20 CELL CELL CELL CELL כנרו CELL CELL SURFACE CELL 167 SURFACE CELL 129 SURFACE CELL 101 SURFACE CELL 20 SURFACE CELL 77 SURFACE CELL 88 LONGTINESTEP Sunint 1.0 Sundtr 1.1 Dest elec

 Figure 10.7. RDOPT

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NASA CHARGING ANALYZER PROGRAM Option Summary

TITLE ENASCAP

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NE GRID SIZE OPTIONSI

9N Z

FULL OUTER ĜRIO ŬŜED \_\_\_\_\_ANKSIZE, ZTRUNC, TANK RADIUS, TANK AXIS Additional option vords: Offset, Tanksize, Ztrunc, Tank Radius, Tank axis LOGICAL UNIT NUMBERS

108J 108PLT 18 19 IROUS IPGCND ILIBL ICNOW IAREA 15 16 11 21 27 ISPARE 14 IFLUX ISPCTR 10 13 RUN MODE OPTIONS: ICREST IPREST NCYC MCYC 101V 25 INPUT FILES: IKEYUD ISAT 26 20 14 14 14 SCRATCH FILES: JAUN RESTART FILES: IP 10

IPART 28

DELTA DELFAC 5.00+000 1.00+000 DEADLIME = NONE ADDITIONAL KEYUORD = ERESTARTJ

POTENTIAL SOLVER OPTIONS: POTCON MAXITA JOUTER SCA SCA SCALING NOTSET AMBIENT SPACE CHARGE OPTION ENEYWÖRD DEBVE 3-DONE **10UTER** HAXITR 99

CONDUCTOR FIXING AND BIASING:KEYWORDS FIXP, BIAS, FLOAT

INTERCONDUCTOR CAPACITANCES: WEYWORD CIJ HE CODE UNIT OF CHARGE IS 1.771-DI3 COULOMBS. HE CODE UNIT OF CAPAGETSE IS 1.771-DI3 FARADS. No interconductor capacitances specified.

LONGTIMESTEP AND DISCHARGE OPTIONS Keynords: Longtimestep, nolongtimestep, discharge, flasmover Longtimestep requested with dvLIM= 1000.0 volts. Discharge Analysis off

•000 ILLUMINATION SPECIFICATIONS: Sunint= 1.000 Sundir = .7071 Shadowing Formulation Energrord=Convexj=Shad

XHE SH= 2.00-002

1ROUSP D

11CUR

I TPART 0

REPEAT

PLOT OPTIONS: TITLE = MASCAP NGPLOT ICON D

365

Figure 10.7. (Continued).

7 SURFACE CELLS SPECIFIED FOR 1/0: 20 21 77 08 129 167 101 Keywords: [surface cell], [surface at], [surface copner]

HIDCEL

E PLOISJ= D LINCEL 08JDEF NO SOME

PRINT ENOPRINTS: POTENT PRINT ENOPRINTS: POTENT

NGPRI LAPRIJ

OUTPUT OPIIONS:

TIMER CNOTIMERS No

= OFF

ENVIRONMENT TYPE AND MESH SIZE Itype= 2 Update=off

SECONDARY EMISSION FORMULATION = ANGL\* EFFECTIVE PHOTOSHEATH CONDUCTIVITY FEFECOND = OFF EIELD-ENHANCEO BULK CONDUCTIVITY FELDEOND = OFF RADIATION-INDUCED BULK CONDUCTIVITY FADCOND = OFI

Figure 10.7. (Concluded).

1 W/H++2. DEST = ELEC Neon = ndir additional keywords: tankcur tanktraj 3d-view matview contour PARTICLE TRACKING OPTIONS; Keyuords; emitter, sheath, sheath self-consistent 00. **6**0 MAGNETIC FIELD OPTIONS: KEYNORDS (BFIELD] (DIPOLE) Constant Magnetic Field =1 .00 No Magnetic Dipoles VECTORS FROM SATELLITE CENTER TOWARD VIENER ARE ٠ NO. OF ADDITIONAL CONTOUR PLOT CUTS = NNNNN m 6 MAIERIAL PLOI VIEW FROM + ACOU NO EMITTERS REQUESTED NO. OF 3-D PLOT VIEUS =

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\$000 \$0000 \$0000

10.9 ROTATE

Sample ROTATE output is shown in Figure 10.8. References are as follows:

- 1. The time elapsed since the beginning of the first cycle is printed.
- 2. The sun direction vector, following rotation of the satellite is printed. This will be the direction for the next call to TRILIN.

\*\*\*\*\*\*ROTATE 5 1 TIME = 7.0920 SECONDS 2 DISTANCE EQUALS 999.99999 FINAL NA1 = 68

Figure 10.8. ROTATE sample output.

10.10. SATPLT

Sample output is shown in Figure 10.9. It is all purely diagnostic.

\*\*\*\*\*\*SATPLT ASGFIL -- AASG DISTANCE EQUALS 999.99998 FINAL NA1 = 95 DISTANCE EQUALS 999.99998 FINAL NA1 = 95 DISTANCE EQUALS 999.99999 FINAL NA1 = 93

Figure 10.9. SATPLT output.
10.11 SPIN

Sample SPIN output is shown in Figure 10.10. References are as follows:

- 1. The normalized sun direction vector for the first view is printed.
- 2. The number of views, and the spin axis vector are echoed.
- 3. Each line represents a call to HIDCEL. In this case there are four views and hence four calls.

\*\*\*\*\*\*SPIN 5 ASGFIL -- BASG 2. . AVERAGE SOLAR ILLUMINATION BEING OBTAINED 1 .000 THE INITIAL SUN DIRECTION IS .707 .707 4 VIEWS WILL BE GENERATED ABOUT THE AXIS DISTANCE EQUALS 999.99998 .000 .000 1.000 2 FINAL NA1 = 62 DISTANCE EQUALS 999.99999 FINAL NA1 = 62 DISTANCE EQUALS 999.99998 3 L NAI = 62 TANCE EQUALS 999.99999 FINAL NA1 = 62

Figure 10.10. SPIN sample output.

# 10.12. STRESS

Sample STRESS output is shown in Figure 10.11. References are as follows:

- 1. The number of cells requested (10) is echoed.
- 2. For each cell in order of decreasing stress, the potential, stress field and descriptive information is printed out.

+++++STRESS 10 Electric Field Stress Cells 1 Through 10 on List of Decreasing Strength

~

| 005111270103<br>0 0 23<br>4 APT 0 2  | 004607170303<br>6 7 15<br>8 0 -1<br>8 APT 0 -1  | 004607220103<br>6 7 16<br>6 0 1<br>8 APT   | 004612170303<br>6 10 15<br>8 10 -1<br>8 APT 0 -1  | 004612220103<br>6 10 19<br>8 4 7 1 0 19<br>8 4 7 1 0 19  | 005307170303<br>11 7 15<br>8 1 0 -1   |
|--|---|--|---|--|---|
| SURFACE CELL NO. 89 CODE = NORMATION = NORMATION = NORMATION = NORMATION = NORMATION = NORMATION = POTENTIAL = -1.000,000,000,000,000,000,000,000,000,00 | SURFACE CELL NO. 1 CODE = NORMAL = NORMAL = NORMAL = NORMAL = NORMATERIAL = FIELD = 1.502+007 VOLTS/METER | SURFACE CELL NO. B CODE = LOCE = LOCHAL = NORMAL = NORMAL = NORMAL = FOCHAL = POTENTAL = -1.0006+003 VOLTS/METER | SURFACE CELL NO. 23 CODE = NORMALON = 1.5824007 VOLTS/METER | SURFACE CELL NO. 30 CODE = LORATION = LORATI | SURFACE CELL NO. 123 CODE =<br>SURFACE CELL NO. 123 CODE =<br>NORMAL =<br>Potential = -1.006+007 SMETER |

Figure 10.11. STRESS sample output.

1.1.1

| 005307220103<br>11 7 15<br>KAPT 0 1  | 005312170303<br>11 10 15<br>0 - 1<br>8 kapt<br>0 - 1   | 005312220103<br>11 10 16<br>0 1 0 1<br>KAPT   | 004610220103<br>6 8 18<br>0 0 1<br>8 APT 0 1   |
|--|--|---|--|
| SURFACE CELL NO. 130 CODE = LORE = LORE = LOREAL = LOREAL = LOREAL = LOREAL = POTENTAL = 1.562+000 VOLTS/METER | SURFACE CELL NO. 145 CODE = 100RAL = 100RAL = 100RAL = 100RAL = 141ERIAL = 1.006+003 VOLTS/METER | SURFACE CELL NO. 152 CODE =<br>Normat =<br>Normaterial =<br>Potential = -1.006+003 volts<br>field = 1.582+007 volts/Meter | SURFACE CELL NO. 15 CODE = NORMAL = NORMAL = NORMAL = FOTENTIAL = FOTENTIAL = -1.006+003 VOLTS = FIELD = 1.562+007 VOLTS/METER |

Figure 10.11. (Concluded).

10.13. TANK

Sample TANK output is shown in Figure 10.12. References are as follows:

- 1. A message is printed, showing that a shadowing table exists from a previous TANK execution.
- 2. The TANK input is echoed.
- 3. Successful definition is confirmed for each of the four guns.
- 4. A fresh call to HIDCEL is made for each gun to create a new shadowing table.

```
*****TANK 5
     OBJECT DEFINITION INFORMATION BEING READ FROM FILE
1 A SHADOWING TABLE WAS PREVIOUSLY GENERATED
    FOR THIS OBJECT USING THE GUNS OPTION
2 GUN AT 0 16 16
   ENERSY 6. KEV
   CURRENT 5.E-6
   BEAMWIDTH 30 DEGREES
   DIRECTION 0 -1 -1
   GUN AT 0 -16 16
   ENERGY 6. KEV
   CURRENT S.E-6
   BEAMWIDTH 30 DEGREES
   DIRECTION C 1 -1
   GUN AT 0 -16 -16
   ENERGY 6. KEV
   CURRENT 5.E-6
   BEANWIDTH 3G DEGREES
   DIRECTION 0 1 1
   6UN AT G 16 -16
   ENERGY 6. KEV
CURRENT 5.E-6
   BEAMWIDTH 30 DEGREES
   DIRECTION C -1 1
   END
3
   GUN DEFINITION -----
   GUN 1 HAS BEEN DEFINED AS AN ELECTRON GUN
   GUN IS LOCATED AT GRID COORDINATES 9.00 25.00 25.00
   GUN DIRECTION IS .00 -1.00 -1.00
BEAM 1: ENERGY= 6.00+003 EV CURRE
                                      CURRENTE 5.30-006 AMPS
  BEAM 1: ENERGY= 6.00+303 EV
                                                                   CUT-OFF ANGLE= 30.0000 DEGREES
    GUN DEFINITION -----
   GUN 2 HAS BEEN DEFINED AS AN ELECTRON GUN
  SUN IS LOCATED AT GRID COORDINATES 9.00 -7.00 25.00
GUN DIRECTION IS .00 1.00 -1.00
BEAM 1: ENERGY= 6.00+003 EV CURRENT= 5.00+006 AMPS
                                                                   CUT-OFF ANGLE= 30.0000 DEGREES
   GUN DEFINITION -----
  GUN 3 HAS BEEN DEFINED AS AN ELECTRON GUN
   GUN IS LOCATED AT GRID COORDINATES 9.30 -7.00 -7.00
   GUN DIRECTION IS .00 1.00 1.00
  BEAM 1: ENERGY= 6.00+CO3 EV
                                      CURRENTE 5.30-006 AMPS
                                                                   CUT-OFF ANGLE= 30.0000 DEGREES
   GUN DEFINITION ----
  GUN 4 MAS BEEN DEFINED AS AN ELECTRON GUN
  GUN IS LOCATED AT GRID COORDINATES 9.30 25.00 -7.00
                       -00 -1.00 1.00
6.00+003 EV CURPENTE 5.00+006 AMPS
  GUN DIRECTION IS .DC -1.00
BEAM 1: ENERGY= 6.00+003 EV
                                                                   CUT-OFF ANGLE: 30.0000 DEGREES
  SHADOWING BEING CALCULATED FOR GUN
                                          1
Δ
   DISTANCE EQUALS 22.627417
                  ZC
  FINAL NA1 =
  SHADOWING BEING CALCULATED FOR SUN
                                           2
   DISTANCE EQUALS 22.627417
  FINAL NA1 =
                   20
  SHADOWING BEING CALCULATED FOR GUN
                                           3
   DISTANCE EQUALS 22.627417
  FINAL NA1 = 20
Shadowing being calculated for gun
  FINAL NA1 =
   DISTANCE EQUALS 22.627417
  FINAL NA1 =
                   20
                        Figure 10.12. TANK sample output.
```

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```

10.14 TRILIN

Sample output from TRILIN is shown in Figure 10.13. The references are as follows:

- 1. The flux definition input is summarized.
- 2. The present state of the charging calculation is summarized.
- 3. A flux breakdown is printed for the cells requested.
- 4. The net current to the whole object at the beginning of the timestep is printed, with and without the effect of electric field suppression of low energy emission.
- 5. The capacitance of the object to infinity is stated.
- 6. The average flux, over the timestep, to the cells chosen for a flux breakdown is printed.
- 7. A summary of charging activity and new conductor potentials for the cycle is printed.
- 8. A summary of final surface cell potentials for the present cycle is printed.

1 CYCLES HAVE BEEN REQUESTED. Delfac= 1.00+000. SECONDS. 5.00+003 ELECTRON VOLTS 3.00+003 ELECTRON VOLTS 1.20+006 METER++1-3) 6.00+005 NETER++(-3) • 000 1.00+000/(4+PI+R) +++ THE SYSTEM IS NOW AT TIME .DOD SECONDS. Delta= 5.00+000 seconds. 1 I HE = AVERAGE PADIUS (RO) = 4.00+000 CODE UNITS ELECTRON TEMPERATURE = POTENTIALS TO BE SET BY SETALL TO ++++\*IRILIN
FLUX DEFINITION SINGLE MAXWELLIAN ELECTRON DENSITY = ION TEMPERATURE = ION DENSITY = BEGIN CYCLE NO.

2

CODE UNITS. 1100 (SCREENING LENGIH= 2.00+002 m.) 9SUM= 1.00+000 10+000 (CORRECTED TO 2.00+000 ITED ELECTRONS. SECONDS. 1000 · 000 1.989-002 LIMITING FACTORS FOR QSUMER FOUND QSUM= 1.000000 AFTER SCREENING CORREC QSCALE: 1.00 PCOND = 1.0 PCOND = 1.0 EXPLICITLY CALCUL DURING THIS TIMES ADDITIONAL EFFECT 

Figure 10.13. TRILIN output.

| 004611216003<br>- 1 0 1<br>KAPT 0 0<br>KAPT 0  | 004612210403<br>6 10 12<br>7 10403<br>7 10403  | 005107211403   |
|--|--|--|
| CODE = NATERIAL = NORMAL = COD2 VOL 15/NETER = 2,25 - 000 VOL15/METER = -6,27 - 007 VOL15/WETER = -6,27 - 000   | CODE ::<br>CODE ::<br>COD | CODE = CODE = CODE = CODE = CODE = COCETION = NORMAL = NORMAL = NORMAL = CODE = |
| 0. 20<br>POTENTIAL :<br>STRESSTAL :<br>STRESSTAL :<br>STRESSTAL :<br>STRESSTAL :<br>EXTERNAL : | NO. 28<br>POTENTIAL ::<br>STRESS ::   | NO. 77<br>POIENITAL  |
| SURFACE CELL N<br>FLUXES IN A/M<br>IN CIDEN<br>IN CIDEN<br>PEC<br>PHOTOCU  | FLUXES IN A/H<br>INCIDEN<br>BULK RE<br>BULK RE<br>PHDTOCC  | SURFACE CELL P<br>FLUXE S IN AN<br>INCIDER<br>BULM CO  |

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Figure 10.13. (Continued).

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|  | •   |  | -  |
|--|---|--|--|
| 005141270103<br>MAPT 0 21<br>MAPT 0 21   | 005307212001<br>1 7 17<br>60LD 0 10<br>60LD   | 01111120302<br>0 0 1 1<br>50LA 0 -1  | 00000111123  |
| CODE E<br>CODE E<br>CODE TION =<br>HATERIAL =<br>H | CODE = CODE = CODE = CODE = CODE = CODE = COOP = COOP = COP | CODE =<br>CODE =<br>CODE =<br>NoRMAL =<br>NoRMAL =<br>NoRMAL =<br>NoRMAL =<br>Normal =<br>Normal =<br>Normal =<br>Normal =<br>Norma<br>1.000 + 000<br>1.15<br>2.555-000<br>1.15<br>2.555-000<br>1.001<br>3.01 -000<br>3.01 -000<br>5.555 -0000<br>5.555 -0000<br>5.5555 -0000<br>5.555 -0000<br>5.555 -0000<br>5.555 | CODE = CO   |
| SURFACE CELL NO. 89<br>FOTENTIAL = 5000<br>FLUXES IN A/N+2<br>FLUXES IN A/N+2<br>F   | SURFACE CELL NO. 129<br>POTENTIAL =000<br>FLUXES IN A/M++2<br>INCIDENT ELECTRONS<br>INCIDENT ELECTRONS<br>INCIDENT PLATONS<br>PHOTOCURRENT MG SECONDARIES<br>PHOTOCURRENT MG SECONDARIES<br>PHOTOCURRENT MG SECONDARIES<br>NET FLUX   | SURFACE CELL NO. 167<br>POTENTIAL = 111 000<br>STRESS = 1.111 000<br>STRESS = 1.111 000<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>F   | BOOM SURFACE CELL NO. 181<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>NCIDENT FLECTRONS<br>INCIDENT FRONS<br>INCIDENT PROTONS<br>INCIDENT PROTONS<br>INCI |
|  |   |  | Figure 10.13. (Conti   |

4 INITIAL NET CHARGING CURRENT (WITHOUT LIMITING) = 3.60-007 ANPERES. 1 INITIAL NET CHARGING CURRENT (WITH LIMITING) = 3.60-007 ANPERES. 8.83-012 FARADS. 49.9 CODE UNITS; AVERAGE FLUXES IONLY AVAILABLE FOR INSULATING CELLSI LEAVING ICCG2 -- VCTRI = 3.040+000 1.726+000 4.00-021/ 9.79+006 1.65-025/ 1.14+006 3.034+000 1.721+000 2.067+005 1.939+005 1.16-014/ 4.16+011 3.53-025/ 1.95+006 1.94+006 •000 •000 CONDUCTOR 1 FIXED TO 3.03 VOLTS. 2.71-025/ •000 .000 TOTAL CAPACITANCE TO INFINITY = ICCG --- RDOTR/RDOTR1 = LEAVING ICCG1 -- VCTRI = NO DISCHARGE ANALYSIS NO DISCHARGE ANALYSIS ഹ

Figure 10.13. (Continued).

Figure 10.13. Continued.

Figure 10.13. (Continued).

CONTINUE CYCLE NO. 1 AT UPDATED TIME = 5.000+000 SECONDS. QSUM = -1,9665+002

| NEW CONDUCTOR POTENTIALS                               |                          |  |       |
|--|--------------------------|--|-------|
| VNEW<br>3.04044000 7.694640<br>1.72564000 -9.7015-0    | 002<br>005<br>005        | 00 VOLD CUNDUCT<br>00                  | 8 - N |
| TOTAL CHANGE IN CHARGE =                               | -1.966+002<br>-3.482-011 | CODE UNITS<br>Coulonrs                 |       |
| AVERAGE NET CHARGING CURRE                             | NI = -6.96               | 55-D12 ANPERES<br>33+DU1 CODE UNITS/SE | :     |
| CONDUCTOR CURRENTS LAMPS; PC                           | SITTLE INTO              | CONDUCTORS):                           |       |
|  | -                        | 2                                      |       |
| NET CURRENTIAVG DQ/DT1:                                | 2.73-008                 | -3.44-018                              |       |
| CONDUCTIVITY CURRENT (NEW)<br>(FROM INSULATING CELLS): | -4.71-013                | -1.86-016                              |       |
| PLASMA CURRENT (INITIAL)<br>(10 Baré Cells);           | 1.42-007                 | 00•                                    |       |
| REMAINDER CURRENT;                                     | -1.15-007                | -1.55-018                              |       |
|  |                          |  |       |

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A/H++2 A/H++2 A/H++2 A/H++2

- 4 • 252 - 007 - 7 • 173 - 008 - 6 • 252 - 007 - 6 • 252 - 007

100 CELLE CELLE CELLE 100 CELLE 100 CELLE 100 CELLE

AVERAGE FLUX 1 AVERAGE FLUX 1 AVERAGE FLUX 1 AVERAGE FLUX 1 AVERAGE FLUX 1

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2 10 \*\* н IPSAVE **IPSAVE** 13 2 READ ... - 11 ISPARE **I SPARE** -5 : out 2 12 15 ... - 14 GRIDS 2 COMPLE TED 2 14 14 -11 11 Я 38 CYCLE ł PCOND = QCOND = NEXTRA= EFPREP 12 ACE н LAST .. SURF 4 4 I (Concluded) Figure 10.13

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POTENTIALS

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9.7655.000 9.7655.000 9.7655.000 9.7655.000 9.7655.000 9.7655.000 9.7655.000 9.7655.000 9.7655.000 9.7655.000 9.7659.0000 9.7659.0000 9.7709.0000 9.7709.0000 9.7709.0000 9.7709.0000 9.7709.0000 9.7659.0000 9.759.00000 9.759.00000 9.759.00000 9.759.00000 9.7

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#### 11. A WORKED EXAMPLE

#### 11.1 INTRODUCTION

In this chapter we work through a real NASCAP example. We describe the NASCAP runs that were made and how we decided on the options and other parameters that were used. In this way, we illustrate the use of NASCAP at a practical hands-on level.

No one example could use all of the features of the code. (This would almost certainly be confirmed by anyone who has just read the previous ten chapters!) Examples showing the use of important options that are not part of this worked example are included in the relevant earlier chapters.

In the example we have chosen to work through, we assume that we are supplied with a design for a proposed satellite, and a description of the type of plasma environment it might be expected to encounter in orbit. This gives us a good starting point for the preparation of two of the three major user input files: The object definition file and the flux definition file. The makeup of the third input file, (the run options file), depends on the type of simulation that we want to carry out.

Let us assume that the satellite is to have a particle detector mounted on its surface. If the satellite charges differentially (i.e., the different dielectric materials acquire different surface potentials) the spectrum of particles collected by the detector might be affected. We want to use NASCAP to analyse

- (a) the charging of the satellite, exposed to the chosen plasma spectrum, to equilibrium.
- (b) how the satellite being charged in this way affects the operation of the detector.

We begin this study by establishing the object, its capacitance, and shadowing. In a series of runs we determine the charging response of the object with the supplied plasma spectrum. Finally, we examine the operation of the detector using the DETECT module.

## 11.2 OBJECT DEFINITION

The first step in our study is to define the object at hand. The satellite in our example consists of a central cuboid and two spherical globes, each at the end of a metallic boom. One of the globes is electrically isolated from the rest and forms a separate conductor. All but one face of the satellite body is covered with KAPTON. The remaining face is covered with GOLD foil. The booms are made of ALUMINUM. One of the globes is covered with SOLAR cell cover glass material - called "SOLAR". This is SiO<sub>2</sub> glass covered with a MgF<sub>2</sub> non-reflective layer.

The object definition file defining a NASCAP representation of this satellite is shown in Figure 11.1. The materials GOLD and SOLAR have their properties definited explicitly. The remaining two materials specified, KAPTON and ALUMINUM are default materials, and their properties are read in from the default materials table. The object consists of five building blocks: The central RECTAN, two BOOMS, and two QSPHERES. The second QSPHERE forms CONDUCTOR 2.

Figure 11.1. Object definition file.

88.8 10000. 1 77.5 1.E+19 10000. 1111.E-13 I. E+3 ZO. CONC. L.ETJ I.E. 12:COMMENT PROPERTIES OF KAPTON AND ALUMINUM FROM DEFAULT TABLE. 13:CONDUCTOR 1 14:COMMENT CENTRAL CUBOID 15:RECTAN 16:CORNER -3 -2 -2 15:RECTAS 6 4 4 œ.--Ŧ .88 .000029 2.05 .00002 14:COMMENT SOLAR SPHERE (ON SEPARATE CONDUCTOR) RIAL GOLD AND SOLAR UORKED EXAMPLE (CHAPTER 11) 79. 135. .E-17 10 MENT BOOM TO KAPTON SPHERE TAXIS 0 2 0 4 READIUS 0.05 Surface Aluminum Rendobj Pomment Boom to Solar Sphere E+3. 14 ZONE SIZE IS 0 DEFINE MATERIA 16:ENDOBJ 17:COMMENT KAPTON SPHERE .000179 13: AXIS 0 0 -2 0 0 -4 14: RADIUS 0.05 15: SURFACE ALUMINUM CE -Y KAPTON CE +Z KAPTON CE -Z KAPTON ð 100 CHATERIAL KAPTON S RIAL SOLAR <u>.</u> ICENTER 0 0 -6 0:DIAMETER 3 1:COMMENT 2:COMMENT 3:COMMENT 4:GOLD 5:1.00 6:53.48 7:1.E-13 9:CENTER 0 **I Q S P H E R E** 8:0SPHERE 48:01AMETE 49:51DE 1 59:51DE 1 50:50100BJ 52:END5AT 61:52 01156.1 **BIENDOBJ** 20 : SURI 18:5UR 1:51DE SUR 9:30 SUF 5

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.92 2000. .45 2000. The choice of coordinates for each building block is determined by the physical size of the object and the choice of XMESH. Let us assume that our object has the following dimensions:

| Part |   | Size | \$ |
|------|---|------|----|
|      | - | _    | -  |

| Globe diameter | 63 mm            |
|----------------|------------------|
| Boom length    | 41.5 mm          |
| Cuboid         | 78 x 78 x 124 mm |
| Boom radius    | 1 mm             |

A choice of XMESH = 0.020 m (20 mm) allows these dimensions to be replaced by mesh units as follows:

| Part           | <u>Size (mesh units)</u>                                     |
|----------------|--|
| Globe diameter | 3 ≡ (60 mm)  |
| Boom length    | 2 ≡ (40 mm)  |
| Cuboid         | $4 \times 4 \times 6$ ( $\equiv 80 \times 80 \times 120$ mm) |
| Boom radius    | $0.05 \ (\equiv 1 \ mm)$                                     |

It is always almost impossible to reproduce the dimensions of the object exactly. XMESH usually turns out to be a compromise choice, giving the best overall representation of the object. We could have chosen XMESH to be smaller and still have been able to fit the object within the  $17 \times 17 \times 33$  inner mesh. However, since the object is fairly simple a detailed representation results in little gain in accuracy compared with the extra computational effort involved.

## 11.3 THE FLUX DEFINITION FILE

Let's suppose we are lucky and the plasma environment we have been given is in Maxwellian form, with the following parameters.

|             | Electrons                  | Ions                     |
|-------------|----------------------------|--------------------------|
| Density     | $1.2 \times 10^{6} m^{-3}$ | $0.8 \times 10^6 m^{-3}$ |
| Temperature | 5.0 keV                    | 3.0 keV                  |

This data can be entered directly into the flux definition file as shown in Figure 11.2.

If the environment description was in some other form it might first be necessary to reduce it to either a single Maxwellian or double Maxwellian form by a least squares fit. Tables of data can be entered directly (5.4.3), but this is not recommended.

The angular distribution of the plasma is isotropic.

|       | 1: SINGLE MAXUELLIAN |
|-------|----------------------|
|       | 215.0 KEV            |
|       | 3:1.2 CGS            |
|       | 413.0 KEU            |
|       | 5:0.8E06 MKS         |
|       | 6:END                |
| EOF:6 |                      |
| 41>   |                      |
| • • • |                      |

# Figure 11.2. FLUX definition file.

#### 11.4 THE OPTIONS FILE

The options file for the first run is shown in Figure 11.3. XMESH has been set to 20 mm, as decided during the object definition. The purpose of our first NASCAP run is to establish the object and make one trial call to TRILIN. Hence, just one short (5 second) cycle is requested using DELTA and NCYC. As we shall see later in Section 11.6, the results of this trial cycle will give us insight into the parameters we shall choose for the subsequent, charging runs.

When orbiting the earth the satellite will find itself exposed to sunlight. We assume that the sun lies in the XY plane of the satellite and shines with a normal intensity. These assumptions are introduced into the run using the SUNDIR and SUNINT cards as shown.

The LONGTIMESTEP option is specifically requested. This is always a good idea, unless a detailed simulation of the transient charging response is required (see Section 6.2.6). Any plots produced are set to be routed to the S-Cubed electrostatic plotter.

Finally, a detailed flux breakdown is requested for the seven surface cells shown using the SURFACE CELL option. These cells are not chosen at random, but on the basis of a preliminary interactive run.

1 \* XMESH 0.02 22 SUNDIR 1 4:DEST ELEC 15 : END E0F 15

Figure 11.3. The OPTION file (first run).

8:>

## 11.5 A PRELIMINARY LOOK AT THE OBJECT

Before submitting the first batch run, it is a good practice to check to see if your object definition file actually defines the object you had in mind. This can be done quickly and easily by running NASCAP interactively from a graphics terminal. The input files are prepared as described in Sections 11.2 - 11.4. NASCAP is executed like any other interactive program and the primary keywords RDOPT, OBJDEF and SATPLT are entered at the keyboard as prompted. Since output is routed to the terminal immediate feedback is available and mistakes can be readily corrected. Plots can be routed to the terminal or plotter using the DEST option (Section 6.6.3).

The same effect can be achieved more easily using the NASCAP auxiliary code NASCAP\*OBJCHECK.<sup>[20]</sup> This is a fully interactive combination of OBJDEF and SATPLT, specifically designed to check out the definition of objects at a graphics terminal.

As a byproduct of an interactive look at the object a surface cell list is displayed. This allows us to pick out the cell numbers to be included on SURFACE CELL cards in the options file. In our example, cells on the cuboid pointing in the  $\pm x$  and  $\pm y$  directions were chosen, along with cells pointing in the  $\pm z$  directions on the globes, and a boom cell. This selection gives an all-around look at the spacecraft and samples all building blocks and all materials. The flux breakdowns from these cells will be very useful in understanding the physics behind the charging of the satellite during the simulation.

#### 11.6 THE FIRST RUN

A UNIVAC version of the NASCAP runstream used for the first run is shown in Figure 11.4. The sequence of cards can be classified into 6 groups, labeled A-F.

- A. Simple utility cards initiate the run and create a heading.
- B. Temporary work files are assigned.
- C. The prefixed, permanent files are copied into their temporary counterparts. (This protects any permanent information.)
- D. The NASCAP absolute is executed.
- E. The NASCAP primary keywords are read by the main program.
- F. If NASCAP has executed successfully, the permanent files are updated. If execution is aborted these steps are never reached.

All NASCAP runstreams follow this pattern. Only the sequence of primary keywords changes.

In this first run RDOPT is the first module to be executed. This is true of every run. The next four modules OBJDEF, SATPLT, CAPACI AND HIDCEL establish the object: OBJDEF formally defines it, SATPLT produces 3D-VIEWS (6.6.1) and MATVIEWS (6.6.4), CAPACI determines its capacitances, and HIDCEL its shadowing table. Finally a call to TRILIN is made for a trial charging cycle.

The printed output produced by this run is shown in Figure 11.5. The graphical output is shown in Figure 11.6.



Figure 11.4. NASCAP runstream (first run).

Figure 11.5. First run printed output.

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| PRINTED.  | PRINTED.<br>Printed.<br>Printed.                       | E PRINTED.<br>E Printed.<br>E Printed.  |   |
|---|--|---|---|
| 96  |  |   |   |
| 10  | 101  | 1 1 1   |   |
| INF ORMATION  | INFORMATION<br>INFORMATION<br>INFORMATION              | INF ORMA TION<br>INF ORMA TION<br>INF ORMA TION                                       |   |
| 20  | 129<br>28<br>77  | 98<br>167<br>181  |   |
| INPUT   | כברך<br>כברך<br>כברך                                   | 1133<br>CELL<br>CELL  | 0 |
| XHESH D.D2<br>Kevword<br>NCVC 1<br>Delta<br>Surface cell 20 | SURFACE CELL 129<br>Surface cell 28<br>Surface cell 77 | SURFACE CELL 80<br>Surface cell 167<br>Surface cell 181<br>Longtimestep<br>Sunthi 4-0 |   |

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(Continued). Figure 11.5. OPTIONS: NY NY NZ NG 17 17 33 2 Full Outer Grid Used Additional Option Words: Offset, Tanksize, Ztrunc, Tank Radius, Tank Axis IPART 28 NASA CHARGING ANALYZER PROGRAM OPTION SUMMARY 108J 108PLT 18 19 LONGTIMESTEP AND DISCHARGE OPTIONS Keywords: Longtimestep. Nolongtimestep. Discharge. Flashover Longtimestep Requested with DVLIM= 1000.0 volts. 7 SURFACE CELLS SPECIFIED FOR 1/01 20 28 77 88 129 167 181 Keywords: Esurface Cellj, Esurface atj, Esurface Copnerj IROUSP IAREA 27 HIDCEL INTERCONDUCTOR CAPACITANCES: KEYWORD CIJ THE CODE UNIT OF CHARGE IS 1.771-D13 COULOMBS. The code UNIT of Capacitance is 771-D13 farads. No interconductor Capacitances Specified. SECONDARY EMISSION FORMULATION = ANGL EFFECTIVE PHOTOSHEATH CONDUCTIVITY EEFFCON3 = OFF FIELD-ENHANCED BULK CONDUCTIVITY (FLDCON) = OFF RADIATION-INDUCED BULK CONDUCTIVITY (RADCON) = OFF POTENTIAL SOLVER OPTIONS: POTCON MAXITR IOUTER SCALE 99 Scaling Keywords: Scale DSCALE Ambient Space Charge Option Emerword DEBVE 3-None .000 RESTART FILES: 10 IROUS IPOCND ILTBL ICNON 10 15 16 17 21 ISPARE 14 XME SH= 2.00-002 CONDUCTOR FIXING AND BIASING:KEYWORDS FIXP, BIAS, FLOAT IFLUX ISPCTR IT CUR PRINT CNOPRINTS: CONVERGENCE PLOTS 3= 0 SOHE ILLUMINATION SPECIFICATIONS I SUNINTE 1.000 Shadoming Formulation Ekeyword=Convex3=Shad TIMER CNOTIMERJ IDIV IU 25 13 I TPART 0 RUN HODE OPTIONS: ICREST IPREST NCVC MCYC DEADLINE 5.00100 1.001000 DEADLINE 5.00100 1.001000 ADDITIONAL KEYWORD = CRESTARTJ INPUT FILES: IKEYND ISAT 26 20 REPEAT 81 27 ENVIRONMENT TYPE AND MESH SIZE Itype= 2 Update=off NGPRT EAPRIJ 0 SCRATCH FILES: JAUN 11 PLOT OPTIONS: TITLE=WASCAP NGPLOT ICON LOGICAL UNIT NUMBERS GRID SIZE OPTIONS: OUTPUT OPTIONS: TITLE =NASCAP

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Figure 11.5. (Continued).

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Figure 11.5. (Continued).

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PREPROCESSING OF MATERIAL PROPERTIES

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1 CYCLES HAVE BEEN REQUESTED. Delfac= 1.00+000. 5.00+003 ELECTRON VOLTS 3.00+003 ELECTRON VOLTS 1.20+006 HETER++(-3) 8.00+005 NETER++(-3) .0793 METERS 1.00+000/14+PI+R) \*\*\* THE SYSTEM IS NOW AT TIME ... DUD ... SECONDS. Delta: 5.00+000 Seconds. 50 POTENTIAL TTERATIONS COMPLETED. -2.1205-0000 88755-000 -3.5565-002 3.5561-002 AVERAGE RADIUS (RO) = 4.00+000 CODE UNITS SMALL INTERCONDUCTOR CAPACITANCES: -2.73+001 2.72+001 CRDEFF --- EFFECTIVE OBJECT RADIUS = ELECTRON TEMPERATURE = POTENTIALS TO BE SET BY SETALL TO ELECTRON DENSITY = ######RILIN FLUX DEFINITION SINGLE MAXWELLIAN ION TEMPERATURE = ION DENSITY = \*\*\*\*\*\*HIDCEL DISTANCE EQUALS 999.99998 62 FINAL NAI = PCOND =

Figure 11.5. (Continued).

005107211403 9 7 17 0 -1 0 KAPT CODE UNITS. 110N (SCREENING LENGTH= 2.00+002 M.) QSUM= 1.00+000 12.000 12.000 19-002 1.989-002 004612210403 6 10 17 0 1 0 KAPT RGES ENTITER OPERATION . SECONDS. CODE = Location = Normal = Material = CODE = Location = Normal = Material = VOL 15 VOL 15/HE TER 000 1.000+000 1.000+000 CODE = LOCATION NORMAL = MATERIAL . , сн. - 000 2.28-006 9.75-007 6.01-007 2.75-007 41-008 41-008 41-008 2.28-006 9.75-007 6.01-007 -6.27-007 1.35-005 2000 200 2000 2 1.989-002 .000 CTOR. POTENTIAL = STRESS = 1. External fie Limiting fac g POTENTIAL = STRESS = 1 External f1 Limiting fa POTENTIAL STRESS = EXTERNAL F LIMITING F EXPLICITLY CALCULATED FLUXES FOR CY DURING THESTEP MASCAP WILL T DURING THESTEP S SURFACE AND VARIATION OF LIMITING FACTORS DU CTRONS NG SECONDARIES NG BACKSCATTER 10NS CTRONS NG SECONDARIES NG BACKSCATTER FLUXES IN A/M++2 INCIDENT ELECTROMS Resulting becondaries Resulting backscatter G SECONDARIES VG SECONDARIES QSUMER FOUND QSUM= 1.00+001 AFTER SCREENING COMPL QSUM = 1 QSUM = 1 PCOND = 1 QCOND = 1 17 20 28 FLUXES IN A/H++2 INCIDENT EL RESULT INCIDENT PR BULK RESULT BULK RESULT PROFOCURREN FLUXES IN A/M++2 INCIDENT EL RESULT RESULT INCIDENT PR BULK CONUT BULK COURREN PHOTOCURREN SURFACE CELL NO. SURFACE CELL NO. SURFACE CELL NO. NET FLUX NET FLUX ............. .......

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Figure 11.5. (Continued).

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|  |  |   | Figure 11.5.  | -                         |
|  | 44PT 0 21<br>KAPT 0 21<br>KAPT 0 21  | 005307212001<br>11 7 17<br>60LD 0 10  | 01111120302<br>0 11<br>50LA 0 -1<br>50LA 0 -1   | 000061111123              |
| 2.75-008<br>4.57-008<br>1.57-014<br>   | CODE =<br>CODE =<br>CO | CODE = CODE = CODE = CODE = CODE = CODE = COPRAAL = COPRAAL = COPPO =   | CODE =<br>CODE =<br>NORMAL =<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>=<br>NORMA<br>NORMA<br>NORMA<br>=<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NORMA<br>NOR | CODE =<br>LOCATION =      |
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Figure 11.5. (Continued)

INITIAL NET CHARGING CURRENT (WITHOUT LIMITING) = 3.60-007 AMPERES. INITIAL NET CHARGING CURRENT (WITH LIMITING) = 3.60-007 AMPERES. DIRECTION = Z MATERIAL = ALUM 8.83-012 FARADS. CONDUCTOR -6.965-012 AMPERES -3.933+001 CODE UNITS/SEC. VOLTS/HETER 1.000+000 1.21-00 49.9 CODE UNITS; AVERAGE FLUXES TONLY AVAILABLE FOR INSULATING CELLSI CONDUCTOR CURRENTS (AMPS; POSITIVE INTO CONDUCTORS); -1.966+002 CODE UNITS -3.482-011 COULOMPS -3.44-018 1.65-025/ 1.14+006 -6.252-007 A/H++2 -7.173-008 A/H++2 -6.252-007 A/H++2 -6.252-008 A/H++2 ICCG --- RD0TR/RD0TR1 = 1.16-D14/ 4.16+D11 2.067+005 1.939+005 3.53-025/ 1.95+006 1.94+006 3.034+000 1.721+000 4.00-021/ 9.79+006 3.040+000 1.726+000 0000 • 0000 • 0000 POTENTIAL = .000 FIELD = .000 LIMITING FACTOR = •000 000 CONDUCTOR 1 FIXED 10 3.03 VOLTS. 2.71-025/ 2.73-008 • 000 .000 ECONDARIES ACKSCATTER NG SECONDARIES TOTAL CAPACITANCE TO INFINITY = AVERAGE NET CHARGING CURRENT = 7.6946+005 -9.7015-005 ~~~~ ICCG --- R00TR/R00TR1 = ICCG --- RD01R/RD01R1 = ICCG --- RDOTR/RDOTR1 = ICCG --- R00TR/RD0TR1 = LEAVING ICCG1 -- VCIRI = LEAVING ICCG1 -- VCTRI = LEAVING ICCG1 -- VCTRI = LEAVING ICCG2 -- VCTRI = TOTAL CHANGE IN CHARGE = LEAVING ICCG1 -- VCTRI = NEW CONDUCTOR POTENTIALS NO DISCHARGE ANALYSIS NO DISCHARGE ANALYSIS NET CURRENTIAVG DQ/DT): AVERAGE FLUX TO CELL RESULT INCIDENT PR RESULT PHOTOCURREN FLUXES IN A/M++ 3.0404+000 1.7256+000 NET FLUX

-1.88-018 -1.55-018 00. 1.42-007 -1.15-007 -4.71-013 CONDUCTIVITY CURRENT (NEW) (FROM INSULATING CELLS): PLASMA CURRENT (INITIAL) 170 BARE CELLS): REMAINDER CURRENT

5.000+000 SECONDS. 11 CONTINUE CYCLE NO. 1 AT UPDATED TIME QSUM = -1.9665+002 s s

2 10 34 POTENTIAL ITERATIONS 3.040-000 34 POTENTIAL ITERATIONS COMPLETED. 3.0904-000 -1.7256-000 7.4010-005 -1.1685-002 11 ... = 13 IPSAVE **IPSAVE** I READ IN. 13 ... 184 CELLS ISPARE ISPARE 1 GRIDS OUT OF : = 12 IP = 12 IR = 14 IU = 10 - ALL LAST CYCLE COMPLETED IS 10 POTENTIALS 14 = 10 1R 1 PCOND = QCOND = NEXTRA= 0N3+++++ ACE NO. EFPREP SURF 4

(Concluded).

Figure 11.5.

**EEND NASCAP3** 

BASG,A NASCAP+PLOTREAD. Fac warning 04000104000

**BXQT NASCAP+PLOTREAD.** Device option = 3.



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Figure 11.6(a). 3D-VIEW of object produced by SATPLT (Hidden lines).



Figure 11.6(b). 3D-VIEW of object produced by SATPLT (No hidden lines).



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Figure 11.6(c). 3D-VIEW of object produced by SATPLT (Hidden lines).



Figure 11.6(d). 3D-VIEW of object produced by SATPLT (No hidden lines).

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Figure 11.6(e). 3D-VIEW of object produced by SATPLT (Hidden lines).



Figure 11.6(f). 3D-VIEW of object produced by SATPLT (No hidden lines).

SURFACE CELL MATERIAL COMPOSITION AS VIEWED FROM THE NEGATIVE Z DIRECTION

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FOR Z VALUES BETHEEN 1 AND 33



SURFACE CELL MATERIAL COMPOSITION AS VIEWED FROM THE POSITIVE Z DIRECTION

FOR Z VALUES BETWEEN 1 AND 33





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Figure 11.6(h). MATVIEW produced by SATPLT.

SLAFFACE CELL MATERIAL COMPOSITION AS VIEWED FROM THE NEGATIVE Y DIRECTION

FOR Y VALUES BETWEEN 1 AND 17

MATERIAL LEGEND





SURFACE CELL MATERIAL COMPOSITION AS VIEMED FROM THE POSITIVE Y DIRECTION

FOR Y VALUES BETHEEN 1 AND 17

MATERIAL LEGEND

| 2    | 3    |
|------|------|
| SOLA | KAPT |



SURFACE CELL MATERIAL CUMPOSITION AS VIEWED FROM THE NEGATIVE X DIRECTION

FOR X VALUES BETWEEN 1 AND 17

MATERIAL LEGEND

| 2    | 3    |
|------|------|
| SOLA | KRPT |



SURFACE CELL MATERIAL COMPOSITION AS VIEWED FROM THE POSITIVE X DIRECTION

FOR X VALUES BETWEEN 1 AND 17

MATERIAL LEGEND







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Figure 11.6(m). 3D-VIEW of object generated by HIDCEL.

The printed output for each module follows the same format described in Chapter 10. The plots have the standard forms discussed in Chapter 9.

The output shows that all modules executed successfully and that the object is fully established. Providing the sun direction is not changed, any further runs need involve only RDOPT and TRILIN modules.

Inspection of the TRILIN output shows that only the KAPTON cells in shadow began to charge negatively. The remaining cells have positive net currents, either due to photoemission or high secondary yields. This is reflected in the last of the cell potentials printed at the very end of the TRILIN output. The shaded KAPTON cells all have potentials of around -10 V. The remaining cells are close to neutral or slightly positive.

When only one part of an object is charging negatively, differential potentials between it and the rest of the object soon build up. However the electric fields associated with this differential charging act to limit its magnitude by causing the rest of the object to begin charging too. This occurs because the electric field inhibits the escape of low energy photo and secondary electrons, thereby cutting off the source of positive current to the non-charging cells. Hence, eventually the charging cells (in this case shaded KAPTON) drive the whole object to a negative potential. This type of charging has been described as "bootstrap",<sup>[21]</sup> "potential barrier",<sup>[22]</sup> and "saddle point".<sup>[23]</sup> Because it occurs via differential charging, its timescale is typically long (minutes rather than seconds).

In our example the KAPTON is charging at about 2 volts per second. We shall want to increase the timestep in the second run so that the potential changes by about 500 V per cycle.

## 11.7 THE SECOND RUN

In this run we call only two modules, and the NASCAP primary keyword input consists of

RDOPT TRILIN END

We begin the charging-to-equilibrium simulation with a run involving 5 cycles. If more are needed we can always RESTART a subsequent run and add further cycles. With the initial charging rate of 2V per second, a timestep of 200 s will increase the KAPTON potential by -400 V each cycle. This is a manageable rate of charging. We continue to use the LONGTIMESTEP option, this time with a dvlim of 500 V, instead of the default value of 1000 V. With a higher value of dvlim there is a danger of potential overshoot and oscillation.

The options file used in the second run is shown in Figure 11.7. Changes have been made to NCYC, DELTA and LONGTIMESTEP as described above. The mechanical capacitance between the two conductors has been introduced with option CIJ (1 x  $10^{-12}$  F).

Contour plots for the last cycle have been requested. The run is RESTARTed from cycle 1.

The output from the second run is shown in Figure 11.8. Inspection of the flux breakdown shows that each cell gradually achieves a negative net current as the low energy emission is suppressed. Consequently more of the cell potentials become negative from cycle to cycle, until the last cycle (number 6) when the whole object has reached almost -1 kV (as measured by the conductor potentials).

```
1:XMESN 0.02

2:NCYC 5

3:DELTA 200

4:SUNFACE CELL 20

5:SUNFACE CELL 20

5:SUNFACE CELL 23

7:SUNFACE CELL 23

7:SUNFACE CELL 23

9:SUNFACE CELL 23

9:SUNFACE CELL 121

11:LOMCTIMESTEP 1000

12:SUNINT 1.0

13:SUNDIR 1 1 0

14:DEST ELEC

15:CIJ 1 2 1.E-12

16:CONTOURS STANDARD MOD 5

17:RESTART

18:END

EOF:18

0:>
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Figure 11.7. The Run Options file (second run).

Figure 11.8. Printed output (second run).

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| 10 BE                                    | 10 8E<br>10 8E                   |                                       | -012        |  |
|--|----------------------------------|---------------------------------------|-------------|--|
| L NOI                                    | L N01                            | L NOI                                 | 1.00        |  |
| RMAT                                     | TAMAT<br>TAMAT<br>TAMAT<br>TAMAT | RMAT                                  | 01          |  |
| INF 0                                    | INF O<br>INF O<br>INF O<br>INF O | INF 0<br>INF 0                        | ) SET       |  |
| 20                                       | 129<br>28<br>77                  | 161                                   | 1, 21       |  |
| NPUT<br>Cell                             | כברו<br>כברו<br>כברו             |                                       | 00 8        |  |
| 40 F                                     |                                  |                                       | DR<br>H     |  |
| (E Y N O<br>.L 20<br>.L 12               | .L 28<br>.L 77<br>.L 88          | 0 20 8                                | -12<br>ANDA | 00000000000000000000000000000000000000 |
| 0.02 <sup>#</sup><br>200<br>500<br>6 CEL |                                  | E CEL<br>Meste<br>Lec 1               | 2 1•E       |  |
| RESH<br>REAS<br>REAS                     | IRFAC:<br>Irfaci<br>Irfaci       | RFAC                                  | U I I SI AR |  |
|  | SL<br>SL                         | S S S S S S S S S S S S S S S S S S S |             | ~~~~~~~~~~                             |

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NASA CHARGING ANALYZER PROGRAM Option Summary

• ç • AXIS OFTIONS: NY NY NZ NG FULLOUTER GTD USED Additional Offion Swords: Offset, tanksize, ztrunc, tank radius, tank • IPART 28 108J 108PL1 18 19 • LONGTIMESTEP AND DISCHARGE OPTIONS WEYNORDS: LONGTIMESTED, NOLONGTIMESTEP, DISCHARGE, FLASHOVER Longtimestep requested with DVLIM= 500.0 Volts. Discharge analysis off IAREA 27 9 INTERCONDUCTOR CAPACITANCES: KEYWORD CIJ The code unit of charge is 1.771-013 coulombs. The code unit of capacitance is 1.77-013 farads. POTENTIAL SOLVER OPTIONS: POTCON MAXITR IOUTER SCALE NOTSET 99 Scaling Revords: Scale Noscale DSCALE Ambient space charge option (revuerd denver)=""" ILTBL ICNON 17 21 ISPARE 14 CONDUCTOR FIXING AND BIASING:KEYWORDS FIXP, BIAS, FLOAT ------• I SPCTR 1U 13 9 IFLUX 22 IPQCND 16 IPREST NCYC MCYC 1 5 1 101V 25 VEADLINE 2. DELTA 1. DELFAC 2. DELTA 1. DELFAC XDDITIONAL WEYWORD = ERESTARTJ • 1547 20 IROUS 15 12 • INPUT FILES: IKEYND 26 SCRATCH FILES: IAUN 11 RESTART FILES: 1P 10 RUN HODE OPTIONS: ICREST • UNIT NUMBERS CIJSUM: 5.6+000 5.6+000 GRID SIZE OPTIONS: TITLE =NASCAP LOGICAL

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(Continued).

Figure 11.8.

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ILLUMINATION SPECIFICATIONS; SUNINT= 1.000 SUNDIR = .7071 .7071 Shadoning formulation [reynord=convex]=Shad

ENVIRONMENT TYPE AND MESH SIZE ITYPE= 2 UPDATE=OFF

XHE SH= 2.00-002

2000 000 1 H/M++2. ÅDITTONAL ÄEYWORDS: TANKCUR TANKTRAJ 3D-VIEW MATVIEN CONTOUR - 5000 PARTICLE TRACKING OPTIONS: keywords: Emitter, Noemitter, Sheath, Sheath Self-Consistent IROUSP 0 7 SURFACE CELLS SPECIFIED FOR 1/0: 20 77 88 129 167 181 8 keywords: Esurface Cellj, Esurface atj, Esurface Cornerj 5.00+003 ELECTRON VOLTS HIDCEL 80. 0000 0000 0000 0000 0000 ULATION = ANGL' CUDUCTIVITY [EFFCON] = OFF CUDUCTIVITY [ELDCON] = OFF CONDUCTIVITY (RADCON) = OFF T DIDIE MAN 000 1 1 1 11CUR D PRINT CONVERT TIMER CNOTIMER CONTINER CNOTINER CONVERGENCE PLOTS CONVERGENCE PLOTS CONSOLE CONVERGENCE PLOTS CONVERTINT CONVERTI CON MAGNETIC FIELD OPTIONS: KEYWORDS CBFIELD] CDIPOLEJ Constant Magnetic Field =1 .00 No Magnetic Dipoles Asgril -- Asg 2. **OBJECT DEFINITION INFORMATION BEING READ FROM FILE** VECTORS FROM SATELLITE CENTER TOWARD VIEWER ARE ITPART 0 GRIDS A SHADOWING TABLE WAS PREVIOUSLY GENERATED For this object using the hidg option flux definition single maxwellian QUESTED DIRECTI DIRECTI DIRECTI DIRECTI DIRECTI DIRECTI ELECTRON TEMPERATURE = . No. REPEAT m SECONDARY EMISSION FORM EFFECTIVE PHOTOBULE CON FIELO-ENVANCED BULK CON PADIATION-INDUCED BULK NO EMITTERS REQUESTED 6 MA TERIAL PLOT VIEW FROM VIEW FROM VIEW FROM VIEW FROM VIEW FROM VIEW FROM DIRECTION CUT VALUE \*\* PLOT OPTIONS: TITLE=NASCAP NGPLOT ICON DEST = ELEC NCON - DDIR 00000 NO. OF 3-D PLOT VIEWS OUTPUT OPTIONS: \*\*\*\*\*TRILIN ASGFIL

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Figure 11.8. (Continued)

3.00+003 ELECTRON VOLTS 1.20+006 METER++(-3) 11 \*\* ELECTRON DENSITY ION TEMPERATURE

HE TER++(-3) 8.00+005 11 ION DENSITY

N NEN CYCLE = \*\*\* RESTART AT

5 CYCLES HAVE BEEN REQUESTED. DELFAC= 1.00+000. QSUMER FOUND QSUM= -1.98+002 CODE UNITS. After Screening Correction Iscreening Length= 2.00+002 m.) QSUM= -1.98+002 +++ QSUMO FROM LAST CYCLE = -1.9836+002 +++ QSUMO FROM LAST CYCLE = -1.9836+002 \*\*\* THE SYSTEM IS NOW AT TIME 5.000+000 SECONDS. Delta: 2.00+002 Seconds.

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 CELLR ACC 
(Continued) Figure 11.8.

005107211403 9717 0-10 KAPT 004612210403 6 10 17 6 1 0 KAPT 

 qsumer found gsum= -1.98+002 code units.

 qsumer found gsum= -1.98+002 code units.

 AFTER Screening correction iscreening length= 0.00+002 m, 0.00m 2.00m 2.00m 2.00m 2.00m 2.00m 2.000 2.00m 2.000 2.00m 2.000 2.00m 2.00m 2.000 2.00m 2.00m 2.000 2.00m 2 004611216003 6 9 17 -1 0 0 \*\*\*\*\*\* 1.91-0081 1.41-0053 9.76-0073 YCLE 2 TIME 5.000+000 SECONDS. TAKE INTO ACCOUNT SUCH UCTIVITY DISCHARGES, EMITTER OPERATION. FOR LOW-ENERGY EMITTED ELECTRONS. CODE = Location = Normal = Material = CODE = Location = Normal = Material = CODE = Location = Normal = Material = 00 VOL TS 10115/HETER 133+002 VOLTS/HETER -000+000 : 1,570+000 VOLTS : 158+004 VOLTS/METER :ELD = 1.694+002 VOLTS/METER .CTOR = 1.837-001 5.000+000 SECONDS. ب ب . 2.28-006 9.74-007 5.99-007 ھ 1.13-006 -6.25-007 TIME = POTENTIAL = STRESS = 1 EXTERNAL FI LIMITING FA POTENTIAL = STRESS = External fi Limiting fa AP WILL TA AP WILL TA ACTORS FO POTENTIAL STRESS = EXTERNAL CTRONS ING SECONDARIES ING BACKSCATTER ING SECONDARIES ING SECONDARIES INS ECONDARIES IACKSCATTER LECTRONS TING SECONDARIES TING BACKSCATTER IVITY 2 EXPLICITLY CALCULATED FLU BURING THIS THEETEP ADDITIONAL EFFECTS AS SUR AND VARIATION OF LIMITING N B N C BEGIN CYCLE NO. 11 20 28 BULK CONDUCT PHOTOCURRENT FLUXES IN A/H++2 INCIDENT ELE RESULT FLUXE S IN A/M++2 INCIDENT EL RESULT RESULT INCIDENT PA BULK CONDUC PHOTOCURREA INCIDENT PL \* SURFACE CELL NO. FLUXES IN A/MAN SURFACE CELL NO. SURFACE CELL NO. NET FLUX NET FLUX

Figure 11.8. (Continued)

000061111123 011111120302 9 9 10 0 0 -1 Sola 005307212001 11 7 17 11 0 0 60L0 4.44-0003 2.05-0053 2.69-0083 1.46-0063 1.83-0061 • 00 CODE = Location = Normal = Material = CODE = LOCATION = Normal = Material = CODE = Location = 14 /MÉTER 02 VOLTS/METER +000 1 VOLTS OLTS/METER 02+001 VOLTS/METER •929-001 CODE = Location = Normal = Material = POTENTIAL = 3.040+000 VOLTS External field = 2.269+002 VOLTS/METER Limiting factor = 1.034-001 --3.21-009 2.22.28 1.455-006 7.775-006 2.13-008 7.05-008 7.05-008 7.05-008 7.05-008 7.05-008 -6.25-007 2 • 76 -008 • • 93 -008 1 • 01 - 011 -6.25-007 1.50-006 ..... 24 POTENTIAL = STRESS = 7 EXTERNAL FI LIMITING FA POTENTIAL STRESS = External f Limiting f LECTRONS 11NG SECONDARIES 1006 ACKSCATTER 1008 11NG SECONDARIES VITY VITY ECTRONS IING SECONDARIES I RONS IG SECONDARIES IG BACKSCATTER INCIDENT PROTONS RESULTING SECONDARIES BULM CONDUCTIVITY PHOTOCURRENT TONS NG SECONDARTES IVITY BOOM SURFACE CELL NO. 181 SURFACE CELL NO. 129 SURFACE CELL NO. 167 88 RESULT RESULT INCIDENT PR INCIDENT PR BULK CONDUC PHOTOCURREN RE SUL RE SUL INCIDENT PR PHOTOCURREN INCIDENT PF BULK CONDUC FLUXES IN A/H++2 INCIDENT E FLUXES IN A/H++2 INCIDENT FLUXES IN A/M++ SURFACE CELL NO. \*\*\*\*\*\*\*\*\*\*\*\*\* BULK CO PHOTOCU NET FLUX NET FLUX NET FLUX NET FLUX \*\*\*\*\*\*\*\* .........

Figure 11.8. (Continued).

3.60-007 AMPERES. 5.92-010 AMPERES. 2-66-0063 8.53-0073 ALUH 8.83-012 FARADS DIRECTION = HATERIAL = CONDUCTOR -8.609-012 AMPERES -4.862+001 CODE UNITS/SEC. INITIAL NET CHARGING CURRENT (WITHOUT LIMITING) = Initial net charging current (with limiting) = -1.36-006 2 • 65 - 006 8 • 55 - 009 8 • 55 - 009 2 • 74 - 0007 8 • 34 - 0007 8 • 34 - 0007 8 • 34 - 0007 8 • 34 - 0007 8 • 34 - 0007 8 • 34 - 0007 8 • 34 - 0007 8 • 34 - 0007 8 • 34 - 0007 8 • 34 - 0007 8 • 34 - 0007 8 • 34 - 0007 8 • 55 - 0007 8 • 5 POTENTIAL = 3.040+000 VOLTS FIELD = 5.774+002 VOLTS/HETE LIMITING FACTOR = 3.107-003 49.9 CODE UNITS; AVERAGE FLUXES (ONLY AVAILABLE FOR INSULATING CELLS) CONDUCTOR CURRENTS (AMPS; POSITIVE INTO CONDUCTORS); -9.724+003 CODE UNITS -1.722-009 COULOMBS -2.76-018 5.52-022/ 7.96+007 -3.707+000 -2.700+000 -3.707+000 -2.700+000 1.03-022/ 5.93+007 LEAVING ICCG1 -- VCTRI = -3,707+000 -2,323+000 1.56-019/ 8.60+009 5.52-022/ 7.96+007 5.80+007 2.264+000 4.392-001 5.127-001 3.0404+000 1.7256+000 VFIX --- 59 0UT OF 164 NODES FIXED. CONDUCTOR 1 FIXED TO 2.26 VOLTS. 8.16-023/ 2.361+000 1.99-008 G SECONDARIES G BACKSCATTER TÕNS NG SECONDARIES TOTAL CAPACITANCE TO INFINITY = AVERAGE NET CHARGING CURRENT = -3-1161-003 ICCG --- RDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = 1CCG --- RD01R/RD01R1 = ICCG --- RDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = LEAVING ICCG1 -- VCTRI = LEAVING ICCG1 -- VCTRI = LEAVING ICCG2 -- VCTRI = TOTAL CHANGE IN CHARGE = LEAVING ICCG1 -- VCTRI = NEW CONDUCTOR POTENTIALS NO DISCHARGE ANALYSIS NET CURRENTIAVG DQ/DT): NO DISCHARGE ANALYSIS RESULTI RESULTI INCIDENT PRO RESULTI PHOTOCURRENT FLUXES IN A/M+4 AVERAGE FLUX TO CI 2.3609+000 5.1266-001 NET FLUX

Figure 11.8. (Continued).

| -2.80-018  | 00*  | 4.47-020           |
|--|--|--------------------|
| -1.42-011  | 1.46-008                                     | 5.29-009           |
| CONDUCTIVITY CURRENT (NEW)<br>(FROM INSULATING CELLS): | PLASMA CURRENT (INITIAL)<br>(10 BARE CELLS): | REMAINDER CURRENT: |

Figure 11.8. (Continued).

 
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 1 SECONDS 2.050+002 11 ETED. 4.62+006 CYCLE NO. 2 AT UPDATED TIME QSUM = -9.9219+003 16 POTENTIAL ITERATIONS COMPLE RDOTR/RDRMAXE 139+002/ A 2.2608+007 -3.1342+002 2.2608+007 -3.1342+002 184 CELLS -ALI 1 S CONTINUE POTENTIAL 44 PCOND = QCOND = NEXTRA= ACE NO. SURF

EFPREP -- 1 GRIDS OUT OF 1 READ IN.

Figure 11.8. (Continued).

003 CODE UNITS. 28 ECTION (SCREENING LENGTH= 2.00+002 m.) 9SUM= -9.99+003 -9.91+003 9.991+003 2.361+007 5.127-001 2.261+007 -3.134+002 004611216003 -6 9 17 -1 0 0 005107211403 9 7 17 0 -1 0 004612210403 6 10 17 ...... 1.900-008 J 1.41-0053 9.76-0073 EXPLICITLY CALCULATED FLUXES FOR CYCLE 3 11ME = 2.050+002 SECONDS. DURING THIS TIMESTEP NASCAP WILL TAKE INTO ACCOUNT SUCH THIS RECONDS. ADDITIONAL EFECTS AS SUBFACE COMPUCTIVITY DISCHARGES. AND VARIATION OF LIMITING FACTORS FOR LOW-ENERGY EMITTED ELECTRONS. : 2.050+002 SECONDS. 60 A A 11 ... .. .. 11 10L 157 HÉ TER 109+003 VOL TS/HETER •020-027 CODE = Location = Normal = Material = 102 VOLTS VOLTS/METER 229+003 VOLTS/METER 1.000+000 CODE = LOCATION = NORHAL = HATERIAL = Z VOLIS 0L1S/METER 95+003 VOLTS/METER •000+000 CODE = LOCATION NORMAL = MATERIAL 2.050+002 SECONDS. 2.11-006 9.02-007 5.55-007 -1.65-006 -5.63-007 i \*\* TIME FIELD : 8.511 CTOR POTENTIAL = STRESS = -6. EXTERNAL FIE LIMITING FAC POTENTIAL = STRESS = 3 External f1 Limiting fa POTENTIAL STRESS = External Limiting ECTRONS ING SECONDARIES ING BACKSCATTER DTONS TIVG SECONDARIES FLUXES IN A/M++2 INCIDENT ELECTRONS RESULTING SECONDARIES RESULTING BACKSCATTER FLUXES IN A/M++2 INCIDENT ELECTRONS RESULTING SECONDARIES RESULTING BACKSCATTER INCIDENT PROTONS BULK CONDUCTIVITY PHOTOCURRENT 7 FOUND QSUM= -9.99+DD3 C AFTER SCREENING CORRECT 05CALE = -9.991 95UM = -9.991 PCOND = 2.26 0COND = 2.26 BEGIN CYCLE NO. 20 28 11 FLUXE S IN A/M++2 INCIDENT FL RESULT RESULT INCIDENT PR BULK COSULT BULK COSULT PHOTOCURREN SURFACE CELL NO. SURFACE CELL NO. SURFACE CELL NO. .............. NET FLUX NET FLUX QSUMER .....

(Continued).

Figure 11.8.

|  | M = 005111270103<br>= 0 0 2 1<br>L = MAPT 0 2 1<br>ER  | $ \frac{n}{2} = \frac{1}{2} \frac{1}{2} \frac{1}{2} \frac{1}{10} \frac{1}{10} \frac{1}{10} $ $ \frac{n}{1} = \frac{1}{2} \frac{1}{10} \frac{1}{10} \frac{1}{10} $ $ \frac{n}{1} = \frac{1}{2} \frac{1}{10} \frac{1}{10} \frac{1}{10} \frac{1}{10} $ $ \frac{n}{1} = \frac{1}{10} \frac{1}{10} \frac{1}{10} \frac{1}{10} $ $ \frac{n}{10} = \frac{1}{10} \frac{1}{10} \frac{1}{10} $  | OM = 01111120302<br>OM = 0 0 1<br>AL = Sola 0 -1<br>TER<br>[ 1.83-006]<br>[ 2.69-008]<br>[ .00 ]  | <pre></pre>               |
|--|--|--|---|---------------------------|
| 3.11-008<br>5.60-008<br>3.11-010<br>-5.63-007  | CODE =<br>1.001 10<br>1.002 VOL 15<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI<br>NATERI | FACTOR = 6-004 +004 FS<br>FACTOR = 6-004 +003 VOLTS/HE<br>FACTOR = 6-004 +003 VOLTS/HE<br>2-350-008<br>1-410-032<br>1-410-032<br>1-56-034<br>-7-56-034   | CODE<br>  | CODE<br>Locat<br>Figur    |
| INCIDENT PROTONS<br>REVENTING SECONDARJES<br>BULK CONDUCTIVITY<br>PHOTOCURRENT<br>NET FLUX | SURFACE CELL NO. 88<br>POTENTIAL<br>STRESS<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>BULL CONDUCTIVITY<br>NET FLUX<br>NET FLUX  | SURFACE CELL NO. 129<br>SURFACE CELL NO. 129<br>POTENTIAL<br>EXTERNAL<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>EXTERNAL<br>FLUXES IN A/M++2<br>FLUXES IN | SURFACE CELL NO. 167<br>SURFACE CELL NO. 167<br>POTENTIA<br>FLUXES IN A/H++2<br>FLUXES IN A/H++2<br>FLUXES IN A/H++2<br>FLUXES IN A/H++2<br>FLUXES FLUXES STRENTES<br>FLUXES FLUXES FCONDARTES<br>BULK CONDUCTIVITY<br>NET FLUX | BOOM SURFACE CELL NO. 181 |

Figure 11.8. INITIAL NET CHARGING CURRENT (WITHOUT LIMITING) = 3.63-DO7 AMPERES. INITIAL NET CHARGING CURRENT (WITH LIMITING) = -7.05-DO8 AMPERES. 2.68-0083 8.53-0073 ALUN 8.83-012 FARADS. DIRECTION : MATERIAL : CONDUCTOR AVERAGE NET CHARGING CURRENT = -1.419-011 AMPERES -8.014+001 Code UNITS/SEC. 2.28-006 2.55-006 2.55-007 2.55-007 2.55-007 -1.40-006 = 2.361+000 VOLTS 1.751+004 VOLTS/HETER FACTOR = 49.9 CODE UNITS; AVERAGE FLUXES (ONLY AVAILABLE FOR INSULATING CELLS) CONDUCTOR CURRENTS (AMPS; POSITIVE INTO CONDUCTORS): -1.603+004 CODE UNITS -2.838-009 COULOMBS 1.55-016 LEAVING ICCG1 -- VCIRI = -1.732+002 -1.313+002 LEAVING ICCG1 -- VCTRI = -1.732+002 -1.259+002 1.59-022/ 9.08+007 6.22-018/ 5.97+009 LEAVING ICCG2 -- VCTR1 = -1.667+002 -1.225+002 LEAVING ICCG1 -- VCIRI = -1.732+002 -1.313+002 1.69-022/ 9.27+007 -1.668+002 -1.226+002 ICCG --- RD0TR/RD0TR1 = 7.94-022/ 1.21+008 7.94-022/ 1.21+000 NNNN \*\*\*\* 2.3609.000 5.1266-001 VEIX --- 59 OUT OF 164 NODES FIXED. CONDUCTOR 1 FIXED TO -166.79 VOLTS. FIELD = 1. FIELD = 1. LIMITING FA 1.66-008 TOTAL CAPACITANCE TO INFINITY = ECONDARIES ACKSCATTER IG SECONDARIES 00 1.8769+007 1.7465-001 888999 11111 ICCG --- RDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = TOTAL CHANGE IN CHARGE = LEAVING ICCG1 -- VCTRI = NEW CONDUCTOR POTENTIALS NO DISCHARGE ANALYSIS NO DISCHARGE ANALYSIS NET CURRENT (AVG DQ/DT): AVERAGE FLUX TO CELL PHOTOCURRI FLUXES IN A/H++ INCIDENT -1.6670+002 -1.2253+002 NET FLUX

(Continued).

Figure 11.8. (Continued).

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CONDUCTIVITY CURRENT (NEW) (FRON INSULATING CELLS): -2.57-D11 7.67-D17 PLASMA CURRENT (INITAL) -5.67-DD9 .0D ATO BARE CELLS): REMAINDER CURRENT: 2.23-DD8 7.79-D17

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| QSUN = -2. |  | 001ENTIAL TI<br>001R/RDRMAX<br>+002 -1.22<br>+007 -4.72      | RIDS OUT OF |
|            | NGE<br>NGE<br>NGE<br>NGE<br>NGE<br>NGE<br>NGE<br>NGE           | 16 P.<br>16 P.<br>16 P.<br>10 E.<br>10 BB94<br>17 RA = 00884 | 3EP 1 G     |
|            | ND<br>JM<br>E<br>E<br>1940120000000000000000000000000000000000 | C CONC   | EFPF        |

(Continued). Figure 11.8.

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005107211403 9 7 17 0 -1 0 Kapt 104 COVE UNITS. 19 ECTION (SCREENING LENGTH= 2.00+002 M.) 9SUM= -2.61+004 2.6063+004 1.6667+002 1.667+002 -1.225+002 4.088+007 -4.721+003 004611216003 6 9 17 -1 0 0 .......... 5.24-0083 1.41-0053 9.39-0073 EXPLICITLY CALCULATED FLUXES FOR CYCLE 4 IIME = 4.050+002 SECONDS. DURING THIS THRESTEP WICL TAKE INTO ACCOUNT SUCH THE POLINIONAL AUDITIONAL EFFECTS AS SUBFACE ONDUCTIVITY, DISCHARGES, EMITTER OPERATION, AND VARIATION OF LIMITING FACTORS FOR LOW-ENERGY EMITTED ELECTRONS. . 4.USD+DD2 SECONDS. Uch CODE = Location = Normal = Material = CODE = Location = Normal = Haterial = .. CODE = Location = Normal = Material = +002 VOLTS 6 VOLTS/METER 8.035+003 VOLTS/METER 1.000+000 2 VOLTS OLTS/METER 27+003 VOLTS/METER •733-035 2 VOL TS 0L TS/METER 55+004 VOL TS/METER •000+000 4+050+002 SECONDS 2,19-006 5,78-007 2,92-008 2,92-008 2,00-011 2,00-01 1.91-006 8.19-007 5.04-007 -4.89-007 TIME = POTENTIAL = STRESS = 5 EXTERNAL FI LIMITING FA POTENTIAL = STRESS = 5 EXTERNAL FI LIMITING FA POTENTIAL = STRESS = 2 External fi Limiting fa CTRONS NG SECONDARIES NG BACKSCATTER NG SECONDARIES ING SECONDARIES ECTRONS ING SECONDARIES ING BACKSCATTER ING SECONDARIES ING SECONDARIES LECTRONS TING SECONDARIES TING BACKSCATTER QSUMER FOUND QSUME -2.61+004 AFTER SCREENING CORRE OSCALE -2. OSUM = -2.6 PCOND = -1.6 4.6 BEGIN CYCLE NO. 17 28 20 RESULT INCIDENT PR RESULT BULK CONDUC PHOTOCURREN FLUXES IN A/M++2 INCIDENT EL RESULT INCIDENT PR INCIDENT PR BULK CURREN PHOTOCURREN M++2 N1+2 N5UL FLUXES IN A/M++2 SURFACE CELL NO. SURFACE CELL NO. SURFACE CELL NO. FLUXES IN A/M Inciden Re NET FLUX NET FLUX

Figure 11.8. (Continued)

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Figure 11.8. (Continued). 1 011111120302 9 9 10 50LA -1 005307212001 11 7 17 1 0 0 000061111123 1.81-0063 2.74-0083 C 1.42-0063 4.70-0083 2.05-0053 GOL • 00 CODE = Location = Normal = Haterial = u н 2 VOLTS 0LTS/METER 44+004 VOLTS/METER •000+000 POTENTIAL = -1.667+002 VOLTS "........ External field = 9.001+003 Volts/Meter Limiting factor = .000 CODE = LOCATION NORMAL = MATERIAL VOLTS 15/METER 4003 VOLTS/HETER 48-016 CODE = Location Normal = Material CODE = LOCATION -4.89-007 -7.48-007 3 - 54 - 008 6 - 554 - 008 5 - 557 - 010 5 - 57 - 010 -4.89-007 2.20-006 1.43-006 2.90-008 2.55-006 2.625-0026 2.668-0027 2.960-000 3.96-0024 -024 -1.46-006 1 POTENTIAL = STRESS = 5 EXTERNAL FI LIMITING FA POTENTIAL = STRESS = -3 EXTERNAL FI LIMITING FA ECTRONS ING SECONDARJES ING BACKSCATTER OTONS ING SECONDARJES ELECTRONS LTING SECONDARIES LTING SECONDARIES PROTONS PROTONS LTING SECONDARIES UCTIVITY NG SECONDARIES NG BACKSCATTER TONS NG SECONDARIES IVITY INCIDENT PROTONS Resulting Secondaries Bulk Conductivity Photocurrent SECONDARIES BACKSCATTER ..... 181 88 129 BOOM SURFACE CELL NO. 167 FLUXES IN A/H++2 INCIDENT ELEC INCIDENT EVESULTIN INCIDENT PROT BULK CONDUCT PHOTOCURRENT FLUXES IN A/H++2 INCIDENT ELL RESULT INCIDENT PR BULK RESULT BULK RESULT PROPUCURREN z RESULT RESULT INCIDENT PR INCIDENT PR PHOTOCURREN FLUXES IN A/M++2 SURFACE CELL NO. SURFACE CELL NO. SURFACE CELL ND. NET FLUX NET FLUX NET FLUX NET FLUX ..............

Figure 11.8. (Continued)

INITIAL NET CHARGING CURRENT (WITHOUT LIMITING) = 3.66-007 ANPERES. INITIAL NET CHARGING CURRENT (WITH LIMITING) = -6.58-000 AMPERES. 2.84-0083 8.24-0073 DIRECTION = Z MATERIAL = ALUM 8.83-012 FARADS. CONDUCTOR -1.631-011 AMPERES -9.211+001 CODE UNITS/SEC. -1.35-006 2.20-006 8.23-007 2.90-006 POTENTIAL = -1.667+002 VOLTS FIELD = 3.150+004 VOLTS/METER LTMITING FACTOR = -000 AVERAGE FLUXES TONLY AVAILABLE FOR INSULATING CELLS 49.9 CODE UNITS; CONDUCTOR CURRENTS (AMPS; POSITIVE INTO CONDUCTORS): -1.842+004 CODE UNITS -3.262-009 COULOMBS 2.66-016 ICCG --- RD0TR/RD0TR1 = 1.53-022/ 1.01.008 1.76-017/ 4.16+009 LEAVING ICCG2 -- VCTRI = -4.163+002 -3.213+002 -4.233+002 -3.291+002 1.64-022/ 1.03+008 LEAVING ICCG1 -- VCTRI = -4.233+002 -3.248+002 -4.164+002 -3.214+002 -4.233+002 -3.291+002 1.06-021/ 1.30+008 ICCG --- RD0TR/RD01R1 = 1.06-021/ 1.30+008 -1.6670+002 -1.2253+002 -3.217-007 A -1.495-008 A -3.217-007 A -3.216-007 A 7.080-008 A CONDUCTOR I FIXED TO -416.40 VOLTS. 1.37-008 CTRONS ING SECONDARIES ING BACKSCATTER TOTAL CAPACITANCE TO INFINITY = TONS SECONDARIES AVERAGE NET CHARGING CURRENT = 00 1.5449+007 3.0019-001 ICCG --- RDOTR/RDOTR1 = ~~~~ ICCG --- RDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = LEAVING ICCG1 -- VCTRI = TOTAL CHANGE IN CHARGE = LEAVING ICCG1 -- VCTRI = •• LEAVING ICCG1 -- VCTRI NEW CONDUCTOR POTENTIALS NET CURRENTIAVG DQ/DT): NO DISCHARGE ANALYSIS NO DISCHARGE ANALYSIS AVERAGE FLUX TO CELL PHO TOCURREN FLUXES IN A/H++ -4.1632+002 -3.2133+002 INCIDENT NET FLUX

| CONDUCTIVITY CURRENT (NEW)<br>IFROM INSULATING CELLS): | -3.51-011 | 1.65-016 |
|--|-----------|----------|
| PLASMA CURRENT (INITIAL)<br>(TO BARE CELLS):           | -5.47-009 | 00.      |
| REMAINDER CURRENT;                                     | 1.92-006  | 1.01-016 |

Figure 11.8. (Continued).
| SECONDS.             |   |
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| 0       | 16 P0<br>-4.1632+<br>A= 5.5913+                        | 1 GR       |
|   | COND =<br>1COND =<br>1COND =                           | EFPREP     |

Figure 11.8. (Continued).

QSUMER FOUND QSUM= -4,46+DD4 CODE UNITS. After Screening Correction (Screening Length= 2.00+DD2 M.) QSUM= -4.46+DD4 QSCALE = -4.4583+DD4 PCOND = -4.4583+DD2 PCOND = -4.4583+DD2 PCOND = -5.591+DD7 QCOND = -5.591+DD7 PCOND = -5.551+DD7 PCOND = 004611216003 6 9 17 -1 0 0 005107211403 9 17 0 -1 0 4APT 004612210403 6 10 17 ........ CHARGES EMITTER OPERATION. 8.91-007J 5.71-0083 1.41-0053 6.050+002 SECONDS D2 VOLTS MATERIAL = VOLTS/METER 971+003 VOLTS/METER •000 11 11 \*\* 11 LŤŠŽHĚTER 0+004 volts/heter 000+000 LOCATION NORMAL = MATERIAL CODE = Location : Normal = Haterial : 13 VUL 13 10L TS/MÉTER 154+004 VOLTS/METER •000+000 6.050+002 SECONDS. CODE = LOCATION NORMAL = MATERIAL ---2.08-006 5.48-007 3.16-007 3.04-011 -1.50-006 -4.15-007 1.73-006 200 5 V 02 • **TIME =** \*\*\*\*\*\*\*\*\*\*\*\* POTENTIAL = STRESS = 7 EXTERNAL FI EXTERNAL FI LIMITING FA P VILL TAN POTENTIAL STRESS = EXTERNAL FI EXTERNAL FI POTENTIAL STRESS = EXTERNAL F LIMITING F URFACE CONDUCTION ECTRONS ING SECONDARIES ING BACKSCATTER OTONS SECONDARIES TRONS 6 SECONDARIES 6 BACKSCATTER VITY VITY FLUXES IN A/M++2 Incident Electrons Resulting Secondaries Resulting Backscatter ŝ CALCULATED FLU S TIMESTEP NAS EFFECTS AS SUB TON OF LIMITING BEGIN CYCLE NO. 20 28 11 FLUXES IN A/M\*\*2 INCIDENT ELEC RESULTIN INCIDENT PROJ BULK CONDUCTION PHOTOCURRENT FLUXES IN A/H++2 INCIDENT EL RESULT RESULT INCIDENT PE RESULT SURFACE CELL NO. SURFACE CELL NO. BULK CONDI PHOTOCURRI SURFACE CELL NO. EXPLICITLY CALC DURING THIS TIM ADDITIONAL EFFE AND VARIATION O NET FLUX NET FLUX .......

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(Continued).

Figure 11.8.

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|  |  |  | Figure 11.8.   | =  |
| 4.01-008<br>7.69-008<br>7.65-010<br>.00<br>-4.15-007                                       | CODE = 005111270103<br>LOCETION = 9 23<br>NORMAL = 4 0 0 1<br>NORMAL = 4 0 0 1<br>NORMAL = 4 0 0 1<br>NORMAL = 4 0 0 0<br>NORMAL = 4 | FIELD = 1.005307212001<br>CODE = 005307212001<br>MATERIAL = 00LD 0<br>MATERIAL = 60LD 0<br>MATERIAL = 60LD 0<br>1.056+004 volts/METER<br>2.10-006 C 1.35-0061<br>1.35-0061<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0063<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-0053<br>1.35-00 | CODE = 0 01111120302<br>CODE = 0 0 10<br>NORMAL = 0 0 11<br>NORMAL = 0 0 1<br>NORMAL = 0 0 0 0<br>NORMAL = 0 0 0 0<br>NORMAL = 0 0<br>NO | CODE = 000061111123<br>LOCATION = 9 9 19 0 |
| INCIDENT PROTONS<br>RESULTING SECONDARJES<br>BULK CONDUCTIVITY<br>PHOTOCURRENT<br>NET FLUX | SURFACE CELL NO. 88<br>POTENTIA<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>ELECTRONS<br>FLUXES<br>BULK CONDARTES<br>BULK CONDARTES<br>BULK CONDARTES<br>BULK CONDARTES<br>FLUX<br>MET FLUX   | SURFACE CELL NO. 129<br>POJENTIAL<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>ECTRONS<br>INCIDENT ELECTRONS<br>ACKSONDARIES<br>INCIDENT PROTONS<br>ACKSONDARIES<br>PHOTOCURRENT<br>NET FLUX   | SURFACE CELL NO. 167<br>POTENTIA<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2   | BOOM SURFACE CELL NO. 181                  |

Figure 11.8. INITIAL NET CHARGING CURRENT (WITHOUT LIMITING) = 3.70-007 AMPERES. INITIAL NET CHARGING CURRENT (WITH LIMITING) = -6.06-008 AMPERES. 7.84-0073 3.09-0083 ALUM 8.83-012 FARADS. DIRECTION = Material = CONDUCTOR -1.704-011 AMPERES -9.622+001 CODE UNITS/SEC. 2.10-006 0.001 3.13-008 0.00 -1.28-006 POTENTIAL = -4.163+002 VOLTS FIELD = 4.293+004 VOLTS/METER LIMITING FACTOR = .000 TOTAL CAPACITANCE TO INFINITY = 49.9 CODE UNITS AVERAGE FLUXES CONLY AVAILABLE FOR INSULATING CELLS) CONDUCTOR CURRENTS LAMPS; POSITIVE INTO CONDUCTORS); -1.924+004 CODE UNITS -3.408-009 COULOMBS 3.94-016 LEAVING ICCG1 -- VCTRI = -7.062+002 -5.600+002 LEAVING ICCG1 -- VCTRI = +7.062+002 -5.600+002 9.32-022/ 1.21+008 9.32-022/ 1.21+008 LEAVING ICCG1 -- VCTR1 = -7.062+002 -5.555+002 ICCG --- RD01R/RD01R1 = 1.69-D22/ 9.67+D07 -6.989+002 -5.521+002 LEAVING ICCG2 -- VCTRI = -6.988+002 -5.521+002 1.53-022/ 9.90+007 1.94-017/ 3.10+009 A/H++22 A/H++2 -4.1632+002 -3.2133+002 -2.747-007 -1.796-008 -2.747-007 -2.746-007 6.788-007 CONDUCTOR 1 FIXED TO -698.88 VOLTS. 1.19-008 FLUXES IN A/M+2 INCIDENT ELECTRONS RESULTING SECONDARIES RESULTING BACKSCATTER INCIDENT PROTONS PHOTOCURRENT PHOTOCURRENT AVERAGE NET CHARGING CURRENT = 1 • 3486+007 4 • 4463-001 ICCG --- RDOTR/RDOTR1 = ICCG --- RD0TR/RD0TR1 = ICCG --- RDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = LEAVING ICCG1 -- VCIRI = TOTAL CHANGE IN CHARGE = NEW CONDUCTOR POTENTIALS NO DISCHARGE ANALYSIS NO DISCHARGE ANALYSIS NET CURRENT (AVG DQ/DT): AVERAGE FLUX TO CELL -6.9885+002 -5.5208+002 NET FLUX

(Continued).

Figure 11.8. (Continued).

| CONDUCTIVITY CURRENT (NEW)<br>(FROM INSULATING CELLS): | -4.33-011 | 2.54-016 |
|--|-----------|----------|
| PLASMA CURRENT (INITIAL)<br>(To Bare Cells):           | -5.18-009 | 00*      |
| REMAINDER CURRENT:                                     | 1.72-008  | 1.40-016 |
|  |           |          |

| SECONDS.      |
|---------------|
| 0.050+002     |
|               |
| TIME          |
| UPDATED       |
| A1<br>004     |
| .3823.        |
| - 0<br>N<br>N |
| C YCLE        |
| CONTINUE      |

NO.

| · ALL 184 CELLS |   | NTIAL ITERATIONS C<br>R/RDRMAX2 1.70+00<br>2 -5.5208+002<br>7 -1.2293+004   |
|-----------------|---|---|
|                 |   | COMPLE TED.<br>102/ 2.24+006  |
|                 | MMMNNNMMNNNNNNNNNNNNNNNNNNNNNNNNNNNNN                       |   |
|                 | 0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.                      |   |
|                 |   |   |
|                 |   |   |
|                 | Manual Multiple       B000000000000000000000000000000000000 |   |
|                 | MMMNMMNMNMNMNMNMNNNNNNNNNNNNNNNNNNNNN                       |   |
|                 | LS - AIL 184 CEILS  | - 411     - 411 |

Figure 11.8. (Continued).

I READ IN.

1 GRIDS OUT OF

EFPREP --

Figure 11.8. (Continued).

| TIME = 8.050+002 SECONDS.<br>NITS.<br>Screening Length= 2.00+002 M.) qSum= -6.39+00<br>-5.521+002<br>-1.229+004   | CLE 16 TIME = 8.050+002 SECONDS.<br>Ake 1110 a clanf = 8.050+002 Seconds.<br>Ctivity discharf such tite operation.<br>Or Low-Energy Emitted Electrons.        | CODE = 004611216003<br>CODE = 004611216003<br>RORMAL = x.P. 0 0<br>RORMAL = x.P. 0 0<br>RAFFIAL = x.P. 0 0<br>FIEL0 = -2.310004<br>1.56-006<br>1.56-006<br>1.56-006<br>0.42-010<br>0.02<br>-3.47-000<br>-3.47-001 | CODE = 004612210403<br>COCATION = 004612210403<br>RAPT = 4APT<br>NORMAL | CODE = 005107211403<br>LOCATION = 9 7 17<br>LOCATION = 9 7 17<br>NORMAL = 00 -1 0<br>NORMAL = 00 -0 0<br>NORMAL  |
|---|---|---|---|--|
| BEGIN CYCLE NO. 6<br>95 UMER FOUND 95 UME - 6.39+004 CODE UM<br>95 UME 5CREENING CORRECTION (1)<br>95 UME - 6.3875+004<br>95 UME - 6.984+002<br>90 04+007<br>90 04<br>90 | EXPLICITLY CALCULATED FLUXES FOR CYL<br>DURING THIS TIMESTEP FLUXES FOR CYL<br>DURING THIS TIMESTEP AS SURFACE CONDUC<br>AND VARIATION OF LIMITING FACTORS FU | SURFACE CELL NO. 20<br>SURFACE CELL NO. 20<br>FOTENTIAL<br>STRESS =<br>EXTERNAL<br>INCIDENT FLECTRONS<br>INCIDENT FLECTRONS<br>INCIDENT PROTONS<br>BULM CONDUCTIVITY<br>NET FLUX<br>NET FLUX                      | SURFACE CELL NO. 28<br>POTENTIAL<br>STRESS =<br>EXTERNAL<br>FLUXES IN A/H++2<br>FLUXES IN A/H++2<br>FLUXES IN A/H++2<br>EXTERNAL<br>FLUXES IN A/H++2<br>FLUXES IN A/H++2<br>FLUX  | SURFACE CELL NO. 77<br>SURFACE CELL NO. 77<br>STRESS =<br>STRESS =<br>EXTERNAL<br>FLUXES IN A/M++2<br>FLUXES |

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Figure 11.8. 00006111123 005307212001 11 7 17 1 0 0 5.61-0083 1.27-0063 1.71-0063 3.01-0083 00. CODE = Location = Normal = Material = CODE = Location = Normal = Material = •• CODE = Location = CODE = Location = Normal = = Material = 3 706/15 06/15/METER 09+004 VOLTS/METER •000+000 POTENTIAL = -6.988+002 VOLTS ...... EXTERNAL FIELO = 1.117+004 VOLTS/METER LIMITING FACTOR = .000 0L157METER 73+003 VOL15/METER •865-022 --3.47-007 -3.47-007 -6.64-007 1.98-006 1.28-006 3.38-008 3.38-008 2 • 13 - 006 7 • 26 - 007 3 • 05 - 007 2 • 05 - 007 1 • 20 - 029 1 • 20 - 029 1 • 20 - 029 -1.37-006 POTENTIAL = -3,30 STRESS = -1,204+0 EXTERNAL FIELD = LIMITING FACTOR : POTENTIAL STRESS = EXTERNAL F LIMITING F FLUXES IN A/M##2 INCIDENT ELECTRONS RESULTING SECONDARIES RESULTING SECONDARIES INCIDENT PROTONS BULK CONDUCTIVITY PHOTOCURRENT ECTRONS ING SECONDARIES ING BACKSCATTER CTRONS NG SECONDARIES NG BACKSCATTER NG BACKSCATTER 110 SECONDARIES NUTY INCIDENT PROTONS RESULTING SECONDARIES BULK CONDUCTIVITY PHOTOCURRENT 181 88 129 167 BOOM SURFACE CELL NO. FLUXES IN A/H4-2 INCIDENT EFLE INCIDENT FELTI INCIDENT PRO INCIDENT PRO PHOTOCURRENT INCIDENESUL INCIDENESUL DULK CONOU FLUXES IN A/M++ SURFACE CELL NO. SURFACE CELL NO. SURFACE CELL NO. NET FLUX NET FLUX NET FLUX NET FLUX ....... 1

(Continued).

Figure 11.8. (Continued)

INITIAL NET CHARGING CURRENT (WITHOUT LIMITING) = -3-33-000 AMPERES. 3.39-0083 C100-1#.1 DIRECTION = Z HATERIAL = ALUM 8.83-012 FARADS. CONDUCTOR AVERAGE NET CHARGING CURRENT = -1.645-011 AMPERES -9.292+001 CODE UNITS/SEC. 1.98-006 7.40-007 3.38-008 3.00 -1.21-006 +988+002 VOLTS 49.9 CODE UNITS AVERAGE FLUXES TONLY AVAILABLE FOR INSULATING CELLSI CONDUCTOR CURRENTS LAMPS; POSITIVE INTO CONDUCTORSI: 5.68-016 -1.858+004 CODE UNITS -3.291-009 COULOMBS 8.90-022/ 1.04+008 LEAVING ICCG1 -- VCIRI = -9.964+002 -7.989+002 8.90-022/ 1.04+008 LEAVING ICCG1 -- VCIRI = -9.964+002 -7.989+002 LEAVING ICCG1 -- VCTRI = -9.964+002 -7.949+002 ICCG --- RD0TR/RD0TR] = 1.46-022/ 8.54+007 LEAVING ICCG1 -- VCTRI = -9.886+002 -7.914+002 1.97-017/ 2.25+009 LEAVING ICCG2 -- VCTR1 = -9.885+002 -7.914+002 1.50-022/ 8.77+007 V0LD -6.9885+002 -5.5208+002 CONDUCTOR 1 FIXED TO -988.58 VOLES. -2.353-007 -1.641-000 -2.352-007 -2.352-007 -2.350-007 6.964-000 POTENTIAL = -FIELD = 5.27 LIMITING FACT 1.00-008 TOTAL CAPACITANCE TO INFINITY = ECONDARIES ACKSCATTER G SECONDARIES 1.1296+007 6.4145-001 ~~~~~ ICCG --- RDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = TOTAL CHANGE IN CHARGE = NEW CONDUCTOR POTENTIALS NET CURRENTIAVG DQ/DT1: NO DISCHARGE ANALYSIS NO DISCHARGE ANALYSIS AVERAGE FLUX TO CELL INCIDENT PRC INCIDENT PRC RESULT -9.8851+002 -7.9138+002 FLUXES IN A/M NET FLUX

CONDUCTIVITY CURRENT INEW) IFROM TNSULATING CELLS): -5.02-011 3.41-016 PLASMA CURRENT (INITIAL) -4.86-009 .00 Remainder Current: 1.49-008 2.27-016 Figure 11.8. (Continued).

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(Concluded) Figure 11.8.

CEL

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By the end of the run we note that neither the change in conductor potential per timestep (~250 V) nor the average net charging current ( $\sim 10^{-11}$  A) has changed substantially. Therefore, we decide to perform a third run to continue the simulation with the same parameters for an additional 5 cycles.

A potential contour plot for cycle 6 is shown in Figure 11.9. Note the appearance of a saddle point at the right of the figure.



POTENTIAL CONTOURS ALONG THE Y-Z PLANE OF X - 0

Figure 11.9. Potential contour plots (second run).

# 11.8 THE THIRD RUN

This run is carried out with the same parameters as the second run, extending the number of cycles out to 11. The printed output and contour plots for cycle 11 are shown in Figure 11.10. The conductor potential has reached -2.1 kV and the KAPTON -4.1 kV. the current breakdown for KAPTON shows that the net current is decreasing as equilibrium approaches. In the next run we increase the timestep and dvlim, to hasten the attainment of equilibrium.

05 CODE UNITS. TECTION (SCREENING LENGTH= 2.00+002 M;) QSUM= -1.43+005 1.4312-005 1.0980+003 -1.621+003 1.0980+008 -2.753+004 004611216003 -6 9 17 -1 0 10 KAP1 004612210403 6 10 17 4 0 1 0 4 APT 005107211403 9 7 17 8 0 -1 0 8 4 P T .......... 6.43-0073 9.39-008J [ .41-005 ] E = 1.805+003 SECONDS. For the second seconds. Res. Entite operation, Hitte electrons. K A P CODE = Location = Normal = Material = CODE = Location = Normal = Haterial = 11 .. CODE = Location = Normal = Material = 13 VOL TS VOL TS/METER 12+004 VOL TS/METER •000+000 3 VOLTS 01 TS/METER 12+004 VOLTS/METER 000+000 1.805+003 SECONDS. Trilin Output for cycle 11 1.05-006 -1.15-007 -1.06-006 EXPLICITLY CALCULATED FLUXES FOR CYCLE 11 AC 11M BURINO ALS TIMESTED SURFACE CONDUCTIVITY DISCHAN ADDITIONAL EFFECTS AS SURFACE CONDUCTIVITY DISCHAN AND VARIATION OF LIMITING FACTORS FOR LOW-ENERGY EN LL = -3.883+003 V 1.499+007 VOLT FIELD = -3.512+ FACTOR = 1.000 i ł н TIME CTOR = POTENTIAL = STRESS = 1 EXTERNAL FI EXTERNAL FI POTENTIAL STRESS = External Limiting 1 ECTRONS ING SECONDARIES ING BACKSCATTER ING SECONDARIES ING SECONDARIES ECTRONS ING SECONDARIES ING BACKSCATTER ING BACKSCATTER ING SECONDARIES ING SECONDARIES FLUXES IN A/H++2 INCIDENT ELECTRONS RESULTING SECONDARIES RESULTING BACKSCATTER Ξ QSUMER FOUND QSUME -1,43+DD AFTER SCREENING CORRESSENCE -1, 95UM = -1, 95UM = -1, 1,1,4 95UM = -1,4 950ND = -1,4 Figure 11.10a. BEGIN CYCLE NO. 20 28 17 FLUXES IN A/H++2 INCIDENT FLECT RESULTING INCIDENT PRESULTING INCIDENT PROTO BULK COURTING PHOTOCURRENT FLUXES IN A/H++2 INCIDENT ELE RESULTI INCIDENT PRC BULK RESULTI BULK CURVENT SURFACE CELL NO. SURFACE CELL NO. SURFACE CELL NO. NET FLUX NET FLUX \* \* \* \* \* \* \* \* \* \*

3.64-007 AMPERES. 1.56-000 AMPERES. 5.74-0073 5.00-008 DIRECTION = Z MATERIAL = ALUM 8.83-012 FARADS. CONDUCTOR -9.465-012 AMPERES -5.345+001 CODE UNITS/SFC. INITIAL NET CHARGING CURRENT IMITHOUT LIMITING) = Initial net charging current imith limiting) = 1.53-006 5.73-007 4.55-008 POTENTIAL = -1.980+003 VOLTS FIELD = 8.294+004 VOLTS/METER LIMITING FACTOR = -000 -9.16-007 AVERAGE FLUXES IONLY AVAILABLE FOR INSULATING CELLS TOTAL CAPACITANCE TO INFINITY = 49.9 CODE UNITS; CONDUCTOR CURRENTS (AMPS; POSITIVE INTO CONDUCTORS): -1.069+004 CODE UNITS -1.893-009 COULOMBS 9.33-016 1.24-018/ 3.35+008 -2.164+003 -1.776+003 Figure 11.10a. (Continued) 8.64-023/ 2.27+007 -2.164+003 -1.777+003 LEAVING ICCG1 -- VCTRI = -2.174+003 -1.783+003 ICCG --- RD0TR/RD0TR1 = 1.10-022/ 2.43+007 LEAVING ICCG1 -- VCTRI = -2.174+003 -1.780+003 2.29-022/ 2.63+007 LEAVING ICCG1 -- VCTR1 = -2.174+003 -1.783+003 2.29-022/ 2.63+007 A/H++2 A/H++2 A/H++2 -1.9796+003 -1.6207+003 3-968-008 CONDUCTOR 1 FIXED TO -2164 NODES FIXED. 3.87-009 ING SECONDARIES ING BACKSCATTER ITONS ING SECONDARIES AVERAGE NET CHARGING CURRENT = 4.3728+006 1.0534+000 ICCG --- RDOTR/RDOTR1 = ICCG --- HDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = vovov ICCG --- RDOTR/RDOTR1 = LEAVING ICCG2 -- VCTRI = LEAVING ICCG1 -- VCTRI = TOTAL CHANGE IN CHARGE = NEW CONDUCTOR POTENTIALS NET CURRENT (AVG DQ/DT): NO DISCHARGE ANALYSIS NO DISCHARGE ANALYSIS RESULI RESULI INCIDENT PR RESULT PHOTOCURREN FLUXES IN A/M++ AVERAGE FLUX TO C AVERAGE FLUX TO C AVERAGE FLUX TO C AVERAGE FLUX TO C -2.1640+003 -1.7765+003 NET FLUX

|  | ETER   |   | = 01111120302<br>IL = 01111120302<br>IL = SoLA 0 -1<br>IL = SoLA 0 -1<br>I + 7 - 006 3<br>[ 3.85 - 008 3<br>[ 3.85 - 008 3<br>[ 3.65 - 008 3  | = 00006111123                            |
|--|--|---|---|--|
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| INCIDENT PROTONS<br>RESULTING SECONDARIES<br>BULK CONDUCTIVITY<br>PHOTOCURRENT<br>NET FLUX | SURFACE CELL NO. 88<br>POTENTIAL<br>FLUXES IN A/M++2<br>EXTERNAL<br>FLUXES IN A/M++2<br>FLUXES IN  | SURFACE CELL NO. 129<br>SURFACE CELL NO. 129<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>INCIDENT ELECTRONS<br>INCIDENT ELECTRONS<br>INCIDENT PROTONS<br>FESULTING SECONDARIES<br>PHOTOCURRENT NG SECONDARIES<br>NET FLUX  | SURFACE CELL NO. 167<br>SURFACE CELL NO. 167<br>POTENTIAL<br>STRESS<br>FXTERNIAL<br>FLUXES IN A/H++2<br>FXTERNIAL<br>FLUXES IN A/H++2<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS<br>FXTERSS | BOOM SURFACE CELL NO. 181<br>Figure 11.1 |

 
Management

M 2+005+003 SECONDS, .... 2 9 16 POTENTIAL ITERATIONS -2:164+003 16 POTENTIAL ITERATIONS COMPLETED. -2.1640+003 -1.7765+003 -1.1409+008 -2.9614+004 CYCLE NO. 11 AT UPDATED TIME QSUM = -1.5381+005 H .. IPSAVE **I P S A V E** 1 READ IN. : 10 \* 184 CELLS . = 13 ISPARE = 13 ISPARE 11. GRIDS OUT OF ALL COMPLETED IS ł IJ 2 CONTINUE S POTENTIAL = 12 12 н IP = 14 IR 1R CYCLE PCOND = QCOND = Nextra= ; SURFACE CELL NO. = 10 EFPREP LAST L L

(Concluded)

Figure 11.10a.

COMDUCTIVITY CURRENT (NEW) (FROM INSULATING CELLS): -7.16-011 6.70-016 PLASMA CURRENT (INITIAL) -3.63-009 .00 REMAINDER CURRENT: 7.57-009 2.63-016

458





AXIS

2

Figure 11.10b. Potential contours for cycle 11.

#### 11.9 EQUILIBRIUM

Two more runs are carried out, adding a further 10 cycles. In each run DELTA is increased to 500s and dvlim to 1000. DELTA 500s LONGTIMESTEP 1000

The printed output and contour plot for the final cycle is shown in Figure 11.11 and Figure 11.12.

The potentials remains steady for cycles 18-21, showing the equilibrium has been achieved. The final equilibrium potentials are as follows:

| Type of cell  | <u>Potential (kv)</u> |
|---------------|-----------------------|
| Shaded KAPTON | - 5.1                 |
| Sunlit KAPTON | ∿ <b>-3</b>           |
| GOLD          | ∿ -3                  |
| SOLAR sphere  | ∿ <b>_2 → _</b> 3     |

From these results we draw the following conclusions:

- The spacecraft will charge considerably in the given environment, but only on a differential charging (long) timescale. Charging is driven by the shaded KAPTON, whose electric field suppresses emission from the other, initially non-charging, surfaces.
- 2. Differential potentials in the  $2 \rightarrow 3$  kV range are likely.

| BEGIN CYCLE NO.   21   TIME = 6.505+003 SECONDS.     QSUMER FOUND QSUME = 1.96+005 CODE UNITS.   6.505+003 SECONDS.     QSUMER FOUND QSUME = 1.96+005 CORECTION (SCREENING LENGTH= 0.2.00+002 M.) QSUM= -1.96+003     AFTER SCREENING CORRECTION (SCREENING LENGTH= 0.2.00+002 M.) QSUM= -1.96+003     AFTER SCREENING CORRECTION (SCREENING LENGTH= 0.2.00+002 M.) QSUM= -1.96+003     AFTER SCREENING CORRECTION (SCREENING LENGTH= 0.2.00+002 M.) QSUM= -1.96+003     QSUME = -1.9655000 SECONDS     QSUME = -1.95654003     QSUME = -1.95654003     QSUME = -1.95654003     QSUME = -1.95654003     QCOND = 1.26614003     QCOND = 1.26614003     QCOND = 1.26614003     QCOND = 1.26614003 | Explicitly calculated fluxes for cycle 21   21   6.505+003 seconds.     DURING THIS TIMESTEP NARGAP WILL TAKE IND ACCOUNT SUCHARGES FOR TITLE OPERATION.   6.505+003 seconds.     DUDITION OF LIMITING FACTORS FOR LOW-ENERGY EMITTED ELECTRONS.     SURFACE CELL NO.   20     SURFACE CELL NO.   20     FULXES IN AMOUNT OF LIMITING FACTORS FOR LOW-ENERGY EMITTED ELECTRONS.     SURFACE CELL NO.   20     SURFACE CELL NO.   20     FULXES IN AMOUNT ELECTRONS   59,113+003 VOLTS     FLUXES IN AMM*2   9.50145004 VOLTS     FLUXES IN AMM*2   9.20-001 | RESULTING BACKSCATTER 2:16-001   INCIDENT PROTONS 7:41-006   BULK CONDUCTIVITY 1:72-000   BULK CONDUCTIVITY 1:00   BULK CONDUCTIVITY 1:01   BULK CONDUCTIVITY 1:01 | FLUXES IN A/H**2   EXTERNAL FIELD = 2.349002     FLUXES IN A/H**2   EXTERNAL FIELD = 2.959002     INCIDENT PRESULTING SECONDARTES   5.07-000   E     INCIDENT PROVE   5.07-000   E   5.28-0073     INCIDENT PROVE   5.55-007   E   1.21-0073     INCIDENT PROVE   5.55-007   E   1.21-0073     BULK CONDUCTIVITY   INCOURTING SECONDARTES   1.36-006   E   1.41-0073     NET FLUX   5.67-007   E   1.41-0053   1.41-0053 | SURFACE CELL NO. 77<br>SURFACE CELL NO. 77<br>SURFACE CELL NO. 77<br>POTENTIAL = -5.113.003 VOLTS<br>NATERIAL = KAPT - 0<br>STRESS = 1.719.003 VOLTS/METER<br>EXTERNAL FIELO = -4.51000-000<br>LIMITING FACTOR = 1.000.000<br>LIMITING FACTOR = 1.000.000<br>S.SL-007<br>RESULTING SECONDARIES<br>2.16-007 |  |
|---|---|---|--|--|--|
|---|---|---|--|--|--|

|  | DE = 005111270103<br>DCATION = 9 23<br>DRHAL = KAPT 0 1<br>ATERIAL = KAPT 0 1<br>TS/HETER   | ODE = 005307212001<br>OCENTION = 11 0 10<br>ATERIAL = 6010 0<br>TS/WETER<br>F 8.14-0073<br>F 2.05-0053  | ODE = 01111120302<br>OCATION = 01111120302<br>OCATIAL = SOLA 0 -1<br>ATERIAL = SoLA 0 -1<br>I'S/HETER<br>[ 1.30-0063<br>[ 4.62-0083<br>[ .00 ]  | ODE = UDUD61111123<br>OCATION = 9 9 19 1 1 1 |
|--|---|---|---|--|
| 7.941-000<br>1.72-009<br>6.00-009<br>6.00-009  | F IF  | L = -2.930.003<br>F IE LD = 0.35.001<br>5 F AC TOR = 2.219015<br>1.821-002<br>8.221-002<br>8.221-002<br>8.221-002<br>1.827-002<br>5.55002<br>1.827-002<br>1.827-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.935-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1.955-002<br>1 | FICTOR :: -4.<br>FICTOR :: -4.<br>FICTOR :: -4.<br>5. FACTOR :: 569805<br>5. 54150<br>5. 5404<br>5. 5404 | )<br> <br> <br> <br> <br> <br> <br>          |
| INCIDENT PROTONS<br>Resulting Secondaries<br>Bulm Conductivity<br>Photocurrent<br>Net Flux | SURFACE CELL NO. 88<br>POTENTIA<br>FLUXE S IN A/M++2<br>FLUXE S IN A/M++2<br>FLUXE S IN A/M++2<br>FLUXE S IN A/M++2<br>INCIDENT FLUX<br>BULK RESULTING BACKSCATTER<br>BULK RESULTING SCONDARTES<br>BULK RESULTING SCONDARTES | SURFACE CELL NO. 129<br>FLUXE S IN A/M++2<br>FLUXE S IN A/M++2<br>RESULTING SECONDARIES<br>INCIDENT FLECTRONS<br>PHOTOCURRENT NG SECONDARIES<br>PHOTOCURRENT<br>NET FLUX  | SURFACE CELL NO. 167<br>POTENTI<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>FLUXES IN A/M++2<br>RESULTING<br>RESULTING<br>BULK<br>BULK<br>CONDARIES<br>BULK<br>CONDARIES<br>PHOTOCURRENTING<br>FCONDARIES<br>BULK<br>CONDARIES<br>BULK<br>CONDARIES<br>BULK<br>CONDARIES<br>FLUX   | BOOM SURFACE CELL NO. 181                    |

Figure 11.11. (Continued).

INITIAL NET CHARGING CURRENT (WITHOUT LIMITING) = 3.91-007 AMPERES. INITIAL NET CHARGING CURRENT (WITH 6-39-0083 1-27-0053 6100-41.4 DIRECTION = Z MATERIAL = ALUM 8.83-012 FARADS. CONDUC TOR 1.292-013 AMPEPES 7.297-001 CODE UNITS/SEC. 1.27-006 .00 8.74-007 5.42-008 .00 -7.41-007 POTENTIAL = -2.930+003 VOLTS FIELD = 9.436+004 VOLTS/METER LIMITING FACTOR = .000 AVERAGE FLUXES (ONLY AVAILABLE FOR INSULATING CELLS) 49.9 CODE UNITS; (Continued). CONDUCTOR CURRENTS LAMPS; POSITIVE INTO CONDUCTORSI: 7.53-016 3.648+002 CODE UNITS 6.461-011 COULOMPS 5.48-020/ 9.18+006 LEAVING ICCG2 -- VCTRI = -2.928+003 -2.431+003 1.49-022/ 2.24+004 -2.928+003 -2.431+003 LEAVING ICCG1 -- VCTRI = -2.942+003 -2.257+003 -2.942+003 -2.435+003 LEAVING ICCG1 -- VCIRI = -2,942+003 -2,435+003 1.15-025/ 4.06+002 1.18-025/ 3.17+002 ICCG --- RD0TR/RD0TR1 = 1.35-024/ 3.57+006 -2-9298+003 -2-4315+003 -1.002-009 -1.092-011 6.043-009 6.150-009 -4.000-010 VFIX --- 59 OUT OF 164 NODES FIXED. "SONDUCTOR 1 FIXED TO -2928.48 VOLTS. -2.56-010 Figure 11.11. CTRONS NG SECONDARIES NG BACKSCATTER TOG BACKSCATTER TOG SECONDARIES fotal capacitance to infinity = AVERAGE NET CHARGING CURRENT = -7.2313+009 2.1257+000 ICCG --- RDOTR/RDOTR1 = ~~~~~ 1CCG --- RD0TR/RD0TR1 = ICCG --- RDOTR/RDOTR1 = ICCG --- RDOTR/RDOTR1 = LEAVING ICCG1 -- VCTRI = LEAVING ICCG1 -- VCTRI = TOTAL CHANGE IN CHARGE = IEW CONDUCTOR POTENTIALS IET CURRENTIAVG DQ/DT): NO DISCHARGE ANALYSIS NO DISCHARGE ANALYSIS AVERAGE FLUX TO CELL Average flux to cell Average flux to cell Average flux to cell INCIDENT PRO INCIDENT PRO RESULTI PHOTOCURRENT FLUXES IN A/M++ -2+9285+003 -2+4314+003 NET FLUX

2.4

(Concluded). Figure 11.11.

9

н

IPSAVE

\*

= 13 ISPARE

DI.

IR = 12

= 10

2 16 POTENTIAL ITERATIONS -2.928+003 16 POTENTIAL ITERATIONS COMPLETED. -2.9285+003 -2.4319+003 1.2594+008 -3.7362+004 ... :P = 14 IR = 12 IU = 13 ISPARE = 10 IPSAVE 1 READ IN. 1 GRIDS OUT OF AST CYCLE COMPLETED IS 21. COND = EFPREP --٩

7.005+003 SECONDS. +1 CONTINUE CYCLE NO. 21. AT UPDATED TIME .0N

3

8.58-016

-7.87-011

(FROM INSULATING CELLS);

LASMA CURRENT (INITIAL) (TO BARE CELLS):

LEMAINDER CURRENT:

1.06-009 -1.23-009

-1.05-016 •00



POTENTIAL CONTOURS ALONG THE X-Z PLANE OF Y = 9

Figure 11.12. Potential contours for cycle 21.

#### 11.10 THE DETECTOR

The question that remains to be answered is, how does this charging affect the operation of an on-board particle detector? Suppose an ion detector is mounted on the shaded side of the SOLAR sphere, looking towards the KAPTON sphere. Will the electric field of the negatively charged KAPTON deflect incoming ions, and affect the sampling of the detector? We can simulate the operation of a detector with a new run using the DETECT module.

11.11 THE DETECT RUN

We choose the spare file number 23 for the detector input file. This is shown in Figure 11.13.

Cell 170 is chosen as the site for the detector, which looks out in the positive y direction.  $\not{0}$  is set to zero. The energy range chosen is 1 - 10,000 eV and the angle theta is scanned over the ZY plane from -88° to + 88°. The cone collecting particles is defined to have a half-angle of 1°. If theta were scanned from -90° to 90° some of the particles would have been emitted <u>towards</u> the object (with an angle 91°!) This causes an execution error.

The energy range is sampled with 12 particles. The cone is so narrow that only one angle sample is used (the default).



Figure 11.13. DETECT input file (MANUAL23).

The NASCAP runstream executing the run is shown in Figure 11.14. The energy flux density plot is chosen to be plotted against theta. The plot is shown in Figure 11.15. A dropout in proton flux occurs at angles of less than about  $-70^{\circ}$ . Inspection of the YZ plane particle trajectories (Figure 11.16) show that this is due to the charged KAPTON sphere capturing the protons coming from this direction. The flux dropout corresponds to particles originating on the KAPTON sphere (which do not, in reality, originate at all).

The electron flux is apparently unaffected. The trajectory plots show however that particles that are apparently arriving at grazing angles  $< -70^{\circ}$ , originally approached at much more normal angles. The detector therefore sees a distorted angular distribution. To be sure of this interpretation, we must compare results with these for an uncharged spacecraft.

NASCAP RUN STREAM . M.R. PRS,11182-00,STANNARD-P,45,500 4 .B,8 .M,88,8,8 Vame,n 150, A NASCAPINPROG. 20PY, A NASCAPINPROG. NASCAP FREE NASCAPINPROG. TPF8.,F///1000 COPY MANUALIO 16 COPY MANUALIS 15 COPY MANUALIS 15 COPY MANUALIS 15 COPY MANUALIS 21 COPY MANUALZ3 23 COPY MANUALZ3 23 ANUALOP AUNA ETECT 23 NOPV # 4: MANUAL 5: BOX 19 6: 4ASG, 1 7: 4ASG, 1 8: 4ASG, 1 9: 4ASG, 1 ID.EL Ž DOPT 200 õ ÷ ឆ លីក្ដី ö õ EOF 150

Figure 11.14. DETECT runstream.



ENERGY FLUX IN EV/(CM2-SEC-SR-EV) AT CYCLE 21 MEASURED BY DETECTOR LOCATED AT CELL NUMBER 170 (INTERPOLATED AT 40 POINTS) PROTON FLUX (HEAVY) SCALED BY 1.00+005 ELECTRON FLUX (LIGHT) UNSCALED.

Figure 11.15. Detector plot for charged spacecraft.



Figure 11.16a. Trajectory plots for charged spacecraft.



TRAJECTORIES AT CYCLE 21 FOR ELECTRONS IN 1 GRIDS RECEIVED BY DETECTOR LOCATED AT CELL NUMBER 170 PROJECTED ONTO THE Y-Z PLANE

Figure 11.16b. Trajectory plots for charged spacecraft.

## 11.12 A DETECTOR ON AN UNCHARGED SPACECRAFT

We can zero the potential on the object using the IPS module. If no parameter cards are included as input this module sets all potentials in accordance with the run options.

The results are shown in Figures 11.17 and 11.18. The trajectory plots show no deflection, and there is no proton flux dropout. The actual magnitudes of the electron and proton energy fluxes are smaller and greater respectively for the charged object compared with the neutral object. This is a reflection of their deceleration and acceleration respectively by the satellite electric field.



ENERGY FLUX IN EV/(CM2-SEC-SR-EV) AT CYCLE O MEASURED BY DETECTOR LOCATED AT CELL NUMBER 170 (INTERPOLATED AT 40 POINTS) PROTON FLUX (HEAVY) SCALED BY 1.00+005 ELECTRON FLUX (LIGHT) UNSCALED.

Figure 11.17. Trajectory plots for uncharged spacecraft.



Figure 11.18a. Trajectory plots for uncharged spacecraft.



TREJECTORIES AT CYCLE O FOR ELECTRONS IN 1 GRIDS RECEIVED BY DETECTOR LOCATED AT CELL NUMBER 170 PROJECTED ONTO THE Y-Z PLANE

Figure 11.18b. Trajectory plots for uncharged spacecraft.

### 11.13 SUMMARY

As a result of these simulations we have learned the following:

- 1. In the environment given the object charges negatively with differential potentials of up to 3 kV.
- 2. The differential potentials affect the operation of a particle detector. In particular, a detector looking at a more negative piece of the spacecraft will underestimate the ambient proton energy flux and see a distorted angular distribution for the electron flux.
APPENDIX A

SUBROUTINE PRECIS

#### SUBROUTINE ADBOOM

Generates polygons for boom cells to be used for shadowing and hidden line satellite plots. Represents booms as square cross sectioned rods for graphical purposes only.

## SUBROUTINE ADDA1

Adds a subdived surface cell polygon to the list of surface polygons. The polygons can be subdivided as part of the shadowing calculations.

#### SUBROUTINE ADDCND

Adds one matrix element between conductor nodes. This is done during the ICCG matrix setup.

### SUBROUTINE ADDME

Adds a matrix element to the sparse matrix being set up for ICCG.

#### SUBROUTINE ADDVXB

Adds vector cross product to another vector. Used to push particles in a magnetic field.

#### SUBROUTINE ADEMIT

Adds emitter fluxes to the net currents of individual surface cells. Also accounts for the charge which returned to the satellite.

#### SUBROUTINE ADF

Advances to the next plot frame.

#### SUBROUTINE ADJRE

Adjusts plot co-ordinates for plots of quantities over more than one grid. Used for potential contour plots.

#### SUBROUTINE ADJUST

Calculates total emitted beam current to adjust return emitter currents.

### SUBROUTINE ANGAVG

Averages shadowing of surface cells over several angles of rotation. Used for the SPIN option.

#### SUBROUTINE ANTERP

Performs linear interpolation to determine anisotropy for given energy and species.

#### SUBROUTINE APRNTV

Prints character string labels on plots. Labels can be horizontal or vertical.

#### SUBROUTINE APRT

Utility routine to print out information in a file. RDOPT keyword APRT governs usage.

## FUNCTION AREA

Calculates surface area of a polygon. Used during shadowing calculations.

# SUBROUTINE ASGFIL

Assigns mass storage files to be used during a NASCAP run.

### SUBROUTINE ASUNDR

Converts 10 character CDC words to 4 character words. Complements TOGETH.

## SUBROUTINE AXISXV

Plot routine to draw line parallel to the X-axis.

# SUBROUTINE AXISYV

Plot routine to draw line parallel to the Y-axis.

## SUBROUTINE A1COMP

Compresses the surface cell polygon list to remove those which are completely obscured from view.

## SUBROUTINE AIGEN

Generates the 3-D co-ordinates of the surface cells for a given perspective. Used for shadowing and satellite plotting.

# SUBROUTINE A2GEN

Generates 3-D and 2-D vertices of object building blocks for use in shadowing and satellite plotting routines.

# SUBROUTINE A2PLOT

Non-hidden line plots of the building block faces. These are diagnostic plots used during object definition.

# SUBROUTINE BADCEL

Find cells where electric fields limit low energy electrons. Part of LONGTIMESTEP algorithm.

# SUBROUTINE BADCOND

Determines which conductors have electric fields which prevent their low energy photo and secondary electrons from escaping.

#### SUBROUTINE BADEMT

Sets trial potentials for conductors having ion or electron emitters. Magnitude of charge is determined taking into account whether the environment is charging in the same or opposite direction as the emitter.

### SUBROUTINE BADTRI

Estimates the potentials of cells whose low energy electron emission (e.g. photo emission) is electric field limited. Assumes the potential exterior to a cell changes half as rapidly as the cell potential.

# SUBROUTINE BAXSET

Sets maximum plot dimensions for SILHOU to take into account the booms.

# SUBROUTINE BDQTRI

Gets trial changes in the charges, DQ's, for boom cells.

## SUBROUTINE BFIELD

Calculates the magnetic field vector for a given point in space from input constant plus dipolar fields.

# SUBROUTINE BIAFIX

Modifies inhomogenous term of the potential equations to take into account biased conductors.

#### SUBROUTINE BINWGT

Calculates interpolation weights for boom mesh interface.

## SUBROUTINE BJOINT

Find conductor or conducting surface cells which contact a boom node. Used when constructing surface conductivity information.

# SUBROUTINE BKSCAT

Performs integrals over the incident spectrum to calculate total electron backscatter from a surface cell. Calls BSCAT for actual backscatter coefficients.

# SUBROUTINE BLARGE

Calculates the capacitance between the outer dielectric coating and the underlying conductor for boom cells. NASCAP refers to these as large capacitances.

### SUBROUTINE BLDCYC

Builds the cycle of surface cells surrounding a given surface node.

#### BLOCK DATA

Contains the weights for use in the three dimensional potential solving routines.

## SUBROUTINE BMAREA

Calculates the fractional boom area which recieves solar illumination.

# SUBROUTINE BMLINE

Determines if a boom and a line segment intersect.

# SUBROUTINE BOOM

Defines boom during object definition. Reads and checks user specifications of size, material, and location.

# FUNCTION BOOMAT

Looks up the material which covers a particular boom surface.

# SUBROUTINE BOOMDQ

Calculates the change in surface charge for boom surfaces both with and without the emission of low energy electrons.

# SUBROUTINE BOOMEJ

Finds edges separating boom surfaces and adds them to the edge list.

# SUBROUTINE BOOMGT

Retrieves surface cell information for boom cells. Information returned includes material coating, area, underlying conductor, potential, and small and large capacitances.

# SUBROUTINE BOOMLT

Constructs the list of boom surface cells during object definition. Also constructs the relevant matrix elements necessary for solving Poison's equation.

# SUBROUTINE BOOMI

Forms the list of insulating boom points for addition to the list of all insulating points.

# SUBROUTINE BOOPLT

Draws a boom or a stub which represents the boom depending upon whether or not the entire boom fits within the first mesh. This routine is called during from the material potting routine.

# SUBROUTINE BOTCEL

Determines whether or not a surface is on the bottom of a thin plate or points into volume element that has even one node which is a bottom point.

# SUBROUTINE BOTMBC

Sets initial potentials for bottom points.

#### SUBROUTINE BOTMDQ

Scales potentials of bottom points based upon net change in total charge.

#### SUBROUTINE BOTSUB

Substitutes bottom point values for ordinary nodal values in the potential array.

## SUBROUTINE BRSSUB

Substitutes bottom point values for regular nodal values in the charge density array.

## SUBROUTINE BSCAT

Calculates back scattering coefficients. Contains the physical models and uses the input or default parameters.

## SUBROUTINE BSKET

Makes calls to the plot package to sketch booms on material plots. The end of the boom is closed if it fits within the first mesh. Otherwise, a jagged end is drawn.

### FUNCTION BETWEEN

Logical function which is true if the first argument lies between the other two.

#### FUNCTION BULKB

Calculates the bulk conductivity between a boom surface cell and its underlying conductor.

SUBROUTINE BULKC Calculates the bulk conductivity current for a given surface cell.

### SUBROUTINE BULKS

Finds bulk conductivity between surfaces and their underlying conductors during object definition.

## SUBROUTINE CALFLX

Calculates charging fluxes to surface cells. Calls routines such as BKSCAT to perform actual physics. This routine loops over the surface cell list and stores the fluxes.

#### SUBROUTINE CAPACI

A major code module called by the main NASCAP routine. This routine uses the large three dimensional potential solver to form the capacitances used by the internal current integration algorithms. Capacitances to space are found by solving Laplace's equation with a single unit of charge on the satellite, finding the structure potential and then determing how the charge was distributed among the surface cells.

### SUBROUTINE CAPERR

This subroutines zeroes out the capacitances for non used conductors - purely a bookkeeping task.

# SUBROUTINE CAPPOT

Calls the matrix inverter (ICCG) during current integration calculation.

## SUBROUTINE CAPPT2

Second routine to call matrix inverter during the current integeration calculation.

# SUBROUTINE CCPRD

Matrix multiplication routine for ICCG.

## SUBROUTINE CCSUM

Includes or excludes the small stray capacitances between conductors for use in the current integration calculations.

# SUBROUTINE CELGET

Calculates and writes out capacitances to infinity, capacitances to underlying conductors, total cell areas, and the areas associated with each note. Called by CAPACI.

### SUBROUTINE CELLGT

Retrieves information about the geometry and orientation of a given surface cell during the GENMTL surface connectivity calculation.

#### SUBROUTINE CELLIO

Fast and general file access utility which transfers block data between main memory and mass storage.

## SUBROUTINE CELLST

Bookkeeping routine which expands or contracts information between the array of all surface cells and the array of insulating cells only.

# SUBROUTINE CFLICT

Determines appropriate action for the case of a 1 0 0 surface which points into a partially filled volume element. Called during OBJDEF.

## SUBROUTINE CHARGE

High level routine called by TRILIN which caluclates explicit particle fluxes and predicts the charge accumulation and distribution.

## SUBROUTINE CIRCLE

Draw a circle around the center of a plot.

### SUBROUTINE CKEDGE

Checks that two points form an edge common to two adjacent surface cell. Called during the construction of the connectivity matrix.

## SUBROUTINE CLARGE

Calculates and writes out the capacitances between the surfaces of insulating cells and their underlying conductors using a one dimensional approximation.

#### SUBROUTINE CLASFY

Used by the free format input routines to classify input as integer, real or literal.

# SUBROUTINE CLINE

Plots the detector flux curves.

#### SUBROUTINE CMPRSS

Compresses the surface cell list by removing any surface cells which are internal to the object and thus play no role in the charging process.

## SUBROUTINE CNDCUR

Calculates the incident conductor particle currents at the beginning of a time step.

#### SUBROUTINE CNDMAT

Assembles the conductivity matrix as a result of the connectivity calculation.

## SUBROUTINE CNDSET

Sets surface cell potentials to the value of their underlying conductors. The insulating cells will be reset by a following call to CELLST.

## LOGICAL FUNCTION CNDTST

Test whether a cell is an exposed conductor for initial potential specification.

## SUBROUTINE CNDUCS

Calculates matrix product for conductor equations during the three dimensional conjugate gradient potential calculations.

#### SUBROUTINE CNTOUR

Finds appropriate levels and call contour routines during plotting.

#### SUBROUTINE CNVGRD

Converts coordinates of a point from one grid system to another.

## SUBROUTINE CNVPLT

Plots convergence parameters during three dimensional potential caluculation.

### FUNCTION COF

Utility which returns the value of a six bit word segment .

### FUNCTION COINV

Determines if a vertex is unique during HIDECEL

#### SUBROUTINE CONDME

Adds conductors to the conductivity list during surface connectivity calculations.

# SUBROUTINE CONDUC

Places conductor numbers with surface cells during OBJDEF.

#### SUBROUTINE CONECT

Connects line segments for contour plots.

## SUBROUTINE CONPLT

Major contour plot routine including labeling.

#### SUBROUTINE CONPOT

Sets potentials on grid points interior to the satellite to the satellite structure potential. These points don't enter the calculation, but would make the plots misleading if they were left at zero potential.

## SUBROUTINE CONTOR

Low level contour plot utility.

## SUBROUTINE CONTUR

Utility to draw a single contour line on an Eulerian grid. Used during contour plotting.

## SUBROUTINE COORD

Generates three dimensional coordinates for each surface cell according to NASCAP's storage conventions. The values are used for the SATPLT and HIDCEL calculations.

#### SUBROUTINE COPROD

Performs multiplication of the finite element matrix with the potential array during the three dimensional scaled conjugate gradient iterative potential solver.

### SUBROUTINE COROUS

Converts code charge to physical units of charge density taking into account grid interfaces.

#### SUBROUTINE CROEFF

Called by CELGET to calculate spacecraft effective radius for use in potential and boundary condition scaling which is dependent upon Debye length.

#### SUBROUTINE CSSCAL

Rescales small capacitances to account for finite screening length. These capacitances are used in the charge integration algorithms.

# SUBROUTINE CUBE56

Called during object definition to define a truncated cube; that is a cube with a tetrahedron removed.

#### SUBROUTINE CURCND

Prints conductor and so called "battery" currents during the current integration calculations.

#### SUBROUTINE CURINS

Calculates low energy emission from insulating surface cells.

### SUBROUTINE CURVV

Low level plot routine to draw curves consisting of connected line segments.

#### SUBROUTINE CUTOFF

Increases effective flux derivatives in anticipation of low energy electron flux being cutoff.

### SUBROUTINE CYLNDR

Places zeroes in the potential array exterior to a cylindrical boundary.

#### SUBROUTINE DATETM

Gets date and time from the system clock.

# SUBROUTINE DCODE

Determines type and value of free format input.

# SUBROUTINE DEADLN

Determines whether NASCAP should exit based upon time of day. Used to prevent computing center personnel from killing a run when shutting down for scheduled system maintenance.

# SUBROUTINE DEDSET

Sets the deadline used in the above routine.

# SUBROUTINE DEFORT

Called by NASCAP to set all default input options.

### SUBROUTINE DELETE

Declares a volume cell to be empty and deletes all surface cells within it or pointing out of it.

# SUBROUTINE DETDUM Dummy routine called by NASCAP to run the detector module. This routine was created to solve a mapping problem. SUBROUTINE DETECT Subroutine to calculate particle energy flux as a function of detector orientation for each detector located on a specific surface cell. Fluxes are determined using reverse trajectory particle pushing. SUBROUTINE DETPLT Plots the particle flux data generated by the detector routines. SUBROUTINE DETRUN High level detector routine which calls other routines which get detector requirements, set parameters, perform calculations, and plot results. SUBROUTINE DETSET Initializes detector parameters using keyword input data. SUBROUTINE DFACST Sets perspective distance factor for use in hidden line satellite plots. SUBROUTINE DEDV Calculates approximate derivative of the particle flux with respect to changes in the surface cell potential. SUBROUTINE DEDVMX Sets the maximum allowable value for the flux derivative to prevent the surface potential of any cell from changing more than DVLIM in a timestep. SUBROUTINE DFIELD Finds electric fields for pushing particles during the detector calculations. SUBROUTINE DIAGNO Print routine for the surface cell list called during object definition. SUBROUTINE DIHEDA Calculates the angle between two adjacent surface cells. Called when calculating the connectivity matrix. SUBROUTINE DIM4 Low level boom matrix routine called during object definition.

## SUBROUTINE DIM4Q

Low level boom matrix routine called during object definition.

# SUBROUTINE DIRINT

Routine to perform direct integration of spectral data points using Gaussian weights.

# SUBROUTINE DISCHG

Checks to see if discharge criteria are satisfied. If so, charge is redistributed according to type of discharge. This routine is called during the integration of particle currents.

## SUBROUTINE DISPAC

Routine to handle the special case of a discharge to space based upon the magnitude of the surface potential.

## SUBROUTINE DIVIDE

Low level routine to check denominator size prior to performing division to prevent divide checks .

# SUBROUTINE DLINEV

Low level routine which draws lines connecting a series of points.

### SUBROUTINE DOPLOT

Prints convergence plots during potential calculations.

## SUBROUTINE DOSRAT

Provides the integrand for the dose rate integral for determining radiation induced conductivity.

#### SUBROUTINE DQSCND

Redistributes charge accumulation taking into account conduction currents.

# SUBROUTINE DRAWV

Low level plot interface which produces vector drawn characters. For labels on plots.

## SUBROUTINE DRISCM

Driver for construction of point list and surface conductivity matrix during OBJDEF. Calls GENMTL.

#### SUBROUTINE DTPUSH

Three dimensional leap-frog particle pusher used by the dectector routines.

## SUBROUTINE DVLMIT

Called during the current integration to restrict the difference between trial potentials and orginal potentials to DVLIM.

# SUBROUTINE ECUBE

Element stiffnes matrix residual evaluator for an empty cube.

# SUBROUTINE EFIELD

Computes the local electric field at a point exterior to the object. Used to push particles by particle tracking routines.

# SUBROUTINE EFPREP

Performs storage manipulations preparing common blocks prior to the use of EFIELD.

## SUBROUTINE ELBEAM

Analytically calculates Rutherford scattering including magnetic field effects. Used for multiple gun tank simulations.

# SUBROUTINE ELFLUX

Calculates the incident, secondary and backscattered electron fluxes to a specific surface cell. Calls lower level routines for models of the physical processes.

## SUBROUTINE ELIMIT

Cuts back emission of low energy electrons to take into account surface electric fields.

## SUBROUTINE ELSEC

Generates electron secondary emission coefficient for a given incident spectrum. Called by ELFLUX.

# SUBROUTINE ELSEC

Identical routine as ELSEC but relabeled for efficient segmentation.

#### SUBROUTINE EMDIST

Sets up the energy and angle distribution of emitter particles.

# SUBROUTINE EMFIXR

Subroutine to handle stubborn cases in which particle refuses to follow a reasonable trajectory which passes through a numbered volume cell just prior to passing through a cell surface.

## SUBROUTINE EMISET

Initializes emitter parameters in common block EMIT using keyword input.

# SUBROUTINE EMITER

Calculates current density array for a given emitter located on a specific surface cell.

# SUBROUTINE EMTFLX

Calculates currents to surface cells resulting from emitter particles returning to the object.

#### SUBROUTINE EMTRUN

High level emitter routine which calls other routines to initialize parameters and perform emitter calculations.

# SUBROUTINE ENPRT

Prints out potential , kinetic and total energies to check conservation in emitter particle pushing routines.

### SUBROUTINE EPBOOM

Evaluates electric fields and potentials in boom cells.

## LOGICAL FUNCTION EQUAL

Compares two packed integers prior to using XORR.

#### FUNCTION ERFC

Calls routine to evaluate error function.

#### SUBROUTINE ESPEC

Calculates electric fields for partially filled cells. The cell is assumed to be in the standard orientation and the resulting fields must be transformed back to the actual cell orientation.

#### SUBROUTINE ESURFS

Calculates effective surface electric fields for all surface cells.

## FUNCTION BSCAT

Calculates the normal incidence backscatter coefficient as a function of atomic number.

#### SUBROUTINE ETNGUN

Forwards particle tracking routine for single monoenergetic gun tank simulation.

### FUNCTION EXPINT

Performs interpolation between two points assuming exponential behavior of the function. If results are inconsistent then linear interpolation is performed.

SUBROUTINE FASTRW ASCII Fortran version of FASTIO rapid disk access. routine to transfer block data to and from mass storage. SUBROUTINE FBREAK Breaks up characters into groups of contiguous characters which were separated by blanks. Used to perform free format reads. SUBROUTINE FCOUNT Count and decode the input types specified in free format routine call. SUBROUTINE FILALL Calls FILINP for all grids. SUBROUTINE FILASG Assigns all required disc files. SUBROUTINE FILINP Fills in internal boundary potentials of an outer grid using values from the grid nested inside . SUBROUTINE FILPX Fills in the entire two dimensional inner rectangle of potentials using values from nested grids to get a plane of constant X for contour plotting. SUBROUTINE FILPY Fills in the entire two dimensional inner rectangle of potentials using values from nested grids to get a plane of constant Y for contour plotting. SUBROUTINE FILPZ Fills in the entire two dimensional inner rectangle of potentials using values from nested grids to get a plane of constant Z for contour plotting. SUBROUTINE FIL111 Creates a 111 filler surface during object definition. SUBROUTINE FINDBP Finds out location of a boom point in the point list. SUBROUTINE FINDPT Finds a given point in the point list. SUBROUTINE FINDTM Finds all the times associated with spectral data and stuffs them into a common block. SUBROUTINE FINFUN Determines what class of data is on a free format input card image. (Multigun test tank.) 492

SUBROUTINE FINISH Called by high level routines to close plot file and exit. SUBROUTINE FINSHV Plot routine to close a graphics file. SUBROUTINE FINTER Interpolates between input spectral data energies and those required to perform gaussian quadratures for surface flux calculations. SUBROUTINE FINVER Adds necessary vertices to complete a partially shielded polygon. Part of the hidden line routines used for shadowing and satellite plots. SUBROUTINE FIXPOT Fixes insulating surface potentials and conductor potentials prior to calling POTENT. SUBROUTINE FLASH Locates pair of cells with largest overvoltage for flashover calculation. SUBROUTINE FLDCON Adds effects of field enhancement to bulk conductivity. SUBROUTINE FLUXT1 Defines incident particle flux parameters from the flux file for single gun tank cases . SUBROUTINE FLXDEF Flux definition high level routine. Sets particle environment. SUBROUTINE FLXSPA Defines incident particle flux parameters from the flux file for space environments. SUBROUTINE FNDSCE Finds surface conducting edges. SUBROUTINE FREAD Reads in experimental particle flux data. SUBROUTINE FREED Free format read routine. Interprets card images where data fields are separated by blank spaces. SUBBOLITINE ESPACE Finds phase space density from DeForest data.

SUBROUTINE FTITLE Writes a plot frame with a user specified line of text, date and time the routine was called, and send a frame eject. FUNCTION GCSTOT Sums the small capacitances over the entire object surface. SUBROUTINE GDQTRI Gets estimated change in charge for use in implicit charge integration algorithims. SUBROUTINE GENMEA Sets markers for interface boom cells. SUBROUTINE GENMTL High level which generates the skeleton of the LONGTIMESTEP matrix and intializes it with surface conductivity contributions. SUBROUTINE GENSCL Generates records for the surface cell sub-list. SUBROUTINE GETBAR Calculates potential barrier height for emitted particles. SUBROUTINE GETBCL Sets up detector on a boom cell. SUBROUTINE GETBFL Calculates incident particle fluxes to boom cells. SUBROUTINE GETCEL Retrieves parameters of a specified surface cell. SUBROUTINE GETCH Generates incomplete Cholesky matrix for ICC6 routines. SUBROUTINE GETDIV Gets diagonal elements from full three dimensional potential matrix for use in scaled conjugate gradient routine. SUBROUTINE GETDQ Gets change in electrical charge on surface cells. Also finds effective field above conductors. SUBROUTINE GETFLX Finds explicit particle fluxes for trial potentials

during current integration calculations.

### SUBROUTINE GETIGE

Opens a plot file if one has not already been opened.

#### SUBROUTINE GETNC

Determines the number of conductors specified in a given object.

#### SUBROUTINE GETROT

Gets rotation matrix to transform vectors for uniform cosine distribution.

# SUBROUTINE GJR

Simple Gaussian elimination matrix inverter for use by hidden line routines.

# SUBROUTINE GJRX

Same routine as GJR but given different name for mapping purposes. Used during object definition.

#### SUBROUTINE GJRY

Same routine as GJR but given different name for mapping purposes. Used during detector calculations.

### SUBROUTINE GUNSHD

Estimates particle shadowing for multiple particle guns in a laboratory tank.

#### SUBROUTINE HBOOST

Increases particle timestep during emitter calculations to increase efficiency.

### SUBROUTINE HIDCEL

High level routine which supervises the shadowing and hidden line satellite plot calculations.

### SUBROUTINE HIGHQ

Called by LIMCEL to unfix nodes with impossibly high fluxes.

#### SUBROUTINE HREDUC

Reduces particle timestep during emitter calculations to increase accuracy.

#### SUBROUTINE HISTORY

Called by TRILIN to dump timeplot information.

#### SUBROUTINE ICCG

Main routine of the Incomplete Cholesky - Conjugate Gradient iterative symmetric linear equation solver. This routine is called during the implicit current integration algorithm.

### SUBROUTINE ICCG1

Sets up matrix and calls ICCG driver.

#### SUBROUTINE ICCG1

Like ICCG1 , called by current integration routines to setup charging matrix and call ICCG driver.

## SUBROUTINE ICORNS

Calculates contributions of corner cells which are at mesh interfaces to the residual vector. Low level routine in the three dimensional potential solver.

## SUBROUTINE IEDGES

Calculates contributions of edge cells which are at mesh interfaces to the residual vector. Low level routine in the three dimensional potential solver.

## SUBROUTINE IFACES

Calculates contributions of cells which form the mesh interfaces to the residual vector. Low level routine in the three dimensional potential solver.

#### SUBROUTINE IGFBUF

Begins updating the plot buffer and write it out as required.

# SUBROUTINE IMPFI

Implict flux routine which calculates the charge required to change the surface voltage from VO to VTRIal .

#### FUNCTION INBCEL

Checks whether a point is within a boom cell.

# SUBROUTINE INCOND

Initializes potentials of fixed voltage conductors during three dimensional potential solution.

#### SUBROUTINE INDATA

Initializes potential and current data in accordance with user options.

### SUBROUTINE INEIMP

Processes input material parameters to get them in the form necessary for secondary yield calculations.

## SUBROUTINE INGUNS

Reads FLXDEF file to setup parameters for multiple guns in a laboratory test tank.

# SUBROUTINE INIPOT

High level routine which supervises initialization of surface potentials.

SUBROUTINE INISET Reads and processes initial potential specifications. SUBROUTINE INPLOT Initialization routine for printer plots. SUBROUTINE INPUT Main input routine for object definition module. FUNCTION INSIDD Double precision routine which determines whether a point is located inside a given polygon. Low level routine in the shadowing section of the code. FUNCTION INSIDE Single precision version of INSIDD. FUNCTION INSID1 Determines whether a particle has penetrated the object. Called by the field routines during particle pushing. SUBROUTINE INSLST Forms the list of insulating surface cells after calculation of the connectivity matrix. SUBROUTINE INTCHK Calculates cell edge intersections with the polygons that make up the major object building blocks. Part of shadowing routines. SUBROUTINE INTSEC Called by INTCHK to calculate the intersection co-ordinates. SUBROUTINE INVERS Driver to call GJRX matrix invertor. SUBROUTINE IOFLX Prints fluxes to a given cell. SUBROUTINE IOSCLP Prints out potentials of all surface cells. SUBROUTINE IOSTRS Prints out electric field stresses for each surface cell. SUBROUTINE IOXFLX Prints out fluxes to a given boom cell.

SUBROUTINE IPSCHG Computes estimated total charge for initially specified potentials. SUBROUTINE IPSCND Sets a given conductor and all cells overlying it to a specified potential. Part of the initialization of potentials. SUBROUTINE IPSMAT Like IPSCND, sets initial potentials , this time for all cells of a specified material with a given illumination. SUBROUTINE IPSPOT Called during intialization of potentials to read list of cells. SUBROUTINE IRCALL Part of three dimensional potential solver which calls mesh interface routines. SUBROUTINE ISPACE Finds matrix product with potentials for the innermost grid during the three dimensional potential solution. FUNCTION IXV Plot routine to convert a user x coordinate to a raster coordinate. FUNCTION IYV Plot routine to convert a user y coordinate to a raster coordinate. SUBROUTINE JACIRC Plots a circle of a specified radius. FUNCTION KBITS Machine dependent low level routine which specified bits from a word. UNIVAC version calls BITS ; CDC version uses a bit mask. SUBROUTINE KINENG Calculated kinetic energy and modified polar emission angle for particles used in the emitter routines. SUBROUTINE LCODE Decodes an entry in the element table and returns cell type and orientation. Used by the electric field routines when particle pushing. SUBROUTINE LCTOUC Converts lower case ASCII character to upper case.

#### SUBROUTINE LIMCEL

Performs cell by cell electric field limiting of low energy emission as part of the current integration step. This is a high level supervisory routine which enables NASCAP to treat barrier effects in spacecraft charging.

## SUBROUTINE LIMITS

Called by mesh interface routines during three dimensional potential calculations to set limits on loop indices.

### SUBROUTINE LINEUV

Plot routine which draws a straight line between two points which are specified in user coordinates.

### SUBROUTINE LINPLN

Calculates the coordinates of the point of intersection of a line with a plane. Part of the hidden line routines.

### SUBROUTINE LINPLT

Printer plotter routine called to plot convergence criteria from the potential solver.

#### SUBROUTINE LINSCH

Low level routine which performs a bit search.

#### SUBROUTINE LLTIV

Called during ICCG to calculate product with lower triangular Cholesky matrix.

## SUBROUTINE LOWQ

Unfixes nodes having impossibly low fluxes during the current integration.

### SUBROUTINE LQUADV

Plot routine to fill in a quadrangle with solid lines; used for material plots.

#### SUBROUTINE LSTMAT

Completes construction of the capacitor model matrix during the current integration.

#### SUBROUTINE LSTMT2

Same as LSTMAT with different name for mapping.

SUBROUTINE MAGCMP Corrects initial particle velocities in the one gun laboratory environment by taking into account magnetic field curvature of orbits. SUBROUTINE MATCAL Retrieves surface cell data for satellite plots. SUBROUTINE MATDEF Contains default surface material properties. SUBROUTINE MATPLT Plots satellite as seen from plus and minus grid coordinae directions. Each surface cell is shaded according to its surface material. SUBROUTINE MATPRO Processes material properties to obtain derived quantities required by the charging algorithms. SUBROUTINE MAXDEL Limits timestep to prevent roundoff errors in the integration of particle fluxes. SUBROUTINE MAXSWR Integrates over a Maxwellian spectrum to obtain an emitted flux. SUBROUTINE MIXG2D Generates two dimensional interpolants for use in boom cell matrices. SUBROUTINE MIXG3D Linearly interpolates 2-D matrices to obtain full boom cell matrix. SUBROUTINE MMPY Low level matrix multiplication routine for rotational matrices. SUBROUTINE MORCOR Calls system routine to get more memory during execution. SUBROUTINE MOVDAT Performs block transfers between core and disc. SUBROUTINE MOVEA1 Moves surface cell polygon to a new location on the polygon list during hidden line calculations. SUBROUTINE MPTWGT Multiplies boom weights during object definition.

### SUBROUTINE MTWGT

Calculates empty cell weights for potential calculations.

## SUBROUTINE MULGUN

Calculates incident particle flux intensity at a cell for a multiple particle gun laboratory environment.

## SUBROUTINE NASCAP

The highest level, main procedure.

### SUBROUTINE NEWFLX

Finds the next spectrum for use with direct integration algorithms.

#### SUBROUTINE NEWGRD

Determines which grid a point is in and returns its location in that grid's units.

### SUBROUTINE NEWMAT

Changes material properties after object definition. Typically changed is the bulk resistivity to simulate degradation.

## SUBROUTINE NICOBJ

Object definition routine to construct large rectangular solids contained in shapes such as right octagonal cylinders.

#### SUBROUTINE NIIOCT

Object definition routine to construct right octagonal cylinders and quasispheres from simpler components.

#### SUBROUTINE NIOTET

Like NIOOBJ except constructs nescessary tetrahedral solids.

#### SUBROUTINE NIOWGE

Like NIOOBJ except constructs necessary wedge solids.

#### SUBROUTINE NORMSK

Generate corner code for right triangle surface. An object definition routine.

#### SUBROUTINE NORM3V

Low level routine to normalize a three component vector.

## LOGICAL FUNCTION NOTEOL

Tests for inequality using exclusive or function.

SUBROUTINE NUMLTB Numbers element table volume cells which border the satellite. This is done during object definition and the resulting list is used by particle pushing routines. SUBROUTINE NUMPTS Counts the number of points in the point list. SUBROUTINE NWVTXL Sets up array which identifies neighbors of an insulating surface cell. SUBROUTINE OBJDEF High level routine which supervises code conversion of user object specification into cell by cell lists for use by the charging sections. SUBROUTINE OCORNS Mesh interface routine from the potential section which handles corner cells in the outer mesh. SUBROUTINE OCTGON Decodes user OCTAGON input for use by object definition routines. SUBROUTINE OCUBE Empty volume element matrix weights called by OCORNS. SUBROUTINE OEDGES Mesh interface routine to handle potential calculations of edge cells in the outer mesh.

SUBROUTINE OFACES

Mesh interface routine to handle potential calculations of face cells in the outer mesh.

SUBROUTINE OLAP

Checks for overlapping of two polygons as part of the shadowing calculations.

SUBROUTINE OLDLIN

Printer plot routine which stores line information.

SUBROUTINE ORCALL

Calculates outer mesh interface element contributions to the potential matrix.

# SUBROUTINE ORDPTS

Orders vertices so that the lowest index is first, then are counter clockwise.

# SUBROUTINE OSPACE

Calculates outer grid empty volume element contributions to the potential matrix.

SUBROUTINE OUTLIN Plot routine to draw an outline around the user plot area. SUBROUTINE PCPDAT Updates potentials as part of the current integration routines. SUBROUTINE PDIL Transforms projected surface cell coordinates for material plots. SUBROUTINE PDIR Same as PDIL but for viewer along a negative axis. SUBROUTINE PERMU Generate permutation vector from element code. Used to transform non cubic elements to the standard orientation. SUBROUTINE PHCMAT Adds photosheath conduction to the surface conductivity matrix. SUBROUTINE PHCOND Calculates effective photoconductivity. SUBROUTINE PHOR Area definition routine for shading for material plots. SUBROUTINE PHOTOC Pushes particles with Maxwellian energy distribution for photosheath calculation. SUBROUTINE PLATE Inputs thin plate parameters during object definition. SUBROUTINE PLEMIT Plots emitter particle trajectories. SUBROUTINE PLOTCV Plots a square array of four dots centered at the current point. SUBROUTINE PLPART Plots detector particle trajectories. SUBROUTINE PMODQ Scales potentials by relative change in total charge. SUBROUTINE POINT

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Printer plot routine which plots a single point. Part of the potential convergence plotting.

# SUBROUTINE POLYN

Eliminates any redundant nodes from a polygon. Part of shadowing calculation.

# SUBROUTINE POTENT

Supervisory routine for the three dimensional potential solver.

# SUBROUTINE POTPLT

Produces potential contour plots from the three dimensional electric potentials.

# SUBROUTINE PPJSET

Sets up the prospective projection matrix for shadowing calculations.

# SUBROUTINE PRFLUX

Calculates proton (positive ion) flux and its associated secondary electrons for use in the charging calculation.

# SUBROUTINE PROLIN

Projects the coordinates of a point on a line onto the viewer plane.

# SUBROUTINE PROSEC

Low level routine which calculates the proton generated secondary electron yield.

# SUBROUTINE PRSPPJ

Projects a point from three space onto the viewer plane.

# SUBROUTINE PRSPPK

Converts from prospective view back to three space.

# SUBROUTINE PRTLIM

Prints information from LIMCEL, the routine that limits the emission of low energy electrons when barriers are present.

# FUNCTION PSURFB

Calculates surface resistance of a boom half-segment.

# FUNCTION PSURFS

Calculates surface resistance of a half-cell.

# SUBROUTINE PSWIT

Switches points in the potential array to take into account bottom points on thin plates.

#### SUBROUTINE PTCOMP

Part of shadowing calculation which checks to see if two points are close enough together to be treated as a single point.

#### SUBROUTINE PTLINE

Checks to see if a point is on a given line segment. Part of shadowing calculation.

## SUBROUTINE PTROUS

Corrects charge density taking into account biased conductors.

# SUBROUTINE PUPDAT

Updates the potential array with the conjugate gradient solution. Part of the three dimensional potential solver.

# SUBROUTINE PUSH

Calculates the incident flux at a given surface cell using reverse trajectory particle pushing.

#### SUBROUTINE PUSHER

Forward trajectory particle pushing routine for tracking emitter particles.

#### SUBROUTINE PVER

Permutes surface cell vertices for material plots.

# SUBROUTINE QCONCP

Calculates the charges on fixed and biased conductors. Used to determine battery currents for output.

### SUBROUTINE QDISTR

Distributes blowoff charge to other cells and conductors. Part of the discharge model.

#### SUBROUTINE QDOT

Plots dotted material surface during object definition plotting.

#### FUNCTION QEQN

Low level routine to solve for secondary yield parameter during material properties input.

#### FUNCTION QEONZ

Low level routine to solve for maximum yield energy durng materials properties input.

#### SUBROUTINE QSPHER

Object definition routine which takes quasi-sphere input and transforms it into a combination of right octagonal cylinders and tetrahedra.

SUBROUTINE QSUMER Sums the change in computational space electric field in order to obtain the total charge on the object via Gauss's law. Used to perform potential scaling. SUBROUTINE RADCON Replaces intrinsic material conductivities with their radiation enhanced values. SUBROUTINE RCPDAT Updates the residual vector during ICCG. Part of the current integration step. SUBROUTINE RDOBJ Reads in object data for a restart. SUBROUTINE RDOPT Read user run time options from the options file. SUBROUTINE READAN Reads anisotropic flux data as part of the environment specification. SUBROUTINE RECTAN Defines volume and surface cells associated with a rectangular parallelepiped as part of the object definition calculation. SUBROUTINE REDCRD Low level routine to read a single card. SUBROUTINE REDFIT Read file of fits to observed spectra to determine range of times available. SUBROUTINE REDO Current integration routine which cuts back the timestep if changes in voltages are too great. SUBROUTINE REFIX Revises potential estimates for barrier limited cells by using information from neighboring cells. Part of the current integration. SUBROUTINE REGRID Reconstructs a potential location code for boom cells which are part of mesh interfaces. SUBROUTINE REORDER Reorders a boom matrix to account for a particular orientation. SUBROUTINE REPLOT Printer plot routine which sets up extrema and increments for plotting real numbers. SUBROUTINE RESCRN Rescales potentials to account for change in plasma screening.

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#### SUBROUTINE RESETQ

Scales charges and potentials through out the mesh.

## SUBROUTINE RETRNO

Low level emergency abort routine which forces a traceback in the case of a code failure.

### SUBROUTINE REVERT

In the case of an internal restart, reverts the capacitances and magnetic fields back to physical input units from code units.

#### SUBROUTINE REWIND

Positions files pointer to the beginning of a mass storage file.

# SUBROUTINE RHOSHE

Plots phosheath electron density contours.

#### FUNCTION RNORM

Computes a rational approximation to a normal distribution.

# SUBROUTINE ROTATE

Rotates the sun direction and magnetic field vectors in time to simulate the shadowing of a spinning satellite.

#### SUBROUTINE ROUSP

Plots charge density contours.

### SUBROUTINE RTSUP

Finds appropriate surface triangles for square surface cells which are superseded by right triangles. This is an object definition routine.

#### SUBROUTINE RUPDAT

Updates the residual vector during the three dimensional conjugate gradient potential calculation.

#### SUBROUTINE SATPLT

High level routine which performs satellite plots.

#### SUBROUTINE SBLIN

Low level routine to print scale values on plot base line.

# SUBROUTINE SCACTR

Routine to find the effective scattering center for the multiple laboratory gun environment.

### SUBROUTINE SCALEP

Guesses new potentials by scaling previous results by the change in total charge. Used to get good initial conditions for iterative potential solver.

## SUBROUTINE SCAT

Rutherford scattering calculation with magnetic field to get current density and angle of incidence for multigun laboratory environment.

#### SUBROUTINE SCCYC

Reorders the surface cells around a point in cyclic order. Part of the surface conductivity matrix generation.

# SUBROUTINE SCREAD

Reads in the surface conductivity list and matrix for initialization.

### SUBROUTINE SEARCH

Searches a two dimensional mesh to find contour levels for plotting.

#### SUBROUTINE SETALL

Sets all potentials to monopole value.

#### SUBROUTINE SETAN

Sets up transformation matricies for particle pushing intial velocities.

#### SUBROUTINE SETAX

Sets up axis values for contour plots. The resolution is that of the coarsest mesh so that mesh interfaces don't cause wiggles on the plots.

### SUBROUTINE SETBMI

Sets up matrices necessary to calculate electric fields in cells which contain booms. Used for particle pushing.

## SUBROUTINE SETBTS

Low level routine to set bits in a computer word.

## SUBROUTINE SETCOM

Sets values in common blocks.

## SUBROUTINE SETEWX

Determines the energies and weights to be used for optimal resolution of emitted spectrum.

## SUBROUTINE SETFAC

Sets bit information telling direction a surface cell is facing.

SUBROUTINE SEFFL Routine to set surfaces of a FIL111 building block. SUBROUTINE SETFOC Fills in surface information for an octagon building block. SUBROUTINE SETFTH Sets surface information for a tetrahedron building block. SUBROUTINE SETFWG Sets surface information for a wedge building block. SUBROUTINE SETIP Sets inner grid potentials to zero for an initial guess. SUBROUTINE SETLST Sets the list of nodes whose potentials are fixed during the three dimensional potential solution. SUBROUTINE SETMAX Sets up environmental parameters for use with Maxwellian distributions for reverse trajectory particle tracking.

# SUBROUTINE SETOP

Sets initial potentials in outer grids to zero with the possible exception of the outermost grid being filled with the monopole potential.

## SUBROUTINE SETPOP

Sets the potentials on the outer surfaces of the outer grid to the monopole value.

#### SUBROUTINE SETROT

Sets up a rotation matrix for use by the particle pushers in the detector and emitter routines.

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SUBROUTINE SEFFL Routine to set surfaces of a FIL111 building block. SUBROUTINE SETFOC Fills in surface information for an octagon building block. SUBROUTINE SETFTH Sets surface information for a tetrahedron building block. SUBROUTINE SETFWG Sets surface information for a wedge building block. SUBROUTINE SETIP Sets inner grid potentials to zero for an initial guess. SUBROUTINE SETLST Sets the list of nodes whose potentials are fixed during the three dimensional potential solution. SUBROUTINE SETMAX Sets up environmental parameters for use with Maxwellian distributions for reverse trajectory particle tracking. SUBROUTINE SETOP Sets initial potentials in outer grids to zero with the possible exception of the outermost grid being filled with the monopole potential. SUBROUTINE SETPOP Sets the potentials on the outer surfaces of the outer grid to the monopole value. SUBROUTINE SETROT Sets up a rotation matrix for use by the particle pushers in the detector and emitter routines. SUBROUTINE SETSHE Sets up data for particle pushing photo sheath calculation. SUBROUTINE SETUAV

Plot routine which defines relationship between user coordinates and plotting raster coordinates.

#### SUBROUTINE SETUPV

Plot routine to open a plot file and establish default parameters.

# SUBROUTINE SETWE

Calculates macro particle energies and weights for particle pushing.

# SUBROUTINE SHIELD

The workhorse routine in the shadowing / hidden line calculations. Does shadowing calculation for a single surface cell by a single large object surface. Shadowing is done by looking for edge intersections and redrawing only the exposed polygon.

#### SUBROUTINE SILHOU

Draws satellite including booms. For use in contour plots.

### SUBROUTINE SKEL1

Initialize circuit matrix skeleton assuming no conductivity as an early step in the conductivity matrix construction.

## SUBROUTINE SKEL2

Adds surface conductivity to the matrix skeleton.

#### SUBROUTINE SLLIN

Plot routine to print scale values along the left vertical axis.

#### SUBROUTINE SMAXMO

Fits input particle spectrum to a double Maxwellian by the method of moments.

### SUBROUTINE SOLFLX

Calculates the photelectron current density for a given surface cell during charging.

## SUBROUTINE SORTER

Simple bubble sort utility for ordering short lists.

#### SUBROUTINE SOURCE

Converts user input specification of a laboratory electron or ion source into code units for use during charging.

#### SUBROUTINE SPACEF

Machine dependent routine to space forwards in a mass storage file.

#### SUBROUTINE SPECEL

Sets up volume element information for partially filled cells for use in the element table.

SUBROUTINE SPIN Simulates the shadowing of a rapidly spinning satellite by averaging the shadowing from several sun angles. SUBROUTINE SQCWGT Performs matrix multiplication with permuted cell vertices during potential calculation. SUBROUTINE SQUARE Defines a square surface cell during object definition. SUBROUTINE SRFCLS Loops through surface cells and gets their contributions to the matrix product during the three dimensional potential solution. SUBROUTINE SRTWDS Sorts a one dimensional array of words using a heapsort. SUBROUTINE STOPAR Stores particle trajectories for sheath plot. SUBROUTINE STRESS Calculates electric field stresses within dielectric surface cell coatings. SUBROUTINE SUMOPT Prints a summary of the run time options. SUBROUTINE SUMOD Sums up the charges on the dielectric surface, that is all surfaces except the exposed conductors. SUBROUTINE SURFB Calculates the surface resistance of half a boom cell during the conductivity matrix setup. SUBROUTINE SURFS Calculates the surface resistance of half a square surface cell. SUBROUTINE SWPEN Plot routine to request pen change in order to plot in a new color. SUBROUTINE SWPPTS Low level routine which swaps the location of data for two point entries. Used when ordering points for geometrical

analysis.
SUBROUTINE S3MCHR Fortran routine which transfers characters. Used in free format routines and is necessary since the language doesn't support string manipulations. SUBROUTINE S3MOVE Do-loop to move an array from source to destination. SUBROUTINE S3SET Do-loop to set all members of an array to a given value. SUBROUTINE SJZERO Do-loop which zeroes an array. SUBROUTINE TABSTF Stuffs the TAB common block with data. SUBROUTINE TERROR Reports errors in the multiple gun input. SUBROUTINE TETDEL Deletes extraneous surface cells for tetrahedral objects during object definition. SUBROUTINE TETRAH Defines surface cells and volume elements for a tetrahedron object. SUBROUTINE THNPLO Performs material plot specifications for thin plates. SUBROUTINE TIMER Low level routine which prints remaining job time. SUBROUTINE TIWARN Checks to see whether enough time remains in a job so that a high-level routine can make a clean exit. SUBROUTINE TLINEV Plot routine which draws thick lines. SUBROUTINE TMULT Low level matrix multiply routine which transforms boom weights during objdef. SUBROUTINE TOGETH Low level routine which packs character data into computer words. ( CDC only ) SUBROUTINE TODOT Plots dots in material plots. SUBROUTINE TRAAN Transforms a rotation matrix by interchanging axial directions.

SUBROUTINE TRANA Transforms eight cubic element vertex potentials according to the cell orientation code. SUBROUTINE TRAND Transforms change in orbit length according to cell orientation. Used during particle pushing. SUBROUTINE TRANE Transforms electric field vector from standard orientation back to element orientation for use in the particle pushing routines. SUBROUTINE TRILIN High level routine which oversees the charging and potential calculations. SUBROUTINE TRIPLT Material plot routine which outlines a triangular cell and colors and fills it according to the surface material type. SUBROUTINE TRIPOT Performs trilinear interpolation in an empty cubic element. SUBROUTINE TRIPRD Calculates triple product of three vectors. Same as the determinant of the matrix composed of the vectors as columns. SUBROUTINE TRISHR Shares cell values to vertices according to trilinear interpolants. SUBROUTINE TRNGLS Stuffs appropriate orientation code into surface cell list for right triangle surfaces. SUBROUTINE TRPLT2 Right triangle plotting routine from material plot section. SUBROUTINE TURNON Modifies flux derivative prior to removing potential barrier and turning on secondary emission. SUBROUTINE TYPEV Prints characters on a plot frame. SUBROUTINE UAU Calculates inner product for three dimensional potential routine.

#### SUBROUTINE UCPDAT

Updates vector at the end of an ICCG iteration.

## SUBROUTINE UNEMIT

Determines whether a particle emitter current is so small that the satellite potential responds over several timesteps. If so, the underlying conductor is floated; if not the conductor potential is fixed by the current intergration routine.

## SUBROUTINE UNEMT1

Calls UNEMIT routine for fixed conductors with emitters.

## SUBROUTINE UNFIX

Unfixes cells when predicted emission exceeds maximum possible.

### SUBROUTINE UNFIXC

Unfixes conductors when predicted emission exceeds explicit estimate.

### SUBROUTINE UNFREE

Low level routine which marks the free format routine as being unloaded by stuffing its memory locations with blanks.

### SUBROUTINE UNLOAD

Low level routine to mark the D-bank above the plot library as unloaded.

## SUBROUTINE UNSTOR

Marks as unloaded D-bank locations that may have been overwritten by the STOR common block.

### SUBROUTINE UNSURF

Decodes thin plate surface cell material information for plotting.

### SUBROUTINE URCSET

Initializes residual and solution vectors for the ICCG potential solver.

### SUBROUTINE URSETO

Initializes residual and solution vector's for three dimensional potential solver.

## SUBROUTINE UUPDAU

Updates the solution vector in the three dimensional potential solver.

SUBROUTINE UXVEC Converts the verticies of a surface cell from NASCAP coordinates to plotter raster coordinates. SUBROUTINE LIXYV Performs the coordinate conversion for a single vertex. SUBROUTINE VADD Low level routine which adds two vectors. SUBROUTINE VADDS Low level routine which adds two vectors after multiplying one by a scalar. SUBROUTINE VCEMT Estimates the voltage change for a conductor which has a particle emitter. SUBROUTINE VCENTR Calculates the effective center of charge for calculating beam deflection for multiple guns in a tank. Presently restricted to the geometrical center. SUBROUTINE VCFIX Fixes potentials of conductors consistent with predicted fluxes. SUBROUTINE VECROT Low level routine which rotates a vector about a coordinate axis. SUBROUTINE VFIX Fixes surface cell potentials to make them consistent with their predicted fluxes. SUBROUTINE VMAX Predicts maximum voltage change for an object during a timestep. Used for cutting back timestep if it is greater than user specified limit. SUBROUTINE VMULT Multiplies a three vector by a matrix. SUBROUTINE VPRED Predicts surface cell potentials by solving implicitly the charging equations. Calls the ICCG potential solver. SUBROUTINE VSURFS Calculates the average surface potential above all surface cells in the element table during CAPACI.

# SUBROUTINE WEDGE Defines a wedge object's sufaces and volume elements. SUBROUTINE WGEDEL Deletes wedge surface cells which are internal or superceded. SUBROUTINE WGTIN Brings in element weights for the inner mesh to be used in the three dimensional potential routines. SUBROUTINE WGTOUT Brings in element weights for the outer mesh to used in the three dimensional potential solver. SUBROUTINE WRDSRT Object definition routine which sorts the surface cell list exclusive of the triangle bits. FUNCTION XORR Low level exclusive or routine which compares words after converting lower case to upper case (UNIVAC) or truncating to four characters (CDC). SUBROUTINE XTRCLS Forms matrix product for boom volume elements during three dimensional potential calculation. SUBROUTINE XTRDIV Calculated diagonal matrix elements for boom cells. Used for scaling the three dimensional matrix. SUBROUTINE XTRFLX Calculates the explicit flux to boom cells as the first step in the charging calculation. SUBROUTINE XTRIR Forms matrix product for inner mesh interface cells which have booms. Part of the three dimensional potential calculation. SUBROUTINE XTROR Forms matrix product for outer mesh interface cells which have booms. SUBROUTINE XTRPTR Calculates charges on fixed and biased boom cells after a potential calculation. SUBROUTINE XTROFX Calculates contributions from fixed and biased boom cells to the total charge on each conductor.

# SUBROUTINE XTRSOL

Calculates the photocurrent for boom cells.

# SUBROUTINE ZDRAW

Low level plot routine which moves the cursor to a given location.

# FUNCTION ZINT

Calculates the z coordinate of a line where the x and y values are that of an apparent intersection in two dimensions with another line. Used for hidden line drawings.

# SUBROUTINE ZSYSTM

Preprocesses electron secondary emission parameters during object definition and new material specification. APPENDIX B

IMPLEMENTATION OF NASCAP ON THE CRAY/IBM SYSTEM



NASCAP, along with several of its utility routines, is now functional on the CRAY/IBM system at Lewis Research Center. The main NASCAP program exists on the CRAY, together with a routine CRAYFILES to maintain NASCAP restart files and CRAYTOIBM to send to the IBM the data required by PLOTREAD, CONTOURS, and TERMTALK, which are resident on the IBM. MATCHG is resident only on the IBM. Libraries of low-level NASCAP utility routines (e.g., FREED) are resident on both machines. All files are currently stored under the username SEMANDEL. On the CRAY, all files have ID=NASCAP, except for restart files, which are currently without ID.

In making this conversion, every effort was made to maximize commonality of NASCAP coding to the various FORTRANS used: UNIVAC ASCII FORTRAN, CRAY FORTRAN (CFT), and CDC FORTRAN V. Only a small number of routines in the main NASCAP/GEO code need be changed among these three FORTRANS, including some low-level I/O routines (MOVDAT, CELLIO, REWIND, SPACEF), some executive request routines (ASGFIL, DATETM, S3MCOR, TIWARN), some machine-specific assembler routines (F2FRT, F2FCA, TIMLFT, SHIFT, XTIME), and a single routine, SETCHR, defining bits per word, characters per word, and bits per character. Many more changes must be made for the version of IBM FORTRAN implemented at NASA/LeRC, which does not properly handle continuation lines.

The documentation which follows is not intended as an operations manual for either system, but rather as a description of the present implementation of the NASCAP family of codes on the composite system.

B.1 FREED (IBM)

The IBM version of the NASCAP utility library may be created by compiling the file SOURCE.FREED. It is currently stored as FRDLIB. When using this library, FT47F001 must be DDEF'd as a scratch file.

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B.2 FREED (CRAY)

The source code for the NASCAP utility library may be stored on the CRAY by SUBMITting the file CRAY.FREED. It is compiled by SUBMITting the file CFREED.COMPILE. The source code is stored in FREEDPROGLIB and the object code in FREEDOBJLIB.

B.3 MATCHG

The source code for MATCHG is stored in SOURCE.MATCHG, with the main routine in SOURCE.MATCHG \$\$. The object code is stored in MTGLIB, and the default material properties in MATCHG.DATA. It may be executed by the command (PROC) MATCHG.

**B.4** CRAYFILES

The NASCAP restart file utility routine CRAYFILES may be created by SUBMITting the file CRAY.FILES. To run it,

ACCESS, DN=FILES, PDN=CRAYFILES, ID=NASCAP. FILES.

Commands are read from \$IN until an /EOF is reached. Available commands are:

ASSIGN prefix - Save a new set of NASCAP files. ACCESS prefix - Make a set of files local and accessible through FORTRAN logical unit numbers. ADJUST prefix - Properly close set of NASCAP files. DELETE prefix - Delete set of NASCAP files. COPY prefix1 TO prefix2 - Copy from one existing set of files to another.

## The files treated by CRAYFILES are:

| Permanent Name | Local Name |
|----------------|------------|
| prefix02       | FT02       |
| prefix10       | FT10       |
| prefix15       | FT15       |
| prefix16       | FT16       |
| prefix17       | FT17       |
| prefix21       | FT21       |
| prefix27       | FT27       |
| prefixOBJ      | FT20       |
| prefixOPT      | FT26       |
| prefixFLX      | FT22       |
| prefix19       | FT19       |

At present, files are SAVEd, etc., with no ID.

# B.5 CRAYTOIBM

The utility routine CRAYTOIBM may be created by SUBMITting the JOB CRAY.TOIBM. It is used to send restart files from the CRAY to the IBM, where they may be read by PLOTREAD, CONTOURS, or TERMTALK. CRAYTOIBM reads from \$IN a card containing the list of units (LUN's) to be sent, or the literal 'ALL'. It writes to local file (LUN+50), which must have previously been TASSIGN'ed, and must subsequently be BINOUT'ed. The files required by the various routines are:

| Routine  | LUN( | (S) |     |
|----------|------|-----|-----|
| PLOTREAD | 2    |     |     |
| CONTOURS | 10,  | 17, | 21. |
| TERMTALK | 16,  | 17, | 21. |

```
To send all five files:
```

```
ACCESS, DN=FILES, PDN=CRAYFILES, ID=NASCAP
ACCESS, DN=TOIBM, PDN=CRAYTOIBM, ID=NASCAP
TASSIGN, A=FT52, DN=FT52
TASSIGN, A=FT60, DN=FT60
TASSIGN, A=FT66, DN=FT66
TASSIGN, A=FT67, DN=FT67
TASSIGN, A=FT71, DN=FT71
FILES.
TOIBM.
BINOUT, DN=FT52, SDN='prefix.FILE02'.
BINOUT, DN=FT60, SDN='prefix.FILE10'.
BINOUT, DN=FT66, SDN='prefix.FILE16'.
BINOUT, DN=FT67, SDN='prefix.FILE17'.
BINOUT, DN=FT71, SDN='prefix.FILE21'.
/EOF
ACCESS prefix
/EOF
2 10 16 17 21
/EOF
```

# Note that

- TASSIGN takes an inordinate amount of memory. Using M=1700, only three files can be TASSIGN'ed.
- The IBM prefix (in the SDN= parameter) need not be the same as the CRAY prefix.
- 3. Any previous IBM file with the name prefix.FILExx should be erased prior to sending a new one from the CRAY. Otherwise, the sent file will appear with a ridiculous system name.
- 4. The files sent from the CRAY will be stored as 'I/O PENDING' files, and should be properly disposed of in a timely fashion.

B.6 NASCAP

/EOF

The NASCAP source (excluding FREED routines and a few modifications) resides on the IBM in the file CRAY.NASCAP (suitable for CRAY submission) and on the CRAY in NASCPROGLIB. The source may be compiled into NASCOBJLIB by submitting CRAY.COMPILE. Sources for routines found to require correction during testing are in CRAY.NASBLD, which will make the corrections to NASCOBJLIB. The absolute, NASCABS, will be created by CRAY.NASTRY.

An initial-run NASCAP runstream might be: ACCESS, DN=FILES, PDN=CRAYFILES, ID=NASCAP ACCESS, DN=NASCAP, PDN=NASCABS, ID=NASCAP FILES. REWIND, DN=FILES. COPYF, 0=FT20. REWIND, DN=FT20. COPYF, 0=FT22. REWIND, DN=FT22. COPYF, 0=FT26. REWIND, DN=FT26. NASCAP. FILES. /EOF ASSIGN prefix ACCESS prefix /EOF Object definition input /EOF Environment definition input /EOF Option input /EOF NASCAP input /EOF ADJUST prefix

- 1. For subsequent run, the ASSIGN command to CRAYFILES should be omitted, and the COPYF commands may be omitted if not needed.
- 2. As in other versions of NASCAP, commands such as OBJDEF 5 cause data to be read directly from NASCAP input rather than from a separate file.
- 3. In the above runstream, if NASCAP exits due to an 'END' command, the ADJUST will not be performed, as FILES will encounter the /EOF. Solutions are either (a) omit the 'END', in which case NASCAP will exit normally on encountering the /EOF; or (b) follow the 'NASCAP." command with

REWIND, DN=\$IN.

SKIPF, NF=5.

which will position \$IN following the sixth '/EOF'

B.7 TERMTALK, CONTOURS, AND PLOTREAD

These routines are accessed by the IBM commands (procedures) TERMTALK prefix CONTOURS prefix PLOTREAD prefix.

Their sources are located in SOURCE.TTALK, SOURCE.CONTOURS, and SOURCE.IBMPLOT, and their objects in LIB.TERMTALK, LIB.CONTOURS, and LIB.IBMPLOT. The procedures contain statements to DDEF the appropriate files with DSNAME=prefix.FILExx (see CRAYTOIBM). Operation on the IBM is similar to the UNIVAC. See the TSS/370 Graphics Manual for plot destinations.

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